



Y. S. M. Anjanan Khairu s am's

POONA COLLEGE OF ARTS, SCIENCE AND COMMERCE

(Affiliated to Savitribai Phule Pune University) ID No. PU/PN/AS/CO/23/1278

ACTIVITY REPORT

(2022 - 2023)

I. Basic Details:

Name of The Activity- Faculty and students Exchange under MOU.			
Date	Faculty	Department/ Committee	Coordinator Name & Phone no.
11 th March to 17 th March	BBA	Department of BBA	Prof. Deepika Kinninge 9405555695
Time	Venue	Activity for class/ group student number	Extracurricular
	BBA	03	

II. Brief Information about the Activity - Criterion no :- 3.5.1

Topic/ Subject of the activity	Faculty and students Exchange under MOU.
Objective for conducting the activity	<ul style="list-style-type: none">The objectives for a faculty and student exchange program at a college is multifaceted, aiming to foster academic growth, cultural understanding, and collaboration.Academic Enrichment:Cultural Exchange and Understanding:Knowledge Exchange:Personal Growth:
Methodology	Participative Learning
Outcome	student exchange programs have fulfilled the objectives that aim to foster academic, cultural, and personal development.

III. Proofs attached: letters/ student list of participation/ certificate/ document/photos/ any other

**AKI's Poona College of Arts Science and Commerce
DEPARTMENT OF BBA**

REPORT

Visit to Damodar College of Commerce and Economics Margoa, Goa

**GOA VISIT (3 Days and 2 Nights)
(11th March to 13th March 2023)**

**(Under Faculty and Student Exchange Program with Damodar
College of Arts Science and Commerce, Verna, GOA)**

Department of BBA along with 06 BBA students and 2 Faculty organized Study tour and Faculty student Exchange Program in collaboration with Damodar College of Arts Science and Commerce, Verna, GOA from 11th March to 13th March under in pursuance of MOU signed between Damodar College, Goa and Poona College. Faculties of BBA presented research paper @ Damodar College and Student enjoyed Mgt games and Cultural Activities on GOAN culture.org by Dept of BBA of Damodar College.



Prof Deepika AND Prof Sozali Kamble (BBA Dept Poona College) visited Damodar College

Goa on 11th March 2023 along with 06 BBA Students.

Dr. Rodney D'silva welcomed BBA faculties and students of BBA.



Professors & PhD MAs of Damodar College Goa welcomed BBA Faculty and Students.

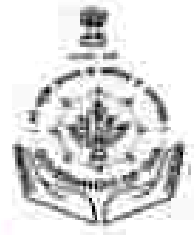


BBA Faculty and Students of Damodar College organized program for BBA students of Pooka College.

Ms. Deepika Kirtaga
BBA Dept.



Golden Jubilee Celebrations



Vidya Vikas Mandal's

SHREE DAMODAR COLLEGE OF COMMERCE & ECONOMICS

Affiliated to Goa University

Accredited by NAAC at 'A' Grade with CGPA of 3.03 on a 4 point scale
Margao - Goa

Department of Commerce & Management

In collaboration with

Directorate of Higher Education (DHE),

Government of Goa



Certificate

This is to certify that Prof./Dr./Mr./Ms.

Deepika Abhijeet Kininge

of Poona College of Arts, Science & Commerce, Pune

has presented a research paper titled A Comparative Study

of Marketing Strategies and Consumer Satisfaction
of Ayurvedic Medicinal Products with Allopathic
Medicinal Products at the National Conference on
in Pune

'Emerging Global Practices in Finance & Management'

organised by the Department of Commerce & Management

in collaboration with Directorate of Higher Education (DHE),

Government of Goa, held on 11th March, 2023

Prof. Arita D. Malliya
Professor and Principal

Dr. Shami Pai
HOD, Commerce &
Management

Dr. Sheetal Arondekar & Mr. Gajanan Haldankar
Conference Coordinators

Attendance Sheet

Date of Activity: 11th March to 12th March 2023

Time:

Activity Name: Activity under TMOU

Coordinator Name: Deepika Khatke

Department: BBA Faculty Student Exchange Program between

Parvat College (Dons + Culture Govt)

Number of Participants: 06 students + 02 Faculty

Sr.No	Name	Class	Roll No	Sign of Participant
1	Nirupam Bhusade	TYBBA	6339	<i>[Signature]</i>
2	Sheikh Mohd. Sohail Y.	TYBBA	6343	<i>[Signature]</i>
3	Sameer Akhmed Shaikh	TYBBA	6365	<i>[Signature]</i>
4	Mohammed Anwar	F.Y.B.A	6128	<i>[Signature]</i>
5	Fidya Tarkat	F.Y.B.A	6151	<i>[Signature]</i>
6	Pooja Bhusar	TYBBA	6360	<i>[Signature]</i>
7	Deepika Akhmed Khatke	Coordinator	BBA	<i>[Signature]</i>
8	Sandip J. Kamble	Faculty	BBA	<i>[Signature]</i>


 Signature of Coordinator

PROJECT REPORT

ON

A STUDY ON E- FILING OF TAX RETURN – INCOME TAX

WITH A CASE STUDY OF

CAFE ADDA IN AURANGABAD

SUBMITTED TO

IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE

DEGREE OF MASTER OF COMMERCE

(ADVANCED ACCOUNTING & TAXATION)

OF

SAVITRIBAI PHULE PUNE UNIVERSITY

SUBMITTED BY

ANSARI SHIFA KHATOON ASIF

Roll No-5901

MCOM II SEM IV

UNDER THE GUIDANCE OF

DR. SYED HAMED HASHMI



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023



CAFE ADDA

Azad Chowk Rd, Rahmania Colony, Kiradpura, Aurangabad Maharashtra
431001

Mobile Number - +91 84848 84855

This is to certify that -Anshri Shifa Khatun Asst of MCOM Part II, SEM 4, and Roll No. 5991 of AKI's
Purna College of Arts, Science and Commerce has successfully completed the internship work as per the
guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement
and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavours.



CAFE ADDA
Prop. Ausaf Khan
8484884855

Authorized Signature

PROJECT REPORT

ON

A STUDY OF TAX AUDIT REPORT OF CORPORATE AND NON-CORPORATE ASSESSEES

IN

YASH PLAST PRIVATE LIMITED PUNE

A PROJECT REPORT SUBMITTED TO

SAVITRIBAI PHULE PUNE UNIVERSITY

IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE

DEGREE OF MASTER OF COMMERCE

ADVANCED ACCOUNTING AND TAXATION.

SUBMITTED BY

CHIKODI MOHAMMAD FAVAAZ MOHSIN

Roll No- 5982

UNDER THE GUIDANCE OF

DR. SYED HAMED HASIMI



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

ART'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023

This is to certify that **CHIKODI MOHAMMAD FAWAAZ MOHSIN** of
MCOM Part II, SEM 4, and Roll No-5902 of AKI's Poona College of Arts,
Science and Commerce has successfully completed the internship work as per the
guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen
interest to learn. The involvement and sustained efforts put in by the student is
highly appreciable.

We wish him all the best in his future endeavors.

The candidate has completed his internship in our organization from 1st January
2023 to 31st March 2023.



A PROJECT ON

"A Case Study of e-filing of Tax Returns of GST in Alfazhat Air Conditioning Systems at MSK & Associates Pune"

A PROJECT REPORT SUBMITTED TO

SAVITRIBAI PHULE PUNE UNIVERSITY

**IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE**

(Advance Accounting & Taxation)

SUBMITTED BY

UNAES ZAKARIYA KOKATE

Roll No-5903

UNDER THE GUIDANCE OF

Dr. Syed Hamed Hashmi



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

Mr. Mohammed Sadique Khan

M.B.A (Fin), B.Com, G.D.C.A, B.Com, D.T.I, G.S.T.P
CSC VLE for Ministry of Electronics and Information Technology,
Government of India New Delhi
IC for Bank of India
Prop. MSK & Associates
Founder of counttax.com
GSTP No. : ZF1800007293GP1

www.counttax.com

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Email us : mskaassociates@gmail.com / countax.com@gmail.com : For queries mail us at mskaassociates@gmail.com

Date: 04/04/2023

TO WHOM SO EVER IT MAY CONCERN

This is to certify that Mr. Unaes Zakariya Kokate of MCOM Part II, SEM 4, and Roll No. 5903 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable. We wish Mr. Unaes Zakariya Kokate him all the best in his future endeavours.

He has completed his internship for a period from 01st January 2023 to 31st March 2023.



For MSK & Associates

Prop. Mohammed Sadique Khan

M.B.A (Fin), G.D.C.A, M.Com, B.Com, D.T.I.

A PROJECT ON
**"A CASE STUDY ON TAX PLANNING OF INDIVIDUAL ASSESSEES
HAVING INCOME FROM BUSINESS WITH RESPECT TO INCOME
TAX ACT 1961, AT MSK & ASSOCIATES**

A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
**IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE**

(Advance Accounting & Taxation)

SUBMITTED BY
SAQLAIN SHOEB SHAIKH

Roll No-5904

UNDER THE GUIDANCE OF
Dr. Syed Hameed Hashmi



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

Mr. Mohammed Sadique Khan

B.B.A (Fin), M.Com, G.D.C.A, B.Com, D.Y.I., G.S.T.P
JSC VLE for Ministry of Electronics and Information Technology,
Government of India New Delhi
IC for Bank of India
Prop. MSK & Associates
Founder of counttax.com
GSTP No. : 271830007393001

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mail us : mskaassociates@gmail.com / counttax.com@gmail.com | For queries mail us at ac.mskaassociates@gmail.com

Date:03/04/2023

TO WHOM SO EVER IT MAY CONCERN

This is to certify that Mr. Saqlain Shoeb Shaikh of MCOM Part II, SEM 4, and Roll No. 5904 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable. We wish Mr. Saqlain Shoeb Shaikh him all the best in his future endeavours.

He has completed his internship for a period from 01st January 2023 to 31st March 2023.

For MSK & Associates

Prop. Mohammed Sadique Khan

MBA (Fin), G.D.C.A, M.Com, B.Com, D.T.L



"COMPUTERIZED ACCOUNTING SYSTEM AT KOKATE ROADLINES"

**A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(ADVANCED ACCOUNTING & TAXATION)**

**SUBMITTED BY
REHAN JAMIL KHAN
Roll No-5905**

**UNDER THE GUIDANCE OF
DR.HANED HASHMI**



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023

This is to certify that REHAN JAMIL KHAN of MCOM Part II, SEM-4, and Roll No. 5905 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish him all the best in his future endeavours.

Authorized Signature with Stamp


29.09.2023

**“A study of Computerized Accounting System in
Future Chip Technologies Pune”**

A PROJECT REPORT SUBMITTED

TO

SAVITRIBAI PHULE PUNE UNIVERSITY

**IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE**

(Advance Accounting & Taxation)

SUBMITTED BY

SADIKA FAIZ AHMED INAMDAR

Roll No-5907

UNDER THE GUIDANCE OF

Dr. Syed Hamed Hashmi



**DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE
AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE**

CAMP, PUNE-1

2022-2023



Future Chip Technologies

Head Office : 13/293, Lam Society, Phulanagar, Behind R.T.O. Office, Alandi Road, Pune - 411 006.
Pune Branch : 928, Sacashiv Path, Near Sadhana Trust Office, Pune - 411 030.
Mumbai Branch : Near Gimar Building, Mumbai-Pune Highway, Khopoli, Dist. Raigod - 410 203.
Call : 98901 41705 | 96659 99705 | Email : ramkantbhujbal@gmail.com | www.futurechiptech.com

TO WHOM IT MAY BE CONCERN

This is to certify that Miss. **SADIKA FAIZAIMED INAMDAR** of M.COM. Part II (SEM-IV), and Roll No.-5907 of AKI's Poona College of Arts, Science and Commerce, Pune has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University, Pune in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by her is highly appreciable.

We wish her all the best in her future endeavors.

She has completed her Internship for period from 01/01/2023 to 31/03/2023

Mr. Bhujbal Ramakant
Director
Future Chip Technologies,
409, Shanwar Path, Pune-30



A PROJECT ON
"A STUDY OF COMPUTERIZED ACCOUNTING SYSTEM IN B K
TOUGHENED GLASS PVT LTD PUNE"

A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE

(Advance Accounting & Taxation)

SUBMITTED BY

Siyam Intiyaz Parkar

Roll No- 3908

UNDER THE GUIDANCE OF

Dr. Syed Hamed Hashmi



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE



CIN : U74900PN2012PTC14405

B K TOUGHENED GLASS PRIVATE LIMITED

Get No: 396, Caubatti Mandir Road, Boppoon, Tal. Parandur, Dist. Pune Pin-412301

Office : 9087720436, Email : bktoughenedglass@gmail.com

TO WHOMSOEVER IT MAY CONCERN

This is to certify that **Siyam Intiyaz Parkar** of MCOM Part II, SEM 4, and Roll No. 5908 of AKJ's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavors.

He has completed his internship for period from 01/01/2023 to 31/03/2023



***PROJECT REPORT ON
"A STUDY OF E-FILING OF TAX RETURN"***

***A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(ADVANCE ACCOUNTING & TAXATION)***

***SUBMITTED BY:
KANNAJIYA SUJEET MISHRILAL***

Roll No- 5909

***UNDER THE GUIDANCE OF
Dr. Syed Hameed Hashmi***



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023



Mohammad Asad & Co.
Chartered Accountants

Ref No: -

Date: -

Date: 18/03/2023

TO WHOM SO EVER IT MAY CONCERN

This is to certify that Mr. Kannaujya Sajeet Mishrilal of MCOM Part II, SEM 4, and Roll No. 5907 of AKT's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

He has completed his internship for a period of 01-12-2022 to 28-02-2023.

We wish Mr. Kannaujya Sajeet Mishrilal him all the best in his future endeavours.

Best Regards

For Mohammad Asad & Co.


Proprietor

Date: 18/03/2023



A PROJECT ON

**"A study on Accounting System of Global Tour and
Travel Business in Pune"**

**A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY**

**IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR
THE DEGREE OF MASTER OF COMMERCE**

**ADVANCE ACCOUNTING
AND TAXATION**

SUBMITTED BY

SANIYA MUSTAFA CHOUDHARY

ROLL NO- 5910

UNDER THE GUIDANCE OF

DR. SAYED HAMED HASHMI



**DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE
AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE**

CAMP, PUNE

2022-2023



This is to certify that **CHOUDHARY SANIYA MUSTAFA** of MCOM Part II, SEM 4, and Roll No. 5910 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish her all the best in her future endeavours.

The candidate has completed her internship in our organization from 1st January 2023 to 31st March 2023.

Authorized Signature with Stamp
For Global Travels

**"COMPUTATION OF TOTAL INCOME WITH RESPECTIVE
INDIVIDUAL RESPONDENT"**

***A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE***

(Advance Accounting & Taxation)

SUBMITTED BY

Pal Punam Premshankar

Roll No-5911

UNDER THE GUIDANCE OF

Dr. Syed Hameed Hashmi



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023



VARSHA JAWALKAR & ASSOCIATES

CHARTERED ACCOUNTANTS


Date:-10/03/2023

TO WHOMSOEVER IT MAY CONCERN

This Is TO Certify That Miss Punam Premshankar Pal a Student Of a Mcom Master Of Commerce Pune University . Has Successfully Completed 3(three) Months (From 1 December 2022 To 28 Feb2023)Long Internship Programme At This Firm. During The Period Of His Internship Programme With Us. She Was Found Punctual, Hardworking And Inquisitive.

Her Associataion With Us Was Very Benifical And We Her All The Best In Her Future Endeavors.




Authorites Signatory
CA Varsha Jawalkar -Ghule

Address : 4th Floor, Sakrupa Building, Pune Solapur Road, Manjari Bk., Tal. Haveli, Dist. Pune
Contact No : 9604590093 | Email : ca.varshajawalkar@gmail.com

PROJECT REPORT

ON

**A STUDY ON AN ACCOUNTING AND TAX PLANNING OF NEW
PARVIN DRESSES PARTNERSHIP FIRM KHADKI PUNE**

SUBMITTED TO

**IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(ADVANCED ACCOUNTING & TAXATION)**

OF

SAVITRIBAI PHULE PUNE UNIVERSITY

SUBMITTED BY

SHAIKH SAINA MURTUZA

Roll No-5912

MCOM II SEM IV

UNDER THE GUIDANCE OF

DR. SYED HAMED HASHMI



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023

NEW PARVIN DRESSES

Shop No - 16, Ambimata Estate, #29 New Bazar, Hingoli, Maharashtra
Mobile Number :- +91 9822834260, +91 9890312316

This is to certify that Saina Murtuza Shaikh of M.COM Part II, SEM 4, and Roll No. 5912 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University on our organization.

During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavors.

Duration of project work: 1 February to 15 April.

M. Shaikh
New Parvin Dresses
Proprietor

Authorized Signature

2022-2023

**“A STUDY OF GST IMPLEMENTATION AND IT'S EFFECTS
ON SALES”**

***A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT
FOR THE
DEGREE OF MASTER OF COMMERCE***

(Advance Accounting & Taxation)

SUBMITTED BY

SINGH ANKITA KUMARI BRAJESH KUMAR

Roll No-5914

UNDER THE GUIDANCE OF

Dr. Syed Hamed Hashmi



**DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE
AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE**



AMP & ASSOCIATES CHARTERED ACCOUNTANTS

TO WHOMSOEVER IT MAY CONCERN

This is to certify that ANKITA BRAJESH SINGH of M.com Part II, SEM-4 Roll No.5914 of Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, she was sincere, hardworking and showed keen interest to learn. The involvement and sustained efforts put by student are highly appreciable.

We wish her all the best for her future endeavor.

For AMP & Associates
Chartered Accountants



CA. Mihir S Sanghir
Partner
M.No. 145407
Date-
Pune

"COST BUDGETING AT MANGEN TECHNOLOGIES PVT. LTD"

***A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR
THE
DEGREE OF MASTER OF COMMERCE
(RECENT ADVANCES IN COST AUDITING & COST SYSTEM)***

SUBMITTED BY

MS. ZAINAB SAYYED

Roll No-5915

UNDER THE GUIDANCE OF

Dr. Riyasat Peerzade



***DEPARTMENT OF COMMERCE, PG AND RESEARCH CENTRE
AK'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2022-2023***



INTERNSHIP COMPLETION CERTIFICATE

This is to certify that Ms. Zainab Sayyed has successfully completed project work in the company under the esteemed guidance and technical support of Sr. Developers toward the fulfillment of the semester.

Project Name: Cost Budgeting

From - 27th Jan 2023 to 10th Feb 2023

She has successfully completed her internship. During the period she was sincere, hardworking & fully devoted to project.

We wish her all success to her future career.

For Maxgen Technology Pvt



Sallama Kukate
Manager - Human Resources

***"A STUDY OF ACTIVITY BASED COSTING METHOD AT
TAMANNA HOTELS PRIVATE LIMITED, PUNE"***

**A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE**

(ADVANCED COST ACCOUNTING & COST SYSTEM)

**SUBMITTED BY
UMARMUKHTAR ASADIMRAN SHAIKH
ROLL NO -5921**

**UNDER THE GUIDANCE OF
Dr. RIYASAT PEERZADE**



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

**AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE**

2022-2023



This is to certify that Umamichur Asaduram Shaikh of M.COM Part II, (SEM- IV) and Roll No-5921 of ACP's Poorna College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 01/03/2023 to 18/03/2023 for the Academic Year 2022-2023.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish him all the best in his future endeavours.


Authorized Signature

This is a computerized generated document and does not require any stamp validation

*"A STUDY OF BUDGETARY CONTROL SYSTEM AT
BRITANNIA INDUSTRIES LIMITED"*

*A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(ADVANCED COST ACCOUNTING & COST SYSTEM)*

*SUBMITTED BY
AFRIN TAUSIF SHAIKH
ROLL NO-5922*

*UNDER THE GUIDANCE OF
DR. RIYASAT PEERZADE*



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023

TO WHOM IT MAY CONCERN

This is to certify that Avin Tansil Shakh of MCOM Part II, SEM 4, and Roll No. 5022 of AIT's Purna College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 27th January 2023 to 15th February 2023 for the academic year 2022-23.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish him all the best in his future endeavors.

Authorized Signature with Stamp
For Britannia Industries Limited.



T.V. Thakur
Company Secretary
Membership No.: J20927

**STUDY OF WORKING CAPITAL MANAGEMENT AT ARTHRIFEET
CAPITAL SERVICES PRIVATE LIMITED**

**A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
ADVANCED COST ACCOUNTING**

**SUBMITTED BY
KATHRAKODE UTHRA ADITHYAN
Roll No- 3923**

**UNDER THE GUIDANCE OF
DR. RIVASAT PEERZADE**



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

**ARTS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAJP, PUNE
2022-2021**

COMPANY CERTIFICATE

This is to certify that **Kalthakode Uthra Adithyan** of **M.Com Part II, SEM 4**, and **Roll No. 5923** of **AKT's Poona College of Arts, Science and Commerce** has successfully completed the internship work as per the guidelines of **Savitribai Phule Pune University** in our organization from **27th January 2023** to **20th February 2023** for the academic year **2022-23**.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish her all the best in his future endeavors.

Authorized Signature

For ARTHRITT CAPITAL SERVICES PVT. LTD.


Director



+91-0201621577, +91-9034747384

info@arthrittcapital.com

www.Arthvrittcapital.com

Office no. 1504, Goodwill Excellency, Sector 17, Vashi, Navi Mumbai 400703

AKPS POONA COLLEGE OF ARTS, SCIENCE AND COMMERCE
"A STUDY OF PROCESS COSTING AT KATHAL DAIRY"

A PROJECT REPORT
SUBMITTED TO
SAYEDRHAJI PHULE PUNE UNIVERSITY

IN THE PARTIAL FULFILLMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(ADVANCE COST ACCOUNTING & COST SYSTEM)

SUBMITTED BY
SOBIYA SAMEER SHAIKH
Roll No-5925

UNDER THE GUIDANCE OF
DILRIVASAT PEERZADE




DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE
AKPS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2022-2023

PUNE ZILHA SAHKARI DUDH UTPADAK SANGH MARYADIT
Katraj Dairy, Katraj Pune -411 046

Date:- 06/03/2023

INDUSTRIAL VISIT CERTIFICATE

This is to certify that Miss. Sobhya Sameer Shaikh the Students of Poona College of Arts, Science & Commerce, Camp, Pune - 411001 has visited to our Pune Zilha Sahakari Dudh Utpadak Sangh Maryadit Katraj Dairy, Katraj, Pune on 06/03/2023.


6/3/23
Incharge Training Center
Pune Zilha Saha. Dudh
Utpadak Sangh Mar.
Pune-Satara Road,
Dairy Dairy, Pune-411001.

A Project Report on
**"ACCOUNTING FOR TOURS AND TRAVELS BUSINESS
(SARVA TOURS AND TRAVELS)"**

**A PROJECT REPORT SUBMITTED TO
SANTORBAL PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE.**

**SUBMITTED BY
FAIZAN ARIF MILANI
Roll No-5927**

**UNDER THE GUIDANCE OF
Dr. Syed Hamid Hashmi**



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

**ARTS PUNE COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2022-2023**



Ref. _____ Date _____

This is to certify that FAIZAN ARIF MULANI of MCOM Part II, SEM 4, and Roll No. 5927 Of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavours.

Thanking You,

For SABA TOURS AND TRAVELS


Proprietor

Proprietor

For SABA TOURS AND TRAVELS

"A Study of Work Culture and Work Ethics at Teebhik Network Pvt Ltd"

**A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(BUSINESS ADMINISTRATION)**

SUBMITTED BY

ABRAR AHMED SIDDIQUE

ROLL NO- 1947

UNDER THE GUIDANCE OF

DR. NASIR KHAN



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

ARTS PUNE COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2021-2021



**Treelink Network
Private Limited**

101, 102, 103, 104
Savitribai Phule
Pune University
K. K. Road, Pune - 411 004

This is to certify that Abrar Ahmed Siddique of MCOM Part II, SEM 4, and Roll No.5942 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 02/02/2023 to 01/03/2023 for the academic year 2022-23. During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student are highly appreciable. We wish him all the best in his future endeavors.

Authorized Signatory with Stamp



A PROJECT REPORT ON
CUSTOMER SATISFACTION STRATEGIES AT HISMILLAH HAJ TOURS AND TRAVELS
SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(BUSINESS ADMINISTRATION)

SUBMITTED BY
SHAFTYA WAHID SAFFED
Roll No-5943

UNDER THE GUIDANCE OF
DR. NASRIN PARVEZ KHAN



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

ARTS/POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2021-2023



بِسْمِ اللّٰهِ الرَّحْمٰنِ الرَّحِیْمِ
BISMILLAH
HAJ TOURS AND TRAVELS PVT. LTD.
Recognized by the Government of India



17th February 2023

This is to certify that Shafiya Wahid Sayyed of MCCM Part II, SEM IV, and Roll No. 5943 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 17 September 2022 to 17 February 2023 for the academic year 2022-2023.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable. We wish her all the best in her future endeavors.

Authorized Signature with Stamp



A STUDY ON 360 DEGREE PERFORMANCE APPRAISAL AT LIFETIME NUMBER

**A PROJECT REPORT SUBMITTED TO
SANTIRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(BUSINESS ADMINISTRATION)**

**SUBMITTED BY
SILAISTA SHAIKH NASIR
ROLL NO -5944
UNDER THE GUIDANCE OF
DR. NASRIN KHAN**



**DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE
AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2022 - 2023**

This is to certify that Shaista Nasir Shaikh of MCOM Part II, SEM 4, and Roll No. 5944 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization. From 20/2/2023 to 20/3/2023 for the academic year 2022-2023.

During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavours.

Authorized Signature with Stamp

For LIFE TIME




21/03/2023

"WORK LIFE BALANCE IN AN ORGANIZATION"

***A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(BUSINESS ADMINISTRATION)***

***SUBMITTED BY
-FAIQUZ INAMUL HAQ
Roll No-5945***

***UNDER THE GUIDANCE OF
-DR.NASRIN KILAN***



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

***AKPS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2022-2023***



AB SOLUTIONS

*Kanark Indrapr Mall Office no.1219 Opposite to Suryanand
Hospital Kandhwa Main Rd Kandhwa Akhurd Pune 411048*

This is to certify that Faizul Inamul Haq of MCOM Part II, SEM 4, and Roll No.5945 of AKT's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 02/02/2023 to 01/03/2023 for the academic year 2022-23

During the training, the student was sincere, hardworking and showed a keen interest learnt. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavours.



AB SOLUTIONS
Kanark Indrapr Mall, 2nd Floor,
Office No. 1219, Opp. Suryanand
Hospital, Akhurd, SOI Bank,
Kandhwa Akhurd, Pune - 411048.

Authorized Signature with Stamp

A PROJECT REPORT SUBMITTED TO
SAYEDIRAJI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
BUSINESS ADMINISTRATION
SUBMITTED BY
NITESH DATTATRAY PANCHAL
Roll No- 5948

UNDER THE GUIDANCE OF
Dr. NASRIN PARVEZ KHAN



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

ARJUNA GROUP OF INSTITUTIONS

CAMP, PUNE

2022-2023

OFFICE ADDRESS

Office No. 2, Sector Post Heights, Near PAF Bus Depot,
Behind Shreech Garden, Kharwad Phata,
Waghodi, Pune - 412 207 Mob No. : 91 9011718227
Email : info@swarajdevelopersonline.com
Website : www.swarajdevelopersonline.com



This is to certify that **Nitesh Dattatray Panchal** of **MCOM Part II, SEM IV, and Roll No. 5946** of **AXI's Poona College of Arts, Science and Commerce** has successfully completed the internship work as per the guidelines of **Savitribai Phule Pune University** in our organization from **01/01/2023 to 01/03/2023** for the academic year **2022 to 2023**

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable. We wish him all the best in his future endeavors.

For Swaraj Developers

Proprietor
Proprietor

Authorized Signature with Stamp

*A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
BUSINESS ADMINISTRATION
SUBMITTED BY
SOURAV KAILAS GAIKWAD
Roll No- 5947*

*UNDER THE GUIDANCE OF
Dr. NASRIN PARVEZ KHAN*



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKPS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023

OFFICE ADDRESS

Office No. 4, Saiar Park Heights Near PNT Bus Depot,
Behind Shreeesh Garden, Ravenshaw Plaza,
Waghodi, Pune - 412 107 Mob No. : 91 9011713239
e-mail : info@swarajdevelopersonline.com
website : www.swarajdevelopersonline.com



This is to certify that **Saurav Kailas Galkwad** of **MCOM Part II, SEM IV,** and **Roll No. 5947** of **AKI's Poona College of Arts, Science and Commerce** has successfully completed the internship work as per the guidelines of **Savitribai Phule Pune University** in our organization from **01/01/2023 to 01/03/2023** for the academic year **2022 to 2023**

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable. We wish him all the best in his future endeavors.

For Swaraj Developers

Proprietor

Authorized Signature with Stamp

A PROJECT REPORT ON

**“A STUDY ON STRESS MANAGEMENT AMONG EMPLOYEES
AT EMSPHERE TECHNOLOGIES Pvt. Ltd.”**

SUBMITTED BY

NUZHAT ASLAM SHAREEF

UNDER THE GUIDANCE OF

DR. NASRIN KHAN

SUBMITTED TO

SAVITRIBAI PHULE PUNE UNIVERSITY

IN PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE

AWARD OF THE DEGREE OF

M.COM (BUSINESS ADMINISTRATION)



THROUGH

DEPARTMENT OF COMMERCE PG & RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023

It is to certify that Nishat Azam Shaukat of MCOM Part II, SEM II, and Roll No. 5315 of ACS's Purna College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Solentec PUNE Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish her all the best in her future endeavours.


Ravi Sonolikar
HR & Finance Manager



**A STUDY OF STRESS MANAGEMENT RELATED TO THE WORK OF
FACULTY MEMBERS IN COLLEGE
A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE**

[Business Administration]

**SUBMITTED BY
MR. MOHD UFAQUE RAFIQUE SHAIKH
Roll No-5950**

**UNDER THE GUIDANCE OF
Dr. Nasrin Parvez Khan**



**DEPARTMENT OF COMMERCE, PG AND RESEARCH CENTRE
AKS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2023-2023**



Anjuman Khairul Islam's

POONA COLLEGE OF ARTS, SCIENCE & COMMERCE



- Affiliated to Savitribai Phule Pune University, ID No. PUNASASCEED1978
- UGC - 2(f) & 12 (B) Status • DEU • FET Funded College
- Government of Maharashtra and Savitribai Phule Pune University Recognized Minority College



K. B. Hidayatullah Road, Camp,
Pune - 411001 (Mz) India



+91-20-2445 4240
2444 6318



principal@poonacollege.edu.in
www.poonacollege.edu.in



Professor Dr. Aftab Anwar Shaikh

M.Com, Ph.D (Qual. Admin.)

PRINCIPAL



+91 98220 21773

dranwarshaikh@gmail.com

TO WHOMSOEVER IT MAY CONCERN

This is to certify that MOHD UFAQUE RAFIQUE SHAIKH of MCOM part II, SEM-4, and Roll no. 5950 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 10 October 2022 to 10 February 2023 for the academic year 2022-23.

During the training, the student was sincere, hardworking and showed a keen interest to learn.

The involvement and sustained effort put in by the student is highly appreciable.

We wish him all the best in his future endeavors.

Authorized Signature with Stamp



PRINCIPAL

Poona College of Arts, Science & Commerce
Camp, Pune-411001
Principal Office

***"E-RECRUITMENT SYSTEM AT INDIA TOURS AND TRAVELS
PUNE"***

***A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE***

[Business Administration]

SUBMITTED BY

MS. TAMANNA BARKAT ALI ANSARI

Roll No-5951

UNDER THE GUIDANCE OF

Dr. Nasrin Parvez Khan



DEPARTMENT OF COMMERCE, PG AND RESEARCH CENTRE

AKT'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023



INDIA TOUR & TRAVELS^{2021/2023}

NEW SHIVAJINAGAR ST STAND, OLD MUMBAI PUNEROAD WARDIWADI PUNE 411003

Importers & Distributors: Transport

Tel: 020 6190612

Cell: 8087088646

Mob: 9175202061

26/02/2023

PROJECT COMPLETION CERTIFICATION

This is to certify that Tamanna Ansari of MCOM Part II, SEM IV, and Roll No. 5951 of AK's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization India Tour and Travels From 27th Jan to 10th Feb-2023 for the academic year 2022-2023

During the training, the student was sincere, Hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish him all the best in his future endeavours.

For INDIA TOUR & TRAVELS

Proprietor

Authorized Signature with Stamp

A PROJECT REPORT ON
IMPACT OF CUSTOMER SATISFACTION STRATEGY AT MASTER TRAVELS

SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(BUSINESS ADMINISTRATION)

SUBMITTED BY
FARAD ZAKIR SHAIKH
Roll No-5952

UNDER THE GUIDANCE OF
DR NASHIN PARVEZ KHAN



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKIS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2822-2823



Master Travels

Haj-Umrah & Air Ticket



416, New Mangawar Path, Hazrat Yez Khan Complex, Wing A/5, 2nd Floor, Pune 411011, (M.S.) India
Mobile : 9890017809 / 7068063400 Tel:- (020) 26053117 | E-mail : mastertravels_haj@yahoo.com

Ref. No.

Date :

Date: 21/03/2023

Ref no: /MT/086/23

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Ms. Farad Zakir Shaikh, Student of M. Com Final year, studying in Poona College of Arts Science & Commerce, has done the Project Work in the company on Master Travels, under the guidance of Mr. Farooque Qasim Shaikh in Master Travels. She was working on the Project from 01/01/2023 to 30/03/2023. During her Project Work, we found that she is a very Sincere Hardworking & Fully Voted to Assignment.

We wish her all the success to her Future Career.



MASTER TRAVELS

FAROOQUE QASIM SHAIKH

***"E-RECRUITMENT SYSTEM AT INDIA TOURS AND TRAVELS
PUNE"***

***A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE***

[Business Administration]

SUBMITTED BY

Mr. ANEESUL HAQUE KHAN

Roll No-5953

UNDER THE GUIDANCE OF

Dr. Nasrin Parvez Khan



DEPARTMENT OF COMMERCE, PG AND RESEARCH CENTRE

ARTS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023



INDIA TOUR & TRAVELS

NEW SHIVAJINAGAR STATION, OLD MUMBAI PORE ROAD WADDEWADI PUNE 411002

Importers & Distributors: Transport

Tel: 020 6180612

Cell: 9820088946

Mail: 9175203061

20/02/2023

PROJECT COMPLETION CERTIFICATION

This is to certify that Aneesul Haque Khan of MCOM Part II, SEM IV, and Roll No. 5953 of AK's Poona College of Arts, Science and Commerce has successfully completed the Internship work as per the guidelines of Savitribai Phule Pune University in our organization India Tour and Travels From 27th Jan to 10th Feb for the academic year 2022-2023

During the training, the student was sincere, Hardworking and showed a keen interest to learn, The involvement and sustained efforts put in by the student is highly appreciable.

We wish him all the best in his future endeavours.

For India Tour & Travels:

Proprietor

Authorized Signature with Stamp

**"EMOTIONAL INTELLIGENCE AMONGST EMPLOYEES AT P S
ENTERPRISES"**

**A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE**

(Business Administration)

SUBMITTED BY-

SINGH PAHAL SUDHEER

Roll No- 5954

**UNDER THE GUIDANCE OF
H.O.D DR. NASRIN KHAN**



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE



P S Enterprises

34, Market Yard, Pune-411037. Tel.: 020-24209499

www.ps-enterprises.co.in

17 Feb 2023

This is to certify that SINGH PAHAL SUDHEER, of MCOM Part II, SEM 4, and Roll No. 5254 of AKP's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 17 September 2022 to 17 February 2023 for the academic year 2022-23.

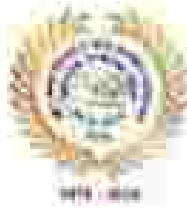
During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish her all the best in his future endeavors.

Authorized Signature with Stamp

For P. S. ENTERPRISES


PARTNER



Anjuman Khairul Islam's
**POONA COLLEGE
 OF ARTS, SCIENCE & COMMERCE**



• Affiliated to Savitribai Phule Pune University, 30 No. PUNE/MA/COM/2018
 • UGC - 20 & 12 (B) State - 1977 - 1987 Pooled College
 • Government of Maharashtra and Savitribai Phule Pune University Recognized
 Minority College



📍 K. B. Nisarullah Road, Camp,
 Pune - 411001 (M.S.)

📞 +91-20-2648 6282
 2648 6218

✉️ principal@poonacollege.ac.in
 www.pcoaccollege.edu.in

Professor Dr. Attab Anwar Shaikh
 M.Com, Ph.D (Dist. Arns)
 PRINCIPAL

📞 +91 90280 21270
 dratarwarshaikh@gmail.com

PROJECT COMPLETION CERTIFICATE

This is to certify that the project report entitled "A Study of Work Culture and Work Ethics at Tredlink Network Pvt.Ltd"

in the subject Business Administration was prepared by Azra Miris Shaikh Class M.COM -II (SEM- II) Roll No 2552 for the academic year 2021-2022 under my guidance and supervision. This project report is based on original study work carried out by him such material as has been obtained from other sources has been duly acknowledged in the report. This project is submitted in partial fulfillment of requirement of the Master of Commerce and project work as per the Rules of Savitribai Phule Pune University.

Project Guide:
Dr. Nasrin Khan

HOD
Dr. Nasrin Khan
 Department of commerce

Exam Seat No. 20415

Date of Exam

External Examiner

Internal Examiner



**Treelink Network
Private Limited**

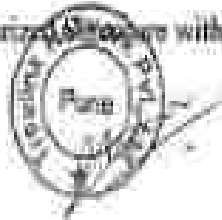
100, MIDC ROAD,
PUNE-411 004

REGD. OFFICE: MIDC ROAD, PUNE-411 004

REGD. OFFICE: MIDC ROAD, PUNE-411 004

This is to certify that Azim Idris Shaikh of MCOM Part II, SEM 4, and Roll No.5955 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 02/02/2023 to 01/03/2023 for the academic year 2022-23. During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement and sustained efforts put in by the student are highly appreciable. We wish him all the best in his future endeavors.

Authorized Signature with Stamp



A Study on Talent Sourcing and Acquisition

At

"TVS Logistics Services Limited."

A PROJECT REPORT SUBMITTED TO
SANTRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(Business Administration)

SUBMITTED BY

Mr. Abdul Waqid Khan

Roll No- 0801, M.Com II, Sem-IV

UNDER THE GUIDANCE OF

Dr. Narsin Parvat Khan



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE
ARTS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023



TVS Logistics Services Limited

Date: 08/06/2023

TO WHOMSOEVER IT MAY CONCERN: INTERNSHIP LETTER

This is to certify that **Abdul Waheed Khan** has successfully completed internship as "Trainee" under the assistance and guidance in connection with his Industrial Training at TVS Logistics Services Limited.

The details of the internship are as follows:

- Internship Position: Trainee
- Duration: 04/01/2023 to 03/06/2023

He was found sincere and hardworking during his tenure.
We wish him all the best for his future endeavors.

Regards,
TVS Logistics Services Ltd.

A handwritten signature in black ink, appearing to be a stylized 'V' or similar character, written over a faint, illegible stamp or text.

TVS Logistics Services Limited, Chakan, Mahabunge Indgate, Maharashtra 410501

A PROJECT REPORT ON
**"A STUDY OF WORK LIFE BALANCE OF EMPLOYEES AT DIGITAL
CONVERGENCE TECHNOLOGIES PVT. LTD"**

SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(BUSINESS ADMINISTRATION)

SUBMITTED BY
MOHAMMED RIYADH
Roll No-5961

UNDER THE GUIDANCE OF
DR NASRIN PARVEZ KHAN



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKT'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

CAMP, PUNE

2022-2023

20th May 2023

TO WHOM SO EVER IT MAY CONCERN

This is to certify that **MOHAMMED RIYADH** of MCOM Part II, SEM (IV), Roll No. S961 of AXI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 15th April to 1st May 2023 for the academic year 2022-23.

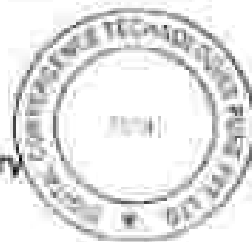
During the training, the student was sincere, hardworking, and showed keen interest to learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavours.

For Digital Convergence Technologies Pune Pvt Ltd



Authorised Signatory



g o d i g i t a l

A PROJECT REPORT ON
**HR CHALLENGES EMPLOYING GENERATION AT ACE VOYAGES
INTERNATIONAL PVT LTD**

SUBMITTED TO
SAYTRIDAI PHULE PUNE UNIVERSITY
**IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE**

(BUSINESS ADMINISTRATION)

SUBMITTED BY
AFREEN ANWAR MEMON

Roll No-5962

UNDER THE GUIDANCE OF
DR NASRIN PARVEZ KHAN



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE



YAGES

ACEVOYAGES INTERNATIONAL PVT. LTD.

INTERNSHIP CERTIFICATE

This is to certify that ARSHITH ANAND MEMON of M COM part II, SEM A, and Roll No 5952 of AKYA Hopes College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish him all the best in his future endeavours.



Author _____ Date _____



- Office No.117, 1st Floor, B-Wing, Piche Sireni Plaza, Convent Street Road, Beale District and Temple Post-411011.
- Info@acevoyagesinternational.com
- www.acevoyagesinternational.com
- +919724600 / 987574185

A STUDY ON TRAINING AND DEVELOPMENT

At

“Direct B2B Media Enterprises.”

**A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(Business Administration)**

SUBMITTED BY

***Ms. Mohsina Mehmood Mujawar
Roll No- 5964, M.Com-II, Sem-IV***

UNDER THE GUIDANCE OF

Dr. Navrin Parvez Khan



**DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE
ARI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2022-2023**



To Whom It May Concern

This is to certify that Ms. Mohsina Mehmood Mujawar of MCOM Part II, SEM 4, and Roll No. 5964 of AKU's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 27th January to 10th February for the academic year 2022-23.

During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish her all the best in her future endeavors.

For:

Direct B2B Media Enterprises

Jasmine Shaikh

Jasmine Shaikh
Chief Executive Officer (CEO)

A PROJECT REPORT ON
TRAINING & DEVELOPMENT AT SUNRISE INSTRUMENTS PVT. LTD.
SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY
IN THE PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTER OF COMMERCE
(BUSINESS ADMINISTRATION)
SUBMITTED BY
FIRDOUS ABDULGAFUR SHAIKH
Roll No-5966

UNDER THE GUIDANCE OF
DR NASRIN FARVEZ KHAN



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE
AKTS POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2022-2023



SUNRISE INSTRUMENTS PVT. LTD.

"Sunrise House" Dr. No. 33/1 and Dr. No.37/1 to 4/1, Near Harsh Agro Pipes,

Til- Harvel, Phale, Pune - 411048, Mob. no. 9889955705

Web Site : www.sunriseinstrument.com Email : info@sunrise.com

Powered by
Solutions

Ref. No.:

Date:
06-01-2021

INTERNSHIP CERTIFICATE

This is to certify that Shaikh Firdous AbdulGafur of MCOM Part II, SEM 4, and Roll No. 5966 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student is highly appreciable.

We wish her all the best in his future endeavours.

Authorized Signature with Stamp



**"A STUDY ON EMOTIONAL INTELLIGENCE AMONGST FEMALE
EMPLOYEES WITH SPECIAL REFERENCE TO XDBS PRIVATE LIMITED,
PUNE"**

***A PROJECT REPORT SUBMITTED TO
SAVITRIBAI PHULE PUNE UNIVERSITY***

***IN PARTIAL FULFILLMENT OF THE REQUIREMENT FOR THE
DEGREE OF MASTERS OF COMMERCE
(BUSINESS ADMINISTRATION)***

***SUBMITTED BY
RAVEENA BASANTANI
ROLL NO- 5967***

***UNDER THE GUIDANCE OF
DR. NASRIN KHAN***



DEPARTMENT OF COMMERCE PG AND RESEARCH CENTRE

***ART'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
CAMP, PUNE
2022-2023***



Date: 10/03/2023

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Ravneeta Bhanuzal of M.COM Part II, SEM 4, and Roll No. 3967 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization.

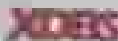
During the training, the student was sincere, hardworking and showed her keen interests learn. The involvement and sustained efforts put in by the student are highly appreciable.

The duration of the internship was from 01/01/2023 to 10/03/2023.

We wish her all the best in her future endeavours.



Authorized Signature
(Pooja Bhat, Marketing Manager)



To,

The Principal
Poona College of Arts Commerce & Science,
Camp, Pune-411001.

Subject : Internship Completion Certificate.

Dear Madam / Sir,

I am happy to inform you that following student of your College have successfully completed the "Sixty Hours Internship Programme" in this Organisation.

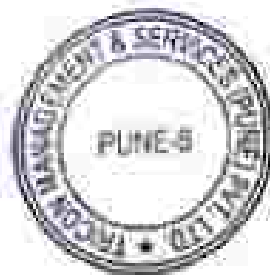
SR. NO.	NAME OF STUDENT	ROLL NO.	AADHAR NO.	SPECIAL SUBJECT
1.	Pratik Ramesh Dhawale	4878	7505 7567 7533	Banking & Finance

This student have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that this student will perform effectively in similar type of organizations.

I wish him every success in future endeavors.

Thank you,



Sincerely,

(Rajesh H. Thakur)
Director.

Regd. & Head Off.: 6/44, Phule Nagar, Nr. New B.T.O. Office, Alandi Road, Pune - 411006.
Cell : 9011039239 / 9011038915 / 9011038907 | E-mail: tricmanagement@rediffmail.com

BRANCH OFFICES

Pune | Satara | Sangli | Kolhapur | Raichur | Shivajinagar | Solapur | Goa | Gubarga | Hubli | Hyderabad City

Country Club Hospitality & Holidays Limited

Koteguan Park Lane II/2, Near Rajyoti Society, Near G. Hotel, Pune Pin 411003.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
AKIS's Purna College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate.

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programmed' in this organization.

Sr.No.	Name of the student	Roll No.	Aadhar Card No.	Special Subject
1.	Khan Ruhida AUF	4834	298927655772	Banking and Finance -I & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I am confident that these students will perform effectively in similar type of associates.

I wish them every success in future endeavors.

Thank you.

Sincerely,

(AUTHORIZED SIGNATORY)

EXCELLENT ENTERPRISES

Commerce Zone IT Park, Vaswada, Pune- 411006
Ph: (020) 64052378 Email: excellententerprises@gmail.com

INTERNSHIP COMPLETION CERTIFICATE

To,

The Principal,

Poona College of Arts, Science & Commerce,
Camp, Pune-411001

Subject: Internship Completion Certificate —

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shresh Gulya Mihir Patil	4800	7200 3612 6480	Banking & Finance II & III
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Excellent Enterprises

Sincerely,

Rohini Dashparde
Name & Signature

(Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
P. G. D. College,
P. G. D. (Place)

Subject: Internship Completion Certificate ---

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Sajjan Sheikh	4829	5440	Banking & Fin
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Reshmi
Name & Signature (Authorised Signatory)

Sincerely,

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider Organisation

To,
The Principal,
----- College,
----- (Place)

Subject: Internship Completion Certificate -----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Rafiq Vard	487		Arts
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you



Stamp of the company

Sincerely,

Name & Signature (Authorized Signatory)

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,
The Principal,
..... College,
..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Sohana Khirchi	4919	46945148 3052	Banking and Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

STATE BANK OF INDIA
The State Bank of India
Head Office, New Delhi
110 001

Sincerely,

Name & Signature
(Authorised Signatory)

Letter Head of the Internship Provider
Organisation

To,
The Principal,
Bansa College,
Panshet (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Rubeshwar Shastri	1936	9417738	Banking & Finance
2.			6217	
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



[Signature]
MANAGER
Kandhwa Branch

Sincerely,

Name & Signature
(Authorized Signatory)



INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,

The Principal,
..... College,
..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

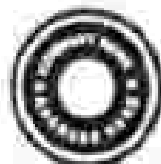
Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Arjun Mishra	11881	582360280	Banking & Finance - IT
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,
.....
AD. RAJESH SHARMA
ADMIN. OFFICER
Name & Signature
(Authorised Signatory)
..... CO-OP BANK
AD. OFFICE

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider Organisation

To,
The Principal,
Peeria College,
Surat (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Rigatunisa Khan	4890	3763274035	Banking & Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,
[Signature]
MD. RAFIQUE SHAMKH
ADMINISTRATIVE
Name & Signature
(Authorised Signatory)

THE MUSLIM CO-OP
ADM
OFFICE

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,

The Principal,
 College,
 (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Mohamud Sheikh	4252	57963249304	Banking and Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

MD. FARUQUE SHAMM
ADMINISTRATIVE SIGNATURE

(Authorised Signatory)



INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,

The Principal,
Lours College,
Lours (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Tehseen Shauka	4583	4321558512	Banking & Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



[Signature]
MD. RAFIQUE THAMH
ADMIN OFFICER

Name & Signature

(Authorised Signatory)



Letter Head of the Internship Provider Organisation

To,
The Principal,
PMS Pimpri College,
Pimpri (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Teacher No.	Special Subject
1.	Hafizul Sahin	4903		Banking & Finance II & III
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you

Stamp: MOUJLA ALI & COMPANY
M. No.: 138699
PUNE
411005
Stamp

Signature: Hafizul Sahin
Name & Company: Hafizul Sahin Danti
Stamp: MOUJLA ALI & COMPANY
M. No.: 138699
PUNE
411005
Authorized Signatory

Sincerely,

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider Organisation

To,

The Principal,
Senna College,
Sena (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Sudhikahidas Durbaraj	4825	102915502143	Marketing and Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,
 MD. RAHIMU SHAKH
 ADMIN OFFICER
 Name & Signature

(Authorised Signatory)



INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,
The Principal,
Feroze College,
Feroze (Place)

Subject: Internship Completion Certificate: _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Maaz Khan	4250		Banking & Finance
2.	Saad Khan	4807		Banking & Finance
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature
(Authorized Signatory)

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To:

The Principal,
...ESHA... College,
...PUR... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Rasul Raig	4233	4264-000-2355	Banking and Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you



Secretary,
Fazal Khan

Name & Signature
(Authorised Signatory)

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Letter Head of the Internship Provider Organisation

1. Name of the Student : KHAN MISBA
2. Name of the College : T.Y.B.Com.
3. Division and Roll Number : 'A' 4879
4. Address : 9272, New Modikhana, Camp, Pune.
5. Contact Number : 9766939056
6. Email ID : khanmisbah119@gmail.com
7. Special Subject : Banking & Finance II SEM
8. Internship start date : 05th Dec, 2022
9. Internship end date : 15th Dec, 2022

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Date	Time		Total Hours	Details of work done	Signature of officer	Signature of student
	From	To				
05/12/22	12:PM	6:PM	6 hr	Passing Journal Entries	<u>[Signature]</u>	<u>Misbah</u>
06/12/22	12:10PM	6:PM	6 hr	Passing Journal Entries	<u>[Signature]</u>	<u>Misbah</u>
07/12/22	12:PM	6:PM	6 hr	Preparing Profit & Loss	<u>[Signature]</u>	<u>Misbah</u>
08/12/22	12:PM	6:PM	6 hr	Preparing Profit & Loss	<u>[Signature]</u>	<u>Misbah</u>
09/12/22	12:PM	6:PM	6 hr	Tally Balance Sheet		<u>Misbah</u>
10/12/22	12:PM	6:PM	6 hr	Tally Balance Sheet		<u>Misbah</u>
11/12/22	12:PM	6:PM	6 hr	Learn Petty Cash Book		<u>Misbah</u>
12/12/22	12:PM	6:PM	6 hr	Learn GST concepts		<u>Misbah</u>
13/12/22	12:PM	6:PM	6 hr	Filing GST		<u>Misbah</u>
15/12/22	12:PM	6:PM	6 hr	Filing GST		<u>Misbah</u>

Letter Head of the Internship Provider Organisation

To,
The Principal,
..... College,
..... (Place)

Subject: Internship Completion Certificate —

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Kalim Shaikh			
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you!

Sincerely,

Name & Signature (Authorised Signatory)

Kalim Shaikh



Letter Head of the Internship Provider Organisation

To:

The Principal,
Road _____ College,
Post _____ (Place)

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Kiran Gujjar	4905	430912424	Banking and Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature (Authorised Signatory)

Stamp of the company



INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,
The Principal,
----- College,
Pune (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shiraf Ghatge	11021	83796157301	
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

For ALPIN TRADERS

Proprietor



Sincerely,

Name & Signature
(Authorised Signatory)

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider Organisation

To,
The Principal,
Green Hill College,
..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shaikh Anwar	4912	6901-3075	Banking &
2.	Najmuddin		4027	Finance
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Chanda Education
Hong Kong
Dean Gym
Mobile - 9700000000



Sincerely,
Fazal Khan
Name & Signature
(Authorised Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
..... College,
..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	ADNAN SAYAD			
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature (Authorized Signatory)
ADNAN SAYAD



HAYAT MEDICAL
EAST SIDE SHOP, GR. FL.,
SR. NO. 12B/12A/12A/17B, PLOT NO. 54,
GOLF CLUB ROAD, TERRADA,
PUNE-411005.

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,
The Principal,
_____ College,
Pune (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Moin Shailch	4923	3896195	
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

for ALPIN TRADERS





Sincerely,

Name & Signature
(Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,
 The Principal,
 College,
 (Place)

Subject: Internship Completion Certificate -----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

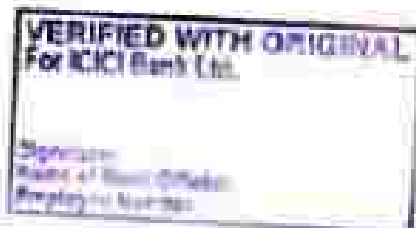
Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Anshu Kati	4910	96751075 2219	Banking Finance
2.				IT & ITII
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature
 (Authorised Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
A.P.S. College,
[Place]

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Khan Anam Mulla	4242		Banking 'I' & 'II'
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Barham Computer Private Limited
Flat No. 103, 9/15, Ghanshi P.O.,
Pune - 411007. Tel: 22250044
22240042 / 22251116
www.barham.com

Stamp of the company

Sincerely,

Name & Signature (Authorised Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
----- College,
----- (Place)

Subject: Internship Completion Certificate -----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Mustafa S. Moinby	4904		
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.


Saswara Creations Tailoring Hub

Sincerely,

Name & Signature (Authorised Signatory)

Stamp of the company

Letter Head of the Internship Provider Organisation
Prathamesh Nagari Pathasurabha Bank

To,
The Principal,
POONA College,
KOLYAJ (Place)

Subject: Internship Completion Certificate ----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	<u>Fatima Bagwan</u>	<u>4897</u>	<u>7567-</u>	<u>Baking of finance</u>
2.			<u>4826-</u>	<u>II & III</u>
3.			<u>8229</u>	
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.



Stamp of the company

[Signature]
Secretary,

Name & Signature (Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
Al-Farooq College,
Dera (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Azfar Shauk	4801		Banking Finance I & II
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you

Sincerely,

M Kashif
Name & Signature (Authorized Signatory)
NAME: MAJED KACHNE

SEKAR & SETHI'S
56, Park Road, New Chak, Lahore
A Public Company

*

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,

The Principal,

----- College,

----- (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aana Shaikh	4812		Banking & finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

For ALFIN TRADERS

Proprietor



Sincerely,

Name & Signature
(Authorised Signatory)

Letter Head of the Internship Provider Organisation

To,
 The Principal,
100183 College,
Uthirakottai (Place)

Subject: Internship Completion Certificate -----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aarav Prakash	4389	64060704329	Banking / Finance - 240
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.




 Name & Signature (Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
AKI'S COLLEGE,
PUNE (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shaikh Zoya	4828	256224813469	Banking & Finance
2.				II & III
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Stamp of the company

Sincerely,
Name & Signature (Authorized Signatory)
Name: Majid Kachlu

X

Letter Head of the Internship Provider Organisation

To,
The Principal,
P.V.S. Pooja's College,
P.V.P.O. (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	zeenat shahin	4806	752126570	BANKING & finance II & III
2.			73	
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Stamp of the company

Sincerely,

Name & Signature (Authorised Signatory)

**Letter: Head of the Internship Provider
Organisation**

To:
The Principal,
POONA COLLEGE OF ARTS, SCIENCE AND COMMERCE College,
CAMB PUNE

Subject: Internship Completion Certificate

Dear Madam / Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Adm No. / ID	Special Subject
1.	NISHAB SINGH RAYED	4001	010627182170	BANKING AND FINANCE
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,


TANMAY DAS
Name & Signature



Letter Head of the Internship Provider Organisation

To,
The Principal,
Akh's poona College,
Pune (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Zaid anari	4872	434363889568	Banking & finance 2 & 3
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



[Signature]
Name & Signature (Authorized Signatory)

Sincerely,

Letter Head of the Internship Provider Organisation

To,
The Principal,
..... College,
..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Sajyed Anam Ashun	4826	6193 4149 6157	Banking & finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Chandan Collection
Hong Kong Lane, Shop No:14/15,
Deccan Gymkhana, Pune-411004,
Mobile - 9422078777

Sincerely,

Name & Signature (Authorized Signatory)

Chandan

Stamp of the company

Letter Head of the Internship Provider Organisation

To,
The Principal,
AKI Poona College of Arts, Commerce & Science,
Pune

Subject: Internship Completion Certificate .

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	SONDE RIHAN RIYAZ	4974	612824608776	Banking and Finance II & III
2.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,


 Name & Signature
 (Authorised Signatory)

Sajid Buraiya

Letter Head of the Internship Provider Organisation

To:

The Principal,
 A. K. P. College,
 _____ (Place)

Subject: Internship Completion Certificate —

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.


Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	_____	4804		Banking Finance II & III
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

 Name & Signature (Authorized Signatory)
 Name: MAJID KACHHI

Stamp of the company



Dear Madam/ Sir,
 Please provide your valuable feedback about the performance of the student on following parameters. Your feedback will enable us to make necessary changes in the Internship process.
 Thank you.
 Coordinator- Internship Programme

Internship Programme feedback form

Sr. No.	Particulars	Date
1)	Name of the Supervisor/ Officer	Shahid Sultan Trade
2)	Department	
3)	Designation	Branch- Manager
4)	Name of the Student	Shahid Mohammed Zishan Riyaz
5)	Name of the College	AGI's Poona College of Arts, Commerce and Science
6)	Roll Number	2014
7)	Special Subject	Banking & Finance II & III

Part - A - Individual Ranking (Please tick the suitable checkbox)

No.	Parameter for feedback	Excellent	Very Good	Good	Satisfactory	Needs Improvement
1)	Domain Knowledge			<input checked="" type="checkbox"/>	<input type="checkbox"/>	
2)	Communication Skills			<input type="checkbox"/>	<input checked="" type="checkbox"/>	
3)	Punctuality & Dedication			<input checked="" type="checkbox"/>		
4)	Ability to work in teams			<input checked="" type="checkbox"/>		
5)	Problem solving skills			<input checked="" type="checkbox"/>		
6)	Quality of work done				<input checked="" type="checkbox"/>	
7)	Effectiveness			<input checked="" type="checkbox"/>		
8)	Efficiency			<input checked="" type="checkbox"/>		
9)	Ability to take initiative			<input checked="" type="checkbox"/>		
10)	Positive attitude		<input checked="" type="checkbox"/>			
11)	Appearance		<input checked="" type="checkbox"/>			
12)	Using full potential at work			<input checked="" type="checkbox"/>		
13)	Work habits			<input checked="" type="checkbox"/>		
14)	Honesty & Integrity		<input checked="" type="checkbox"/>			
15)	Creativity			<input checked="" type="checkbox"/>		


 AGI'S POONA COLLEGE OF ARTS, COMMERCE AND SCIENCE
 PUNE - 411 004
 CONTACT - 020-26123456

Letter Head of the Internship Provider Organisation

To,
 The Principal,
 Ch. VETPA College,
 Gandhinagar (Place)

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Prashant C. Chavhan	4815		Banking & Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.




 Name & Signature (Authorized Signatory)

Sincerely,

Roopchand Khandelwal & Co.

A-111/A-112, Kalpataru Plaza, 1st Floor, 224 Bhawani Peth,

To,
The Principal,
AKI'S Poona College of Arts, Science and Commerce College,
Pune (Place)

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Gayatri Shinde	4957	NO196554 4455	Banking & Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you

Sincerely,

Name & Signature (Authorized Signatory)

Stamp of the company



@Khandelwal

Letter Head of the Internship Provider Organisation

To,

AKT) The Principal,
Panna College,
Pune (Place)

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	ANMAN KACHHI	4813	51534799 5227	Banking & Finance II & III
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.




 Sincerely,
 Name & Signature (Authorized Signatory)
 Name: MATID KACHHI.

Letter Head of the Internship Provider Organisation

To,
The Principal,
PMS, BSNL College,
Pune (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Venkatesh.	4817	5399087	Banking & Finance II & III
2.	Asmagan		36998	
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Stamp of the company

Sincerely,

Name & Signature (Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,

The Principal,
Akl. Feana College,
Pune..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aayasha Mulla	4219	681569858548	Banking and Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



[Handwritten Signature]
Sincerely,
Name & Signature (Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
MHI DOORJA College,
DOTE (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Huson Saipal	HSH		Banking & Finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Stamp of the company

[Handwritten signature]

Sincerely,

Name & Signature (Authorized Signatory)

Sandhya Nair
[Handwritten signature]

Letter Head of the Internship Provider Organisation

To,
The Principal,
AKS College,
(Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Monika Agarwal	4843	9955 9246 5056	Banking + Finance
2.				IT & III
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Digital Computer Private Limited
Flat No. 103, 401, Bhawan Peth,
Pune - 411002, Tel: 25351111
20247957 / 7

Sincerely,

Name & Signature (Authorised Signatory)



Stamp of the company

Letter Head of the Internship Provider Organisation

To,
 The Principal,
 PCCO College,
 PUNE (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	shaikh Arif	4835	8728	Banking finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Stamp of the company

Setna

Sincerely,

Name & Signature (Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
Davies College,
Pune (Place)

Subject: Internship Completion Certificate -----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	<u>Arshif Rezwani</u>	<u>4853</u>	<u>1942</u>	<u>Banking & Finance</u>
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature (Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
AKI'S Poona College of Arts, Science and Commerce,
Pune.

Subject: Internship Completion Certificate.

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Sayyed Naved Ayub	4810	7531 0893 0391	Banking & Finance II&III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature (Authorized Signatory)

Arshad Raza

Stamp of the company

GLOBAL BAKERS
S NO 45 BHAGYDAM NAGAR,
11/1 NEHRA KUNRD, PUNE 48

Letter Head of the Internship Provider Organisation

To,
The Principal,
AKI Poona College,
Pune (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Tasmija Tamboli	4869	33544780 0874453 8789	Banking & Finance
2.				IT & IIL
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

M. Kachhe
Name & Signature (Authorised Signatory)
Name: MAJID KACHHE

ABASHITE - All the
things you need for your business
from the company

Letter Head of the Internship Provider Organisation

To,
The Principal,
..... College,
..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Siddhant Anand	401		banking & finance
2.	Siddhant Anand	401		banking & finance
3.	Siddhant Anand	401		banking & finance
4.	Siddhant Anand	401		-
5.	Anand	401		-
6.	Anand	401		-
7.	Anand	401		-
8.	Anand	401		-

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

For S. N. TRADER

Proprietor

Sincerely,
Name & Signature (Authorised Signatory)

Stamp of the company

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Letter Head of the Internship Provider Organisation

1. Name of the Student : Sayyed Afya Sanam
2. Name of the College : T.Y.B.Com.
3. Division and Roll Number : [A] 4832
4. Address : 370/1728 Babajan Nagar near agurum,
colony camp pune 411001
5. Contact Number : 9675260466
6. Email ID : Sayyedafya2002@gmail.com
7. Special Subject : Banking II & III
8. Internship start date : 05th December, 2022
9. Internship end date : 24th December, 2022

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Date	Time		Total hours	Details of work done	Signature of officer	Signature of student
	From	To				
05/12/22	12 pm	6 pm	4 hrs	Tally BRS 9	Machhi	Afya
to	12 pm	6 pm	9 hrs	ITR	Machhi	Afya
24/12/22	12 pm	6 pm	11 hrs	Boc work	Machhi	Afya
				Bank Reconciliation stat	Machhi	Afya

Date	Time		Total Hours	Details of work done	Signature of officer	Signature of student
	From	To				
5/2/22	10 am	6 pm	9 hrs	Introduction of Tally	M Kashli	Alga
6/2/22	10 am	6 pm	9 hrs	How to open P. Case	M Kashli	Alga
7/2/22	10 am	6 pm	9 hrs	Tally checked by	M Kashli	Alga
8/2/22	10 am	6 pm	9 hrs	Tally ERP 9.	M Kashli	Alga
9/2/22	10 am	6 pm	9 hrs	ROC walk.	M Kashli	Alga
10/2/22	10 am	6 pm	9 hrs	Bank Reconciliation	M Kashli	Alga
11/2/22	10 am	6 pm	9 hrs	Basic Account how	M Kashli	Alga
12/2/22	10 am	6 pm	9 hrs	To Register ROC.	M Kashli	Alga
13/2/22	10 am	6 pm	9 hrs	What document	M Kashli	Alga
14/2/22	10 am	6 pm	9 hrs	forgoten How to	M Kashli	Alga
15/2/22	10 am	6 pm	9 hrs	Register	M Kashli	Alga
Total Hours						

Certified that Alga Saggad (name of the student) has satisfactorily completed the internship programme assigned to him.

Name & Signature of supervisor: _____
 Name & signature of manager: _____
 Name & signature of section in charge: _____

Date: _____

NARASHTE MS
 H. Hathi Path, Near Chaudhary
 - 411002
 Stamp of the company
 M Kashli

FEEDBACK FROM INTERNSHIP PROVIDER ORGANISATION

Dear Madam/ Sir,

Please provide your valuable feedback about the performance of the student on following parameters. Your feedback will enable us to make necessary changes in the internship process. Thank you.

Coordinator- Internship Programmes

Internship Programme feedback form

Sr. No.	Particulars	Details
1)	Name of the Supervisory Officer	
2)	Department	
3)	Designation	
4)	Name of the Student	Sache Abiza
5)	Name of the College	Poona College
6)	Roll Number	4888
7)	Special Subject	Banking & finance

Part - A - Individual Ranking (Please tick the suitable checkbox)

No.	Parameter for feedback	Excellent	Very Good	Good	Satisfactory	Needs improvement
1)	Domain Knowledge	✓				
2)	Communication Skills		✓			
3)	Punctuality & Dedication	✓	✓			
4)	Ability to work in teams		✓			
5)	Problem solving skills		✓			
6)	Quality of work done		✓			
7)	Effectiveness		✓			
8)	Efficiency		✓			
9)	Ability to take initiative		✓			
10)	Positive attitude		✓			
11)	Appearance		✓			
12)	Using full potential at work		✓			
13)	Work habits		✓			
14)	Honesty & Integrity	✓	✓			

**Letter Head of the Internship Provider
Organisation**

1. Name of the Student : Ahmad Shakh
2. Name of the College : J.Y.B. College
3. Division and Roll Number : BSIS-B-1A
4. Address : Lakshmi Nagar
Yeravada Pune
5. Contact Number : 756548255
6. Email ID : ahmadshakh2003@gmail.com
7. Special Subject : banking and
finance
8. Internship start date : 1/03/2023
9. Internship end date : 12/03/2023

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Date	Time		Total Hours	Details of work done	Signature of Supervisor	Signature of Student
	From	To				
1/03/2023	2:00pm	11:00pm	9	Payroll team interaction	<i>Ahmad Shakh</i>	<i>Ahmad Shakh</i>
2/03/2023	2:00pm	11:00pm	9	Analysis of accounting data of the company	<i>Ahmad Shakh</i>	<i>Ahmad Shakh</i>
3/03/2023	2:00pm	11:00pm	9	Calculating the employee login hours	<i>Ahmad Shakh</i>	<i>Ahmad Shakh</i>
4/03/2023	2:00pm	11:00pm	9	Analysis of how to maintain employee data	<i>Ahmad Shakh</i>	<i>Ahmad Shakh</i>
5/03/2023	2:00pm	11:00pm	9	Training for refund process	<i>Ahmad Shakh</i>	<i>Ahmad Shakh</i>
6/03/2023	2:00pm	11:00pm	9	Training preparing salary sheet for employee	<i>Ahmad Shakh</i>	<i>Ahmad Shakh</i>
7/03/2023	2:00pm	11:00pm	9	Processing refund for customer	<i>Ahmad Shakh</i>	<i>Ahmad Shakh</i>
8/03/2023	2:00pm	11:00pm	9	Processing sodexo refund	<i>Ahmad Shakh</i>	<i>Ahmad Shakh</i>

Certified that Pushendra lakhami kushwah,, has satisfactorily completed the internship programme assigned to him,

Name & Signature of
supervisor

Name & signature
of manager

Name & signature of
section in charge



Date :

A handwritten signature in black ink is written over a circular blue stamp. The stamp contains the text "PUSHENDRA LAKHAMI KUSHWAH" around the perimeter and "10" in the center. The signature is a stylized, cursive representation of the name.

Certified that Alimul Haq, has satisfactorily completed the internship programme assigned to him.

Name & Signature of
Supervisor

Date:

[Handwritten Signature]

Name & Signature of
manager

Madhura Khosla

Name & Signature of
Section in charge

[Handwritten Signature]



Letter Head of the Internship Provider Organisation

To,
 The Principal,
 _____ College,
 _____ (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aman Gaur Mohan	4918	28899917 1948	Banking and Finance (A. Audit)
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature (Authorised Signatory)



For Years Enterprise

 Proprietor
 Stamp of the company

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Letter Head of the Internship Provider Organisation

1. Name of the Student : NARSHI NIDHARAJ BUISO
2. Name of the College : T.Y.B.Com.
3. Division and Roll Number : 'A' 4884
4. Address : Karami Nagar, Kharvela
5. Contact Number : 8208842553
6. Email ID : narshibuiso09@gmail.com
7. Special Subject :
8. Internship start date :
9. Internship end date :

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Date	Time		Total Hours	Details of work done	Signature of officer	Signature of students
	From	To				
					<i>[Signature]</i>	<i>[Signature]</i>
					<i>[Signature]</i>	<i>[Signature]</i>
					<i>[Signature]</i>	<i>[Signature]</i>
					<i>[Signature]</i>	<i>[Signature]</i>
					<i>[Signature]</i>	<i>[Signature]</i>

Date	Time		Total Hours	Details of work done	Signature of officer	Signature of student
	From	To				
Total Hours						

Certified that _____ (Name of the student) has satisfactorily completed the internship programme assigned to him.

Name & Signature of supervisor

Name & signature of manager

Name & signature of section in charge



Stamp of the company

Date:

28/11/2020
ASIF Pathan



M/S SHRINIWAS KADBANE & ASSOCIATES
CHARTERED ACCOUNTANTS

The No. 02 A, 'C' Wing, Ashwin Paradise Society,
Bhamburda, Pune-411037.

Contact No. - 999378129

Email: kadbaneshrinivas@gmail.com

INTERNSHIP COMPLETION CERTIFICATE

DA: 13-01-2023

To,
The Principal,
Poona College of Arts, Science & Commerce
Camp, Pune - 411001.

Subject: Internship Completion Certificate.

Dear Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Saud Sayeed Lambe	4836		Banking and Finance II & III

These students have been provided with adequate exposure and necessary hands- on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you. Shrinivas Kadbane & Associates
Chartered Accountants

(CA Shrinivas S. Kadbane)
Proprietor
M. No. 611147



1. Name of the Student : Dilani Kallal Tanaji
2. Name of the College : Poona College Arts Science & Commerce
3. Division and Roll Number : A (4845)
4. Address : Sr. No 46/34, dattarajgar ambegian telco colony lane no 7
5. Contact Number : 9503437134
6. Email ID : kallandilani2859@gmail.com
7. Special Subject : Banking & Finance
8. Internship start date : 23rd January 2023
9. Internship end date : 3rd February 2023

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Date	Time		Total Hours	Details of work done	Signature of officer	Signature of student
	From	To				
23-01-23	11:00	2:00	3	Basic Training		<i>[Signature]</i>
24-01-23	11:00	2:00	3	Basic Training		<i>[Signature]</i>
25-01-23	10:00	2:00	4	TDNY		<i>[Signature]</i>
26-01-23	10:00	4:00	6	Ms Excel		<i>[Signature]</i>
27-01-23	10:00	3:00	5	Basic training		<i>[Signature]</i>

28-01-23	10:00	3:00	5	ENDING OF RETURNS	Kaalia
30-01-23	10:00	4:00	6	BANK AUDIT	Kaalia
31-01-23	10:00	4:00	8	BANK AUDIT	Kaalia
1-02-23	10:00	5:00	10	BANK AUDIT	Kaalia
02-02-23	10:00	3:00	6	ENDING OF RETURNS	Kaalia
03-02-23	10:00	3:00	5	ENDING OF RETURNS	Kaalia

Certified that Dikara Kaalia Tani has satisfactorily completed the internship programme assigned to him.

(Signature)

CA. Sarvesh Mehendale
 Name & Signature of
 Supervisor

Name & Signature of
 Manager



Stamp of the Company

Date: 03-02-2023



BANDARKAR & CO

Chartered Accountants

Abdus samad A S Bandarkar
ACA, M.Com (FRN. 152474W)

To,
The Principal,
AKI's POONA COLLEGE OF ARTS, SCIENCE AND COMMERCE,
Pune-411 001.

Subject: Internship Completion Certificate.

Dear Madam/ Sir,

I am happy to inform you that Mr. AVEES M SALEH MULLA, having Roll No: 4830, Adhaar No: 2781 8475 5791 and special subject: Banking and Finance, a student of your college has successfully completed the 'Sixty Hours Internship Programme' in this organisation.

The student has been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that this student will perform effectively in similar type of organisations.

I wish them every success in future endeavours.

Thank you.

Sincerely,



CA. Abdus samad A. S. Bandarkar
(Proprietor)
Date: 01/05/2023
Place: Pune

Address: Office No. F-4, Royal Plaza, 2122, Sardar V P Road, Opp. Thacker Apartment,
Camp, Pune 411 001.
Email: ca.abdusamad@bandarkar.in
Phone: +91 78756 34622



**STEAM
Equipments**

An ISO 9001 : 2015 Certified Company
CIN: U29119PN2004PTCO19820

Steam Equipments Pvt Ltd

No-44, Toy Co-Op, Industrial Estate,
Kandhwa Road, Pune - 411048,
Phone: 020-26030968, 26030951
Email: sales@steamequipments.com
http://www.steamequipments.com

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
AKI Poona College of Arts Commerce and Science,
Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aschar No.	Special Subject
1.	Sufiyan Irfan Galsulakr	4902	B140 2234 2065	Banking and Finance II&III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature (Authorised Signatory)



Stamp of the company

- Steam & Water Analysis system (SWAS)
- Shelter manufacturer (Safe/ Hazardous Area)
- Gas Analyser & Sampling System
- Continuous Emission Monitoring System (CEMS)

- Liquid & Gas Analyser, WENS
- Steam Trap
- Trap Module
- Different types of Valves

- Condensate Recovery
- Condensate Pump
- Automatic Blow down Control System
- FDS, AS FDS
- De-aerator heads etc.

CHIRAG ASSOCIATES

INDIRANAGAR PUNE

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Poonawala Hussain Mohammad	4802	449364241104	Banking and Finance - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Shantika Talwar
Name & Signature
(Authorized Signatory)

Total Hours					

Certified that Kable Awwab Mohamed Hanif (Name of the student) has satisfactorily completed the Internship programme assigned to him.

Appointed Advisor



Name & Signature of manager section in charge Name & signature of supervisor of

Date :

INTERNSHIP COMPLETION CERTIFICATE



To,
The Principal,
AKS. Pedda College,
Camp. Puna. (Place)

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	<u>Kable Awwab</u>	<u>4875</u>	<u>653927527340</u>	<u>Banking & Finance II & III</u>
2.				
3.				
4.				

Ref: 88845 /1955775/Permit

Mr. Arshad Aif Shaikh

FMC office

Room no 27 Koba path, Kopol Park near FMC office (Maharashtra) - 411001

Phone No: 9284754622

Subject - Offer of Appointment

Dear Mr. Arshad Aif Shaikh,

It is our pleasure to welcome you to Tech Mahindra Limited.

1. With reference to our discussions, we are pleased to offer you appointment in our Organization as Associate Customer Support on IT band, operating out of our Pune office.
2. Your "Annual Total Cash Compensation" will be Rs. 175000. Please refer Annexure-A for details on the compensation and statutory deductions.
3. Your remuneration package is strictly confidential between you and here after, referred as The Company and should not be discussed with anyone nor divulged to anyone in any manner whatsoever.
4. Your employment with us will be governed by terms and conditions as specified in Annexure-B.
5. You are required to join on 04-Jan-2023 at the below mentioned location. The offer stands withdrawn thereafter, unless the date is extended and communicated to you in writing.
6. On the date of joining, you are requested to report to Sushant Pawa at 9:30 AM to complete the joining formalities at Tech Mahindra Limited, [Plot no:02, Rajiv Gandhi Infotech Park, Phase-3, Hinjewadi, Pune Special Economic Zone, Pune-411007, Maharashtra (India)]. At the time of joining, you are expected to carry originals of the documents as per Annexure - D and submit the copies of the same to the HR Team.
7. Please note that this Offer is subject to your being given a clear background check either at the time of reporting/joining or thereafter depending upon our receipt of the background check report from the agency.
8. Kindly acknowledge acceptance of this Offer of Appointment by signing and returning the 'acceptance copy' to Sushant Pawa latest by 04-Jan-2023.

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider Organisation

To,

The Principal,
Anji Ranga College,
Pongu, Madhavaram (Ranga)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Smith Arshad Araf	4795	40845933601	Banking and finance
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature
(Authorized Signatory)

Wow Travels

Shop No 10 Capital Mall Kausar Baugh Kondhwa Khurd Pune
Mobile: 8380898801
Skype: shalikh@wowtravels.com
website: www.wowtravels.in

1. Name of the Student : Shaikh Nadeem Farookh
2. Name of the College : T.Y.B.Com.
3. Division and Roll Number : (A) 4932
4. Address : Kondhwa Khurd
5. Contact Number : 7020249499
6. Email ID : nadeemshalkh@gmail.com
7. Special Subject : Banking & Finance
8. Internship start date : 01/01/2023
9. Internship end date : 10/01/2023

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Date	TIME		Total Hour	Details of work done	Signature of officer	Signature of student
	From	To				
01/01/23	12:00	6:00	6	Sales Training		
02/01/23	12:00	6:00	6	Sales Training		
03/01/23	12:00	6:00	6	Product Knowledge		
04/01/23	12:00	6:00	6	Product Knowledge		
05/01/23	12:00	6:00	6	Backend Knowledge		
06/01/23	12:00	6:00	6	Backend Knowledge		
07/01/23	12:00	6:00	6	Clients Handling		
08/01/23	12:00	6:00	6	Clients Handling		
09/01/23	12:00	6:00	6	Clients with Clients		
10/01/23	12:00	6:00	6	Proceed the Work		

Certified that Mr. Shaikh Nadeem Farookh has satisfactorily completed the internship programme assigned to him.



Name & Signature of supervisor



Name & signature of manager



Name & signature of section in charge

CHIRAG ASSOCIATES

INDIRANAGAR PUNE

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	SHEIKH SUHANA FBROZ	4858	407670455487	Banking and Finance -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Pratiksha Nimbalkar
Name & Signature

(Authorized
Signatory)

(100/1) N-1111

Koralkoti, Amalner Road, Pune, Maharashtra - 411010
Mobile - 952319740
E-mail - info@namdarco.in
Website :- www.namdarco.in

To,
The Principal,
Aki's Poona College
Camp Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Amalata Sadhana Shukh	4933	711878284130	Banking & Finance
2.	Ita Ajar Shukh	4811	992795881433	Banking & Finance
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.



Sincerely,
Chhaya Jayant Namdar
Name & Signature
(Authorized Signatory)



FIVTECH AUTOMATION COMPANY

Phone: 8090060071 | Email: fivtech.in@gmail.com

To,

The Principal
Poona College of Arts Commerce & Science,
Camp, Pune-411001.

Subject : Internship Completion Certificate.

Dear Madam / Sir,

I am happy to inform you that following student of your College have successfully completed the " Sixty Hours Internship Programme" in this Organisation.

Name of Student:- DUBEY VIMAL RAMESHCHANDRA
Roll No.- 4803
AAadhar No. 361803572809
SPECIAL SUBJECT:- BANKING & FINANCE II & III

This student have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that this student will perform effectively in similar type of organizations.

I wish him every success in future endeavors.

Thank you,

FIVTECH AUTOMATION COMPANY

PROPRUETOR

Sincerely

(Ramesh Chandra Dubey)
Director.

Office No.- 49 Amba Bazar, Opp. Wonderland M. G Road Pune - 411001 | Hadapsar Pune - 411028

Shah Khandelwal & Jain Associates

Riverside Business Bldg, Wellesley Road, near RTD, Pune, Maharashtra
4111001

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Abhishek Chohan Shaikh	4911	5102 101144	Banking and Finance - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,


Name & Signature

(Authorized Signatory)

Partner: Rishabh Patni
M.B. - 165240

















CHIRAG ASSOCIATES

INDIRANAGAR PUNE

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

1. Name of the Student : Shalkh Aadil Sharif
2. Name of the College : T.Y.B.Com.
3. Division and Roll Number : Div A, Roll No:4841
4. Address : Hadapsar gadital Pune
5. Contact Number : 9359758368
6. Email ID : shalkhadil623@gmail.com
7. Special Subject : Banking and Finance-II & III
8. Internship start date : Feb 1st, 2023
9. Internship end date : Feb 16th, 2023

LOG SHEET OF WORK PERFORMED DURING INTERNSHIP

Date	Time		Total Hours	Details of work done	Signature of officer	Signature of student
	From	To				
01-02-2023	12:00 PM	05:00 PM	5 HRS.	observation service		
02-02-2023	12:00 PM	05:00 PM	5 HRS.	customer client info into excel		
03-02-2023	12:00 PM	05:00 PM	5 HRS.	Excel basic		
06-02-2023	12:00 PM	05:00 PM	5 HRS.	observation service		
07-02-2023	12:00 PM	05:00 PM	5 HRS.	basic tally		
08-02-2023	12:00 PM	05:00 PM	5 HRS.	basic tally		
09-02-2023	10:00 AM	05:00 PM	5 HRS.	send collection data to service for approval		
10-02-2023	10:00 AM	05:00 PM	5 HRS.			

13-02-2023	10:00 AM	05:00 PMS HRS.			
14-02-2023	10:00 AM	05:00 PMS HRS.			
15-02-2023	10:00 AM	05:00 PMS HRS.			
16-02-2023	10:00 AM	05:00 PMS HRS.			

Certified that Shaikh Saad Sharif (Name of the student) has satisfactorily completed the Internship programme assigned to him.

Name & Signature of supervisor

Name & signature of manager

Name & signature of section in charge

Date / /



Shaikh Talha

(Signature)

To,

The Principal

AKI's Poona College of Arts, Science & Commerce,

Pune -411001

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following student of your college has successfully completed the '60ty Hours Internship Programme' in this organisation.

Name of the Student	Roll Number	Aadhar Number	Special Subject
Rahil Yunus Shaikh	4804	581687142515	Banking & Finance

The student has been provided with adequate exposure and necessary hands on training pertaining to his special subject.

I am confident that the student will perform effectively in similar type of organisations.

I wish him every success in future endeavours.

Thank you.

Sincerely,



Regreen Excel EPC India Pvt Ltd

MADINA BAKERY

Shop No.01, MADINA BAKERY,
2130, New Modikhana, Camp, Pune, Maharashtra -411001.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shubham Dashrath Dhondalkar	5119	-	Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorized Signatory)



PROGRAMME: VITEEE

MADINA BAKERY

Shop No.01, MADINA BAKERY,

2130, New Medikhana, Camp, Pune, Maharashtra -411001.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation:

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shubham Dinkarath Bhandalkar	5119	-	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorised Signatory)



SHREE DATTA BAKERY

Datta Chowk, Mundhwa, Pune, Maharashtra 411036.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aarbij Shakir Aatar	5130	222935496431	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Shree Datta Bakery
Datta Chowk Mundhwa
Pune - 411036
Mob - 97


Name & Signature

(Authorised Signatory)

INTERNSHIP COMPLETION CERTIFICATE

Arya interprise

To,

The Principal,
AKI's Poona College of Arts, Science and Commerce
PUNE

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Program' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shankh Ansh Jami	5123	89497840916	COST AND WORKS ACCOUNTING- II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,


Arya Khire

(Authorized
Signatory)

Arya Enterprises

Shop No. 2, 1st Floor, Ground
Near City Pool, P. O. ...
Bachmor Path, P. O. ...
Mob. 902290173, 9707209200

[Type here][Type here][Type here]

M. S. Engineering Works

Gym Equipments & Weightstack Manufacturer

To,

The principal,

AK'S Poona College,

Coorg, Pune.

Subject: Internship Completion Certificate

This is certify that Bhajan Muskan Malsud student of 6th Sem of T.Y.B.com Roll no: 5102 has completed 60 hours internship.

At M. S. Engineering Works from 2 February 2023 to 19 February 2023.

At work he had proven satisfaction results and highly dependable. This is to certify also that he has no pending assignments in relation to his work, and so she is therefore cleared.

We wish them all the best for future endeavors.

M. S. Engineering Work

For Exellent Fab & Engg

(Proprietor)

ABDU QADIR PATEL

Proprietor

Bhajan Muskan Malsud

DATE: 6/5/23

SHREE DATTA BAKERY

Datta Chowk, Mundhwa, Pune, Maharashtra 411036.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Abbas Nijam Sayyed	5104	697650676631	Cost and Work Accounting -II & III

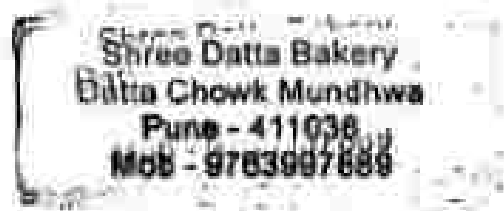
These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Adig. Anand

Name & Signature
(Authorised Signatory)

SHREE DATTA BAKERY

Datta Chowk, Mundhwa, Pune, Maharashtra 411036.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01.

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aaysha Iqbal Shaikh	5129	4516 9345 8556	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Shree Datta Bakery
Datta Chowk Mundhwa
Pune - 411036
Mob - 9761937889


Name & Signature
(Authorised Signatory)

CITY CARS & COACHES

400, NASTA, PETH, BHIND FATMA, BUILDING NO. 6-411011

INTERNSHIP COMPLETION CERTIFICATE

To,

The Principal,

Poona College of Arts,

Science & Commerce,

Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	MAYURI AMBADAS DAULATABAD	2111	338879728062	Cost and Work Accounting - I & II

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

CITY CARS & COACHES

Pratishtha

Name & Signature

(Authorised Signatory)

GALAXIE INTERIOR SOLUTIONS

Storey no 10/13 Tektid Dharmavat petrol pump, pisoli,

Pune, Maharashtra 411040

Email: info@galaxieinteriorsolutions.com , mobile no:-9673565786

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Noorbanu Hishanuddin Khan	5171	624339034961	Cost and Work, Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

GALAXIE INTERIOR SOLUTIONS

GALAXIE INTERIOR SOLUTIONS

Harish

Partner



Sunrise Bakery
सनराइज बेकर्स
Sadar Bazaar, New Modikhanda, Pune Cantonment,
Pune, Maharashtra 411001

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Pune College of Arts,
Science & Commerce,
Pune-01.

SUNRISE Internship Completion Certificate

Dear Madam/ Sir,

I am pleased to inform you that the following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the Student	Roll Number	Author No.	Special Subject
1.	Shakthi Zaverat Mukhtar	5146	4296 3696 7532	Cost and Work Accounting -I & II
2.	Ansari Sawleha Mohammed Shamsiad	5103	2303 3934 6508	Cost and Work Accounting -I & II
3.	Fatima Anshin Neerthan	5099	3057 6547 8700	Cost and Work Accounting -I & II
4.	Khan Sahida Naverulla	5072	9695 7735 0483	Cost and Work Accounting -I & II

These students have been provided with adequate exposure and necessary funds on training pertaining to their special subject. I am confident that these students will perform effectively in similar type of organizations I wish them every success in future endeavors.

Thank you.

Sincerely,


Name & Signature
(Authorized Signatory)

Sunrise Bakery, The Cafe Shop, New Modikhanda, 2130 Camp, Pune - 411001
Email: sunriseshops@gmail.com phone no. 020 26180822/2617 / 91 9300726147

SUNRISE BAKERS
NEW MODIKHANDA, 2130 CAMP,
PUNE - 411 001.

H.H.GYP STEEL

Gat No. 75 nr Fine Weigh Bridge, Moshi Road, Jadhavwadi,
Chikhli, Pune - 411014

INTERNSHIP COMPLETION CERTIFICATE

To,

The Principal,

Poona College of Arts,

Science & Commerce,

Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Mohammad Hamza Jawalid Sheikh	5147	882526113176	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorized Signatory)

MS ENGINEERING WORKS



To,

The Principal,

AK's Poona College,

Camp, Pune

Subject: Internship Completion Certificate

This is certify that Mr DHITEKAR LIMRA ASIF student of 8th sem of TyBcom Roll no 5081, has completed 60 hours Internship.

At Ms engineering works from 2 February 2023 to 19 February 2023.

At work he had proven satisfaction results and highly dependable. This is to certify also that he has no pending assignments in relation to his work, and so she is therefore cleared.

We wish them all the best for future endeavors.

Dhitekar Limra Asif

Date:

Ms engineering works
For M. S. Engineering Works


Proprietor

Abdul qadir patel

LIVE CASE'S

Sacred Heart Town, Wanaworle, Pune, Maharashtra -411040

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Afrin Zulqarnain Qureshi	5143	881552328503	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorized Signatory)
FOR LIVE CASE'S

Proprietor





CloudAge,
C/71A, Bavaria Industrial Estate,
Kondhwa Wasti Junction, Pune - 411007
Tel: +91 8067101590

01-05-2023

Internship Completion Letter

To,
The Principal,
Poonja College,

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr.No	Name of Student	Roll no.	Aadhar no	Special Sub
1	Sohail Baig	5339	324197694147	Marketing Management

We appreciate Sohail Baig contribution to our team and their willingness to learn and grow. Their dedication and positive attitude have been an asset to our company, and we are confident that they will continue to succeed in their future endeavors.

We wish Sohail Baig all the best in their future career and hope that they will stay in touch with our company.

Thank you.

Your Sincerely,



Harris Zed

Hr Head- Human Resources

Shivom Industries Pvt. Ltd.

To,
The Principal,
AKI'S Poona College,
Camp, Pune

Subject: Internship Completion Certificate -----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr.no.	Name of the student	Roll no.	Aadhar no.	Special Subject
01	Tejashree Ashok Shewale	5094	622419280103	Cost and Works Accounting

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

FOR SHIVOM INDUSTRIES



Patil

Sincerely,

Near KF Bio Plant ,Munjarl, Pune 412307

Email: Shivomindustries20212@gmail.com Phone: +91 9764113146

Shivom Industries Pvt. Ltd.

To,
The Principal,
Aki's Poona College,
Camp, Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hour Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Alka Rajkumar Nager	5862	659167449194	Cost and Works Accounting

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.


For SHIVOM INDUSTRIES
Sincerely,

Near KJ Bld, Marjari, Pune-411007

Email: Shivomindustries29212@gmail.com Phone: +9194113346

**Letter Head of the Internship Provider
Organisation**

To,
The Principal,
Pooja College,
Pune (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

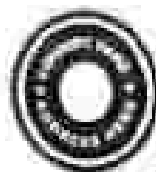
Sr. No.	Name of the student	Roll No.	Aadhar No.	Spncial Subject
1.	Shashik Sajiwa	53101	618595161447	Marketing Management
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

(Handwritten Signature)
Name & Signature

(Authorised Signatory)

Letter Head of the Internship Provider Organisation

To,
 The Principal,
PODVA College,
PLANE (Place)

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

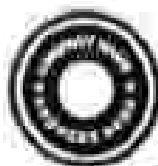
Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Tamboli/Saahil	5303	7602-61501	Marketing Management
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature
 (Authorised Signatory)

MS ENGINEERING AND WORKS



To,

The Principal,

AIIT's Poona College,

Subject: internship completion certificate

This is to certify that Ms. SAYYED IRAM SHAH Student of 6th Semester of TYBCOM Roll NO: 5082
Has completed 80 hours of internship.

At MS ENGINEERING WORKS FROM 2 February 2023 to 16 February 2023.

At work he had proven satisfied results and highly dependable. This is to certify also that he has
no pending assignments in relation to his work, and so she is therefore cleared.

We wish them all the best for future endeavors.

MS ENGINEERING AND WORKS

For S. S. Engineering World


PROPRIETOR

Abdul Qadir Patel

SAYYED IRAM SHAH

Date:

WOXMAN PVT.LTD

INDUSTRIAL TRAINING ORGANIZATION

To,

The Principal,

Poona College of Arts,

Science & Commerce,

Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No	Name of the student	Roll No	Aadhar No.	Special Subject
1.	Vikas Jha	5057	95167606 7415	Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you

Sincerely,


NATK & SOFTWARE
(Authorised Signatory)

MADINA BAKERY

Shop No.01, MADINA BAKERY,
2130, New Madhavana, Camp, Pune, Maharashtra -411001

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Ponna College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Madani Manoj Khin	2114	467217333035	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,
Name & Signature
(Authorised Signatory)

SalesGarners Marketing

TEAM LEADERSHIP & CO-OPERATION

5th floor office number 523 Cluster 10th, Plaza NIMB Road, MukherjeePark, Pune

MOBILE: 9307441063

sales@salesgarners.com

Website: www.salesgarners.com

To,
The Principal,
AITS Prosa College
Camp Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that the following students of your college has successfully completed the "Sixty Hours Internship Programme" in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Zohiya Iqbal Shaikh	5319	366433034163	Marketing
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar types of organizations. I wish them every success in future endeavors.

Thank you,
Sincerely,



Name & Signature
(Authorized Signatory)

M. S. Engineering Works

Gym Equipments & Weightstack Manufacturer

To,
The principal,
AK'S Poona College,
Camp, Pune.

Subject: Internship Completion Certificate

This is certify that Mr/ GHARATKAR URUSA IMRAN student of 6th sem of T.Y.B.com Roll no: 5107 has completed 60 hours internship.

at M. S. Engineering Works from 2 February 2023 to 25 February 2023.

At work he had proven satisfaction results and highly dependable. This is to certify also that he has no pending assignments in relation to his work, and so she is therefore closed.

We wish them all the best for future endeavors.

M. S. Engineering Work

For M. S. Engineering Works


[Proprietor] Proprietor

ABDULGADIR FATEL

GHARATKAR URUSA IMRAN

Date: 20-Feb-2023

ARSYS Pvt.Ltd

LOTUS, 703, KUMAR SURAKSHA HSG SOCIETY, PARGE NAGAR, OPP.OMKAR GARDEN, KONDHWA, PUNE-411048

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

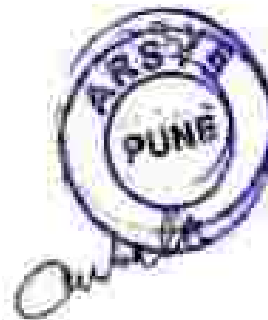
Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shikalgar Yashfess Itelkar	5068	501105537905	Cost and Work Accounting -I & II

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Quibell
Arif Jambale

Name & Signature

(Authorised Signatory)

RAJDHANI BAKERY

Shop No.01, RAJDHANI BAKERY, Opp. Dinshaw Hall And Near Nishat Talkies,
New Nana Petli, Pune, Maharashtra -411003.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shukh Hamza Aytz	5053	64654533636	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Signature
(Authorized
Signatory)

ARSYS PVT. LTD

LOTUS 703, KUMAR SURAKSHA HSG SOCIETY, PARGI, NAGAR, OPP OMKAR GARDEN, KONDHWA PUNE - 411048

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

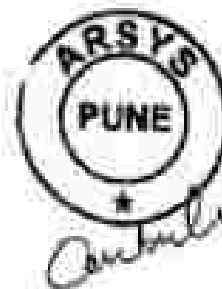
Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Mahesh Anis Yamboli	3066	387206016387	Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Amrute Ramesh

Name & Signature

(Authorized Signatory)

HARIDAS MADHAVDAS SUGANDHI

451, Ravivar Peth Rd, next to ICICI Bank Phadke Haud, Chowk, Pune,
Maharashtra 411002

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01.

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Musakin Kamroddin Pujade	3051	370844115478	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

HARIDAS MADHAVDAS SUGANDHI
451, Ravivar Peth, Pune-411 002. (India)
Telefax: +91 20 26458022
Email: hmsugandhi@gmail.com

Name & Signature
(Authorised Signatory)

Inamdar & Co.

Cost Accountants

Revurik Wadi Khandwa Khurd, Pune, Maharashtra - 411048

Mobile - 952319748

Info@inamdar.co.in

Website :- www.inamdar.co.in

To,
The Principal,
Akl's Poona College
Camp Pune

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Nadal Suresh Santoshkumar	5067	335143402190	Cost and Works Accounting

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you,

Sincerely,

Proprietor
(NAMDAR & CO.)
Firm No. 005401


Name & Signature
(Authorized Signatory)

PRECISE LASER TECH

SUNSHAGERNAGAR , PUNE MAHARASHTRA 411018

To,

The Principal,

AKI's Poona College of Arts, Science and Commerce

PUNE

Subject: Internship Completion Certificate

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Program" in this organization.

Sr.No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	SHUBHAM MOHAN KHAIRE	5139	694256089332	COST AND WORKS ACCOUNTING- II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name &

Signature (Authorized
Signatory)

Precise Laser Tech

[Type here] [Type here] [Type here]

DISHA LABELS AND BARCODE SOLUTION

W130/1, 'S' Block, Near Indrayani Chowk, MIDC, Bhosari, Pune, Maharashtra
411026

INTERSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Vinayak Suresh Nazare	5052	856249533809	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature
(Authorised Signatory)

TREELINK FURNITURE NETWORK

H & M Royal Society shop no 1 near talab factory, Pune;

Maharashtra 411008

Email:-treelinknetwork@gmail.com, mobile no:-8698320404

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shruti Mahommed Ameer Nazeemuddin	5105	75982846014	Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,


TREELINK FURNITURE NETWORK



TUSHARWORK

Experts for: *Yield Building, Maintenance, Job, Painting, Waterproofing, Tiles, Plumbing, All Types of Chemical Waterproofing for W.C., Bathrooms, & Terrace, Swimming Pool, Coatings & Groutings.*

N.No. 4, Kakade Nagar, Kundhwa Bk., Pune - 411 048.

Cell No. - 9504230117, 9830183548 Email ID - tusharworks1977@gmail.com

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programed' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Tushar Rahul Dahire	5154	264821908885	Cost and Work Accounting - II & III.

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Tushar Works
No. 4, Kakade Nagar,
Kundhwa Bk., Pune - 411 048.



Name &
Signature (Authorized S

ignatory)

Vijaylaxmi Foods

Near Khadi Machine Chowk, Dnyaneshwar Nagar Industrial Area, Kondhwa Budruk
Maharashtra Pune - 411048

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Farheen Shamrullaka Khan	5049	428756329448	Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similarity to other organizations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

VIJAYLAXMI FOODS
Signature
(Authorised Signatory)

New Empire Bakery
575, Sachpir St, Camp, Pune, Maharashtra 411001

INTERNSHIP COMPLETION CERTIFICATE

To,

The Principal,

Peona College of Arts,

Science & Commerce,

Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Ayeosha Azhar Khan	5055	497779914240	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

NEW EMPIRE BAKERY
575, BACHAPIR STREET,
CAMP, PUNE-411001.
PH 020-28340571
PHONE-PE: 1385365...

Sincerely,


Name & Signature
(Authorised Signatory)

SUNRISE BAKERS THE CAKE SHOP

NEW MOTIKHANA 2130, CAMP PUNE, MAHARASHTRA 411001

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of
Arts, Science &
Commerce, Pune-01

Subject: Internship Completion Certificate

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1	Ausari Sawlela Mohammed Shamsad	5103	2303 3034 5308	Cost and Work Accounting -II & III
2	Patil Arshin Neeraj	5099	5657 6547 8706	Cost and Work Accounting -II & III
3	Khan Sahila Neeraja	5072	9665 7735 9453	Cost and Work Accounting -II & III
4	Abdul Kareem Nisar Shaikh	5128	3635 2179 9814	Cost and Work Accounting -II & III
5	Mohi. Abazar Iqbal Shaikh	5138	7157 7468 7836	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish the every success in future endeavors.

Thank you.

Sincerely,

SUNRISE BAKERS
NEW MOTIKHANA 2130 CAMP,
PUNE - 411 001

TREELINK FURNITURE NETWORK

T.R. & M. ROYAL SOCIETY SHOP NO 1 NEAR TALAJI

FACTORY Pune, Maharashtra 411041

Email: treefurniturenetwork@gmail.com , mobile no: 8698320104

INTERSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Majumdar Muskan Umair	5751	805682644768	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,


TREELINK FURNITURE NETWORK



MUNDHIWA BAKERY

RESHAUNAGAR CHOWK MUNDHIWA PUNE-411036

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Pareej Uyskat Shyam	5145	902386850016	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature
(Authorized Signatory)

MAJIC BAKERY

PROPRIETOR

Shivom Industries Pvt. Ltd.

To,
The Principal,
Akl's Poona College,
Camp, Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Adhar No.	Special Subject
1.	Anjali Rajkumar Nager	5078	721635499249	Cost and Works Accounting

These students have been provided with adequate exposure and necessary hand-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

For SHIVOM INDUSTRIES

Partner

Secretly

Near KF Bld, Manjari, Pune 411007

Email: Shivomindustries2011@gmail.com/Phone: +9164113166





Go Do Good Pvt. Ltd.

To,
The Principal,
Alk's Poona College,
Camp, Pune

Subject: Internship Completion Certificate

Dear Maam,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.



Sr.No.	Name of the student	Roll no.	Aadhar No.	Special subject
01	Jasmeen Harun Shaikh	5097	627514274476	Costs & Works Accounting II & III

This students have been provided with adequate exposure and necessary hands on training pertaining to their special subject.

I am confident that this students will perform effectively in similar type of organisations.

I wish her success in future endeavors.

Thank you.



Sincerely,

Go Do Good Pvt. Ltd.

Sadhana Sadan, Sr. No. 12/1/A, Plot no.3 Trimbakeshwar Housing Society,
Mulk Nagar, Wadgaonsheri, Pune Maharashtra 411014
Email: hello@go-dogood.com Phone: 7304401177



Better Precision Technology

TAMBOLI ENGINEERS PVT. LTD.

Manufacturing of Precision CNC Machined Components and
Age & Future for Aerospace and Defense Application



To,
The Principal,
Poona College,
Camp, Pune.

Date :- 15.03.2023.

Subject: Internship Completion Certificate

Dear Madam/ Sir,

We are happy to inform you that following student of your college have successfully completed the 'Sixty Hours Internship Programme' in our organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Khan Nahira Ayaz	5108	548653927421	Cost & Work Accounting

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

We are confident that this student will perform effectively in similar type of organizations.

We wish them every success in future endeavors.

Thank you.

For, Tamboli Engineers Pvt. Ltd.

Nazir Bashir Tamboli
Managing Director



MS ENGINEERING WORKS

To,

The Principal,

Akl's Poona College,

Camp, Pune



Subject: Internship Completion Certificate

This is certify that Mrs/ DHOTIKAR AYISHA MAQSOOD, student of 6th sem of TyBcom Roll. no: 5085 has completed 60 hours Internship

At Ms engineering works from 7 February 2023 to 19 February 2023.

At work he had proven satisfaction results and highly dependable. This is to certify also that he has no pending assignments in relation to his work, and so she is therefore cleared.

We wish them all the best for future endeavors.

For M. S. Engineering Works


Ms engineering works

Proprietor

Proprietor

Abdul qadir patel

Date:

Dhotekar Ayesha Maqsood

Date:



Clean Technologies

To,
The Principal,
Aki's Poonia College,
Camp, Pune

Subject: Internship Completion Certificate

Dear Ma'am,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll no.	Aadhar No.	Special subject
01	Khan Farheen Khalilullah	5090	686004844256	Costs & Works Accounting I & II

This students have been provided with adequate exposure and necessary hands on training pertaining to their special subject.

I am confident that this students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Kabira Clean Technologies



Sadhana Sudan, Sr. No. 12/1/A, Plot no.3 Trimbakeshwar Housing Society,
Mulik Nagar, Wadgaonsheri, Pune Maharashtra 411014
Email: hello@go-dogood.com Phone: 7304401177

Shalimar ENTERPRISES

DHANORI ROAD , BHAMBAY NAGAR , PUNE , MAHARASHTRA 411047

To,
The Principal,
AKI's Poona College of Arts, Science and Commerce
PUNE

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Program' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Khus gaur arafal (sahin)	3127	5413 3300 6090	COST AND WORKS ACCOUNTING- II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorized

Signatory)

SHALIMAR ENTERPRISES
Dhanori Road, Bhambay Nagar, Pune
Sahin
3127

[Type here][Type here][Type here]

INTERNSHIP COMPLETION CERTIFICATE

Contact Number:

9923364835
7823842089

THE MASTER SOFA



Address:

5, 6th Floor, No. 37/5/5,
Dattatraya Chaudhari,
Pune, Maharashtra-40

To,
The Principal,
AKF's Poona College
Camp, Pune

Subject: Internship Completion Certificate

Dear Madam,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

The student have been provided with adequate exposure and necessary hands on training pertaining to their special subject.

I am confident that the student will perform effectively in similar type of organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject	
1.	Zainab Syed	5113	88882408632	Cost & Works Accounting - 3	

I wish them every success in future endeavors.

Thank you.

Sincerely,

For THE MASTER SOFA

Proprietor

Name & Signature
(Authorised Signatory)

2



OMEGA HEATERS

To,
The Principal,
AKI's Poona College of Arts Science and Commerce
Camp, Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

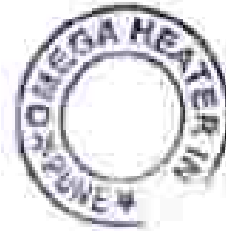
SR.NO.	NAME OF THE STUDENT	ROLL NO	AADHAR NO.	SPECIAL SUBJECT
01	SHAIKH FURQAAN RIYAZ	5079	737212495516	COST & WORKS ACCOUNTING II & III

These students have been provided with adequate exposure and necessary hands on training pertaining to his special subject

I wish them every success in future endeavors.

Thank you.

Sincerely, Omega Heaters



KOHINOOR BAKERY

Sionagar Road, TQ. Ravhalyan Dist. Bidar

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shaikh Sara Mukhtar Ahmed	5112	435541727339	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Talib
Name & Signature
(Authorised Signatory)

GALAXIE INTERIOR SOLUTIONS

Survey no 10/13 Behind Dharmavat petrol pump, pisoli,

Pune, Maharashtra 411048

Email: hsh.hussain@gmail.com , mobile no:-9673565786

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Ayesha Akhtar Shaikh	5134	486904113605	Cost and Work Accounting -I & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

GALAXIE INTERIOR SOLUTIONS

INTERNSHIP COMPLETION CERTIFICATE

NIRANJAN AUTO COMPONENTS PVT. LTD.

S BLOCK J 48 MIDC BHDSARI, PUNE 411026

To,

The Principal,

AKJ's Poona Collage,

Camp, Pune,

Subject: Internship Completion Certificate

Dear Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Patel Amaan Abdulgeffar	5075	408872087669	Cost and Works Accounting-II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavours.

Thank you.



Sincerely,

Nirajan Auto Components PVT. LTD

S.I. AND COMPANY

06/ No.43/44, Kanner Bangli Rd, Society, Ronliwa, Pune- 411048

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Atif Riyaz Ahmed Shaikh	5088	412824743046	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorised Signatory)

INTERNSHIP COMPLETION CERTIFICATE

MUNDIWA BAKERY

Keshavnagar Chawl, Mundhwa, Pune - 411016

To,

The Principal,

Poona College Of Arts,

Science and Commerce,

Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Adnis Kashal Sutar	3603	8113 9077 3677	Cost and Work Accounting II-III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

MUNDIWA BAKERY
Keshavnagar Chawl,
Mundhwa, Pune - 411016

Sincerely,

Name & Signature

(Authorized Signatory)

MS ENGINEERING AND WORKS



To,

The Principle,

Alk's Peona College,

Camp, Pune

Subject: Internship Completion Certificate,

This is certify that MS/ BAGWAN BUSHRA FERDZ student of 6th semester Tytocom roll no.5101
Has completed 60 hours internship.

At MS engineering works from 2 FEBRUARY 2023 TO 19 FEBRUARY 2023.

At work he had proven satisfaction results and highly dependable. This is to certify also
That he has no pending assignments in relation to his work, and so s/he is therefore cleared.
We wish them all the best for the best for future endeavors.

BAGWAN BUSHRA FERDZ

DATE:

MS engineering works

607/15, Engineering Works

proprietor

Proprietor

Abdul qadir petel

RAJDHANI BAKERY

Shop No.01, RAJDHANI BAKERY, Opp. Dindhuw Hall And Near NI shat Talkies,
New Itana Peth, Pune, Maharashtra -411001.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Fardeen Sameer Beediwala	5063	770698758217	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

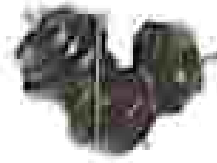
I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature
(Authorized Signatory)

MENGINEERINGWORKS



To,
The Principal,
Aki's Poona
College, Camp, Pune

Subject: Internship Completion Certificate

This is certify that Ms/ MominRahat Abdul Karim student of 6th sem of
TYBcom Roll no: 5142 has completed 60 hours internship

At Mengineeringworks from 2 February 2023 to 19 February 2023.

At work he had proven satisfaction results and highly dependable. This is to certify
also that he has no pending assignments in relation to his work, and so he is therefore cleared.
Wish him all the best for future endeavors.

MominRahat Abdul karim

Date:

Mengineeringworks
for M. S. Engineering Works
Proprietor
Abdulqadirpatel

PRIDE BAKERY

Sayed Nagar Hadapsar, Post No. 22/A
Maharashtra, Pune, 411028

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr.No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shakthi Anand Dattajir	5110	67783330409	Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

For BAKERS PRIDE

Proprietor


Name & Signature
(Authorised Signatory)



DISHA LABELS AND BARCODE SOLUTIONS

For Quality Barcode Solutions

ADDRESS-W-130, 5 Block, Near Sai Engr, Indraprastha Nagar, Bhamburda, MIDC, Pune - 411026,
Maharashtra, India.

EMAIL: response@dishabarcode.com

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	KUTURAJ RAJU PSL	5124	263497371130	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature (Authorised Signatory)
FOR DISHA LABELS & BARCODE SOLUTIONS



To,
The Principal,
ANI's Poona College of Arts, Science and Commerce,
Camp, Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following student of your college has successfully completed the 'Sixty Hours Internship Programme' in this organisation.

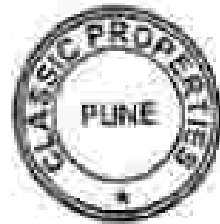
Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	IRUM IMTIYAZ PASWARE	5070	444067464376	Cost & Works Accounting II & III

The student has been provided with adequate exposure and necessary hands-on training pertaining to the special subject.

I am confident that the student will perform effectively in similar type of organisations.

I wish her every success in future endeavors.

Thank you.



Sincerely,
Classic Constructions

J. S. Shaikh



CAKE STORY DESSERTS

To,
The Principal,
AK's Poona College,
Camp, Pune

Subject: Internship Completion Certificate —

Dear Madam/ Sir,

I am happy to inform you that following student of your college has successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	KHUSHI YOGESH AGARWAL	5054	1989 0384 2694	Cost and Works Accounting

The student has been provided with adequate exposure and necessary hands on training pertaining to their special subject.

I am confident that the student will perform effectively in similar type of organisations.

I wish her every success in future endeavors.

Thank you.

KANHAIYA BAKERS
Survey No 1547, 1st Floor, Kanhai Building
Near Dehaya Ganpat Mandir, Dhule,
Tel: 98221, Dist: Pune-411001
Mob: 9710041010

Sincerely,

Aniket Raut

Cake Story Desserts

Manager





TAMBOLI ENGINEERS PVT. LTD.

Manufacturing of Precision Cast Aluminium Components and
High Precision for Aerospace and Defense Applications



Better Precision Technology

Date :- 15.03.2023.

To,
The Principal,
Poona College,
Camp, Pune.

Subject: Internship Completion Certificate

Dear Madam/ Sir,

We are happy to inform you that following student of your college have successfully completed the 'Sixty Hours Internship Programme' in our organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Kafiya Asad Tamboli	5073	3265 2451 2394	Cost & Work Accounting

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

We are confident that this student will perform effectively in similar type of organizations.

We wish them every success in future endeavors.

Thank you.

Sincerely,

Tamboli Engineers Pvt. Ltd.


Nazir Bashir Tamboli
Managing Director



Choudhary Carpet House

373 Nana Peth, Sairth Kabir Chowk, OPP, Modern Bakery Pune - 02

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the Sixty Hours Internship Programme in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Misba Feruz Khan	5074	888731855341	Cost and Work Accounting - I & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

For Choudhary Carpet House



Proprietor

Name & Signature

(Authorised Signatory)

Choudhary Carpet House

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Tauhid Satafraz Inamdar	5092	413291104085	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Harshali Koye
Name & Signature

(Authorised Signatory)

Regd. Office :
Shri Ram Kunj, S. No. 40 1st Floor,
Chandole Nagar, (Dhore), Pune - 411014,
Tel. No. : 9822274568, 9880052232

CIN No. U24100PNG015FTC0155383

Factory Address :
Gate No. 1002, Bhorot Gas Road,
At Post. Gondawadi, Tal. Shirur,
Dist. Pune - 412208

Email : zenithbc015@gmail.com

HARIDAS MADHAVDAS SUGANDHI

451, Raviwar Peth Rd, next to ICICI Bank, Phadke Haul, Chowk, Pune,
Maharashtra 411002

INTERNSHIP COMPLETION CERTIFICATE

To:

The Principal,
Peons College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Audhar No.	Special Subject
1.	Mishel zahoer firs	5121	547888391379	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

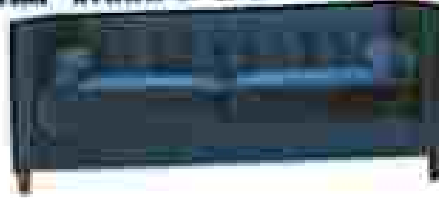
Sincerely,

Name & Signature
(Authorised Signatory)

Contact Number

9923364835
7823842099

THE MASTER SOFA



Address

S.no.32 hissa no.3/5/5,
Behind angraj dhaba,
pune, kondhwa-48

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate.

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Mohd Umair Clanda	5064	891053135411	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

For THE MASTER SOFA

Proprietor

Name & Signature

(Authorised Signatory)



SUJATA INDUSTRIES

Khadi-machine check, Sujata Industries, Pune 411060

Maharashtra

INTERSHIP COMPLETION CERTIFICATE

To,

The Principal,

Poona College of Arts,

Science & Commerce,

Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student.	Roll No.	Aadhar No.	Special Subject
1.	Abdus Samad.	5060		Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature
(Authorised Signatory)

For SUJATA INDUSTRIES

Partner

SUJATA INDUSTRIES

Khadli machine track, Sujata Industries, Pune-411061
Maharashtra

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shalch Jamar / A	5051	62101576 8525	Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary foundation training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature
(Authorized Signatory)

For SUJATA INDUSTRIES

Partner

INTERNSHIP COMPLETION CERTIFICATE

To,

The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Hepsiba Devaprasad Mamidi	0135	323207209322	Cost and Work Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorised Signatory)

for LIVE CARE'S

Proprietor

VSPS ENTERPRISE

Adarsh nagar Colony No 2 Dighi Bhosari Road Dighi 411015

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Rohan Vasant Jadhav	5061	588613161792	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



PURANDAR COCONUT BARFI & SWEETS

Jejuri MIDC, next to Jambhare Ice Factory, Jejuri, Pune, Maharashtra 412303

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation,

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Purandar Akram Ayub	5098	242306352470	Cost and Works Accounting - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorized Signatory)



JK ENTERPRISES

KOLHEWADI SHOP NO.2 NEARSK HOTEL CANARA BANK PUNE-24

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aman Abba Sheikh	3065	644493950687	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

J.K. ENTERPRISES

Abha P. J.

Proprietor

Abha P. J.
Name & Signature
(Authorized Signatory)

VIKHAR ENTERPRISES

DHANORI ROAD , BHAIRAV NAGAR , PUNE MAHARASHTRA -411047

To,

The Principal,

AKI's Poona College of Arts, Science and Commerce

PUNE

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Program' in this organization.

Sr. No.	Name of the student	Roll No.	Aachar No.	Special Subject
1.	SHAIKH MUNWAR JAVED	5067	251938149397	COST AND WORKS ACCOUNTING- II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you,

VB

Sincerely,



[Type here]

[Type here]

[Type here]



DURVESH ENGINEERING WORKS

At/post lhed shiwapur taluka -raveti, dist-pune,near toll naka, pincode
412205, maharashtra

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Saadat Imtiyaz Mujawar	5117	459609049966	Cost and Work Accounting -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature

(Authorised Signatory)



OMEGA HEATERS

To,
The Principal,
AKI's Poona College of Arts, Science and Commerce
Camp, Pune.

Subject: Internship Completion Certificate.

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr.No.	Name of the student	Roll No.	Aadhar No.	Special Subject
01	Sayyed Umar Mushtaque	5125	467670564433	Cost & Works Accounting II & III

These students have been provided with adequate exposure and necessary hands on training pertaining to his special subject.

I am confident that this student will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Omega Heaters



VERTEX COMMERCIAL SERVICES

Inamdar & Co.

Cost Accountants
Korruk Mall, Kondhwa Khurd, Pune, Maharashtra - 411048
Mobile - 9552319748
Info@inamdar.co.in
Website :- www.inamdarco.in

5

To,
The Principal,
Aki's Poona College
Camp Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	SHAIKH ALFIYA HUSAIN	5307	677128622471	Marketing Management
2.	ANILM PIROZ KHAN	5408	687352716273	Marketing Management
3.	ZAID SHAIKH	5252	67698286361	Marketing Management
4.	SANIYA SIDDIQUE	5386	910596752013	Marketing Management
5.	MUZAMMIL ZAKIR INAMDAR	5310	608375539334	Marketing Management
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Proprietor
INAMDAR & CO.
Firm No. 005401

Sincerely,
Chaitanya Inamdar
Name & Signature
(Authorized Signatory)

VERTEN COMMERCIAL SERVICES

Office no 210, Navur Trade Centre, Phase 2, Chinchwad Pune 411019
Zakir Shaikh (Tax Consultant)
+91 2066532109

To:
The Principal,
Aki's Poona College
Camp Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that Tabassum Tanvir Shaikh of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Tabassum Tanvir Shaikh	5333	382759701880	Marketing Management

She has been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that she will perform effectively in similar type of organizations.

I wish her every success in future endeavors.

Thank you



Sincerely,

(Authorized Signatory)

Zakir Shaikh

AG FURNITURE

Undri Pooji Road, Near Khadi Machine Chowk

Mobile: 8822400048

agfurniture2018@gmail.com

website: www.agfurniture.in

To,

The Principal,

All's Poona College,

Camp, Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sl. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shoikh Muhammad (Hassam Jaffer)	5347	901437971070	Marketing Management
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

For A&G Furniture


Proprietor

Sincerely,


Name & Signature

(Authorised Signatory)



UST PIPES AND FITTINGS

272, Gaurav path near dalal chowk Mominpara

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Khan Anas Salim	5158	705550117641	Marketing Management - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely,


Name & Signature
(Authorized
Signatory)

The Director's Institute

Genark Mall, Keshavnagar, Pune, Maharashtra - 411048

Mobile - 9553319743

WhatsApp - 9553319743

Website :- www.inamdarco.in

To:
The Principal,
Aki's Poona College
Camp Pune.

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Sneha Chaudhari	5313	523273320451	Marketing Management
2.	Shan Meera Jindal	5376	510127008604	Marketing Management
3.	Kaif Shaikh	5185	822132343769	Marketing Management
4.	Nareen Inamdar	5405	991922228521	Marketing Management
5.	Nurhan Sayed	5304	578859408942	Marketing Management
6.				
7.				
8.				


These students have been provided with a/adequate exposure and necessary hands-on training pertaining to their special subject.

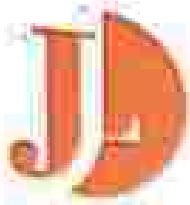
I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Proprietor
INAMDAR & CO.
Firm No. 005401

Sincerely,

CMA Bajrang Inamdar
Name & Signature
(Authorized Signatory)





Date - 01/05/2023

TO WHOM IT MAY CONCERN

This is to certify that Mr. Zaid Zahoor Chiplunkar, S/O- Mr. Zahoor Hajimiya Chiplunkar, a student of TYBCOM, Savitribai Phule Pune University Pune has successfully completed 03 (Three) months (From 3rd December, 2022 to 28th February, 2023) long internship program with our Company. During the period of his internship program with us he was found punctual and hardworking.

We wish him every success in his life.

For,
JYTE LOGISTICS PVT. LTD.

Authorized Signatory 

INTERNSHIP COMPLETION CERTIFICATE

75

To,
The Principal,
All's Floors College of Arts Commerce and Science College,
Pune-411014

Subject: Internship Completion Certificate

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the Sixty Hours Internship Programme in this organization.

Sr.No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Tashad Mustakin Khan	5378	55961647109	Marketing Management
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively similar type of organizations.

I wish them every success in future endeavors.

Thankyou.



Lohil
Sincerely,

Lohil Patil

Name & Signature

(Authorized Signatory)

INTERNSHIP LETTER

Date: 21st April 2023

To,

WHOMSOEVER IT MAY CONCERN

Subject: Internship Letter

Respected Sir/Madam,

This letter certifies that Ms. Nabeesha Shaikh a student of Aiswarya college of arts science and commerce, Hidayatulla Rd, Katad Khana, Pune, Maharashtra 411002, Maharashtra, India has successfully completed his internship at Spee Manning Solutions LLP under the guidance of Mr. Ashok Murdikar for 10 days.

In the internship period her punctuality, hardworking nature, eagerness to learn and ability to understand and grasp concepts were the qualities that made her stand out and lead among the rest.

We wish her the very best in his future career.

Authorized Signatory



Ashok Murdikar

Manager,

SPEs Manning Solutions LLP.

Address : Office No. 23A/24A, Yogesh House,
2nd Floor E-Steel, Comp. Pune-411001.
Contact : (020) 30571441 E: info.spes.in Website : www.spes.in



Direct B2B Media Enterprises

Office No. 57A, Building Number 15, HPSJ Rajaraj, Madurai, Tamil
nadu 625 002 Tel: +91 8213349589

Date: 16th Dec 2022

To,
Employee Name: Shalith Naziya,
Designation: Digital marketing Executive Department:
Marketing

Internship Completion Letter

Dear Sir/Ma'am,

This is an Internship Completion Certificate for Ms. Naziya Shalith from
DirectB2B Media

We state on record that Naziya Shalith has successfully completed an internship
project in the role of Digital Marketer at Direct-B2B Media, from 21st Nov 2022
to 09 Dec 2022 (15 Days).

During Internship, Naziya worked in " Digital Marketing Sales ". Her performance
exceeded expectations and was able to complete the Internship successfully. We wish
her all the best for her future career.





DIAMOND ENGINEERING WORKS

•Manufacturers & Suppliers•

285, Mangalwar Path, Baram Road, Pune - 411011 tel. (020) 39071450
Gat No 73, Jadhavwadi, Near River Residency Datta Masti Road, Chikhli, Pune - 411016
Email: diamondengg1994@gmail.com

15
31/07/2025 (2025)

REF.:

DATE:

To,
The Principal,
Poona college of Arts, Science & Commerce,
Camp, Pune - 411 001.

Subject: Internship Completion Certificate-Aliya Naim Shaikh

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in our organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aliya Naim Shaikh	C 5432	658894262396	Marketing Management

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish her every success in future endeavors.

Thank you.

Sincerely,
DIAMOND ENGINEERING WORKS

Salma Adhoni
PARTNER

-S^B SAHYADRI ENTERPRISES

640 Gursivar Petli, Maharana Pratap Road, Nure - 421 042. / Mob. • 9850258134, 9922236886 ;

sahyadri4spkex@gmail.com

Ref. No. **To Whom It May Concern**

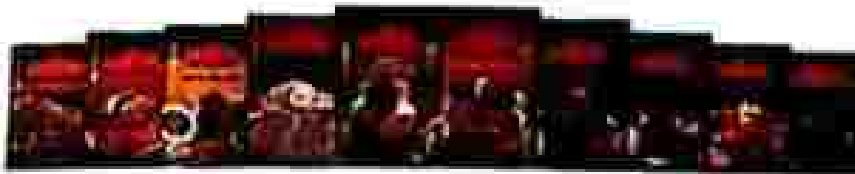
This letter is to certify that **Moshin Khan** has successfully completed his internship program of 10 days with **SAHYADRI ENTERPRISES**.

His internship tenure was from 15 Dec 2022 to 25 Dec 2022. He was working with Sales & Marketing And Billing Department He was actively & diligently involved in the projects and tasks assigned to him.

During the span, we found him punctual and hardworking person. His learning powers are good and he picks up swiftly. His feedback and evaluation proved that he learned keenly. Moreover, his interpersonal and communication skills are brilliant.

We wish him a bright future.

40 वर्षांचा विश्वास, चारमिनारची चव खास



खास | खेवरी | चव

Super Store Best & Catering Distributors of Charminar Masala

Marketing Agency

Office UB1, UG Floor, Clover Hills Plaza, NIBM Road, Pune,
Maharashtra 411004, IN
Mobile-736792176
Website:-www.tbmain.com

To,

The Principal,
Aki's Poona College
Camp Pune

Subject: Internship Completion Certificate

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organization.

Sr.No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	SHAIKH JUNED KAMAR	5412	895192895690	Marketing Management
2.				
3.				

These students have been provided with adequate exposure and necessary hands on training to their special subject.

I am confident that these students will perform effectively in similarity of organizations.

I wish them every success in future endeavors.

Thank you.



Sincerely,
Name & Signature (Authorized Signatory)



TITANIC FIRE CORPORATION

(A Fire - 2nd, certified company)

(SALES & SERVICE OF FIRE FIGHTING EQUIPMENTS/AMC. CONTRACTORS)

OFF/WORKS - T/1, VISHAJ AANGAN, POBHAL PARK, OFF TANK ROAD, OPP HP GAS GODOWN,
ALANDI ROAD, YENWADE, PUNE - 411006.

(MOBILE NO : 9850507468, 9107167776, 9106172199 - E.MAIL : www.titanicfire.com)



To,
The Principal,
AKI's Peona College,
Camp, Pune.

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Sayyad Afsan Iqbal	5337	333936869733	Marketing Management
2.	Kazi Talha Anwar	5369	380634490859	Marketing Management
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

TITANIC FIRE CORPORATION
Sales & Service of Fire Fighting Equipments
Plot No. 1, Visal Aangan, Pobhal Park
Off. Tank Road, Opp. HP Gas Godown,
Alandi Road, Yenwade, Pune - 411006

Sincerely,

Name & Signature (Authorized Signatory)



Vertedge Business Solutions LLP

To
The Principal,
Ab's Poona College,
Camp, Pune

Subject: Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty hours Internship Programme' in this organisation.


Sr No	Name of the student	Roll No	Aadhar No.	Special subject
01	Shaikh Amir Abdul Rashid	5390	547503395778	Marketing Management II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.


Vertedge Business Solutions LLP
Vertedge Business Solutions LLP
Pune

Purmar Gallery, Office no 300 to 311, 3rd floor, Warwek, Pune, Maharashtra 411048

Email: info@vertedgebs.com Phone: +91 74085 66938

22

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider
Organisation

To,

The Principal,

Prerna College,

Camp (Place)

Subject: Internship Completion Certificate _____

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Shaikh Shifa	5311		Marketing management
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature

(Authorized Signatory)

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider Organisation

To,
The Principal,
Akis Pooch College,
Camp (place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Uzma Sundke	5402	9438544244	Marketing.
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you,



[Handwritten Signature]

Sincerely,

Name & Signature
(Authorized Signatory)



KK LIGHTS AND DECORATORS

To,
The Principal,
Poona College, of Arts, Science and Commerce
Camp, Pune

Subject: Internship Completion Certificate.

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Iftekar Nasir Khan	5416	466729515679	MARKETING MANAGEMENT

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these student will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

For K. K. Lights/Decorators & Mandap

Name & Signature

(Authorised Signatory) Proprietor



Konark param Mall Kondhwa Khand, Pune, Maharashtra - 411048
Mobile :8669331503
info@alpha.in
Website : www.alpha.in

To,
The Principal A/c's
Poona College
Camp Pune

Subject: Internship Completion Certificate ----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Khan sana Juned	5328	56012700860	Marketing Management 5
2.	Alsha namdar	5392	97577353045	Marketing Management 1
3.	Ashraf Shaikh	5368	89763284376	Marketing Management 0
4.	Afreen Zuber shaikh	5468	97192222852	Marketing Management 1
5.	Khan sekib	5338	57978689464	Marketing Management 2
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.



Name & Signature
(Authorized Signatory)

NOORI MENHDI PRODUCTS

20-02-23

This is to certify that Taufiq Javed Tamboli S/O Javed Tamboli. A Student of AKIS'S Poona Collage. Has Done Intership of Manufacturing and Managing the Business in my organization of 10 Days From (11-02-2023) to (20-02-2023) Working Hours – 9.00 to 3.00 Daily 6 Hours

I Wish Him Success in his Life

Date 20-12-2022

Place- Pune


Signature

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider Organisation

For PREMIER SERVICES

Atrol

Proprietor

To,
The Principal,
POORNIMA College,
PUNE (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	SHAIKH JOHAIL			
2.	AYAZ	5320	2460 870	Marketing
3.			6347	Management
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



For PREMIER SERVICES

Atrol

Name & Sign *Proprietor*

(Authorised Signatory)

TAURUS

BPO services

Swargate, Shankarshethi rd, 199, Pune - 411042

Mobile - 8097519496

5 (5)

To,

The Principal,

AKI's Poona College

Camp Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Khalid Nabil Sayyed	6306	5001 1524 4614	MARKETING
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Md
Sincerely,

Sh

Name & Signature

(Authorized Signatory)



HARI OM REALTY

Associates Beyond Sales

5
24

Date:-

To Whomsoever It may Concern

Branch Address: Silver Estate Co-op. Hg. Society, NIBM Road, Kondhwa,
Pune -411048

Name of the Student: Mr. Hadim Inam Sayyed

Name of the Course: Intern for Marketing Strategies

About Hari Om Realty:

Our Company is a Real Estate Company. We makes people dream by helping them to purchase their own homes. Hari Om Realty is a Proprietor Company. Our office is located to Mohli Area. Giving Proper Sales Service is our biggest strength which helps us to enhance our business through referral and satisfied customers.

Nature of Business

- Strategic Partner - Sale Selling of Projects
- Channel Partner
- Selling and Purchasing of Flats/ Plots
- Rentals
- Leasing of Offices/ Shops
- Pre Lease Offers

Following Work was done by Mr. Hadim Sayyed

- 10 Hours were given to survey the Project /Developers/competitors, find out competitors rate, specification and amenities. To know about Schools, Hospitals, Transportation, Hotels, Post Office, mail connectivity to vicinity areas.
- 5 Hours training was given to compile competitive data and put it in Excel Format. This helps us to understand the product well and tackle customer queries and objections related to flats.



RAMA EQUATOR, Office No 411, Fourth Floor, Near City International School, Marwad, Pune 411018
Contact: +91 90999 37283, 83082 98289 | Email: realtyhario@gmail.com
REG. NO. A52100011274 | GST No.: 27AFRPV165TA126



Scanned with OKEN Scanner

- 5 Hours training was given how to market the project on Media. Online platforms like Whatsapp, Facebook, Micro Website have helped home buyers to view the project sitting home on one Click. Various online Paid application were shown how we can market our products such as Magic bricks, 99 Acres, No Broker.com and Housing.com This have helped NRI customers to review the project and invest in real estate. Online platform have helped us in generating the leads.
- 5 hours training was given to Call the database, understand customer requirement, Explain the exact product which suits him.
- 10 hours training was given to him to communicate with the customer, Show him different projects, make him understand the market. Give details about home loan of different banks.
- 5 hours training was given to him to follow up with the customer and make him finalise the project which ever Customers likes.
- 5 hours training was given to him to coordinate with the Project Sales team and to brief about the customer requirement in their specific project.
- 5 hours training was given to him to act as a mediator between the Builder and the Customer. To make the situation a win win one for both the customer and builder. Take the customer to the site and show him the actual flat. Explain them the main amenities and interact with the customer.
- The whole above exercise was done to sell the flat and was to have knowledge of negotiation. 10 hours training was given to Mr. Hadin. The main focus was to build relationship with the customer and give such service to the customer that he refers more customer to us to make our organization grow.

Following the overall experience with Mr. Hadin, we found him more hard-working, more sincere and honest. We wish him all the best for his future.



For Hari Om Realty

Authorized Signatory



Website: www.al-khalifa.com
Al-Khalifa

Tours & Travels India Pvt. Ltd.

HAJ - UMRAN - ZIYARAT

AMIR SHAIKH ☎ 8669280314 📞 7038109891

(Managing Director)

724, Chudama Talim, Bhawani Path, Opp. Navin Hindi School Pune - 411 042, Email: amir@al-khalifa.com

To:
The Principal,
POONA College,
PUNE-411001

Subject: Internship Completion Certificate .—

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	HASHAM FERDZ MEMON	5332	N/A	MARKETING MANAGEMENT
2.	ARBAZ SIRAJ KHAN		N/A	

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely




Name & Signature
(Authorized signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
A.K. Sarda College,
Pune..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Table with 5 columns: Sr. No., Name of the student, Roll No., Aadhar No., Special Subject. Row 1 contains handwritten entries: 1, Saniya Tamboli, 5384, Marketing Management.

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you



Stamp of the company

Signature
Sincerely,
Name & Signature (Authorized Signatory)

Wow Travels

29

Shop No 10 Capital Mall Karver Dargh Kondhwa Khurd Pune

Mob: 9380998891

Sk: wowtravels@gmail.com

Website: www.wowtravels.in

To,

The Principal,

AI'S Panna College,

Camp, Pune

Subject: Internship Completion Certificate _____

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Tutur Kamras Shalbir	5372	738102264935	Marketing Management
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Name & Signature

(Authorized Signatory)



Corporate Office: Office No. 404
Core, The Latitude NIBM Pune - 411048
iv@anakeleer.io

To,
The Principal,
POONA College,
PUNE-411001

Subject: Internship Completion Certificate -----

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Ansari Sarkis Nasim	5373	N/A	MARKETING MANAGEMENT
2.			N/A	

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

[Handwritten Signature]
Name & Signature
(Authorized signatory)

Dear Madam/ Sir,
Please provide your valuable feedback about the performance of the student on following parameters.
Your feedback will enable us to make necessary changes in the Internship process. Thank you.
Coordinator- Internship Programme



ABM Dental Laboratory

A wing, Ashwini Paradise Bilewad, Kondhwa Rd., Pune-37
MobileNo.- 848481
email add.- abmdental24@gmail.com

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Mr Shaikh Mustakaim Mukhtar has successfully completed 2 weeks of an internship program from 19th Jan 2023 to 30th Jan 2023 in the Quality department of our organization.

He was highly motivated and hardworking. He worked sincerely at his tasks and did a very good job.

Sincerely,

As. Mudgal



EXLENZE BPO SERVICES Pvt. Ltd.

OFFICE 915, CLOVER HILLS PLAZA, HIMM LINDRI ROAD, PUNE, MAHARASHTRA 411048

Date: 15th Jan 2023

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Mr. Hussain Bohra has successfully completed 3 weeks of his internship in lease administration at Exlenze BPO Services Pvt. Ltd (TermaLenze Technologies PVT. LTD.), Pune from 19th Dec 2022 to 31st Dec 2022.

During the internship he demonstrated good reading and communication skills with a self-motivated attitude to learn new things. His performance exceeded expectations and was able to complete the assigned task successfully on time.

We wish him all the best for his future endeavors.

Yours faithfully,

Exlenze BPO Services LLP



Authorized Signatory
(Mohamed Junaid)



Regd Office:
Exlenze BPO Services LLP
LLPIN - AAJ-0011
B-132, First Floor, Agency Plaza,
Near Kalyan Ulhasnagar Border Gate, Ulhasnagar 421 001,
Maharashtra, India T : (+91) 0203-261 7937

Pune Office:
Exlenze BPO Services LLP
Office 915, Clover Hill Plaza HMM Lindri Road,
Pune 411 048, Maharashtra, India
www.exlenze.com

MARIYA'S BIRDS FOOD STORE

10-02-23

This is to certify that Danish Akram Maniyar S/O Akram Maniyar, A Student of AKS'S Poona College, Has Done Internship of Accounting And Billing in my organization of 10 Days from (1-02-2023) to (10-02-2023) Working Hours - 12.00 to 6.00 Daily 6 Hours.

I Wish Him Success in His Life

Date 10-02-2023

Place- Pune

MARIYA'S BIRD FOOD STORE
St. No. 74/2 Opp. Al-Anam Building
Banodi, Pune - 411 020.
Mob. - 9351682077

TAMBOLI SERVICES

Office Address: Shop No.1, Plot No.38, Sanjay Park, Pune 411032
Phone No: 9422518443 Email: tamboliservices321@gmail.com

Date: 17/02/2023

TO WHOM IT MAY CONCERN

This is to certify that Mr. Tamboli Mohd Umar iftekhar, student of Poona College, has successfully completed a internship in the field of Document Analyzer and Uploader from 01/02/2023 to 17/02/2023 under the guidance of Salauddin Yakil.

During the period of his internship program with us, he had been exposed to different processes and was found diligent, hardworking and inquisitive. His performance exceeded our expectations and he was able complete the given task on time.

We wish him every success in his life and career.



TAMBOLI SERVICES
Shop No.1, Plot No.38, Lane No.50,
Mohammed Ali Chowk, Sanjay Park,
Pune 411032. 9422518443

Authorised Signature.

Office: 102, City Centre, Sivagangue Street,
Convent Camp, Pune - 411001, MH INDIA
Tel.: +91 20 48609777 / +91 80874 30793
Email : orangecommoditiesindia@gmail.com

**Orange
Commodities**

Regd. Address : S. No. 52, Bldg. No. 2/B, Jai Jawan Society, Wankar, Pune - 411 040, MH INDIA

To,
The Principal,
Poona College of Arts, Science & Commerce,
Pune

Subject - Internship Completion Certificate

Dear Sir/Madam,

I am happy to inform you that Marya Mujahid Sheikh have successfully completed the "Sixty Hours Internship Programme" in Business Administration - Special Subject in my organisation.


She has been provided with adequate exposure and necessary hands on training pertaining to her special subject.

I am confident that she will perform effectively in similar type of organisation.

I wish her success in future endeavours.

Thank you.

Sincerely,


Mudasir Shaikh

Name & Signature

(Authorised Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
AXI'S Poona College
Arts, Commerce & Science
Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Iqbal Mihirak Babude	3535	801704825293	Business Administration II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,



Stamp of the company

Name & Signature (Authorized Signatory)



VLS Loan Consultant Pvt. Ltd.
Trust Made to Big / Registered.

Date : 15/11/2023

15/11/2023

Yashraj - Internship Completion Certificate

We are pleased to report that **Yashraj Mubarak Babudu** has successfully completed an internship project in **Life Insurance Department** with **VLS LOAN CONSULTANTS PVT LTD.**

The internship start date was **2nd Dec 2022** and date **15th Dec 2023** and the location of the internship was **Pune**. During this period, he has successfully met the objective that were set the beginning of the project.

We are pleased to commend him and we wish him all the best for his future endeavours.

For: **VLS LOAN CONSULTANTS PVT LTD.**



DEEPAK DESHMUKH

(Human Resource Department)

PH 7066738814
PH 8300115443

 yankatreshkash@vlsloanconsultants.com
kunal@yankatreshkash@gmail.com

 **Sr.No. 19 A3B, Shop No.01, 3rd Floor,
K.K. Market, Dhantowadi, Pune - 411043**

www.vlsloanconsultants.com

PBC Pharmaceuticals & Drug Store

Address: Lane no:3, Momin Building Shop no 2, Meetha Nagar, Kondhwa,

Pune-48

Phone:9967378533

Date: 10/02/2023

TO WHOM IT MAY CONCERN

This is to certify that Mr. Jyoti Ibrahim Desai, student of Poona College, has completed a internship in the field of Medical service from 01/02/2023 to 10/02/2023 under the guidance of Mr. Shaikh.

During the period of his internship program with us, he had been exposed to different processes and was found diligent, hardworking and inquisitive, time management, customer satisfaction.

We wish him every success in his life and career.

PBC PHARMACEUTICALS
Shop No. 02, Gr. Floor, Momin Bldg,
Methanagar, Kondhwa Rd, Pune-48

Authorized Signature:



Letter Head of the Internship Provider Organisation

To,

The Principal,
..... College,
..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Ismail Doshi	5601	23010395 5400	Business Administra- -tion
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

.....
.....
.....
Stamp of the company

Sincerely,

Name & Signature (Authorised Signatory)

Irfan Iqbal Shaikh
I. Shaikh

The logo for Xpress Bees, featuring the text "XPRESS BEES" in a bold, sans-serif font. The word "XPRESS" is in black and "BEES" is in orange. Below it, in a smaller font, is the tagline "Delivering Happiness".

Address: 83/84 Shivaji Nagar Old topkhana, Near Bhagwat Garage.
Phone: 7972921151
Email: customercare@xpressbees.com

Date: 10/02/2023

TO WHOM IT MAY CONCERN

This is to certify that Mr. Ayaz Mumtaj Shah, student of Poona College, has completed a internship in the field of Courier service from 01/02/2023 to 10/02/2023 under the guidance of Bipin Gore.

During the period of his internship program with us, he had been exposed to different processes and was found diligent, hardworking and inquisitive, Time Management.

We wish him every success in his life and career.

A handwritten signature in black ink, appearing to be "Bipin Gore".

Authorized Signature



TAMBOLI SERVICES

Office Address: Shop No. 1, Plot No. 38, Sanjay Park, Pune-411032
Phone No: 9422518443
Email: tamboliservices321@gmail.com

Date: 28/02/2023

TO WHOM IT MAY CONCERN

This is to certify that Ms. Ansari Nazrana Shamshad, student of Poona College, has successfully completed a internship in the field of Document Analyzer and Uploader from 13/02/2023 to 28/02/2023 under the guidance of Salauddin Vakil.

During the period of her internship program with us, she had been exposed to different processes and was found diligent, hardworking and inquisitive. Her performance exceeded our expectations and she was able complete the given task on time.

We wish her every success in his life and career.



TAMBOLI SERVICES
Shop No. 1, Plot No. 38, Lane No. 50,
Mohammed Ali Chowk, Sanjay Park,
Pune 411032. MOB - 9422518443

Authorised Signature

AG FURNITURE

Vodre Pisall Road, Near Khatti Machine Chowk
Mobile: 9822476900
mail: agfurniture2018@gmail.com
website: www.agfurniture.in



To,
The Principal,
AK's Poom College,
Camp, Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

We are glad to inform that Miss. Qureshi Nashara Ashfaq from AG Furniture has successfully completed her internship from 1st January to 10th January 2023.

During her internship, she was exposed to the various activities in office assistant management and administration as assistant Admin.

We found her extremely inquisitive and hard working. She was very much interested to learn and also willing to put her best efforts and get in to the depth of the subject to understand it better.

Her association with us was very fruitful and we wish her all the best in her future endeavours.

Thank You

Sincerely,

Shubhar Syyed

For A&G Furniture

Proprietor

Letter Head of the Internship Provider Organisation

To,

The Principal,
POONA College,
PUNE (Place)

Subject: Internship Completion Certificate ----

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hour Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Abdul Shaiq	5604	34957995-4003	Business Administration
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature (Authorized Signatory)

For **AKBAR & CO.**

Lakshmi
Proprietor

Stamp of the company

AKBAR & CO.
Skin Merchant
125758, Bhamburda Path,
Pune - 411 002

AKBAR & CO

SKIN MERCHANT

1758 Mhawon (with Post) 02.

Mob: 9922881177

9637134933

TO,
Akbar Sayyed,
Poona College of Arts Science and Commerce,
Camp, pune-01.

Subject- 60 Hours Internship Program.

Dear Sir,

I zaheeruddin SHAIKH, I'm writing this letter to inform you that, MR. MOHAMED ABRAR ZAHEERUDDIN SHAIKH will be doing Internship as a PURCHASE, SALES AND MARKETING under my guidance. He will be working 60 HOURS. 6 DAYS per day according to his convenience.

Zaheeruddin
05/05/23
Authorized Sign.

SAFAMOTORS

Where You Can Find The Right Car

Shop No-267, New Nona Path, Island Park, Pune-02.

Mob: 7385441604

TO,
Akbar Sayyed,
Poona College of Arts Science and Commerce,
Camp, pune-01.

Subject- 60 Hours Internship Program.

Dear Sir,
I ASAD SHAIKH, I'm writing this letter to inform you that, MR. MUAVIN MANSOOR SHAIKH will be doing Internship as a SALES AND MARKETING under my guidance. He will be working ~~60~~ ⁴⁵ DAYS. 6 HOURS per day according to his convenience.

ASAD SHAIKH
SALES & MARKETING

Authorized Sign,



SYSTEM FINANCE

TO WHOMSOEVER IT MAY CONCERN

This is to certify that **Mr. Fardeen Abdulrauf Bagwan** has successfully completed 2 weeks of an internship program from 21 Dec 2022 to 30 Dec 2022 in the Quality department of our organization.

He was highly motivated and hardworking. He worked sincerely at his tasks and did a very good job.

Sincerely,



IQRA ENTERPRISES

Kashiwadi Bhawani Peth, Near 10 No Colony
Pune-411042 Maharashtra.

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/Sir,

I am happy to inform you that following students of your college have successfully completed the 'SixtyHours Internship Programme' in this organisation.

Sr.No	Nameofthestudent	RollNo	AadharNo.	Specialsubject
1.	Shweta Arora	5566	452829837403	Business administration -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

IMRAN SHAIKH

Name & Signature

(Authorised Signatory)

IQRA ENTERPRISES

Kashiwadi Bhawani Peth, Near 10 No Colony
Pune-411042 Maharashtra.

LOGSHEET OF WORK PERFORMED DURING INTERNSHIP

1. Name of the student : Shahh Arbaz Biyar

2. Name of the College : IT.Y.B.Com.

3. Division and Roll Number : Div D, Roll No:5586

4. Address : Kashiwadi bhawani peth near 10 no colony pune-411042

5. Contact Number : 7410741328

6. Email ID : arbazshahh63112012@gmail.com

7. Special Subject : Business administration - II & III

8. Internship start date : December 01, 2022

9. Internship end date : December 15, 2022

LOGSHEET OF WORK PERFORMED DURING INTERNSHIP

Date	Time		Total hours	Detail of work done	Signature of officer	Signature of student
	From	To				
01-12-2023	10:00 AM	02:00 PM	4 HRS.	Shop Visit and Information	<i>[Signature]</i>	<i>Arbaz</i>
02-12-2023	10:00 AM	02:00 PM	4 HRS.	Analysis the Machineries	<i>[Signature]</i>	<i>Arbaz</i>
03-12-2023	10:00 AM	02:00 PM	4 HRS.	Calculating the future profit by calculating invested money in business	<i>[Signature]</i>	<i>Arbaz</i>
04-12-2023	10:00 AM	02:00 PM	4 HRS.	Labour Management	<i>[Signature]</i>	<i>Arbaz</i>
06-12-2023	10:00 AM	02:00 PM	4 HRS.	Material used for demolition of scrap materials	<i>[Signature]</i>	<i>Arbaz</i>
07-12-2023	10:00 AM	02:00 PM	4 HRS.	How to handle and collaborate with labours to get done the	<i>[Signature]</i>	<i>Arbaz</i>

UNDERTAKING FROM STUDENT

To,
The Manager (HR),
ICRA ENTERPRISES
Pune - 42

Subject: Undertaking from Student

Respected Madam/Sir,

I am a student of Poona College of Arts, Science And Commerce, Camp, Pune-01.
I am studying in semester VI of T.Y.B.Com. I am going to join your esteemed
organisation for my sixty hours Internship programme during 01st December
2022 to 15th December 2022.

I assure that I will follow all the rules and instruction issued by you. I will be solely
responsible for my behavior and performance during the internship period.

I will not disclose any information that is made available to me to anyone during
or after the internship period.

I assure you that I will do my best and the internship opportunity provided to me
will be a mutually rewarding experience.

Thank you.

Yours sincerely,

Abbaz Shaikh

Abbaz

(Name & signature of the student)

Date:

Place:

UNDERTAKING FROM STUDENT

1. Name of the Student : Shaikh Arbaz Muzt
2. Class : T.Y.B.Com.
3. Division and Roll Number : DIV D, Roll No. 5166
4. Present address : Bakhwanji bhawani path, near 10 no colony
Pune-411042
5. Permanent address : Bakhwanji bhawani path, near 10 no colony
Pune-411042
6. Contact Number : 9418741328
7. Contact Number (Parent) : 9921603985
8. Email ID : arbazshaiikh03112012@gmail.com

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Undertaking From Student

Respected Madam/Sir,

I am studying in semester V/VI of T.Y.B.Com. I am going to join IQRA ENTERPRISES for my sixty hours' internship programme during 01st December 2022 to 15th December 2022.

I assure that I will follow all the rules and instruction issued by the internship providing organisation. I will be responsible for my behaviour and performance during the internship period.

Thank you.

Sahida Shaikh.
सहिदा शेख

(Name & Signature of parent)

Date:

Yours obediently,
Arbaz Shaikh.
Arbaz

(Name & signature of the student)

Internship Certificate

This is to certify that Ms. Gajala Jamil Zari, T.Y.B.Com. Student at Poona College of Arts, Science & Commerce, Pune, has completed her Desktop Support Internship at 3C IT SOLUTIONS & TELECOMS (I) PVT. LTD. She worked under the guidance of Mr. Govind Sahu from 05th Jan to 20th Jan 2023.

Ms. Zari worked under 'Desktop Support Engineer'. As a part of the project, she understood how the Desktop Support Management works.

She is a self-motivated, hard worker that is always looking to learn new skills. Ms. Zari has done more than her role's responsibilities. We wish her all the best in all her future endeavors.

For 3C IT Solutions and Telecoms (i) Pvt Ltd


Govind Sahu

GM- Service & Operation.



Microsoft | IBM Certified

3C IT SOLUTIONS & TELECOMS (I) PVT. LTD.

ZAMZAM FURNITURE

THE COMPLETE FURNITURE DESTINATION

Date: 17-02-2023

TO WHOM IT MAY CONCERN

This is to Certify that Mr. Mohammad Shoalb Ajim Raj has done his internship in Production Manager in Zam Zam Furniture from 01/02/2023 to 17/02/2023 under the guidance of Zaid Sayyed.

During the time frame he has been a sincere and thoroughly professional employee. He had been exposed to different processes and was found diligent, hardworking and inquisitive.

We wish him every success in his life and career.

Zam Zam Trading
All Types Furniture Manufacturer & Supplier
Kamlat Project, Kothrud - Pune Khurd,
Pune-40. Mob. 9823116812



Authorised Signature

Zam Zam Trading
All Types Furniture Manufacturer & Supplier
Kamlat Project, Kothrud - Pune Khurd,
Pune-40. Mob. 9823116812

S.NO. 27/14/2, Opp. AGARBHATTI FACTORY, BURNANI INDUSTRIAL ESTATE, PUNYADHAM AHIRAM

ROAD, KONCHWA BUDRUK, PUNE-411018.

PHONE: 7228348434 / 9850265075. E-MAIL: zamzambfurniture@gmail.com.



SUNSHINE FIELD PVT LTD

Address: Section 10 East of Nagar near Yashwantrao Chavan Pratishthan
Mumbai - 400 006

Email: hr@sunshinefield.com

Contact: 7875677824

To,

The Principle,

Poorba College of Commerce,

Subject: Internship completion certificate of Aliya Shaikh

DEAR SIR,

I am happy to inform you that following student of your college have successfully completed the sixty hours of internship programmed in this organization

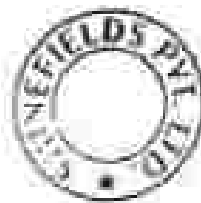
I have found her to be a hardworking and focused towards work who is always ready to learn new things. She performs excellent with well behavior and she is punctual at time to report before me day to day. she worked sincerely on his assignments and his performance was par excellence

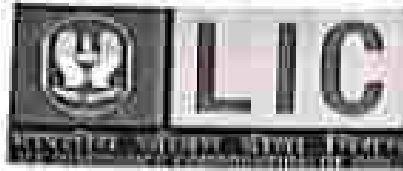
I wish her best of luck for her further.

Sincerely,

Munawar Shaikh

Thankyou





ASMA SAYYED
(Manager)

Ref no 12745263-25

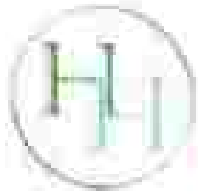
This is to certify that Sidra Rafil Sayyed O/O Rafil Sayyed, A Student of ARIS'S Poona Collage, Had Done the Customer Care Representative Internship in our organization of 10 Days From (10-02-2023) to (20-02-2023) A short Internship in A STUDY ON CONSUMER PRECEPTION ABOUT LIFE INSURANCE at this branch.

We wish her every success in life.

Date 21-02-2023

Place: Pune

Authorized Signature



HAKIMI HARDWARE

TO WHOMSOEVER MAY CONCERN

This is to certify that **Mr. Mohammed Hakim** has successfully completed 1 week of an internship program from 02 Feb 2023 to 10 Feb 2023 in the Sales department of our organization.

He was highly motivated and hardworking. He worked sincerely at his tasks and did a very good job.

HAKIMI HARDWARE
Pudhi Siddhi Apt, Solapur Road,
Vadgaonki, Madhapur PUNE

Sincerely,

Internship Training Certificate

This to certify that Shaikh Adil Haidar Pursuing His B.Com in 2nd year has successfully completed internship at Rahil Cosmetics Bhawan Peth Near Santa Dairy A11602 from 02/04/2023 to 10/04/2023.

We found him sincere, hardworking, technically sound and talented. He worked well as a part of team during her tenure.

We take this opportunity thank him and wish him all the best for future.

Your Sincerely
For Rahil Cosmetics



Rafique Shaikh
Proprietor

FOR RAHIL COSMETICS

PROPRIETOR



Suhaba Interior designs

Specialist in Interior Designing, Decorative interiors, Decorative exteriors
55, Bhasani Path, Pune 411007

REF NO:-4538

DATE:- 01/03/2023

This is to certify that Anubhav Kamble of BCOM Part II, SEM 6, and Roll No.5637 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 02/01/2023 to 01/02/2023 for the academic year 2022-23

During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavours.



SUHABA

Partner Contractor
55 Bhasani Path, Pune
9022804666
www.suhabainteriors.com
Pune Maharashtra India

Authorized Signature with Stamp

Suhaba Interior designs

Specialist in: Painting, Interior designing, Decorative Interiors and exteriors
BNS, Bhamburda Peth, Pune 411012

REF NO:-4523

DATE:- 01/03/2023

This is to certify that Toufiq shaikh of B.COM Part II, SEM 5, and Roll No.5605 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 02/02/2023 to 01/03/2023 for the academic year 2022-23.

During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavours.


SUHABA
Printing Contractor
All Type of Flat Bungalow
New Bhandari Peth, Near Police Chowk, Pune
Mob: 9823405482, 9823405482
Prop. Farhadkhan I. Shaikh

Authorized Signature with Stamp



11th April - 17th April 2023

Dear Team Front Staff,

Over the past 60 hours of internship, you worked with our team of dedicated and hardworking individuals where you learnt about the food industry and customer service.

During the time at Madina Foods you have been able to gain hands-on experience in various areas of the business, including food preparation, customer service, and inventory management. You also had the opportunity to work with a diverse group of customers, and learned how to handle a variety of situations in a calm and professional manner.

Thank you for your continued hard work and dedication.

Sincerely,

Madina Foods

MADINA FOODS

Shop No. 30, C. S. Market,
Camp, Pune-411 001.
Tel.-020-26334784 - - Parvati

Mukul Shinde

Sr Manager

Shop No 30 C-S Market Camp, Pune- 411001

ADRENALINE SPORTS

HOYATE, UNDRE - 411060

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Peona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Arshad Mohammadhasan Miya	5660	881917020940	Business Administration -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,
FOR ADRENALINE SPORTS



Authorized Signatory
Name & Signature

(Authorised Signatory)



AM ENTERPRISES



Mr. Faris Kasim Shaikh
Owner of AM Enterprises
Yilmam Nagar Wakdevwadi pune 41

Dear Faris Kasim Shaikh

Sincerely,

AM Enterprises is a RTD Consultant & Services. Here we are doing all types of RTD works. We also have motor driving school. We collect work from RTD, also from private customer. Car sales company's, Online car market, etc.

We provide this internship to Mr. Faris Kasim Shaikh who is student of Panna college of arts, commerce and science pune 01. for his educational purpose.

We hope this internship programme is easy, helpful and understanding for him for further studies.

Mr. Faris Kasim Shaikh

Date 12/07/2022

Place : Pune



Mo : 9122728901

Office no : 8237231230

Email-id : amenterprises7121@gmail.com





Anil Mardikar & Co.

CHARTERED ACCOUNTANTS

2, Bhingwadevi, Madhuranath, Jadhav, Fl. 3 (B), 2nd Floor, B, No. 883, Keshavnagar, Poonacollege Apartment, Poonam, Maharashtra, Post Code - 411005, Mob. - 9122601000, E-mail - anil@anilmardikar.com

TO,
THE PRINCIPAL,
POONACOLLEGE,
CAMP 411001

Subject : Internship Completion Certificate.....

Dear Madam / Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this or organization.

Sr.No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	AKASH ANIL TITKARE	5607	884240512521	Business Administration

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organization.

I wish them every success in future endeavors.

Thank you.

For ANIL MARDIKAR & CO.
Chartered Accountants


(GA. MADHURNATH S. JADHAV)
Partner
M. No. 150373

Name & Signature

(Authorized Signatory)

Letter Head of the Internship Provider Organisation

To,
The Principal,
____ College,
____ (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Alfat Khuntia	5668	27925341-2389	Business Administration 152
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

For, ADORN MEDIA LLP

Authorized Signatory
Stamp of the company

Sincerely,
Name & Signature (Authorized Signatory)
KARIM TAMBOLI

INTERNSHIP COMPLETION CERTIFICATE

Letter Head of the Internship Provider Organisation

To,
The Principal,
..... College,
..... (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.


Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Aman Bagwan	5635		Business Administration
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.


Jalkishan Enterprises
537 Market Yard, Gate No.3,
Pune-411087



Sincerely,

Name & Signature
(Authorised Signatory)

INTERNSHIP CERTIFICATE

This is to certify that Ms. Tejal Makite has successfully completed her Internship program at Right Move Staffing Solutions Private Limited as a HR Recruiter.

Internship Duration- 01/12/2021 - 21/12/2021

During her tenure, she excelled in executing all assigned tasks and was competent and enthusiastic throughout.

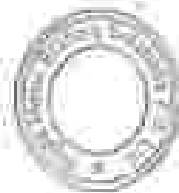
We wish her great success in all of her future endeavors.

Right Move Staffing Solutions Pvt. Ltd.



Garima Singh Walle

Director



RIGHT MOVE STAFFING SOLUTIONS PRIVATE LIMITED

T-313, Ashoka Mall, Next to Parita Jewellers, Bhand Garden Road, Pune - 411 001, (India)

Tel: +91-20-41227397 Mob: +91-9162020493 E-Mail: info@rightmoveconsultants.com

www.rightmoveconsultants.com CIN: U76100MH2018PTC177424

Maklumz.co

Ganpatibhai Lalwade Hall Lillanagar road, Pune, Maharashtra
Mobile - 7447810603

To,

The Principal,

Aki's Poona College,

Camp Pune

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that Aman Afzal Inamdar student of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

This student have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

A handwritten signature in black ink is written over a circular stamp. The stamp contains the text 'MAKUMZ.CO' and 'PUNE' around the perimeter. The signature is written in a cursive style.

Sincerely,

Name & Signature

(Authorized Signatory)



RADHESHAWARI NAGAR PROMOTERS & DEVELOPERS

GAT NO 881854, AT WAGHOLI, BARDOLI ROAD, TALUKA HAVELI, DISTRICT-PUNE.

REG NO: PNA (A) / HSG / (14) / 159 / 1915-20.

PH. NO: 020-46020537, Email: radheshwarinagar@gmail.com

CERTIFICATE OF INTERNSHIP

This is to certify that MRS. RUKSANA DARUWALA student of PONDNA COLLEGE OF ARTS, SCIENCE & COMMERCE Camp, Pune – 411001 having a Roll no, 5633 Division D has successfully completed the Internship Programme from 6th December to 28th December in our organization RADHESHWARI NAGAR PROMOTERS AND DEVELOPERS at Wagholi Pune.

Radheshwari Nagar
Promoters & Developers

[Handwritten Signature]
Date

Signature Authorities

ADRENALINE SPORTS

HOTEL, DINDI - 411060

INTERNSHIP COMPLETION CERTIFICATE

To,
The Principal,
Poona College of Arts,
Science & Commerce,
Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Azmat Amjad Shaikh	5655	657798804407	Business Administration -II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,
FOR ADRENALINE SPORTS


Authorised Signatory
Name & Signature

(Authorised Signatory)



Inamdar & Co.

Konark Road, Kharolpada Khurd, Pune, Maharashtra - 411048
Mobile - 9552319748
inamdar@inamdar.com
Website :- www.inamdar.co.in

To,
The Principal,
Aki's Poona College
Camp Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Bhagy Sushela Muthala	5008		Administration
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Proprietor
INAMDAR & CO.
Firm No. 005401

Sincerely,

Name & Signature
(Authorized Signatory)

28 January 23

Internship Training Certificate

This to certify that Axel Joshua Sarjoo (Residing) His B Comp in 3rd year has successfully completed internship at Sr No 35 Plot No 43, 46 Jambhwal, Thelewall, Katra 411045 from 01/08/2022 to 31/08/2022.

We found him sincere, hardworking, technically sound and oriented. He worked well as a part of team during his tenure.

We take this opportunity thank him and wish him all the best for future.

Your Sincerely,
For Satyam PVC Doors.



Sanjay Sonwane,
Proprietor



CAFE QUICK STORIES
CLOD'S HILL ROAD, KIRIBATHA-411048

Date: 15th Dec 2023

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Mr. Aban Howan Petrick has successfully completed 2 weeks of his internship in Server at Cafe Quick Stories from 19th Dec 2022 to 31st Dec 2022.

During the internship he demonstrated communication skills with a self-motivated attitude to learn new things. His performance exceeded expectations and was able to complete the assigned task successfully on time.

We wish him all the best for his future endeavours.

Yours faithfully,

Authorized Signatory

(Tamil Sanyal)


For Saubhagy Ganguly (OPC) Pvt. Ltd

Directr



tamil.sanyal@gmail.com



www.cafequickstories.com



8390065556

SUNSHINE FIELD PVT LTD

Address : S.No.10 (2nd) Nagar West Tinsuk (Chh.durg) Westwada pin- 05

Email : banshihahlu0944@gmail.com

Contact: 9875877930

To,

The Principle,

Peena College of Commerce,

Subject: Internship completion certificate of -----

DEAR MADAM,

I am happy to inform you that following student of your college have successfully completed the sixty hours of internship programmed in this organization.

SR.NO	NAME OF THE STUDENT	ROLL NO.	AADHAAR	SPECIAL SUBJECT
1	Taskia Panwale	5634		BUSINESS ADMINISTRATION

The student has been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that the student will perform effectively in similar type of organisations.

I wish them every success in future endeavours.

Thanks

Sincerely,

Name and Signature



OM SAI ENTERPRISES

DECEMBER, 2022

✉ omsaienterprises@gmail.com

🌐 www.omsaigroup.in

📍 @omsaienterprises

Subject - Internship Completion Certificate

We state on record that **MD ABDULLAH MD RAHMATULLAH** has successfully completed an internship project in Sales Department with **OM SAI ENTERPRISES**.

The internship start date was **01 Dec 2022** & end date **15 Dec 2022** and the location of the internship was in Pune. During this period, he has successfully met the objective that were set the beginning of the project.

He is a promising candidate and we wish him all the best for his future endeavors.

For, **OM SAI GROUP.**

For OM SAI ENTERPRISES


Proprietor

DHAIRYA CHAUDHARI
(Managing Director)



ACTIVE ELECTRICALS

MAYUR PANCH APARTMENTS, KONDHWA MAIN ROAD, KONDHWA, PUNE, MAHARASHTRA 411018

Date: 15th Jun 2023

INTERNSHIP COMPLETION CERTIFICATE

This is to certify that Mr. Bilal Sadique Bagwan has successfully completed 2 weeks of his internship as a Salesman at Active Electricals, from 01 Jan 2023 to 09 Jan 2023.

During the internship he demonstrated good reading and communication skills with a self-motivated attitude to learn new things. His performance exceeded expectations and was able to complete the assigned task successfully on time.

We wish him all the best for his future endeavours.

Yours faithfully,

ACTIVE ELECTRICALS

Authorized Signatory
(Javed Sheikh)

ACTIVE Electricals

Mayurpankh Apts, Kondhwa Main Rd,
Opp. Sheetal Petrol Pump, Pune - 411018.
Mob- 9823117861

Contact no.- 8530266135 E-mail - info@activeelectrical.co.in www.activeelectrical.com

Page 12/12002

Internship completion

letter

To,
Saidat Ishaq Sheikh
4th Floor, Flat no 416
Galaxy AS building
411045
Contact No- 7307865026

This is to Certify that Saidat Ishaq Sheikh has done his internship in JK Events Planners -
Pune-411 046, from 1/12/22 To 10/12/22

During the time frame he has been a sincere and thoroughly professional employee. Below

are the key projects he has worked on successfully

JK EVENTS PLANNERS
Event Planning Services
Pune, Maharashtra
www.jkeventsplanners.com

For JK EVENTS PLANNERS

PROPRIETOR

MIL AKBAR SAYYID





DCC Infotech Pvt. Ltd.

Reg. Off. : Office No. 12/1A/1, 1st Floor & 2nd Floor, 11A, Old, 1st, 175 & 176, Ashwamedh Place
Apartment Complex, 1st Block, Deccan, Pune City, Pune, Maharashtra, India - 411004
Tel : +91 20 4705547 / 548, Mob : +91 98 10121449 / 9875501775
E-mail : hr@dccinfotech.com, Website : www.dccinfotech.com

Date: - 01st Dec. 2022.

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Ms. Pratiksha Lakshmi Pawar has done her internship in at DCC Infotech Pvt. Ltd., Pune, from 01st Dec. 2022 to 31st Dec. 2022.

She has worked on co-ordinating the Customers, Follow up of Customers.

During his internship she has demonstrated her skills with self-motivation to learn new skills.

Her performance exceeded our expectations and she was able to complete the project on time.

We wish her all the Best for her upcoming career.

For DCC Infotech Pvt. Ltd.


Authorized Signature



To,
The Principal,
Pooza College Arts Science Commerce,
Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Mohammed Alam Sarfaraz Alam Shaikh	5591	6624 7649 4302	Business Administration Paper II and III

These students have been provided with adequate exposure and necessary handson training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

A. B. Xerox
Shop No. 17, Aashiyana Apartment,
Opp. Pooza College, Pune-41.
Mob.: 9922676915



kangaroo kids

Dear Sir/Ma'am,

This is to update you that Saloni Aru was working as a Intern in our school Kangaroo Kid's , Viman Nagar Branch and she completed her 6 months here .She is a very hardworking girl and we wish her a good luck for her future.

Thanks and Regards,

Priya Malhotra

Center Manager

Date : 1/09/22

Kangaroo Kids / Viman Nagar
Pre School / Day Care / Activity Centre
Contact: 9145121888



Plot No 63, Parkland Society,
Sakore Nagar, Viman Nagar, Pune - 411014
9145121333, 9145121888
pune.vimannagar@kangarookids.co.in



Scanned with OKEN Scanner

Letter Head of the Internship Provider Organisation

To,
The Principal,
AK's Peona College,
Pune-411048

Subject: Internship Completion Certificate.

Dear Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	(ca) Mohammad Shouk Ajam	5263	726277773111	Business Administration (R & IT)

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Name & Signature (Authorized Signatory)

Zam Zam Training
All Types Furniture Repair & Polishing
Khadki Road, Khandwa Road,
Pune-48. Mob. 9823116812

Stamp of the company

BEAUTY LIFE

Address: Near Baba Jee, MIDC Camp, Pune-411

Phone: 922889888

Email: beautylife@gmail.com

Date: 27/02/2023

TO WHOM IT MAY CONCERN

This is to certify that Mrs. Hajar Waseem Hale, student of Poona College, has completed a internship in the field of Makeup artist assistant from 01/02/2023 to 27/02/2023 under the guidance of Snehal Karnawat.

During the period of her internship program with us, she had been exposed to different processes and was found diligent, hardworking and inquisitive.

We wish her every success in her life and career.


Authorised Signature
BEAUTY LIFE
NEAR BABAJEE
CAMP PUNE 01

DiZiLeads™

Management Solutions Pvt Ltd

DiZiLeads Management Solutions Pvt. Ltd.
Office No. 606/607, Confluence Galata Mall, Atcharya Road, Mandwa, Pune.
Telephone: Pune - 411028
info@dizileads.com
Date: 13th Feb 2023

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Mr. Muhammad Rabim Khan has successfully completed 2 weeks of an internship program from 19th Jan 2023 to 30th Jan 2023 in the Quality Department of our organization.

He was highly motivated and hardworking. He worked sincerely at his tasks and did a very good job.

We wish him/her great success in his/her future endeavours.

Sincerely,



Authorized Signature

CONTACT US



info@dizileads.com



Office No. 606/607, 6th Floor, Confluence Galata Mall, Atcharya Road, Mandwa, Pune.



www.dizileads.com

Strawberry Kids Pre-School

The First Step towards Success
along with Happiness!



SUB : INTERNSHIP COMPLETION LETTER

We are glad to inform you that Miss. Anisa Gaus Khan from Strawberry Kids Pre-School has successfully completed her internship from 1st February to 31st March 2023.

During her internship, she was exposed to the various activities in office assistant management and administration as assistant Admin.

We found her extremely inquisitive and hard working. She was very much interested to learn and also willing to put her best efforts and get in to the depth of the subject to understand it better.

Her association with us was very fruitful and we wish her all the best in her future endeavours.


Strawberry Kids Pre-School
Principal



— R. A. Dhurapat



Shivneri Nagar, Lane 1
Kondhwa, Pune 411048



+91 7038779295



strawberry.preschoolpune@gmail.com

www.StrawberrySchool.com



Scanned with OKEN Scanner

GLOBAL BAKERS

Address: Survey No.49, Lane No.6, Bhagyoday Nagar, Kondhwa, Pune - 41
Phone: 9422866793
Email: globalbaker@gmail.com

Date: 10/02/2023

TO WHOM IT MAY CONCERN

This is to certify that Mr. Anand Manoj Dadas Mahad Jirhad, student of Pooza College, has completed a internship in the field of Marketing from 01/02/2023 to 10/02/2023 under the guidance of Anant Rane.

During the period of his internship program with us, he had been exposed to different processes and was found diligent, hardworking and inquisitive.

We wish him every success in his life and career.



Authorized Signature
GLOBAL BAKERS
E.NO.48 BHAGYODAY NAGAR
KONDHWA KHURD, PUNE-48

India Lock & Key Maker

A-30 New Mangalwar Path Near Mangalgarh Check Post-11

Dehra Dun, Uttarakhand

Contact No. 01772940008

Email id: Indialock&keymaker@gmail.com

DATE: 5/5/2013

To
The Principal,
Ari's Poona College,
Camp, Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "60 Days Hours Internship Programme" in this organization.

Sr. No.	Name of the student	Roll No.	Adhar No.	Special Subject
1.	Shankh Zaid Alim	6657	4431 3479 5867	Business Administration
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

Sincerely, For India Lock Key Maker



Proprietor

Name & Signature (Authorized Signatory)

To,
 The Principal,
 Mrs. Pooja College,
 Camp, Nagpur

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sl. No.	Name of the student	Roll No.	Roll No.	Special Subject
1	Shakthi Mohanrao Puzari Hanf	5531	5531	Business Administration
2				
3				
4				
5				
6				
7				
8				
9				
10				

These students have been provided with adequate exposure and necessary funds, so training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you

Sincerely,

(Signature)



Name & Signature (Authorized Signatory)

For B. NERKAR AND ASSOCIATES



IQRA ENTERPRISES

All Types of Scrap Depot Sales & Purchase

Kashinadi, Bhawanil Pad, Opp. PMC Colony, Pune 42.
Mob : 9921003985 / 9040889346



Date :

Ref. No. :

IQRA ENTERPRISES

Kashinadi, Bhawanil Pad,

Opp. PMC Colony, Pune-42.

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Mr. Arbaz Shaikh, has successfully completed his internship in the Organisation named IQRA ENTERPRISES from 1-Dec-22 to 15-Dec-22.

During his tenure, we found him to be honest, dedicated, hardworking and well-behaved and his services were found to be satisfactory.

Name : Imran Shaikh,
Designation : Owner (Supervisor)
Date : 15th Dec'22.

IQRA ENTERPRISES
Kashinadi, Bhawanil Pad,
Opp. PMC Colony No. 10,
Pune - 42. No-9921003985

TechnoS Media Industries (I) Pvt.Ltd

210, The Capital, Karam Bazar NIBM Pune-411046

Email: hr@technosol.com

Internship Certificate

This is to certify that Mr. Sahil Sheikh student of Ael's Poona College has completed internship in Learning Business Development Process with TechnoS Media Industries (P.L., Pune)

His Internship started on 1st February 2023 to 10th February 2023.

During this period the student learn more and up to the mark.

We wish him all the best in all his future endeavors.

Place: Pune

Date:

IMRAN

Imran Khan

(HR - Manager)



Registered Office : 205, Marishi Plaza NIBM Pune-411046

Website: www.technosol.com



Scanned with OKEN Scanner



ALISA TRAVELS

app: alisa Travels app | alisa@alishatravels.com | www.alishatravels.com

Date: 10/02/2023

TO WHOM IT MAY CONCERN

This is to certify that Mr. Ibaad Naim Shaikh student of Poona College, has completed a internship in the field of Travels service from 01/02/2023 to 10/02/2023 under the guidance of Sameer Shaikh. During the period of his internship program with us, he had been exposed to different processes and was found diligent, hardworking and inquisitive, Time Management. We wish him every success in his life and career.



Authorized Signature:

INT. & DOMA PACKAGE: TICKETING, WORLDWIDE VISA, PASSPORT ASSISTANT, HOTEL BOOKING, WAKALA VISA STAMPING, BILLANCE, FOREIGN MFA / APOSTILLE, VFS/EMBASSY APPOINTMENT





Website : www.al-khalifatur.com

Al-Khalifa

Tours & Travels India Pvt. Ltd.

HAJ - UMRAH - ZIYARAT

AMIR SHAIKH ☎ 8669280314 📞 7038109891

(Managing Director)

77A, Chudaman Talim, Bhawani Peth, Opp. Navin Hindi School Pune - 411 042. Email : amir@al-khalifatur.com

Ref. No.

Date :

Internship completion letter

To
Kaif Rauf Sayyed
7/ Salisbury park near
Team jug dargar madrasa building
2 floor pune-411 007
Contact No- 98341 96468

This is to Certify that kaif Rauf Sayyed has done his internship in Jr. Accountant at AL-KHALIFA TOURS AND TRAVEL IND.PVT.LTD , office no 736 Shop no 2 Chudamantalim Bhawani peth Pune-411 042, from 02/12/2022 To 09/12/2022

During the time frame he has been a sincere and thoroughly professional employee. Below are the key projects he has worked on successfully



Your Faithfully,

AMIR SHAIKH



NS ENTERPRISES

Address: Plot No. 12, Near Pimpri Chinchwad Bypass, Pimpri Chinchwad, Pune-411 006
Contact: Email: ns@nsenterprises.com / 98220 4126 / 98220 4127

Ref. No.

To,
The Principal,
AAI's Pimpri College of Arts,
Science & Commerce College,
Pune (Pune)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organization.

Sr. No.	Name of the student	Poll No.	Aadhar No.	Special Subject
1.	ANISH KUMAR SARDI	2020	2008 0103 7703	BUSINESS ADMINISTRATION

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.



NS Enterprises
Name's Signature
(Authorized Signatory)

Date: 26/04/2023

Ref: HR/2023/023

EXPERIENCE CERTIFICATE

To Whosoever It May Concern

This is to confirm that Mr. FAHAD SAADH worked as an "Social Media Marketing Executive" in Support Department, from 1st September, 2021 to 31 March 2023.

During his tenure we found him sincere, dedicated and hard working.

As we observe him (dedicated and honest about his work).

We wish him success in his future endeavours.

For:

HR Team



Mairraads
Authorized Signatory

To,
The Principal,
_____ College,
_____ (Place)

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Afrag thakla	5814	8131-5210-5220	Business Administration
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.


I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

शरद साईन हार्डिंग अँड स्टोर्स प्राइवेट लिमिटेड
महाराष्ट्र, विदर्भ क्षेत्र
कोल्हापूर, पुणे-५११ ०६६
mgr of the company

Sincerely,

Name & Signature (Authorised Signatory)
Afrag thakla


Admission Certificate

Office Address: Shree Sai H. Srinivasulu, Poojapada, Palle, CC

Contact: 9325229968

Email: info@shreesaih.com

Date: 11/03/23

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Alim Shauk has done his/her internship in [Designation of Internship] at [Admit, Samsam and Decorators], Palle, from [02/02/23] to [10/03/23]

He has worked on a project titled Project P21. This project was aimed at Marketing the party. As part of the project, he/she has managed to execute the event.

During his internship he has demonstrated his skills with self-motivation to learn new skills. His performance exceeded our expectations and he was able to complete the project on time.

We wish him all the best for his upcoming career.



Authorizing Signature

Alim Shauk and Decorators

Alim Shauk and Decorators

Shree Sai H. Srinivasulu

Poojapada, Palle - 521102



MONDIAL BUSINESS PROCESS

Office Address: Brachina Estate Building 1st Door, near Lynd Hotel, Pune, Kondhwa
Email: mondialprocess01@gmail.com Phone No: 8889003319

Date: 28/02/2023

SUBJECT: INTERNSHIP COMPLETION CERTIFICATE

This is to certify that Ms. Asfiya Rafique Shaikh, student of Poona College, has successfully completed a internship in the field of document analyzer and uploader from 13/02/2023 to 28/02/2023 under the guidance of Azim Shaikh.

During the period of her internship program with us, she had been exposed to different process and was found diligent, hardworking and inquisitive. Her performance exceeded our expectations and she was able complete the given task on time.

We wish them all the best for future endeavors.



Mondial Business Process

Proprietor

Authorized Signature





10/10/2023 11:00 AM
Satyam DOOR
10/10/2023 11:00 AM

1 April 23

Internship Training Certificate

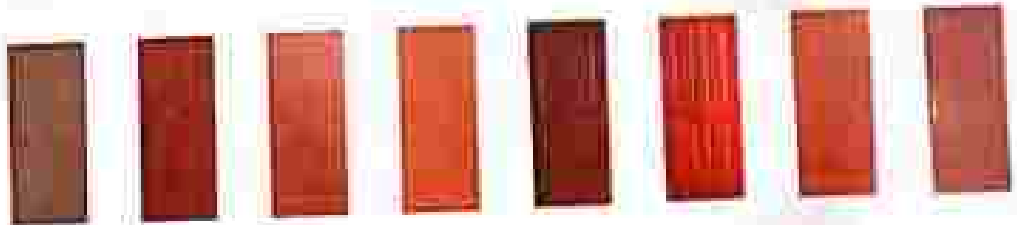
This to certify that Asmita Kalyan Jagtap Pursuing her B Com in 3rd year has successfully completed internship at Sr.No 25 Flat no :43, 46 (ambhivadi , Cholewad), Kozari 411046 from 01/03/2023 to 31/03/2023.

We found her sincere, hardworking, technically sound and oriented. She worked well as a part of team during her tenure.

We take this opportunity thank her and wish her all the best for future.

Yours Sincerely,
Satyam RYC DOOR

FOR SATYAM DOOR
Kalyan Jagtap
Proprietor



Internship Certificate

This is to certify that Ms. Asiya Fahim Khan, T.Y.B.Com. Student at Poonia College of Arts, Science & Commerce, Pune, has completed her Desktop Support Internship at 3C IT SOLUTIONS & TELECOMS (I) PVT. LTD. She worked under the guidance of Mr. Govind Sahu from 05th Jan to 20th Jan 2023.

Ms. Khan worked under 'Desktop Support Engineer'. As a part of the project, she understood how the Desktop Support Management works.

She is a self-motivated, hard worker that is always looking to learn new skills. Ms. Khan has done more than her role's responsibilities. She has always been keen on taking new tasks. We wish her all the best in all her future endeavors.

For 3C IT Solutions and Telecoms (I) Pvt Ltd


Govind Sahu

GM- Service & Operation.



ISO 9001: 2015 Certified

3C IT SOLUTIONS & TELECOMS (I) PVT. LTD.

INTERNSHIP COMPLETION CERTIFICATE

CHIRAAG ASSOCIATES

556, Gate no 5, Near Naya Bazar, 411037,
Market yard Gullabadi Pune

To,

The Principal,

AKS Deoria college of

Arts, Science and

Commerce Pune

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Anvita Sahasrabhusan	5616	20252196433	Business administration
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely,

Poojita Nimbalkar
Name & Signature

(Authorized Signatory)



Regd Address : 55A, Gate No. 5, Near Naya Bazar, 411007, Market Yard, Ghatkoti, Pune.

Maharashtra, Pin- 411007

Email ID : chiraagassociates@gmail.com

Mobile No : 8531076638

CERTIFICATE OF COMPLETION

This certificate is awarded to **SALIMUNNISA TABARAK ANSARI** for successfully completing 60 hours of Internship at CA CHIRAAG ASSOCIATES from February 1, 2023 to February 10, 2023.

During the course of the internship, she demonstrated a strong work ethic, dedication to their assigned tasks, and a willingness to learn and grow. She worked collaboratively with other team members, took constructive feedback positively, and contributed to the overall success of the organization.

We wish her all the best in their future endeavors and hope that this internship experience has provided them with valuable skills and knowledge that will benefit them in their professional career.


Pratiksha Nimbadkar





WEANIMATES

Weanimates Salunke Office (H/F/13 SUPER) (M)
Salunke vihar road Pune-411045

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Ms. Ayesha Sayyed was working at Weanimates as a
Research Analyst & Email Marketing from 1st Feb'23 to 25th Feb'23.

During her tenure, we found her to be honest, dedicated, hardworking and well-
behaved and her services were found to be satisfactory.

Name : Sadique Sheikh
Designation : Marketing Manager, Producer.
Date : 25th Feb'23.



WEANIMATES

Wanimates Salimke Office no f/11 Super mall

Salimke vihar road Pune-411040

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Ms. Saadaka Tamboli was working at Weanimates as a Research Analyst & Email Marketing from 1st Feb'23 to 25th Feb'23.

During her tenure, we found her to be honest, dedicated, hardworking and well-behaved and her services were found to be satisfactory.

Name : Sadique Shaikh.
Designation : Marketing Manager, Producer.
Date : 25th Feb'23.



HAKIMI HARDWARE

TO WHOMSOEVER MAY CONCERN

This is to certify that Mr. Mohin Mulani has successfully completed 1 week of an internship program from 02 Feb 2023 to 10 Feb 2023 in the Sales department of our organization.

He was highly motivated and hardworking. He worked sincerely at his tasks and did a very good job.

HAKIMI HARDWARE
Rajdhani Siddhi Apt, Solapur Road
Vaidavadi, Hadapsar - PUNE

Sincerely,

VIKAS PACKERS & MOVERS

CARGO SERVICES



SHOP NO. 01, COMMON RACE HALL, MARKET YARD, PUNE - 41. PHONE : 8371833377, 8372318871 E-mail: vikas Packers@rediffmail.com
 101/101111-CUMPLEYCHOWANIPURKAL

To:
 The Principal,
 Purna College of Arts,
 Science & Commerce,
 Pune-01

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the "Sixty Hours Internship Programme" in this organization.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Kan Anant Ashi	1603	31854814572	Business Administration - II & III

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organizations.

I wish them every success in future endeavors.

Thank you.

For Vikas Packers & Movers
(Signature)
 Proprietor

 101, Common Race Hall, Market Yard, Pune - 41. Phone: 8371833377, 8372318871

 Shop No. 101, Market Yard, Common Race Hall, Pune - 41. Phone: 8371833377

 Shop No. 101, Market Yard, Common Race Hall, Pune - 41. Phone: 8371833377

EXPRESS BEES
SOLUTIONS EXPERTS

Address: 83/S4 Shivaji Nagar Old Lokhana, Near Bhagwat Garage.

Phone: 7972021151

Email: customer@expressbees.com

Date: 10/03/2023

TO WHOM IT MAY CONCERN

This is to certify that Mr. Anshu Achar (B.A.B student of Poona College) has completed a internship in the field of Career service from 01/02/2023 to 10/03/2023 under the guidance of Miss. Gant.

During the period of his internship program with us, he had been exposed to different processes and was found diligent, hardworking and inquisitive, Time Management.

We wish him every success in his life and career.





NEW TAJ BAKERY

214, Highway, Pune, Pune-411 012

PH: 26 25 25 50
26 25 25 51
CIN: 1622002701
TENDR7713

Ref. No.

Mr. Anshay Anis Ultaf Husain Date: 05/05/2020

~~Mr. Anshay Mohd. Altamash
Tarnar. Ahmed~~

Is working with our firm
New Taj Bakery for the
last one year

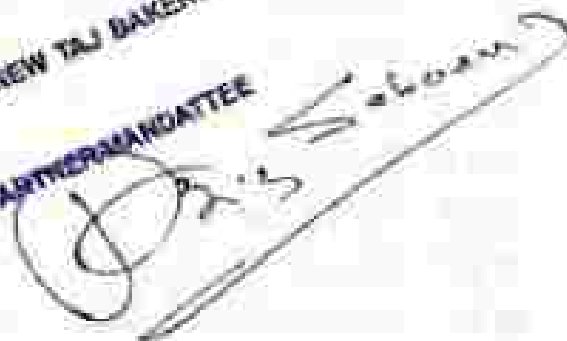
He has developed good relations
with customers & good in
keeping accounts.

Right now he is study in
T.Y. Bcom Pune College in
Commerce section

He is very dedicated to his
work and knows his responsibility

FOR NEW TAJ BAKERY

PARTNER/MANAGER





NEW TAJ BAKERY

75, 100, and 150g. Phone: 437 012

Ph: 26 25 26 52
26 25 26 51
Cell: 9922912709
9910547773

Date: 05/05/2023

Ref No:

Mr. Anwar Moud ALTAMASH
ISRAEL AHMED

Is working with our firm
New Taj Bakery for the
last one year.

He has developed good relations
with customers & good in
keeping accounts.

Right now he is studying in
T.V. Beou Poona College in
Commerce section.

He is very dedicated to
his work & knows his
responsibility.

FOR NEW TAJ BAKERY

PARTNER/QUALITIES

[Handwritten Signature]

EXCELLENT FABRICATION & ENGG. WORK

Industrial Fabrication & Engg. Works

To

The principal

MTC Pooné College,

Camp, Pune

Subject: Interable Completion Certificate

This is certify that Ms/ Madha Sameer Meimon student of 8th sem of T.Y.&com roll no: 5554 has completed 60 hours internship.

At EXCELLENT FABRICATION AND ENGG. WORK from 3 February 2023 to 19 February 2023.

At work he had proven satisfaction results and highly dependent. This is to certify also that he has no pending assignments in relation to his work, and so she is therefore cleared.

We wish them all the best for future endeavors.

AND ENGG WORK

EXCELLENT FABRICATION

For Exctia

(Proprietor)

(Signature)

HISAIN MEHROOB SWAMI



Taurus BPO Service

Date: 10/01/2023

TO WHOM IT MAY CONCERN

This is to certify that Mrs. Anel Bagan Suggs Khan student of Poona College, has completed a
Internship in our organization Taurus BPO Services India LLP. As a designation Customer Service
Associate in our Sales (Outbound) department at Pune Centre from 20/02/2022 to 04/03/2022.

During the period of her internship program with us, she has been exposed to different processes and
was found diligent, hardworking and motivated.

We thank her for contribution and wish her success in future endeavours.

For Taurus BPO Service India LLP



Employee Name:

Intermedia Cable Communication Pvt. Ltd.

REGD. OFF. - 101B, KCC CENTER, NEW NANGRA, PUNJAB
174012
TEL: 91-98152-22222 FAX: 91-98152-22222
E-MAIL: info@intermedia.net

KIRONGAULTER

17th January, 2023

To:

Mr. Madhvir Mohitar Mehta

174012 Bahajian chowk, Bahajpur, Goll no-23, 411011

With reference to your application and subsequent interview you had with us the Management is pleased to appoint you as New Executive w.e.f. 15th May, 2023. Also note that your Temporary Employment can be terminated at any time before completion of a year or the discretion of the Management without assigning any reason therefore, without pay or pay in lieu of notice.

1. Please note that you will be paid consolidated service charges of Rs.9,000/- per month during the period.
2. You will carry out such duties and during such hours as shall be assigned to you from time to time by your Superior.
3. You are liable to be transferred to any Department, Section at any time at the convenience of the Company, and at the same time you are liable to be transferred to any of our branches in India at the same terms and conditions of your original appointment.
4. At present you are required to attend your duties at following address: 101B, KCC Center, New Nangra, PNB, PNB 141002.
5. Please note that you shall be physically and mentally fit for your assignment work during this period.
6. You shall follow all safety rules and regulations of the company during this period.
7. You shall return in good condition, all tools instruments given to you for practical Assignment work in the Company on the last day of your working day in the company if monetary value of such unaccountable tools instruments will be recovered from your Assignment charges.
8. Please note that if you want to leave the job you have to complete notice period for 1 month, if any reason notice period is not accepted by you then company is liable to an action against you.
9. At the time of joining duty please bring two copies of certificates, testimonials for our record Along with the originals for verification. Please also bring with you your recent passport Size Photograph.
10. Please sign & return duplicate copy of this letter in token of your acceptance of the Appointment on the above terms and conditions.
11. Employee will not work in similar field like cable service industry for 1 year from the date leaving our organization.

Thanking you

Mr. Prateek Khanna

Hr. Dept



WNS

EXTENDING VALUE BEYOND

Date: 05th May 2023

Subject: Internship completion

To Whosoever It may concern,

This is to certify that MR. Ayaz Sadik Sayyed, a student of Akl's Panna College of Arts, Science and Commerce has completed his three month Internship in the field of Insurance from 22nd November 2022 to 22nd February 2023.

During the period of his internship program with us, he had been exposed to different processes and found him extremely diligent, hard-working and inquisitive. He was interested to learn the functions of our core division and also willing to put his best efforts and get into depth of the subject to get the understanding of process.

We wish him all the best and phenomenal success in his future endeavours.



Anshu Kumar

Lead HR Executive

WNS Global Services (P) Ltd | www.wns.com

WNS

ONE WNS ONE GOAL OUTPERFORM



Letter Head of the Internship Provider Organisation

To,

The Principal,
College,
Place (Place)

Subject: Internship Completion Certificate _____

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Aadhar No.	Special Subject
1.	Manish Tamboli	5011		Business Administration
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Shahid
Sincerely,

Name & Signature (Authorized Signatory)
Shahid Shaikh

INTERSHIP COMPLETION CERTIFICATE

Letter head of the Internship provider organisation

To,

The principal

POONA COLLEGE,

PUNE.

Subject: Internship Completion Certificate

Dear Madam/Sir

This is to certify that Ms. Firdos Begam (T.Y.B.COM) Student at Poona college of Arts, science and commerce, Pune has completed internship in this organisation Healing and Health Clinic. I am happy to inform you that following Student your College have successfully Completed the sixty hours Internship Programme in this organisation.

This students have been provided with adequate exposure and necessary hands on training pertaining their special.

I am confident that this student will perform effectively in similar Type Of Organisation.

I wish them every success in future endeavours.

Thank you.

Sincerely,



Name of signature

(Authorized Signature)

Dr. Seena S. Pathan

HEALING & HEALTH

Dr. Mrs. S. PATHAN

B.A.M.S. REG. No. 1217-D

Shop No.43, Scheme - 1, Rajawade, MIDC Road,
Near Kasur Bugh, Korhira, Pune - 41



RIYA BAGS SALES & REPAIRS

38 M.G. Road Kamal chamber ,Next to bala.pune -411001

INTERNSHIP COMPLETION CERTIFICATE

To,
The principal,
Poona collage
Pune-

Sub-Internship completion certificate

Dear Sir/Madam,

This is to certify that Mr.singh Deepak sher T.Y.B.COM student at poona college of Arts ,Science and Commerce,Pune has completed internship in this organisation Riya Bags sales and repairs . I am happy to inform you that following student your collage have successfully completed the sixty hours internship programs in this organisation .

This students have been provided with adequate exposure and necessary hands on training pertaining their specials.

I am confident that this student will perform effectively in similar type of Organisation .

I wish him very success in future endeavours.

Thank you

Sincerely

Kanahisald Sori

(Authorised Signatory)

RIYA BAGS
38 M.G. ROAD
BALA, PUNE-411001
(M) 9802798812

COMPUMECH

Specialist in second hand laptops selling laptop parts and chip level
Shop no 9, opp to lun royal Kowliwa Indrakh pune 41

REF NO:-4508

DATE:- 10/02/2023

This is to certify that Hafeez Kadri of BCOM Part II, SEM 6, and Roll No.5647 of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines of Savitribai Phule Pune University in our organization from 01/02/2023 to 10/02/2023 for the academic year 2022-23. During the training, the student was sincere, hardworking and showed a keen interest to learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavours.



Authorized Signature with Stamp

MOHAMMADI GLASS

Specialist in: Beveling, Polishing Etching, Decorative Mirrors
85A, Bhawal Path, Bharat Churnas Compound, Pune 411052

REF NO: 4896

DATE: 02/03/2023

To whomsoever it may concern,

This is to certify that **Mohammed Amin Munir** of TYB.com of AKI's Poona College of Arts, Science and Commerce has successfully completed the internship work as per the guidelines in our organization from **02/02/2023** to **01/03/2023** for the academic year 2022-23.

During the training, the student was sincere, hardworking and showed a keen interest learn. The involvement and sustained efforts put in by the student are highly appreciable.

We wish him all the best in his future endeavors.



Authorized Signature with Stamp



MAVEN BIZTECH

INSPIRE AND IMPACT

Date: 24th February 2023

Subject: Internship completion

To whomsoever it may concern,

This is to certify that Ms. Prema Shivapu Vachhe, a student of AKIS Purna College of Arts, Science and Commerce has completed her Internship in the field of Data Analytics from 10th February 2023 to 21st February 2023 under the able guidance of Ms. Farzin Khan.

During the period of her internship program with us, she had been exposed to different processes and we found her extremely diligent, hard-working and inquisitive. She was very much interested to learn the functions of our core division and also willing to put her best efforts and get into the depth of the subject to understand it better.

We wish her all the best and a phenomenal success in her future endeavors.

For Maven Biztech LLP

Regards,
Soniya Mohammed
Sr. HR Generalist

Regards,
Farzin Khan
Assistant Ops Manager



Clover Metropole Office 201, 2nd Floor NIBM, Mohammad Wadi Rd, Kondhwa, Pune, Maharashtra (INDIA) 411048



9923480249

महाराष्ट्र



Natraj cafe



Breakfast | Lunch | Dinner



प्लेट

Date: 30 March 2023

Lane C, 37 B,

Ragvilas Society,

Koregaon Park,

Pune - 411001

Email - kavraj987@gmail.com

TO WHOM IT MAY CONCERN

This to certify that Mr. Chandrashekhar Yadav student of Poona College, has completed a internship in the field of Restaurant and Hospitality from 21/03/2023 to 30/03/2023 under the guidance of Mr. Alok.

During the period of internship program with us, he had been exposed to different kind of works as a team, understand the nature of business, hospitality, interacting with guest time management.

We wish him every success in his life and career.

For NATRAJ FOOD

Rajkumar

Proprietor
Authorized Signature



Igt Solutions

Mansi IT Park, Vimanagar,

Pune, Maharashtra-411014

TO WHOMSOEVER IT MAY CONCERN

This is to certify that Mr. **Musaib Majeed Yalal** has successfully completed her internship in the field of Customer care executive from **1-Dec-22 to 25-Dec-22**.

During her tenure, we found her to be honest, dedicated, hardworking and well-behaved and her services were found to be satisfactory.

Name : Paras Chavan
Designation : Team Leader
Date : 25th Dec - 22

A handwritten signature in black ink, appearing to read 'Parag Chavan', written over a horizontal line.



HAJ - UMRAN - ZIYARAT

AMIR SHAIKH ☎ 8669280314 📞 7038109891

(Managing Director)

724, Chudaman Talim, Bhawanipetki, Opp. Navro Hind School Pune - 411 042. Email: amir@al-khalifatours.com

To,

The Principal,
POONA College,
PUNE-411001

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Hall No.	Aadhar No.	Special Subject
1.	HASHAM FEROZ MEMON	5332	N/A	MARKETING MANAGEMENT
2.	ABBAZ STRAJ KHAN		N/A	
3.	Ayaan shafi bagwan	5336	N/A	ACCOUNTING PERSON

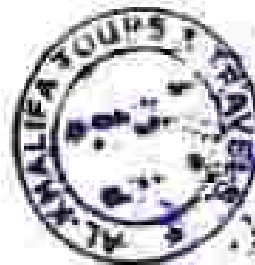
These

Student have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.



Sincerely

Name & Signature
(Authorized Signatory)

MONDIAL BUSINESS PROCESS

Office Address: Business Centre Building 17 Floor, 44th Ave, Sector 29, Gurgaon
Email: mondialbusiness103@gmail.com Phone No: 9999991113

DATE: 28/07/2023

SUBJECT: INTERNSHIP COMPLETION CERTIFICATE

THIS is to certify that Mr. Aamir Aamir Shaikh, student of Poorna College, has successfully completed a internship in the field of document analyzer and uploader from 13/07/2023 to 28/07/2023 under the guidance of Azim Shaikh.

During the period of his internship program with us, he had been exposed to different process and was found diligent, hardworking and inquisitive. His performance exceeded our expectations and he was able complete the given task on time.

We wish them all the best for future endeavors.

Mondial Business Process



Proprietor

Authorised Signature.

MAKHUZ.CO

Office Address: Alkhalid premises, Makhrusaft, half program road,

Email: makhrusaft@gmail.com

Phone No. 0482263441/7647810601

Date: 01/01/2023

SUBJECT: INTERNSHIP COMPLETION CERTIFICATE

This is to certify that Mr. Ebad Abdul Hauf Shaikh, student of Poonja College, has successfully completed a internship in all the field of the organization from 01/01/2023 to 17/01/2023 under the guidance of mamul Hasan Shaikh.

During the period of his internship program with us, he had been exposed to different process and was found diligent, hardworking and inquisitive. His performance exceeded our expectations and he was able complete the given task on time.

We wish them all the best for future endeavors.



Authorized Signature



Letter Head of the Internship Provider Organisation

To,
The Principal,
[Name] College,
[Place] (Place)

Subject: Internship Completion Certificate

Dear Madam/ Sir,

I am happy to inform you that following students of your college have successfully Completed the 'Sixty Hours Internship Programme' in this organisation.

Sr. No.	Name of the student	Roll No.	Author No.	Special Subject
1.	Kunal Singh	5096	81015802 5745	Business Administration
2.				
3.				
4.				
5.				
6.				
7.				
8.				

These students have been provided with adequate exposure and necessary hands-on training pertaining to their special subject.

I am confident that these students will perform effectively in similar type of organisations.

I wish them every success in future endeavors.

Thank you.

Sincerely,

Name & Signature (Authorized Signatory)

Stamp of the company

S. K. Stores
Village Park,
Phone- 411032
300020

S. K. Stores
Village Park,
Phone- 411032
300020



Anjuman Khairul Islam's
POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

• Affiliated to Saheed Dr. Ambedkar University, ID No. (11)PUN/ANCI/2017/15
• Jaipur College Index No. J-11, 15-204
• Government of Maharashtra and Saheed Dr. Ambedkar University Recognized Minority College
• UGC - 20 & 12(B) Status • NAAC Re-accredited College • OBT - 1ST Ranked College

• K. B. Hridayalal Road, Camp,
Pune - 411001, (MH), India

• +91-20-2645 4240 / 2641 5375

• principal@pcscollge.edu.in
• www.pcscollge.edu.in

Ref: PC/SC/Bot/Visit/ 354 /2022-23

Date: 17/11/2022

To,
Mr. Dilip Jadhav
Director,
A-One Biotech and Tissue Culture Laboratory,
(Horticultural Training Centre),
Tilgaon, Pune - 411033

Subject: Regarding visit to your A-One Biotech and Tissue Culture Laboratory,
Tilgaon on 24th November, 2022.

Respected Sir,

As per our telephonic conversation, staff of Department of Botany would like to visit your esteemed A-One Biotech and A-One Biotech and Tissue Culture Laboratory (Horticultural Training Centre) on 24th November, 2022 with S.Y.B.Sc. (Botany) students. This visit is a part of curriculum that will educate students for techniques in Plant Tissue Culture and Horticulture. Staff and students will definitely get enriched with knowledge and information by this visit. We look forward for a positive reply.

Yours Sincerely

Dr. Aftab Anwar Shaikh
Principal



**Anjuman Khairul Islam's
POONA COLLEGE OF ARTS, SCIENCE & COMMERCE**

- Affiliated to Savitribai Phule Pune University (U No. PUN/NAAC/02/2015)
- Junior College Index No. J-11, 15, 204
- Government of Maharashtra and Savitribai Phule Pune University Recognized Minority College
- UGC - 2 (I) & 12 (B) Status - NAAC Re-accredited College - DST - FIST Funded College

📍 K. B. Madgulkar Road, Camp,
Pune - 411001, (MG) India.

📞 +91-20-2648 4343 / 2644 4318

🌐 www.poonacollege.edu.in

Date: 24/11/2022

To,
Mr. Dilip Jadhav
Director,
A-One Biotech and Tissue Culture Laboratory,
(Horticultural Training Centre),
Talgaon, Pune - 411033

Subject: Letter of Thanks.

Respected Sir,

The Staff and students of Department of Botany, Poona College appreciated and thank you for permitting us to your esteemed training centre. The visit has enriched our students with knowledge on cultivation of horticulture plants and entrepreneurship.

Thanking you



(Handwritten Signature)

Yours Sincerely

(Handwritten Signature)

Dr. Absh Anwar Shaikh

(Handwritten Signature)

Poona College of Arts, Science & Commerce,
Camp, Pune-411001
Principal Office



**ACTIVITY REPORT**

Academic Year: 2022-23

BASIC DETAILS

Title of the Activity:			
Date	Faculty	Department/Committee	Coordinator Name & Phone No.
24/11/2022	Science	Botany	Dr. Aafreen A. Ahmed
Time	Venue:	Activity for Class/Group	Nature: Co-curricular/ Extra-curricular/ Extension/ Outreach
7.30 am - 3.30 pm	A-One Biotech and Tissue Culture Laboratory, (Horticultural Training Centre), Talegaon, Pune	S.Y.B.Sc. Botany	Co-curricular

BRIEF INFORMATION OF THE ACTIVITY

Objectives	Hands on Training of making of pots in horticulture industries
Outcome	Students learn how to make a pot by different techniques in horticulture industries. They also learn that how propagation is done for getting multiple plants through tissue culture technique.
No. of Participants	33

DOCUMENTS ATTACHED:*Note: Please attach original documents. Photocopy/ Xerox will not be accepted.*

Detailed Report	Geotagged Photos with Caption	Notice/Brochure
Attendance	Letters if any (Invitation/Thanks)	Any other relevant Documents (Recourse Person CV/Feedback)



Anjuman Khairul Islam's

POONA COLLEGE OF ARTS, SCIENCE & COMMERCE



Camp, Pune - 411001 (Maharashtra)

(AFFILIATED TO SAVITRIBAI PHULE PUNE UNIVERSITY)

DETAILED REPORT

Educational Visit to A-One Biotech, Talegaon

In charge: Dr. Aafreen A. Ahmed

No. of Beneficiaries: 53

Date: 24/11/2022

Time: 9.30 am to 5.30 pm

A-One Biotech Pvt. Ltd. is a distributor of horti-micropropagated plants based in MIDC, Talegaon, Pune. The organization was established in 2005 by Mr. Dilip Jadhav (M.Sc., Botany) with specialization in Plant Pathology after working for Ten years with Padamjee. His hard work is seen in the various successful tie-ups he has with several renowned companies such as Reliance Group, Government Projects such as beautification of Nazik Highway and Chhatrapati Shivaji Maharaj International Airport, Mumbai etc.

Horticulture Training Center (HTC), situated in the campus of National Institute of Post Harvest Technology (NIIPH), Talegaon imparts training in production of tissue culture plants and aeroponics.

The Department of Botany arranged a visit to a horticulture industry A-One Biotech and Horticulture Training Centre (HTC), at Talegaon Dabhade, Pune for SYBSC Botany students on 24/11/2022. All reached A-One Biotech by 11.00 am. Mr. Shaikhe, the manager received us, gave us a brief insights into the aims and objectives of A-One Biotech, its functional outgrowth in the past few years as a leading horticulture industry. He took students around the entire Polyhouse while explaining the kinds of plants nurtured there, their importance and need in the outside world. Students enquired about irrigation facilities, fertilizers used to maintain growth and the chemical control undertaken to keep away pest and disease. Every query was answered in detail by Mr. Shaikhe. He trained the students for preparation of pots for vertical garden. He also explained the insights of tissue culture technique by taking the students to its unit.

The educational visit helped students experience the functioning of a budding industry- the Horticulture industry and Tissue culture industry. In all 53 students benefitted from the visit under the supervision of Dr. Aafreen Ahmed, and Dr. Rafik Shaikh.



Anjuman Khairul Islam's

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Camp, Pune - 411001 (Maharashtra)

(AFFILIATED TO SAVITRIBAI PHULE PUNE UNIVERSITY)



A group photo at A-One Biotech Industry, Talegaon (24/11/2023)



Mr. Shelke explaining students about Polyhouse and pot making (24/11/2023)



Students performing pot making technique (24/11/2023)



Anjuman Khairul Islam's

POONA COLLEGE OF ARTS, SCIENCE & COMMERCE



Camp, Pune - 411001 (Maharashtra)

(AFFILIATED TO SAVITRIBAI PHULE PUNE UNIVERSITY)

AKI's Poona College of Arts, Science & Commerce, Pune-01				
Attendance Sheet for Students				
Date of Activity: 24 th NOVEMBER 2022		Time Slot: 9:00 am to 1:00 pm		
Activity Name: VISIT TO A-CAD HUBTECH & ICL, TALASARI, PUNE	Teacher Incharge: Dr. Jyoti A. Patil			
Organizing Dept/Committee: BOTANY				
Total Number of Students Attended: 33		Report Generated by: Dr. Jyoti A. Patil		
Sr. No.	Name	Class	Mobile No.	Signature
1.	Madira Iqbal Khan	S.Y.B.Sc.	9171551949	[Signature]
2.	Imamun Javed Shaikh	S.Y.B.Sc.	9440091221	[Signature]
3.	Sadiya Mond-Yusuf Tariq	S.Y.B.Sc.	8837669042	[Signature]
4.	Fiza Nisar Shaikh	S.Y.B.Sc.	8747367197	[Signature]
5.	Afifah Anwar Deshmukh	S.Y.B.Sc.	9820201762	[Signature]
6.	Fatima Shaikh	S.Y.B.Sc.	9649806823	[Signature]
7.	Ais Khan	S.Y.B.Sc.	9096882291	[Signature]
8.	Roshni Shaikh	S.Y.B.Sc.	9019932605	[Signature]
9.	Husna Pathan	S.Y.B.Sc.	9351044660	[Signature]
10.	Kamsha Shaikh	S.Y.B.Sc.	8202242720	[Signature]
11.	Rubina Haddi	S.Y.B.Sc.	8482088789	[Signature]
12.	Martisha Anvari	S.Y.B.Sc.	8087620023	[Signature]
13.	Mishal Anvari	S.Y.B.Sc.	7870984477	[Signature]
14.	Saniya Saad Shaikh	S.Y.B.Sc.	9816851766	[Signature]
15.	Nazreen Shaikh	S.Y.B.Sc.	9002255795	[Signature]
16.	Fatima Begum	S.Y.B.Sc.	8469418197	[Signature]
17.	Aarsha Pathan	S.Y.B.Sc.	9195226605	[Signature]
18.	Aysha Shaikh	S.Y.B.Sc.	8080354240	[Signature]
19.	Hanan Shaikh	S.Y.B.Sc.	9694371830	[Signature]
20.	Fareen Shaikh	S.Y.B.Sc.	7385904774	[Signature]
21.	Trupti Chaudhariya	S.Y.B.Sc.	9067945023	[Signature]
22.	Pooja S. Shaikh	S.Y.B.Sc.	9673280407	[Signature]
23.	Mahesh S. Shaikh	S.Y.B.Sc.	9172278793	[Signature]
24.	Zoya Saiged	S.Y.B.Sc.	9857961001	[Signature]
25.	Lakshmi Thirumagan	S.Y.B.Sc.	7674103311	[Signature]

[Signature]
Incharge of Faculty Incharge



POONA COLLEGE OF ARTS, SCIENCE & COMMERCE



Camp, Pune - 411001 (Maharashtra)
(AFFILIATED TO SAVITRIBAI PHULE PUNE UNIVERSITY)

AKP's Poona College of Arts, Science & Commerce, Pune-01				
Attendance Sheet for Students				
Date of Activity: 24 th NOVEMBER, 2022		Time Slot: 8:00 AM to 6:00 PM		
Activity Name: VISIT TO A ONE BIRTHDAY TGL, TALEGAN, PUNE		Teacher Incharge:	Dr. Shafiq - H	
Organizing Dept/Committee: BOTANY				
Total Number of Students Attended:		Report Generated by: Dr. Shafiq A. Khan		
Sl. No.	Name	Class	Matric No.	Signature
26	Saiba Samra Khan	Sy Bsc	7620720119	Shafiq
27	Sonoya Ayub Sheikh	Sy BSc	731170043	Shafiq
28	Mishal Ayub Sheikh	Sy BSc	7344710303	Shafiq
29	Fazail Ullah Khan	Sy BSc	7334710307	Shafiq
30	Mariya Javed Khan	Sy BSc	7760981268	Shafiq
31	Kazi Goharunnaz Akhila	Sy BSc	6961600249	Shafiq
32	Palhan Zeba Masood	Sy BSc	7341140547	Shafiq
33	Ragwan Aifa Ismail	Sy BSc	7490217331	Shafiq

Shafiq
Signature of Faculty Incharge



Office Address: 127/128, S. H. Tower, Anand Vidya Bhawan, Near Dnyanesh, Kharavela, Pune-411 004.
E-mail: hr@webcrypttechnology.com Website: www.webcrypttechnology.com

REF: HR-Webcrypt570-2023

Date: 02/04/2023

TO WHOM IT MAY CONCERN

This is to inform that Ms. Abheen Irfan Shaikh student of ARI Panna College of Art, Commerce & Science is pursuing her internship with our organization as a Java Developer-Intern, the duration of internship is 6 months effective from 11th February 2023 to 31st July 2023. Currently she is associated with Java Developer team and learning various development processes.

Project Name: Web Based Smart Green Homes

During the period of internship with us she was found punctual, hardworking and responsible.

As stated by Intellectual property and confidentiality policy of Webcrypt Technology Pune, she is unable to produce the source code of above mentioned project.

We wish her every success in life.

YOURS KINDELY,

HUMAN RESOURCE MANAGER

www.webcrypttechnology.com



Internship Certificate

This is to certify that **Mr. Dange Shoaib Rajekhan** a student of **A.K.'S Poona College of Arts, Science, and Commerce, Camp, Pune**, was assigned a project titled **"HandWritten Digit Recognition ML"** from **6th Dec 2022** to **17th May 2023** and has partially completed his project with us. He will continue working on till same till **15th June 2023**.

He was involved in ML development as a team member. During the period of project work with us, we found him sincere, obedient and hard-working.

We wish him all the best in his future endeavors.

Sincerely,
Internship Program Manager,
PHN Technology Pvt. Ltd.



Solitaire Business Hub, E-wing 5010,
Near Phoenix Mall, Vihar Nagar,
Pune, Maharashtra, 411014



1800 209 2788



www.phntechnology.com



Internship Certificate

This is to certify that Mr. Junaid Majeed Bagwan is student of A.K.J'S Poona College of Arts, Science, and Commerce, Camp, Pune, was assigned a project titled "Movie Ticket Booking System" from 6th Dec 2023 to 17th May 2023 and has partially completed his project with us. He will continue working on till same till 15th June 2023.

He was involved in front-end development as a team member. During the period of project work with us, we found him sincere, obedient and hard-working.

We wish him all the best in his future endeavors.

Sincerely,
Internship Program Manager,
PHN Technology Pvt. Ltd.



Solitaire Business Hub, E-wing 5010,
Near Phoenix Mall, Vihar Nagar,
Pune, Maharashtra, 411014



1800 209 2788



www.phntechnology.com



Internship Certificate

This is to certify that Mr. Shaikh Alim Shahabuddin, a student of A.K.I'S Pooná College of Arts, Science, and Commerce, Camp, Pune, was assigned a project-titled "Student Result Management System" from 6th Nov 2023 to 17th May 2023 and has partially completed his project with us. He will continue working on till same till 15th June 2023.

He was involved in front-end development as a team member. During the period of project work with us, we found him sincere, obedient and hard-working.

We wish him all the best in his future endeavors.

Sincerely,
Internship Program Manager,
PHN Technology Pvt. Ltd,



Solkara Business Hills E wing 5010,
Near Phoenix Mall, Viman Nagar,
Pune, Maharashtra, 411014.



1800 209 2288



www.phntechology.com



Internship Certificate

This is to certify that Mr. Shaikh Sadik Abdul Razzak, a student of A.K.'S Poona College of Arts, Science, and Commerce, Camp, Pune, was assigned a project titled "Audio Chat App" from 6th Nov 2022 to 17th May 2023 and has partially completed his project with us. He will continue working on till same till 15th June 2023.

He was involved in front-end development as a team member. During the period of project work with us, we found him sincere, obedient and hard-working.

We wish him all the best in his future endeavors.

Sincerely,
Internship Program Manager,
PHN Technology Pvt. Ltd.



Solitaire Business Hub, E-wing 5010,
Near Phoenix Mall, Vihar Nagar,
Pune, Maharashtra, 411014



1800 209 2288



www.phntechnology.com



Internship Certificate

This is to certify that Mr. Hamza Shakil Mungaye, a student of A.K.J'S Poona College of Arts, Science, and Commerce, Camp, Pune, was assigned a project titled "E-learning website with ai chatbot" from 5th Dec 2022 to 15th May 2023 and has partially completed his project with us. He will continue working on till same till 15th May 2023.

He was involved in front-end development as a team member. During the period of project work with us, we found him sincere, obedient and hard-working.

We wish him all the best in his future endeavors.

Sincerely,
Internship Program Manager,
PHN Technology Pvt. Ltd.

Internship Certificate

This is to certify that Mr. Aafan Jameer Tamboli, a student of A.K.'S Poona College of Arts, Science, and Commerce, Camp, Pune, was assigned a project titled "E-Worker" from 6th Nov 2022 to 17th May 2023 and has partially completed his project with us. He will continue working on till same till 15th June 2023.

He was involved in front-end development as a team member. During the period of project work with us, we found him sincere, obedient and hard-working.

We wish him all the best in his future endeavors.

Sincerely,
Internship Program Manager,
PHN Technology Pvt. Ltd.



Internship Certificate

This is to certify that Mr. Altamash Ashpak Tamboli, a student of A.K.I'S Poona College of Arts, Science, and Commerce, Camp, Pune, was assigned a project titled "Automation Testing" from 21st May 2022 to 17th May 2023 and has partially completed his project with us. He will continue working on till same till 17th June 2023,

He was involved in front-end developments as a team member. During the period of project work with us, we found him sincere, obedient and hard-working.

We wish him all the best in his future endeavors.

Sincerely,
Internship Program Manager,
PHN Technology Pvt. Ltd.



Solitaire Business Hub E-wing 5010,
Near Phoenix Mall, Viman Nagar,
Pune, Maharashtra, 411014.



1800 209 2288



www.phntechnology.com



Profecia Links Consulting Pvt. Ltd.

www.profecialinks.com

Date: 19/04/22

This is to certify that Mr. Fareed Muslim Sheikh student of MCA (CS) from "AO Pooja college of Arts Commerce and Science" has successfully completed his internship as Software Developer Intern at Profecia Links Pvt Ltd, Pune.

He worked on a project called 'Aid' - Web App. It is an e-commerce platform for any e-commerce application. Aid Framework is a software-developer's product that can be hosted in the cloud or on-premise. With the fundamental principle of "Build by configuration not by code" various features can be built by an admin or a business user without requiring a developer who is usually needed. Building a new business functionality such as order management (CRM), and advertising can be done in a few days or a single person instead of months of user effort.

During his internship, he has demonstrated his skills with a focus on his team work skills. His performance exceeded our expectations, and he was able to deliver the project on time.

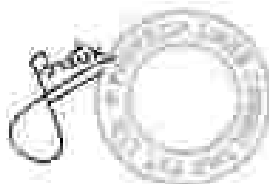
Branch: MCA (CS)

Technologies: Java, CSS, HTML5, Bootstrap

As decided by intellectual property and confidentiality policy of Profecia Links, We wish to remain

Best for his upcoming career.

For Profecia Links,



Pratik Satra

Email: pratik@profecialinks.com



REF: INT-SSP452-2023

Date: 02/06/2023

TO WHOM IT MAY CONCERN

This is to certify that Ms. Muskan Nisar Sheikh, student of M.Sc. (Computer Science) from AKPS Poona College of Arts Science And Commerce has successfully completed a project on "Municipal Corporation Online Complaint Handling Process" as a partial fulfillment of requirement towards 04th semester of her M.Sc. (Computer Science) program.

Duration- 02nd February 2023 to 30th July 2023

Technology- Java and MySQL

During the period of internship with us she was found punctual, hardworking and inquisitive. As abided by intellectual property and confidentiality policy of SSP Technology Pune. She is unable to produce the source code of above mentioned project.

We wish her every success in life.



AUTHORIZED PERSON SIGN

SSP TECHNOLOGY PUNE



SSP TECHNOLOGY PUNE

Office Address: SSP Pune, Akshay Sagar Road, New Knowledge Park, Pune-411 004

Phone No: 020-25812817, Email: hr@sspindia.com

Website: www.sspindia.com

SSP/INT/2022-0022

Date: 18/05/2022

INTERNSHIP LETTER

This is to certify that **Mr. Akhil Akhshay Makh**, a student of **AJ's Poona College of Arts Science and Commerce, Pune** was assigned a Project titled "**Simple Key Based Email Contact Book**" from **Dec 03, 2021 to May 15, 2022** and has partially completed his Project with us.

He was involved in **Software Development and Analysis** as **Team Member**. During the period of project work with us, we found him **sincere, obedient and hard working**.

We wish him all the best in his future endeavors.

As stated by intellectual property and confidentiality policy of SSP Technology Pune.

We wish him every success in life.



(Signature)

AUTHORIZED PERSON SIGN

SSP TECHNOLOGY PUNE



Web Soft IT Solution

WEB SOFT IT SOLUTION

Office Address: 1st Floor, Office No -2, Building G-2, Marimachi Complex, Near Jirandhara Hospital, Pune- Satara Road, Katraj Chowk, Pune- 411040.

Mobile No: +91-9579980670 E-mail: websoftsolutionpune@gmail.com

Website: www.websoftsolution.com

REF: Int-WS2011389-2022

INTERNSHIP CERTIFICATE

This is to certify that Mr. Mohd Ayub Armi student from "AKI Poona College of Science, Commerce & Arts, Pune" has successfully delivered Internship on "DevOps Toolchain For CI/CD" as a partial fulfillment of requirement towards of his project.

University Name- Savitribai Phule Pune University, Pune.

Duration-5th December 2022 to 20th May 2023

As abide by intellectual property and confidentiality policy of WEBSOFT IT SOLUTION Pune.

We wish him every success in life.



[Handwritten Signature]

AUTHORIZED PERSON SIGN

WEB SOFT IT SOLUTION PUNE

www.websoftsolution.com



Web Soft IT Solution

WEB SOFT IT SOLUTION

Office Address: 1st Floor, Office No -2, Building G-2, Maniknadi Complex, Near Jnanadhara Hospital, Pune- Satara Road, Katraj Chowk, Pune- 411046,

Mobile No: +91-9579380870 E-mail: webssoftsolutionpune@gmail.com

Website: www.webssoftsolution.com

REF: Int-WS2011389-2022

INTERNSHIP CERTIFICATE

This is to certify that Mr. Saqeesb Arslan Attar student from "AKI Poona College of Science, Commerce & Arts, Pune" has successfully delivered Internship on "Web Development Lvl -1" as a partial fulfillment of requirement towards of his project

University Name- Savitribai Phule Pune University, Pune.

Duration-5th December 2022 to 30th May 2023

As guided by intellectual property and confidentiality policy of **WEBSOFT IT SOLUTION** Pune.

We wish him every success in life.



AUTHORIZED PERSON SIGN

WEB SOFT IT SOLUTION PUNE

www.webssoftsolution.com

Date: 25/ 05/ 2023

TO WHOM IT MAY CONCERN

This is to certify that Mr. Abdul Rehman Abdul Gaffar Jakati, a student of M.Sc. (Master of Computer Science) from Pooona College of Arts, Commerce and Science, Camp, Pune has successfully completed the development of the various project.

He has undergone Industrial training in this organization (ConsociateSolutions Private Limited) from 17th December 2022 to 16th May 2023. During this period, he has worked on Php and Javascript for development of projects.

During the period of his internship programme with us he was found punctual, hardworking and inquisitive.

As a part of company policy, source code of the project is intellectual property of the company. Hence, he is not liable to share the code of the project.

The overall rating for his performance during the project is V. Good. We wish him every success in life.

For, Consociate Solutions Private Limited.



Irfan Mukadam



Director:



SGMS INFOTECH LLP

SGMS INFOTECH LLP

DN: 24-2481

Email: contact@sgmsinfotech.com

Web: www.sgmsinfotech.com

Contact: +91 8276220022

Ref. No. : SGMS/2023/110123

Date : 26 / 06 / 2023

INTERNSHIP COMPLETION LETTER

This is to certify that **Mr. Sarvath Parvatharam Lakshmi** Major of Computer Science Final year student of **Prasad College of Arts, Science and Commerce, Channarayana, Mysore**, has successfully completed a Final / Project Titled **"Local Shopper E-Commerce Application"** in Java Technology with SGMS Infotech LLP, Mysore, Part of a part of his 4th semester project.

He has done his project during the period of 02nd January 2023 To 10th June 2023 in the completion of his project under the guidance of **Mr. Rishu P. Sangeet**.



SGMS Infotech LLP

Address: Titled No.6, 2nd St, 5th Cross, Front of Prasad College, Mysore,
Mysore, Karnataka, India - 571004



SGMS INFOTECH LLP

SGMS INFOTECH LLP
City: SA-5845
Email: contact@sgmsinfotech.com
Web: www.sgmsinfotech.com
Contact: +91 9279329225

Ref. No. : SGMS/2023/100127

Date : 28 / 05 / 2023

INTERNSHIP COMPLETION LETTER

This is to certify that Mr. **Sagar Nageshwar Murkh** student of Computer Science Final year student of Panna College of Arts, Science and Commerce, Camp, Panna, has successfully completed a Partial Project titled "Ticket Master Travel Reservation System" in Java Technology with SGMS Infotech LLP. Alank, Panna as a part of his 4th semester project.

He has done his project during the period of 02nd January 2023 To 30th June 2023 to the completion of his project under the guidance of Mr. **Rakesh K. Srivastava**.



SGMS Infotech LLP

Address: Office No 4, 3rd Fl, Ashi Junction, Panna of Apana, Panna, Madhya Pradesh, Panna - 471004



SGMS INFOTECH LLP

SGMS INFOTECH LLP
CIN: AA 6689
Email: info@sgmsinfotech.com
Web: www.sgmsinfotech.com
Contact: +91 8295328128

Ref. No. | SGMS/2023/000126

Date: 26 / 05 / 2023

INTERNSHIP COMPLETION LETTER

This is to certify that Mr. Geetanjay Singh Kachan, Master of Computer Science, Third year student of Panna College of Arts, Science and Commerce, Panna, has successfully completed a Paid Internship titled "Drug Awareness and Resistance Education" at Jiva Technology with SGMS Infotech LLP, Anand, Patna as part of his 4th semester project.

He has done his project during the period of 02nd January 2023 To 07th June 2023 to the completion of his project under the guidance of Mr. Ramesh K. Saranya.



Internship Completion Certificate

TO WHOMSOEVER IT MAY CONCERN

02/06/2023

We hereby certify that Mohammed Aayat Kazi was an Intern of CloudAge Global Service Pvt.Ltd from 20/12/2022 to 01/06/2023.

Project assigned: Web developer

The project was successfully completed and we found Mohammed Aayat Kazi very sincere and result oriented.

We wish you all the best for your future endeavors.

Sincerely,



Haaris Zed
HR Head- Human Resources

www.callistomedia.com

C/111, 2ND FLOOR, BRAHMA ESTATE COM.
COMPLEX, NIBM Rd, Kothrud, Pune.

Met/West/411018

9764666435

CALLISTO
media

May 25th 2023,

Internship certificate

This is to certify that **Mr. Shah Hamza Abdul Majid**, a student of A.K.I's Poona College of Arts, Science, Commerce, Camp, Pune was assigned as Project titled "Company Portfolio website" from 7th December 2022 to 7th June 2023 has partially completed this Project with us. He will continue working on the same till June 15th 2023.

He was involved in Software Development and Analysis as a Team Member. During the period of project work with us, we found him sincere, obedient and hard working.

We wish him all the best for his future endeavors.

Salman Shaikh

Sincerely,
Salman Shaikh
Project Manager

Ref: OmVSab IT Solution/HRD/2023

Certificate Of Completion

To whom it may concern,

This is to certify that Mr. Abdul Razzak Khan, student of final year MSc Computer Science from A.K.I'S Poona College of Arts, Commerce and Science, Camp, Pune, has completed internship Project in this Organization. During his training in team, he has completed work on project of "Showroom ERP" from 12th December 2022 to 12th May 2023 and has partially completed his project with us.

He will continue working on till same till 12th September 2023.

We wish him all the best for his future assignment and work.

Managing Director

For Omvsab IT Solution.

OMVSAB IT SOLUTION.

Registered Office: Sr No: 19/1/8, Karve Nagar, Pune – 411052. (India)

Tel: +91-20 65222250 Website: www.omvsabitsolution.in

Ref: OmVSab IT Solution/HRD/2023

Certificate Of Completion

To whom it may concern,

This is to certify that Mr. Sohel Hamid Shaikh, student of final year MSC Computer Science from A.K.I'S Poona College of Arts, Commerce and Science, Camp, Pune, has completed internship Project in this Organization. During his training in team, he has completed work on project of "Gym Management ERP" from 12th December 2022 to 12th May 2023 and has partially completed his project with us.

He will continue working on till same till 12th September 2023.

We wish him all the best for his future assignment and work.

Managing Director

For Omvsab IT Solution.

OMVSAB IT SOLUTION.

Registered Office: Sr No: 19/1/8, Karve Nagar, Pune – 411052. (India)

Tel: +91-20 65222250 Website: www.omvsabitsolution.in

Date: - 30th May 2023

Project Completion Certificate

This is to certify that Ms. Shaikh Nida Nisar, Student of Puna College of Arts, Science and Commerce, Pune, has completed her project work in our organization under the esteemed guidance & Technical Support of Sr. Developers toward the fulfillment of the MSc Computer Science, 4th Semester.

Project name: - Online Shopping Store

Technology: Python with Django

From- 05th March 2023 to 30th May 2023

She has successfully completed her Internship. During the period she was sincere, hardworking & fully devoted to project.

We wish her all success for her future career.

For Maxgen Technology Pvt Ltd



Dr. Mamta Yerawar

Manager - Human Resources

Date: - 30th May 2023

Project Completion Certificate

This is to certify that Ms. Soleha Akbar Sayyed, Student of Poona College of Arts, Science and Commerce, Pune, has completed her project work in our organization under the esteemed guidance & Technical support of Sr Developers toward the fulfillment of the MSc Computer Science, 4th Semester.

Project name: Online Quiz Application

Technology: Python with Django

From: 01st March 2023 to 30th May 2023

She has successfully completed her internship. During the period she was sincere, hardworking & fully devoted to project.

We wish her all success for her future career.

For Maxgen Technology Pvt Ltd



Dr. Mamta Yerawar

Manager - Human Resources



Date: - 30th May 2023

Project Completion Certificate

This is to certify that Ms. Ibra Patel, Student of Poona College of Arts, Science and Commerce, Pune, has completed her project work in our organization under the esteemed guidance & Technical support of Sr. Developers toward the fulfillment of the MSC Computer Science, 4th Semester.

Project name: - Online Furniture Store

Technology- Python with Django

From- 05th March 2023 to 30th May 2023

She has successfully completed her Internship. During the period she was sincere, hardworking & fully devoted to project.

We wish her all success for her future career.

For Maxgen Technology Pvt. Ltd



Dr. Mamta Yerawar

Manager - Human Resources

Date: 20th May 2023

INTERNSHIP COMPLETION CERTIFICATE

This is to certify that Ms. Hediye Shahn has successfully completed project work in the company under the esteemed guidance and technical support of St. Developers toward the fulfillment of the semester.

Project Name: Online Quiz Application
Technology: - Python
From - 6th March 2023 To 1st August 2023

She has successfully completed her internship. During the period she was sincere, hardworking & fully devoted to project.

We wish her all success to her future career.

For Maxgen Technology Pvt Ltd

Sadhana Kokate
Manager - Human Resources



TO WHOMSOEVER IT MAY CONCERN

Date: 24/05/2023

This is to certify that Mr Mohammed Taher Electricwala a student of A.K JS Poona College of Arts, Science and Commerce, Camp, Pune was assigned a project title "BTC CHANNELS" from 1st January 2023 to 25th May 2023 and has partially completed his Project with us at Rootware Technologies, Pune. He will continue his Internship till 30th June 2023.

During the internship program, we found him sincere & hardworking.

We wish him success in future endeavors.

Yours Sincerely,

Date: 24/05/2023

Vijayendra Shinde



For ROOTWARE TECHNOLOGIES
HUMAN RESOURCE

CERTIFICATE OF COMPLETION OF INTERNSHIP

This is to certify that

Danish Chandle

from

AKI'S POONA COLLEGE OF ARTS, SCIENCE & COMMERCE
Savitribai Phule University, Pune
has completed the internship program at Infosys Limited during

01 February 2023 – 13 May 2023

Satheesha B.N.

Satheesha B Nanjappa

Vice President and Head, Global Education Center



Synergist Advance IT Solutions LLP

Office No-22, Raj Garden SN-43 BLD-D
Kondhwa, Khurd Pune-40

Internship Completion Certificate TO WHOMSOEVER IT MAY CONCERN

15/05/2023

We hereby certify that Ganesh Ramadhar (Jaiswal) was an Intern of Synergist Advance IT Solutions LLP from 10/12/2021 to 9/05/2023.

Project assigned: Laptop Sales & Services.

The project was successfully completed and we found Ganesh Ramadhar (Jaiswal) very sincere and result oriented.

We wish you all the best for your future endeavors.

Sincerely,

(Chief Executive Officer)
Synergist Advance IT Solutions LLP, Pune.

Office No-22, Raj Garden SN-43 BLD-D
Kondhwa, Khurd Pune-40



Anjuman Khairul Uloom's
POONA COLLEGE
OF ARTS, SCIENCE & COMMERCE

Approved by Government of Maharashtra, Pune University, 45/96, POONA-411001
 UGC - 2018-2020 Status - 2017 - 2018 - 2019
 Department of Mathematics and Statistics, Poona University, Deemed
 University College



B. A. H. Road, Poona, Dist. Pune
 Poona - 411001 (Maharashtra)



+91 20 2645 4241
 2644 9175



www.anjumankhairululoom.org
 www.poonauniversity.edu.in

DEPARTMENT OF MATHEMATICS

Date: 13/04/2023

NOTICE

Department of Mathematics in association with Internal Quality Assurance Cell (IQAC) would like to organize *one day educational trip* to Indian Institute Technology (IIT), Powai, Mumbai on 29/04/2023 for the students of F. Y./S.T./T.Y. B.Sc. (Mathematics) and B.Sc. (Computer Science). The objective to organize this educational trip is to help students to acquire practical knowledge about theories taught in classroom and to appreciate about career opportunities in Mathematics through actual exposure to highly reputed educational institutes.

All the interested students are advised to submit their names along with undertaking form to coordinator on or before 20/04/2023.

Coordinator: Dr. Amjad Shaikh

Dr. Amjad Shaikh
 Head

Department of Mathematics

Head Department of Mathematics

Anjuman Khairul Uloom

Poona College

of Arts, Science and Commerce,
 City, Pune - 411001

**ACTIVITY REPORT**

Academic Year: 2022-23

BASIC DETAILS

Title of the Activity:			
Date	Faculty	Department/ Committee	Coordinator Name & Phone no.
19 th April, 2023	Science	Mathematics	Dr. Amjad Shaikh Mob No: 9890627503
Time	Venue	Activity for Class Group	Nature: Co-curricular/ Extra-curricular/ Extension/ Outreach
One Day (8:30 am to 10:30 pm)	Indian Institute of Technology(IIT), Powai, Mumbai	F.Y/S.Y/T.YB.Sc (Maths) and F.Y/S.Y-B.Sc (Computer Science) 32 students	Co-curricular

BRIEF INFORMATION OF THE ACTIVITY

Objectives:	<ul style="list-style-type: none"> To encourage and motivate students for higher studies in reputed institutes To explore future prospect of mathematics and statistics To explore renowned institutes in India
Outcome	Faculty members from department of mathematics, IIT, Mumbai interacted and guided students about further teaching and research opportunities and industrial applications of mathematics and statistics
No. of Participants	32 Students of S.Y/T.YB.Sc have participated and had an amazing experience. Students have learned and gained valuable information about further career opportunities in mathematics and pursuing higher studies at premier education institutes in India.

DOCUMENTS ATTACHED:*Note: Please attach original documents. Photocopy (Xerox) will not be accepted.*

Detailed Report	Geotagged Photos with Caption	Notice/Brochure
Attendance	Letters if any (Invitation/Thanks)	Any other relevant Documents (Recourse Person CV/Feedback)



Anjuman Khairul Islam's

POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

Camp, Pune – 411001 (Maharashtra)
(AFFILIATED TO SAVITRIBAI PHULE PUNE UNIVERSITY)



DETAILED REPORT

Educational Trip To IIT Mumbai

Department of Mathematics had organized an educational trip to IIT Mumbai, Powai on 29th April, 2023.

The HOD of the Mathematics department of IIT institute set the tone for the program which was followed by the felicitation of professors from the coordinator Dr. Amjad Shaikh head, department of Mathematics.

There was a student teacher interaction in which they discussed various career opportunity related with the field of Mathematics and Computer Science. They also discussed about different entrance exams like JAM, GATE, JEE etc. The session was very interesting and motivating and had a very beautiful interaction with JAM, Phd Scholars and PG students.

The HOD of Mathematics of IIT institute U.K Anandavardhan and professors Monika Bhattacharya & Dr. Ayan Bhattacharya guided them about various scopes and career opportunity in Mathematics.

Then we got a wonderful opportunity of visiting a massive library having numbers of various kinds on books, and easily access to e-books bounded with a lot of facilities.

Dr. Amjad Shaikh, Ms. Nida Kazi and Fareen Shaikh accompanied the trip.



Anjuman Khairul Islam's

POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

Camp, Pune - 411001 (Maharashtra)
(AFFILIATED TO SAVITRIBAI PHULE PUNE UNIVERSITY)



GEOTAGGED PHOTOS WITH CAPTIONS



Dr. Anjad Shaikh Head Department of Mathematics felicitating professor of IIT Mumbai



Professors of IIT Mumbai interacting with students



Students of Poona college giving votes of thanks



Group Photo of IIT Mumbai

AKI's Poona College of Arts, Science & Commerce students' visit to IIT Bombay

Wed, Apr 10, 2023 at 10:58 AM

सन्दीप शिंदे shinde.sandeep@pcc.ac.in
To: Anand Shinde anandshinde@maths.iitb.ac.in
Cc: IIT Bombay hr@iitb.ac.in, Head Mathematics head.maths@iitb.ac.in


Dear Dr. Shinde,
This is to confirm that an interaction with some faculty and students of
Mat. Department can be arranged on Saturday, Apr 29th, 2023
11:00 a.m. to 12:30 p.m.
A copy of this email is being sent to the PRO office, whom they will
will need to get permission to enter campus, as well as to arrange a
passing note to the library.
Thank you for your patience.
Best wishes,
Anand

Anandshinde An H
Assistant Professor
Department of Mathematics
IIT Bombay
anandshinde@maths.iitb.ac.in
10221 2578 9445

Forwarded Message
Subject: AKI's Poona College of Arts, Science & Commerce, Pune as part
of their educational visit
Date: Mon, 13 Mar 2023 11:24:06 +0530
From: PRO IIT Bombay pro@iitb.ac.in
To: Head Mathematics head.maths@iitb.ac.in
Cc: office math office office.math@iitb.ac.in

Dear Sir,
As it is most possible for a visit to the Dept of Mathematics,
Students of AKI's Poona College of Arts, Science & Commerce, Pune have
expressed their wish to visit the Dept of Mathematics.
Regards,

सन्दीप शिंदे
Public Relations Officer,
आपण आता कोणत्याही वेळी www.pcc.ac.in वर भेट द्या
आपण आता कोणत्याही वेळी www.pcc.ac.in वर भेट द्या


Head Department of Mathematics
Anand Shinde
Poona College
of Arts, Science and Commerce
Camp, Pune - 411004

Date: _____

To,

The Principal,

Pune College of Arts, Science and Commerce,

Pune, India.

Subject: Permission for Educational trip to Indian Institute of Technology (IIT), Powai, Mumbai.

Respected Sir,

Department of Mathematics in association with Internal Quality Assurance Cell (IQAC) would like to organize an edutour educational trip to Indian Institute of Technology (IIT), Powai, Mumbai on 28/09/2023 for the students of B. Y.S.V.T.X. B.Sc. (Mathematics) and B.Sc.(CS). The objective to organize this educational trip is to help students to acquire practical knowledge about theories taught in classroom and to make aware about career opportunities in Mathematics through actual exposure to highly reputed educational institute. I assure you that our students will observe the rules and regulations that are prescribed by IIT for the visitors and will not disturb the functioning of the institute during visit. I also arrange for necessary permission and undertaking from parent/guardian as well as from students. Therefore, I am requesting you for your kind permission of educational trip to IIT, Powai, Mumbai.

Yours faithfully,
Dr. Anand Mishra

Thanking You

Forwarded
to Head
12/09/2023

Head
Department of Mathematics
Pune College
of Arts, Science and Commerce
Pune - 411004



Received
19/9/2023

Principal
Pune College of Arts, Science and Commerce
Pune - 411004





POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

Approved by Savitribai Phule Pune University, 37th PUNE CAMPUS
 100, MIDC Road, Shivajinagar, PUNE-411 007, Pooana College
 Department of Mathematics and Statistics, Pooana College, Shivajinagar
 Pune-411 007, Maharashtra



P. A. Jambhalekar, Pooana, Collge,
 Pune-411007, Maharashtra



+91-20-25484297
 25484319



www.pooanacollege.edu.in
 www.pooanacollege.ac.in



+91 98226 47574

www.pooanacollege.edu.in

Professor Dr. Attab Anwar Shaikh

M.Com. Ph.D. (Hons. Degree)
PRINCIPAL

Department of Mathematics Educational Tour to IIT, Powai, Mumbai List of Participants

Date: 26/04/2023

Following students of I.V.S. Y.T.Y.B.S. (B.Sc. CS) are visiting for one day educational tour to Indian Institute of Technology (IIT), Powai, Mumbai on 29th April 2023.

Sr. No.	Name of student	Sr. No.	Name of student
1	Shahid Iqbal Zaki	17	Khan Alisha Aali
2	Shaikh Ayesha Noor	18	Aman Fatima
3	Qureshi Parvez Iqbal	19	Sagun Shaikh
4	Farooq Shaikh	20	Ahmad Raja Shaikh
5	Khan Umair	21	Iqbal Baig
6	Shaikh Fady	22	Saniya Hussain Muzam
7	Khadim Zahir Shaikh	23	Mahar M. Shaikh
8	Munira Khan	24	Iqbal Jibber Ismail
9	Shaikh Mehdi Fatima	25	Saniya Shaikh
10	Ilina Mamoor	26	Roman Sayyed
11	Aman Anam	27	Zaid Aali Dogra
12	Ravona Iqbal Noor	28	Alisha Khan
13	Ammal Sumaiyya	29	Shaikh Shuhin
14	Shaikh Raheem Raza	30	Pathan Sajida
15	Shaikh Shams	31	Shaikh Alys
16	Shaikh Zahir Elor	32	SARUJIE Tarkatkar

List of teachers accompanied:

- 1) Dr. Attab Shaikh - Coordinator (9890627507)
- 2) Ms. Nida Kazi
- 3) Ms. Farooq Shaikh



Prof (Dr.) Attab Anwar Shaikh

Principal
 Pooana College of Arts, Science & Commerce

Pooana College of Arts, Science & Commerce
 Collge, Shivajinagar
 Pooana-411007



Department of Mathematics
POONJA COLLEGE OF ARTS, SCIENCE & COMMERCE

Address: Poonja Road, Poonja, Dist. Poonja, Gujarat
 Phone: 079-27700000
 Website: www.poonjacollege.ac.in

Principal: Dr. J. Ashok Kumar Shinde
 Vice-Chancellor: Dr. J. Ashok Kumar Shinde
 Registrar: Dr. J. Ashok Kumar Shinde
 Director of Studies: Dr. J. Ashok Kumar Shinde
 Head of Department: Dr. J. Ashok Kumar Shinde

Department of Mathematics
 Educational Tour to IIT, Powai, Mumbai
 List of Participants

Date: 29/04/2022

Attendance Sheet (F.Y, S.Y & T.Y B.Sc)

Sl. No.	Name of student	Class	Mobile no.	Sign	Photo
1.	Shashikumar Zahir	F.Y.B.Sc	8523090112 8023090112		
2.	Rishi Hirdah	F.Y.B.Sc	705860478 705860487		
3.	Shashikumar Zahir	F.Y.B.Sc	808428428 9021650790		
4.	Shashikumar Zahir	F.Y.B.Sc	878215938 708441701		
5.	Fatima Zahira Shakh	F.Y.B.Sc	76630629 9030910642		
6.	Qureshi Parvez Ishtiaq	F.Y.B.Sc	8587463923 902117066		
7.	Chaitanya Zuber Shakh	T.Y.B.Sc	902162996 728321991		
8.	Isha Mansoor	S.Y.B.Sc	8548101317 9211901971		
9.	Muskan Khan	S.Y.B.Sc	726844965 9022401734		
10.	Ravesh Jignesh Meena	S.Y.B.Sc	8421619111 905153012		
11.	Ashraf Anisqaq Mansoorji	S.Y.B.Sc	9052294256 9021586202		
12.	Ayush Mansoor	S.Y.B.Sc	749842298 9021543738		
13.	Deshmukh Feroz Zuber	S.Y.B.Sc	705860776 9011358484		
14.	Qureshi Nourul Jannat	S.Y.B.Sc	766919369 811828024		
15.	Nikita Subhash Kakade	S.Y.B.Sc	8834042798 9032021368		
16.	Shashikumar Zahir	S.Y.B.Sc	7219202130 9172215992		
17.	Shashikumar Zahir	T.Y.B.Sc	7335292311 9021650661		



PUNNA COLLEGE OF ARTS, SCIENCE & COMMERCE

Department of Mathematics and Statistics, Puna, District: Solapur, Maharashtra
 Puna, Dist. Solapur, Maharashtra - 431001
 Phone: 020-22045117, 22045118, 22045119, 22045120, 22045121, 22045122, 22045123, 22045124, 22045125, 22045126, 22045127, 22045128, 22045129, 22045130, 22045131, 22045132, 22045133, 22045134, 22045135, 22045136, 22045137, 22045138, 22045139, 22045140, 22045141, 22045142, 22045143, 22045144, 22045145, 22045146, 22045147, 22045148, 22045149, 22045150, 22045151, 22045152, 22045153, 22045154, 22045155, 22045156, 22045157, 22045158, 22045159, 22045160, 22045161, 22045162, 22045163, 22045164, 22045165, 22045166, 22045167, 22045168, 22045169, 22045170, 22045171, 22045172, 22045173, 22045174, 22045175, 22045176, 22045177, 22045178, 22045179, 22045180, 22045181, 22045182, 22045183, 22045184, 22045185, 22045186, 22045187, 22045188, 22045189, 22045190, 22045191, 22045192, 22045193, 22045194, 22045195, 22045196, 22045197, 22045198, 22045199, 22045200

Dr. Anand Shankar (H.O.)
 PRINCIPAL

Department of Mathematics and Statistics
 Puna, Dist. Solapur, Maharashtra

Department of Mathematics
Educational Tour to IT, Puna, Mumbai
List of Participants

Date: 20/04/2017

Attendance Sheet (F.Y.B.Sc.(CS) and S.Y.B.Sc.(CS))

Sl. No.	Name of student	Class	Mobile no.	Sign	Sign
1	Shakthi Adya Hamam	F.Y.B.Sc.(CS)	8830981194 9975703002	<i>Shakthi</i>	<i>Shakthi</i>
2	Shakthi Rubiya Jameel	F.Y.B.Sc.(CS)	7820881951 9970064253	<i>Rubiya</i>	<i>Rubiya</i>
3	Saniya Husain Mubam	F.Y.B.Sc.(CS)	7887978566 9860836206	<i>Saniya</i>	<i>Saniya</i>
4	Iqra Aash Bilal	F.Y.B.Sc.(CS)	8767415348 8680156622	<i>Iqra</i>	<i>Iqra</i>
5	Ayami Shaikh	F.Y.B.Sc.(CS)	9511668541 8830711707	<i>Ayami</i>	<i>Ayami</i>
6	Maharaj Shaikh	F.Y.B.Sc.(CS)	7875002149 9896257147	<i>Maharaj</i>	<i>Maharaj</i>
7	Wajeeed Abdul Wahid	F.Y.B.Sc.(CS)	7880038004 8830822342	<i>Wajeeed</i>	<i>Wajeeed</i>
8	Iqbal Zaid Asif	F.Y.B.Sc.(CS)	8609627667 7276699398	<i>Zaid</i>	<i>Zaid</i>
9	Roshan Sameer Sayyad	F.Y.B.Sc.(CS)	9834111577 9637668378	<i>Roshan</i>	<i>Roshan</i>
10	Afrid Shaikh	F.Y.B.Sc.(CS)	9549902347 9822350143	<i>Afrid</i>	<i>Afrid</i>
11	Saqib Shaikh	F.Y.B.Sc.(CS)	8421116749 8667120730	<i>Saqib</i>	<i>Saqib</i>
12	Shakthi Adya Rafique	S.Y.B.Sc.(CS)	9160813576 9822097913	<i>Shakthi</i>	<i>Shakthi</i>
13	Pallavi Shreya Firoz	S.Y.B.Sc.(CS)	7262847884 7083313845	<i>Pallavi</i>	<i>Pallavi</i>
14	Tarunima Arshad	S.Y.B.Sc.(CS)	9880280878 9160385754	<i>Tarunima</i>	<i>Tarunima</i>

Dr. Anand Shankar (H.O.)
 Coordinator

FILE NO. TAP/02/00004
SCIENCE & ENGINEERING RESEARCH BOARD (SERB)
 A statutory body of the Department of Science & Technology, Government of India

24-5A, Lower Ground Floor
 Vasant Square Mall
 Plot No. A, Connaught Place
 Sector-8, Pocket-5, Vasant Kunj
 New Delhi-110070

Date: 23-Nov-2019

ORDER

Subject: Financial sanction under Teachers Associateship for Research Excellence (TARE) to Dr. Parvez AbdulAziz Shaikh, Poona College Of Arts Science & Commerce, Camp, Pune, Pune, Maharashtra-411001 under the mentorship of Dr. Rajesh S Verma, Indian Institute of Technology, Indore Khadwa Road, Simrol, Indore - 453552. Release of 1st grant.

Sanction of Science and Engineering Research Board (SERB) is hereby accorded to the above mentioned grant at a total cost of Rs. 18,50,000/- (Rupees Eighteen Lakh Fifty Thousand Only) for a duration of 36 months.

The date of start of the project will be 05 November 2019. The items of expenditure for which the total allocation of Rs. 18,50,000/- has been approved are given below:

The following budget is proposed for
Poona College Of Arts Science & Commerce, Camp, Pune, Pune, Maharashtra-411001 (Partner)

Sl. No.	Budget Head	Amount
1.	Fellowship	Rs. 07 (00%) per month (60000/- total)
2.	Research Grant	Rs. 150,000/- per annum
3.	Overheads	Rs. 25,000/- per annum

Indian Institute of Technology, Indore Khadwa Road, Simrol, Indore - 453552 (Host)

Sl. No.	Budget Head	Amount
1.	Fellowship	Rs. 06,00,000/- (on the basis of 90 days mandatory attendance in the host institute every year)
2.	Research Grant	Rs. 150,000/- per annum
3.	Overheads	Rs. 25,000/- per annum

2. Sanction of the SERB is also accorded to the partner of Rs. 2,75,000/- (Rupees Two Lakh Seventy Five Thousand only) to Poona College Of Arts Science & Commerce, Camp, Pune, Rs. 3,50,000/- (Rupees Three Lakh Fifty Thousand only) to Indian Institute of Technology, Indore Khadwa Road, Simrol, Indore - 453552 being the first installment of the grant for the year 2019-2020 for implementation of the said research project.

3. The expenditure incurred is debitable to Fund for Science & Engineering Research (FSER).

This release is being made under Teachers Associateship For Research Excellence (TARE), (Condensed Matter (Physics and Materials Science)).

4. The Sanction has been issued to with the approval of the competent authority vide D.O. No. SERB/06/11/2019-2020 dated 28 November, 2019.

5. Remission of the grant is subject to the conditions as detailed in Terms & Conditions available at website (www.serb.gov.in).

A overhead expenses are credit to the host institute towards the cost for providing infrastructural facilities and general administrative support etc. including benefits to the staff employed to the project.

7. As per rule 28 of GFR, the accounts of project shall be open to inspection by auditing authority/audit whenever the institute is called upon to do so.

8. The release amount of Rs. 2,75,000/- (Rupees Two Lakh Seventy Five Thousand only) will be drawn by the Under Secretary of the SERB and will be disbursed by means of RTGS over account as per their bank details given below.

Poona College of Arts Science & Commerce, Camp, pune, Pune, Maharashtra-411001 (Partner Institute):

PFMS Unique Code	PCASE
Account Name	Principal A/C Poona College UOC Grant A/c
Account Number	2026411485
Bank Name & Branch	Bank of Maharashtra Camp Branch, Camp, Pune-411001
PFMS/RTGS Code	56418000076
Email address of PI	pvc_arts@iitb.ac.in@gmail.com
Print Id of A/C Holder	www@bojha.com@gmail.com
Email address of concerned officer	ms_lare@iitb.ac.in

The release amount of Rs. 3,75,000/- (Rupees Three Lakh Fifty Five Thousand only) will be drawn by the Under Secretary of the SERB and will be disbursed by means of RTGS over account as per their bank details given below.

Evaluating the Potential of Lead-Free Nontoxic $\text{Cs}_2\text{BiAgI}_6$ -Based Double Perovskite Solar Cell

Mohamed Alla, Vishesh Manjunath,^{*} Ekta Choudhary,[‡] Manopriya Samtham, Siddhant Sharma, Parvez A. Shaikh, Mustapha Rouchdi, and Boubker Fares

Recently, the efficiency of single-junction perovskite solar cells has been competing with the crystalline Si solar cells. However, the perovskite absorbers are toxic and susceptible to moisture. Herein, the performance of an environmentally benign and durable $\text{Cs}_2\text{BiAgI}_6$ light harvester using the 1D Solar Cell Capacitance Simulator (SCAPS-1D) software package is evaluated. The primary physical parameters, namely, defect and doping densities and thickness of the subsequent layers, are varied to achieve high efficiencies. The optimized $\text{Cs}_2\text{BiAgI}_6$ -based double perovskite solar cells with three distinct hole-transporting layers (HTLs) (i.e., MuO_3 , CuSCN , and spin-DMTAD) deliver a power conversion efficiency of $\sim 28\%$ with AZrO as electron transport layer (ETL). Further, a variety of possible rear electrodes are explored, and their effect on the performance is estimated. For real-time examination of the $\text{Cs}_2\text{BiAgI}_6$ -based double perovskite solar cells, the variation of power conversion efficiency (PCE) concerning the operating temperature is estimated. The thickness of the $\text{Cs}_2\text{BiAgI}_6$ light harvester layer and the bulk defect density are the key aspects in obtaining high power conversion efficiencies in $\text{Cs}_2\text{BiAgI}_6$ -based double perovskite solar cells.

1. Introduction

Accounting from high absorption coefficient ($\sim 10^4 \text{ cm}^{-1}$),^[1] long charge diffusion length ($\sim 1 \mu\text{m}$),^[2] ease of processing, low recombination rates, etc.,^[3,4] the power conversion efficiency

(PCE) of single-junction thin film solar cells comprising perovskite light absorbers has witnessed a quantum jump from 3.8% to 25.6%, approaching the matured crystalline silicon solar cell at 26.7%.^[5] Owing to the tunability of their crystal structure and optoelectronic properties, the perovskite light harvesters can be tailored into 3D perovskites, layered double perovskites, double perovskites, etc.^[6,7] Despite these advances, the high-efficiency perovskite solar cells contain carcinogenic Pb^{2+} , and the crystal structure disintegrates when exposed to moisture, hindering their real-time implementation.^[8,9] Various encapsulation techniques are experimented to address the poor stability of the perovskite absorbers.^[10] However, the intrinsic direct visible light absorption in perovskites originates from filled *t_{2g}* orbitals at the valence band maximum and empty *e_g* orbitals at the conduction band minimum of the Pb cation.^[11,12] Therefore, replacing the Pb atom in the crystal structure is crucial for achieving high efficiency. Thus, initially, Pb^{2+} was substituted with Ge^{2+} or Sn^{2+} cations, but the higher energy of 4s and 5s orbitals of Ge^{2+} and Sn^{2+} cations, respectively, produce oxidation centers in the crystal structure resulting in poor stability.^[13] However, lately, several nontoxic lead-free layered double perovskites (1D and 2D) attained by heterovalent substitution of Pb^{2+} with Bi^{3+} or Sb^{3+} , and 3D double perovskites are studied for their suitability as a light harvester.^[14,15] Nevertheless, a stable and nontoxic perovskite light harvester with optoelectronic properties akin to lead-containing 3D perovskites is yet to be uncovered. Among all the Pb-free alternatives, perovskites obtained by transmutation of M^{2+} cation with a combination of monovalent and trivalent cations result in 3D double perovskite with chemical formula $\text{A}_2(\text{M}'\text{M}'')\text{X}_6$, where A, M' , M'' , and X are monovalent cation, monovalent metal ion, trivalent metal ion, and halogen, respectively. Thus, the unit cell is doubled, and a pair of M^{2+} cations are replaced with M'^+ and M''^+ cations and form the 3D double perovskite structure, which crystallizes in the cubic crystal system with $\text{Fm}\bar{3}\text{m}$ space group.^[16] Though the 3D double perovskites possess relatively high indirect bandgap, yet several approaches, namely, M'' site doping,^[17] dilute alloying,^[18] and pressure-assisted bandgap tuning,^[19] can be applied to reduce the bandgap toward punch-through absorption. Further, depending on the M' and M'' combinations, the lead-free halide double perovskite can be classified as

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1) nitrogen/alkali metals ($M^+ = Sb^{3+}$, Bi^{3+} and $M^+ = N^+$, K^+);
2) nitrogen family/transitional metals ($M^+ = Sb^{3+}$ and Bi^{3+}
and $M^+ = Ti^+$, In^+); 3) posttransitional/noble metals
($M^+ = In^+$, Cu^+ and $M^+ = Cu^+$, Ag^+); and 4) nitrogen fam-
ily/metal metals ($M^+ = Sb^{3+}$, Bi^{3+} and $M^+ = Cu^+$, Ag^+).
Unlike the AMX_3 structure, in double perovskites, there is a need
to consider a specific octahedral factor for each type of
octahedron. However, for the tolerance factor, the average ionic
radius of the M' and M'' sites can be used. The theoretical
conditions for a stable structure are $\mu > 0.41$ and $0.75 < t < 1$.
The theoretical conditions for a stable structure are $\mu > 0.41$
and $0.75 < t < 1$.^[28]

Consequently, the Pb atom can be replaced with Bi and Ag
heteroatomic substitution to form Cs_2BiAgI_4 double perovskite
crystal structures. Moreover, Cs_2BiAgI_4 and $Cs_2BiAgBr_4$ double
perovskites are experimentally synthesized via solid-state reac-
tions and solution processing. Such double perovskite crystal-
line lattice structure (symmetric face-centered cubic
double perovskite) with corner sharing octahedra, with Cs in
the middle of the cubic octahedral cavity. The centers of the octa-
hedra are either occupied by Bi or Ag, alternating in a rock salt
configuration considering isotropic carrier transport properties.^[21]
Additionally, the Cs_2BiAgI_4 double perovskite having a relatively
low bandgap is inorganic, environmentally benign, and can
provide long-term stability. On the other hand, apart from the
perovskite light absorber, two carrier-selective transport layers
are required to achieve effective carrier extraction at both external
terminals. The optoelectronic properties of electron and hole
transport layers play a crucial role in attaining high performance.
Among the compatible electron transport layers (ETLs),
aluminum-doped zinc oxide (AZnO) is a promising n-type wide
bandgap semiconductor (3.3 eV) with high transparency and
excellent optoelectronic properties.^[22,23] Several industrial
processes, namely, spray coating, dip coating, screen printing,
bar coating, etc.^[24,25] are developed to coat large area conformal
thin films. Further, owing to better band alignment and process-
ibility, molybdenum oxide (MoO_3),^[26] copper thiocyanate
(CuSCN), and spiro-OMeTAD have been extensively investigated
for extracting holes toward the external terminal.^[24] Additionally,
producing high PCE solar cells requires precise tuning of thick-
ness, doping, and bulk defect densities of the subsequent
layers.^[27,28] However, experimentally tailoring these properties
and achieving high performance is a myriad task. Therefore,
researchers use various software packages, namely, Silvaco
ATLAS, waAMPs, finite difference time domain method, etc.
All these software programs generally solve basic semiconductor
second-order differential equations by applying boundary
conditions at the interfaces.^[29] Among all the software packages,
1D Solar Cell Capacitance Simulator (SCAPS-1D) offers
multi-junction and hetero-junction simulations.^[30,31]

This study employs the SCAPS-1D software package to model
and scrutinize perovskite solar cells with a double perovskite
light harvester and three distinct hole-transporting layers
(HTLs). The modeled device structure, FTO/AZnO (ETL)/
 Cs_2BiAgI_4 /HTLs (MoO_3 , or CuSCN or spiro-OMeTAD)/rear
metal contact, is shown in Figure 1. The Cs_2BiAgI_4 -based double
perovskite solar cells are optimized in terms of thickness, bulk,
and doping densities, with three distinct HTLs (i.e., MoO_3 ,
CuSCN, and spiro-OMeTAD) and AZnO as ETL. Various



Figure 1. Schematic depicting the device structure of Cs_2BiAgI_4 double perovskite solar cells considered in the present study.

possible rear electrodes are selected, and the effect on the
performance of the Cs_2BiAgI_4 -based double perovskite solar cells
is analyzed. Further, to assess the real-time application of
 Cs_2BiAgI_4 -based double perovskite solar cells, the performance
is also evaluated concerning the change in operating tempera-
ture. The present technique used for optimization can provide
guidelines for experimental implementation and can be extended
to other optoelectronic devices.

2. Device Modeling and Simulation Procedure

The planar double perovskite solar cell in $n-i-p$ configuration is
modeled as FTO/AZnO (ETL)/ Cs_2BiAgI_4 /HTLs (MoO_3 , or
CuSCN or spiro-OMeTAD)/rear metal contact (Figure 1).
Owing to thermal stability and chemical inertness, fluorine-
doped tin oxide (FTO) layered glass substrates are employed
as transparent conducting substrates. Gold (Au) is chosen as
the counter electrode for all simulations except for the simula-
tions in which the work function of the counter electrode is varied.
Global AM1.5 spectrum with an irradiation intensity of
 1000 W m^{-2} is used for all simulations.

In principle, the SCAPS 1D software solves the basic semi-
conductor equations which dictate the charge transport in the semi-
conductor.^[32] However, various other additional requirements
are needed to realistically simulate polycrystalline thin solar cells.
Therefore, along with these semiconductor equations, SCAPS
offers grading of all input parameters, namely, the type of excita-
tion, defect levels (bulk and interfacial), charge type (idealiza-
tion, charge type (donor or acceptor), and valency (monovalent,
divalent, or multivalent)), defect level distribution (Gaussian,
single level, uniform, or combination), optical properties
(direct excitation of light), and contact properties (flat band or

work function. Voltage, frequency, and operating temperature can also be controlled to perform reasonable computations. Therefore, the three underlying equations that regulate the carrier transport in semiconductors are listed below:

Poisson Equation (Equation (1))

$$\frac{d^2\psi}{dx^2} = -\frac{q}{\epsilon} \left[p(x) - n(x) + N_D^-(x) - N_A^+(x) + N_t(x) \right] \quad (1)$$

where ψ represents the electrostatic potential, q is the charge of an electron, ϵ denotes the dielectric constant of the material, p is the concentration of holes, n is the concentration of electrons, N_D^- indicates ionized acceptor density, N_A^+ signifies ionized donor density, n_t and p_t represent electron and hole traps, respectively, and x is the position coordinate.

Electron (Equation (2)) and hole (Equation (3)) continuity equations:

$$\frac{dn}{dt} = G_n - \frac{n_p - n_0}{\tau_n} + q\mu_n \frac{dE}{dx} + q\mu_n \frac{dn}{dx} + D_n \frac{d^2n}{dx^2} \quad (2)$$

$$\frac{dp}{dt} = G_p - \frac{p_p - p_0}{\tau_p} + q\mu_p \frac{dE}{dx} + q\mu_p \frac{dp}{dx} + D_p \frac{d^2p}{dx^2} \quad (3)$$

where G_p and G_n represent generation rates of hole and electron, n_p and n_0 denote concentrations of hole and electron in the n and p region, respectively, p_0 and n_0 indicate equilibrium concentrations of hole and electron in the n and p region, respectively, τ_p and τ_n represent a lifetime of hole and electron, μ_p and μ_n denote the mobilities of hole and electron, E signifies the electric field, and D_p and D_n indicate the diffusion coefficient of holes and electron. The carrier transport happening due to drift and diffusion for electrons (Equation (2)) and holes (Equation (3)) is expressed as:

$$J_n(x) = qn\mu_n E + qD_n \frac{dn}{dx} - qn_0 \frac{dE_{Fn}}{dx} \quad (4)$$

$$J_p(x) = qp\mu_p E - qD_p \frac{dp}{dx} - qp_0 \frac{dE_{Fp}}{dx} \quad (5)$$

where E_{Fn} and E_{Fp} denote the hole's and electron's quasi Fermi levels. The physical and defect parameters used in the simulation of PSCs are tabulated in Table 3. Further, the series and shunt resistances are $5 \Omega \text{ cm}^{-2}$ and $1 \text{ M}\Omega \text{ cm}^{-2}$, respectively.

3. Results and Discussion

The AZnO film is considered ETL in the present modeling. The AZnO accomplishes the following functionalities: 1) serves as the template for perovskite overlayer, 2) shields UV radiation from striking the unstable perovskite over layer, 3) blocks hole transport, and 4) aids in dissociation of electron-hole pairs at the AZnO/double perovskite interface. Therefore, it is essential to optimize the thickness and donor doping density of the AZnO ETL. Experimentally, there are several scalable techniques to synthesize large area conformal AZnO thin films. Thus, the thickness of AZnO is varied from 30 to 180 nm, as shown in Figure 2a. Increasing thickness beyond 180 nm may lead to parasitic optical losses. Though the thickness of AZnO film is varied from 30 to 180 nm, the PCE remained constant ($\approx 25.55\%$), originating from unaltered open-circuit voltage (V_{oc}) and short-circuit current density (J_{sc}). However, a minute variation in fill factor (FF) with increasing thickness of the AZnO can be ascribed to a minor increase in series resistance in the thicker AZnO film. Further, the donor doping density in the AZnO ETL is varied from 10^{17} to 10^{19} cm^{-3} , as shown in Figure 2b. With increasing donor doping concentration in AZnO ETL, the PCE and V_{oc} of the double perovskite solar cell remained constant. Marginal increase in the J_{sc} and decrease in FF at higher doping can be ascribed to an increase in carrier conductivity in the AZnO

Table 3. The physical parameters used as input in extensive and optimized solar cells.

Parameter	FD	AZO	$\text{CH}_3\text{NH}_3\text{PbI}_2$	$\text{CH}_3\text{NH}_3\text{SnI}_3$	CH3CN	Me_6Tl_2
Thickness (μm)	0.1	0.02 ^a	0.00 ^a	0.00 ^a	0.00 ^a	0.00 ^a
Bandgap E_g (eV)	1.1	1.21	1.4	1.88	1.8	1.6
Intrinsic affinity χ (eV)	4	4.22	3.28	3.05	3.7	3.3
Effective permittivity (relative)	9	8.11	9.5	9.8	9.9	11.1
Effective density of states in CB (N_c , cm^{-3})	2.2×10^{19}	4.1×10^{19}	1×10^{19}	2.2×10^{19}	2.2×10^{19}	2.2×10^{19}
Effective density of states in VB (N_v , cm^{-3})	1.8×10^{19}	4.2×10^{19}	1×10^{19}	1.8×10^{19}	1.8×10^{19}	1.8×10^{19}
Velocity of electrons (thermal) $v_{th,n}$ ($\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)	1×10^7	1×10^7	1×10^7	1×10^7	1×10^7	1×10^7
Velocity of holes (thermal) $v_{th,p}$ ($\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)	1×10^7	1×10^7	1×10^7	1×10^7	1×10^7	1×10^7
Mobility of electrons μ_n ($\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)	30	300	300	1×10^3	300	25
Mobility of holes μ_p ($\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$)	10	20	2	1×10^2	2.5×10^2	100
Shallow electron donor density N_D (cm^{-3})	2.1×10^{17}	1.1×10^{16}	0	1	0	0
Shallow electron acceptor density N_A (cm^{-3})	0	0	1×10^{18}	1×10^{18}	1×10^{18}	1×10^{18}
Density of defects N_t (cm^{-3})	1×10^{17}	1×10^{17}	1×10^{16}	1×10^{17}	1×10^{17}	1×10^{17}
References	[28]	[29]	[28]	[29]	[29]	[29]

^aThe parameters used in the present study.

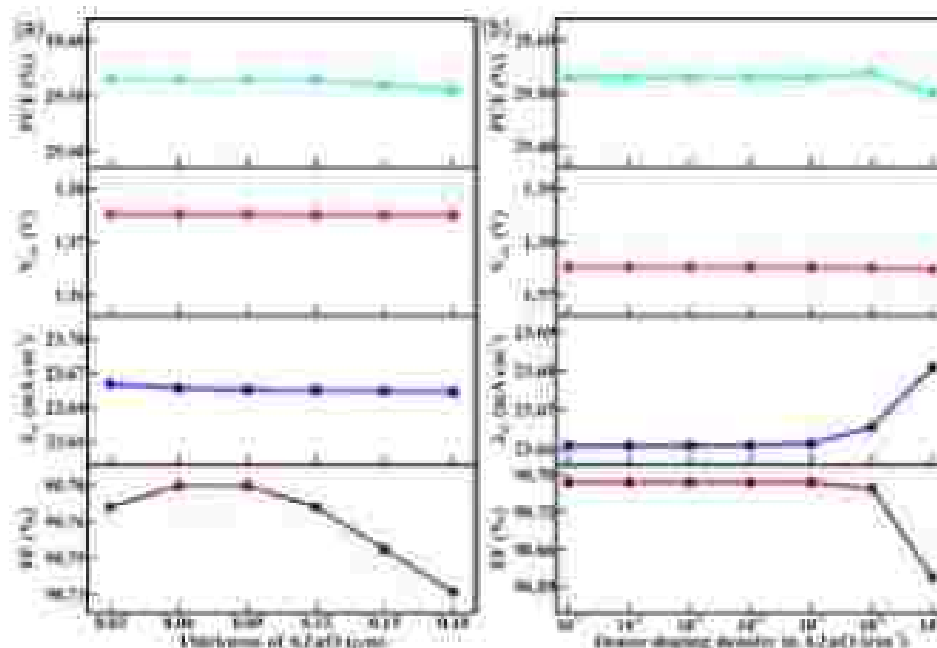


Figure 3. a) Thickness and b) donor doping density of AZnO layer-related description of solar cell parameters (with other parameters as tabulated in Table 1).

films. These results indicate that the Ca_2BiAg_2 double perovskite-based solar cells are independent of the thickness and donor doping density in the AZnO HTL.

Furthermore, the thickness of the Ca_2BiAg_2 double perovskite light absorber is varied from 100 to 900 nm, as shown in Figure 3a. As the thickness of the Ca_2BiAg_2 double perovskite increases, the corresponding rise in the PCE of the Ca_2BiAg_2 double perovskite-based solar cells increases, owing to the rise in J_{SC} resulting from higher photo-generation in the thicker Ca_2BiAg_2 film. At the thickness of 900 nm, the Ca_2BiAg_2 double perovskite-based solar cell delivers a PCE of ~20%. The marginal decrease in V_{OC} and FF in thicker Ca_2BiAg_2 film can be ascribed to higher recombination and a minor rise in series resistance, respectively. Besides the thickness, experimentally, the bulk defect density of the Ca_2BiAg_2 double perovskite absorber varies depending on the synthesis protocol. The bulk defect density in the Ca_2BiAg_2 double perovskite is varied from 10^{14} to 10^{19} cm⁻³, as shown in Figure 3b. As the bulk defect density rises, a steady decrease in the PCE is observed (PCE declines from ~20% to ~14% when bulk defect density increases from 10^{14} to 10^{19} cm⁻³), owing to the corresponding decline in the V_{OC} , J_{SC} , and FF. The decline in V_{OC} , J_{SC} , and FF can be associated to change in Fermi level, trap-assisted recombination, and an increase in resistance, respectively, in Ca_2BiAg_2 films with high bulk defect density. These results illustrate the thickness and bulk defect density in the Ca_2BiAg_2 double perovskite absorber plays a crucial role in achieving high performance.

To understand the effect of HTL thickness on the performance of Ca_2BiAg_2 double perovskite solar cells, the thickness of HTL is varied from 30 to 180 nm (Figure 4a). Similar to the thickness of the ETL, the increase in thickness of the HTLs did not affect all the solar cell parameters. However, depending on the type of

HTL, the PCE varied independently. Ca_2BiAg_2 double perovskite solar cells with MoO_3 as HTL showed the highest efficiency of ~20.51%, followed by CuSCN (~20.10%) and spiro-OMeTAD (~20.22%). Further, upon increasing the acceptor doping density from 10^{17} to 10^{19} cm⁻³, the PCE and all other solar cell parameters remained constant for MoO_3 and CuSCN HTLs (Figure 4b). However, at higher doping concentrations, an increase in PCE of the Ca_2BiAg_2 double perovskite solar cell with spiro-OMeTAD HTL is observed, ascribed to the rise in the FF of the solar cells. The increase in FF is associated with lower resistance in highly doped spiro-OMeTAD films.

The interfacial properties between the subsequent layers in the perovskite solar cells are crucial in achieving better performance.^{13,14} Thus, the interfacial defect density at AZnO/perovskite and perovskite/ MoO_3 is varied from 10^{19} to 10^{24} cm⁻³, as shown in Figure 5a,b, respectively. As the interfacial defect density at AZnO/perovskite interface is increased from 10^{19} to 10^{23} cm⁻³, the PCE steadily declines from ~21% to 12%. This decline in PCE can be ascribed to a decrease in the V_{OC} and FF of the solar cells. However, the J_{SC} remains constant, but the V_{OC} and FF decrease due to interfacial losses originating change in band offset developed at the AZnO/perovskite interface. Conversely, when the defect density at the perovskite/ MoO_3 is increased up to 10^{24} cm⁻³, the PCE remains constant, indicating high defect tolerance of the perovskite/ MoO_3 interface. Further, when the defect density increases beyond 10^{23} cm⁻³, the PCE decreases owing to the decrease in J_{SC} . The decline in J_{SC} is attributed to the defect-assisted recombination losses at the perovskite/HTL interface.

Vacuum near contacts possessing distinct work functions are assessed for their applicability in Ca_2BiAg_2 -based double perovskite solar cells, as shown in Figure 6. However, the identical

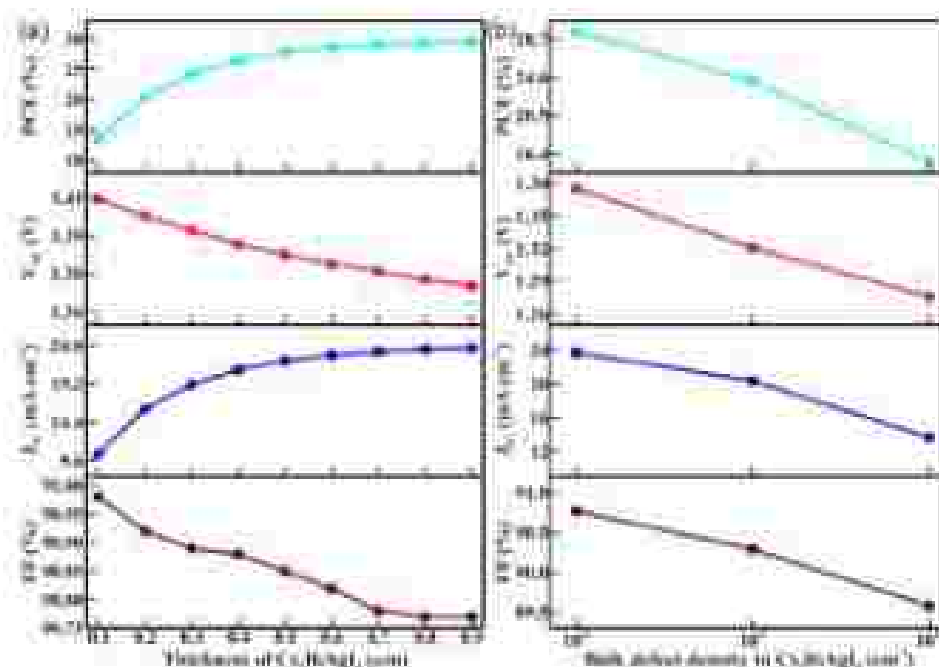


Figure 3. a) Thickness and b) work function of Cs₂BiAg₄ double perovskite absorber-related deviation of solar cell parameters (with other parameters as tabulated in Table 1).

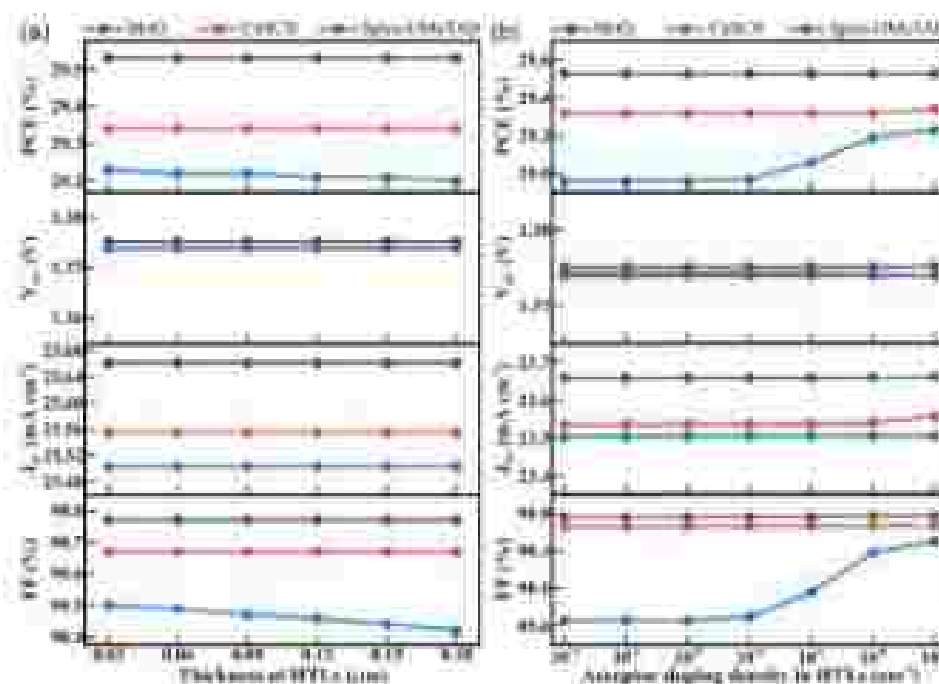


Figure 4. a) Thickness and b) acceptor doping density of HTL (MnO₂/CuSCN/Spin-OMeTAD)-related deviation of solar cell parameters (with other parameters as tabulated in Table 1).

reactivity, conductivity, and processing directly influence the cost and performance of solar cells.^[57] The work function of the rear contact directly impacts the performance of the solar cells. The PCE of the Cs₂BiAg₄-based double perovskite solar cells increased with increasing the work function of the rear metal contact up to 5 eV. However, employing rear contacts having a

work function beyond 5 eV had a minor change in the PCE. These results indicate every cost-effective carbon as counter electrodes can deliver ~20% PCE.

Understanding the effect of operating temperature on the performance of solar cells is essential for real-time implementation.^[58,59] Thus, the influence of operating temperature is

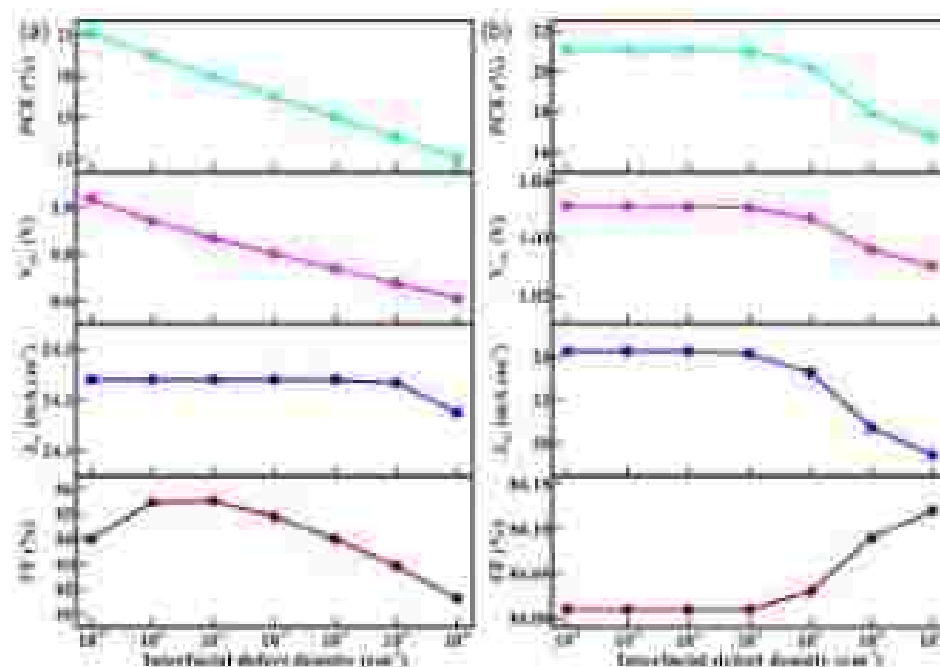


Figure 2. The solar cell parameter variation associated with the interfacial defect density changes at a) TiO_2 /polymer and polymer/HTL interface.

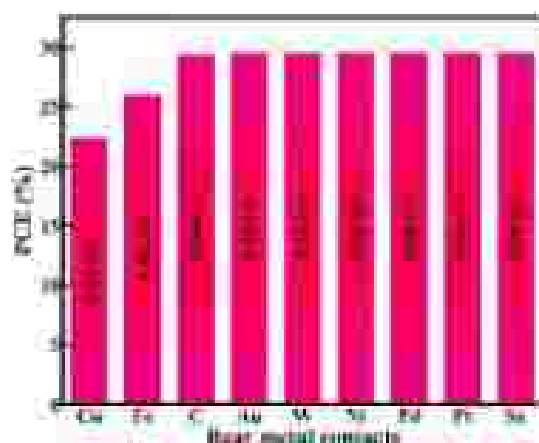


Figure 3. Change electrode-related distance in PCE (with other parameters as tabulated in Table 1).

analyzed for temperatures ranging from 300 to 400 K, as shown in Figure 7. As the operating temperature rises from 300 to 400 K, a steady decline in the PCE is observed due to the reduction in V_{OC} and FF. The V_{OC} reduces due to an increment in the reverse saturation current in the Cs_2BiAg_3 -based double perovskite solar cell. However, the increase in J_{sc} with an increase in the operating temperature, can be attributed to the thermal generation of electrons. Conversely, it is to be noted that even when the operating temperature shoots to 400 K, the Cs_2BiAg_3 -based double perovskite solar cell delivered a PCE of $\sim 26\%$.

Evaluating the spectral response of the solar cells is essential in understanding the incident photon to electron conversion

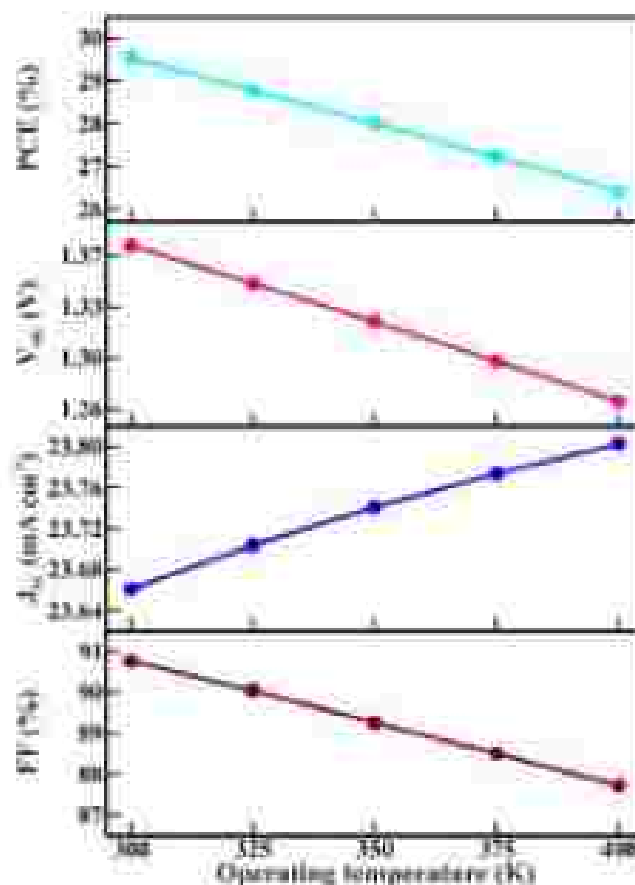


Figure 4. Operating temperature-related variation solar cell parameters (with other parameters as tabulated in Table 1).

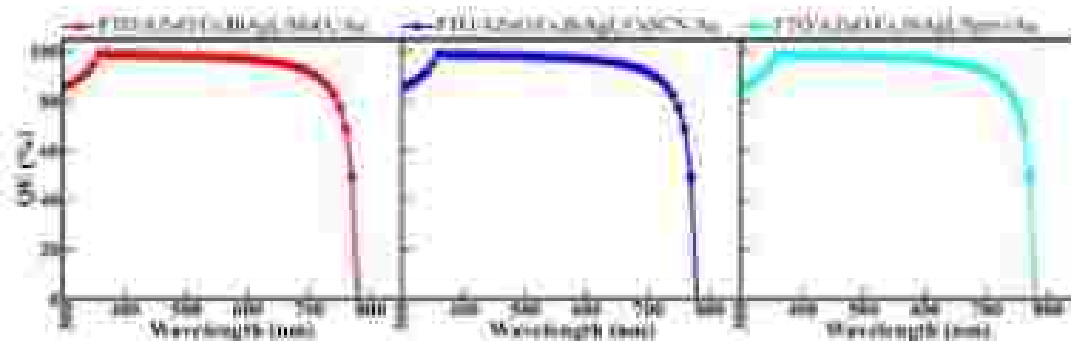


Figure 8. Quantum efficiency curves for the Cs_2BiAg_4 -based double perovskite solar cells comprising various HTLs ($\text{MgO}/\text{TiO}_2/\text{CuInGa}_2\text{S}_4$).

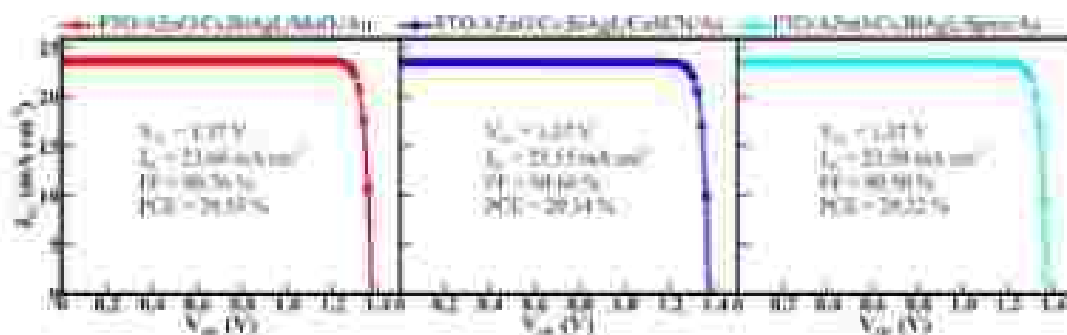


Figure 9. J - V curves for the Cs_2BiAg_4 -based double perovskite solar cells comprising various HTLs ($\text{MgO}/\text{TiO}_2/\text{CuInGa}_2\text{S}_4$).

efficiency or quantum efficiency. The quantum efficiency of the Cs_2BiAg_4 -based double perovskite solar cells is shown in Figure 8. Cs_2BiAg_4 -based double perovskite solar cells with different HTLs showed a broad absorption in the complete visible range (300–800 nm). Further, the J - V curves of Cs_2BiAg_4 -based double perovskite solar cells with different HTLs are shown in Figure 9. The optimum solar cell parameters evaluated for all Cs_2BiAg_4 -based solar cells show high efficiency of $\approx 29\%$. The solar cells show V_{oc} , J_{sc} , and FF in the range of ≈ 1.37 V, $\approx 21 \text{ mA cm}^{-2}$, and $\approx 80\%$, respectively.

4. Conclusion

In conclusion, the theoretical potential of the Cs_2BiAg_4 double perovskite light harvester is evaluated using the SCAPS-1D soft ware package. Cs_2BiAg_4 light harvesters are environmentally benign and render long-term stability. The high efficiency solar cells are optimized based on the MgO ETI and three different HTLs. Solar cells based on all three HTLs at optimized conditions delivered PCEs $\approx 29\%$. Compared to all the physical parameters varied in the optimization, the thickness and bulk defect density of the Cs_2BiAg_4 double perovskite light harvester had the highest control over performance. The cheap and economical carbon electrodes could deliver a PCE of $\approx 29\%$ in the modeled Cs_2BiAg_4 -based double perovskite solar cells. Further, even when the operating temperature shoots up to 400 K, the Cs_2BiAg_4 -based double perovskite solar cells delivered a PCE of $\approx 26\%$. Therefore, while experimentally fabricating

Cs_2BiAg_4 double perovskite solar cells, it should be noted that Cs_2BiAg_4 perovskite is unstable. Hence, it is imperative to produce films with very low bulk defect density and prefer a practical rear contact. The present preliminary analysis accurately illustrates the factors which govern the PCE of Cs_2BiAg_4 solar cells. The procedure employed in this assessment can provide guidelines for experimental implementation and be further expanded to examine additional light harvesters for space-remote applications.

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Conflict of Interest

The authors declare no conflict of interest.

Data Availability Statement

The data that support the findings of this study are available from the corresponding author upon reasonable request.

Keywords

Cu₂Se/Ag₂S, double junction, buffer, 1D Solar Cell Capacitive Simulator (SCAPS-1D), simulation, solar cell

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REVIEW

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Understanding the role of inorganic carrier
transport layer materials and interfaces
in emerging perovskite solar cellsVishesh Manjunath^a, Santosh Birni^a, Parvath A. Shaik^b,
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In the last decade, organic–inorganic hybrid and metal halide perovskite materials have shown tremendous tunability properties and capacity to harvest solar energy efficiently via conceptually new solar cell architectures. Recently, third-generation thin-film solar cells employing perovskite light absorber produce a power conversion efficiency of ~25%, which is attributed to their exceptionally unique and direct-energy gap semiconductor properties. Although the perovskite light absorber plays a main role in the harvesting process, the corresponding device architecture must contain other lacking layers, such as electron and hole transport layers, which are crucial for the efficient and stable electronic functioning of the solar cell. Thus, understanding the functional significance of these transport layers and synergistically optimizing them with respect to the perovskite light absorber is highly significant for further developments in this area. Therefore, this review focuses and critically analyzes the electron and hole transport layers used in perovskite solar cells, highlighting their functional significance and critical role. Their functionality basically originates from their crystal structure, chemistry, electronic and optical properties, and compatibility with their corresponding synthesis protocols of perovskites. Overall, this work aims at developing a comparative analysis and enhanced understanding of the transport of photo-generated charges across the active interfaces in the perovskite solar cells.

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1. Introduction

Renewable energy has shown great promise to combat the surging energy demand globally, with its contribution to the energy sector increasing fairly rapidly.¹ Among the renewable energy resources and their harvesting approaches, solar energy conversion into electrical energy has shown excellent promise towards sustainable development.² Solar cells are devices that convert incoming light energy into usable electrical energy. Although a myriad of efforts has been undertaken in the past 30 years to achieve a high power conversion efficiency (PCE) through different solar cell designs and architectures, a knowledge gap still persists in the comprehensive understanding of how different material interfaces can affect the overall advancement of solar cell technology.³



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Silicon-based solar cells are one of the earliest solar cells making use of crystalline silicon with a bandgap of 1.11 eV, which is well-positioned in the optimum range for broadband light absorption. At present, first-generation silicon solar cells continue to dominate this field, with significant progress being made towards a high photovoltaic conversion efficiency (PCE) due to the developed purification and fabrication technology and earth abundance of the required materials.⁴ Recently, the greater supply than demand has also reduced the costs of other materials, and thus the corresponding improved yields have reduced the projected price of photovoltaic technology.⁵ Moreover, over the years, various materials such as amorphous-Si, GaAs, CdTe, PbSe, Ge, and GaInP have been successfully deposited and optimized into thin films with required thickness and quality and are used as absorbers in second-generation solar cells to further address and combat related problems.^{6–11} The advantages of these second-generation solar cells include their low production cost, flexibility, and light weightiness.¹²

During the last few decades, third-generation solar cells based on nanocrystals, polymers, sensitized dyes, organic-inorganic and inorganic halide perovskites have shown tremendous progress bringing a high degree of novelty and versatility in both the design of new materials and solar cell architectures.^{13–18} Specifically, the emerging perovskite solar cells (PSCs) have gained enormous interest in the last decade with the corresponding conversion efficiency (~23%) competing with their first-generation silicon counterparts.¹¹ Also, the newly introduced perovskite/III-V tandem cells have already delivered a remarkable efficiency of 23.5% (refer to the NREL website for more details).

Hybrid perovskites are molecularly assembled organic-inorganic compounds that absorb incoming light energy efficiently across a significant portion of the solar spectrum. They can be highly tuned to generate various desirable optical and



Rakesh S. Desai

architectures and hybrid materials for applications in supercapacitors, solar cells, photodiodes, green hydrogen generation, and water remediation.

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optoelectronic properties. These organo-inorganic perovskite materials form the ABCX₃ structure, where A represents an organic cation (R₃NH₃⁺, Cs⁺, etc.), B represents a divalent metal (Pb²⁺, Sn²⁺, etc.) and X is a halogen (I⁻, Br⁻, and Cl⁻). The size of these three ions is strictly confined by the tolerance factor (*t*) for a stable perovskite structure.²⁰ Moreover, the perovskite light absorbers possess a high absorption coefficient in the visible region (~250 to 800 nm), high extinction coefficient (~10⁵ cm⁻¹ at 550 nm), long charge diffusion lengths, and ease of processing, which have led to the fabrication of low-cost PSCs at room temperature consuming a lower amount of material.²¹ These intrinsic properties of perovskite light absorbers can be tailored to meet the requirements by merely substituting the ions in perovskite materials.²² However, compared to the perovskite light absorbers, the transport layers are equally important in the solar cell design to ensure high efficiency and stability.

Two different carrier-selective transport layers are required to achieve effective carrier extraction at both external terminals. These transport layers preferably perform selective charge carrier extraction (i.e., n-type or p-type) by blocking the transport of the other (i.e., p-type or n-type). The deposition of a p or n-type transport layer on the light exposure side of the solar cell first, followed by an intrinsic layer results in the device configuration of the conventional negative-intrinsic-positive (n-i-p) and inverted positive-intrinsic-negative (p-i-n). Theoretically, both the (n-i-p) and (p-i-n) device architectures should give the same efficiency, but they differ due to their optical properties, transmittance in the UV-Vis-NIR region, material compatibility, and formation of an ohmic contact with the transparent side of the electrode. Additionally, the investigation of an inverted (p-i-n) architecture that alters optical behaviour was reported in the literature.²³ Generally, the recombination process involves both types of carriers present within the proximity of the charge diffusion pathway, where the extraction of particular types of charge carriers at different ends will reduce their recombination. However, without other qualities such as high conductivity for selected carrier types, reduction of the unfavourable effect at the interfaces, closely matching mobilities of the charge carriers across the interface and tuning of the bandgap for smooth charge transfer of the interfacial charge carrier-type selective transport layers contribute to the realization of high efficiency in PSCs.

In this review, we critically discuss and compare different possible inorganic transport layers (electrons and holes) mainly used for the PSCs. The functionalities, properties, and requirements of these transport layers to achieve efficient PSCs are the main focus. We primarily present, analyse, and discuss the developments pertaining to highly efficient inorganic electron transport layers (ETLs) composed of TiO₂, SnO₂, ZnO, and ternary metal oxides and hole transport layers (HTLs) composed of NiO_x, VO_x, CuO_x, CuI, CuI, and CuSCN. Further, the effect of the physical, chemical, and photoelectrical properties of these widely used inorganic transport layers on the performance of PSCs is discussed in depth. Finally, we also include a brief section on the most extensively used organic transport layers towards the end of this review article.

2. Importance of transport layers

The transport layers in PSCs perform specific functions similar to that in dye-sensitized solar cells (DSSCs) (Fig. 1). However, the term 'division of labour' has been widely used to understand the functionalities of each component in PSCs,²⁴ which include (i) perovskite light absorber: absorbs the majority of the solar spectrum and creates electron-hole pairs, (ii) transport layers: selectively dissociate the excitons generated in the light absorber, and (iii) electrodes: establish an electronic high-quality interface between the device and the external circuit with minimal resistance. Accordingly, the systematic synchronization of these basic components in terms of optical, chemical, structural, and electronic properties leads to a high performance in PSCs. The range of coverage, uniformity, and thickness of the transport layers depend on the employed coating technique. Notably, the interface at the transport layer/perovskite absorber plays a crucial role in the overall device performance. Depending on the structure of the employed transport layers, PSCs are classified into planar and mesoporous device architectures (Fig. 2). Theoretically, the device architecture with a large charge diffusion length (*l_d*) than the thickness of the perovskite absorber (*t_a*) (i.e., *l_d* > *t_a*) is identified as a planar device architecture, which is the opposite to the mesoporous device architecture (i.e., *l_d* < *t_a*). This structure is further divided into two configurations, namely,

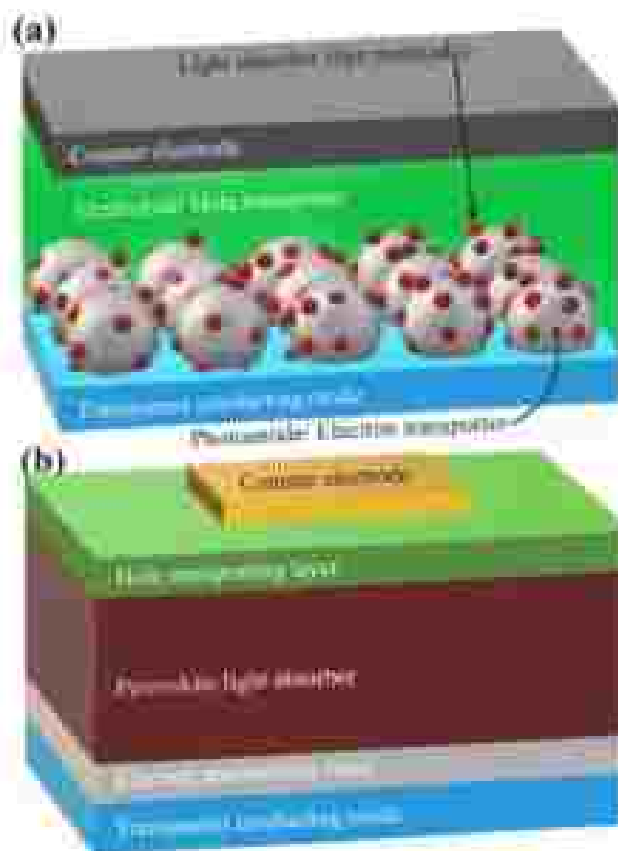


Fig. 1 Schematic representation of (a) dye-sensitized solar cell (DSSC) and (b) perovskite solar cells (PSC).

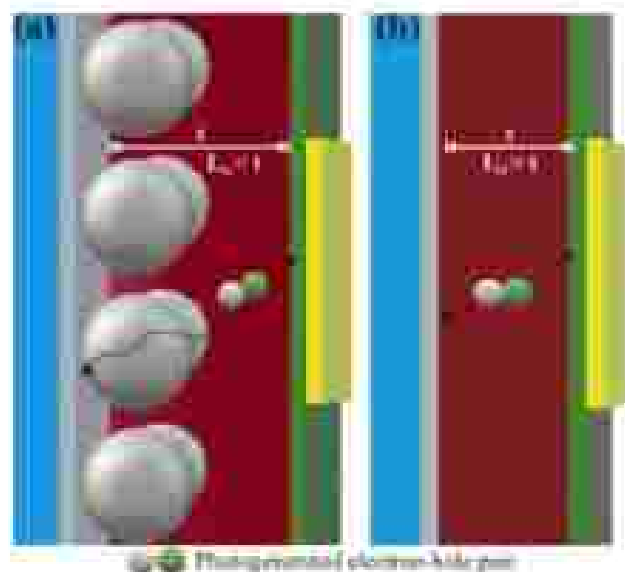


Fig. 2 Schematic of (a) nonplanar and (b) planar PSC.

regular planar with negative intrinsic positive ($n + p$) and inverted planar with positive intrinsic negative ($p + n$), to facilitate excellent optical transparency in the transport layer and allow maximum light illumination on the perovskite-like absorber.⁴² Alternatively, the nonporous structure demonstrates a large effective interface between the transport layer and perovskite, facilitating dissociation of the generated excitons, but lacks charge collection efficiency due to the grain boundary-associated recombination.⁴³ The transport layers are found to guide the growth of the perovskite absorber, but the lattice mismatch between the perovskite and transport layers alters the charge transport. Also, chemical compatibility aspects such as stability and reactivity of the transport layer with the perovskite layer are equally important. Moreover, the transport layers optically protect the perovskite absorber from high energy UV radiation, enhancing the device stability. Leijens *et al.*⁴⁴ observed higher stability in mesoscopic PSCs (similar) with metal oxide than non-sensitized PSCs. The surface adsorbed oxygen states of metal oxides possess deep trap sites for the injected electrons upon continuous exposure to the UV spectrum and may leak into the hole transport material. Furthermore, the presence of defects, interstitials, and impurities in the transport layer, and thereby at its interface with perovskite, strongly influences the charge mobility, transport, and recombination. The oxygen vacancies and interstitial atoms at the interface are known to create shallow or deep levels near the band edge, which form recombination centres.⁴⁵ Therefore, the selection of defect tolerant interfaces is a prerequisite for smooth charge transfer and to avoid charge recombination. The charge mobilities of the transport layers, when closely matched with the perovskite light absorber, drastically reduce the charge accumulation at the transport layer/perovskite interface and enhance the collection efficiency. Therefore, engineering of the transport layers by doping, facetting, or growing nanostructures is required to address these charge recombination issues.^{42–44} Although a

wide range of transport layers has been employed to efficiently transport electrons from the perovskite absorbers to the contacts, the bandgap and band alignment of the transport layers with perovskite light absorbers are fundamental prerequisites for the fabrication of a working device. Usually, wide bandgap semiconductors are employed to allow the maximum visible spectrum illumination on the perovskite films. Band alignment or band edge alignment guides the electrons through the transport layers to reduce the leakage of excited charges to the opposite direction. Besides these functionalities, the ease of processing, use of earth abundant materials, chemical stability, stability under light illumination, non-toxicity, and feasibility of multiple operation are the main concerns to realize the commercial availability of PSCs. Usually, the high processing temperature of metal oxides restricts the use of plastic substrates in PSCs. Overall, in the continuing search for ideal transport layers, different material systems with a wide range of approaches are discussed in the present review.

3. Role of interface and carrier transport in PSCs

3.1 Interfaces

When the perovskite layer absorbs light, the photo-generated charge carriers drift towards the respective interfaces (perovskite/HTL or perovskite/ETL) under the influence of the built-in electric field, where an ultrafast charge extraction process takes place. The efficient charge extraction depends on smooth charge transport through the interface, which is hindered by peculiar features related to the interface such as the surface energy of the two constituent layers, energy level alignment at the interface, interfacial layer, defects, mobile ions, trap states, charge recombination, and charge accumulation. These obstructions result in the recombination of charges, hysteresis effect, and light soaking in PSCs. Consequently, the precise control of these issues (discussed here and shown in Fig. 3) strongly influences the performance and stability of PSCs, which is discussed in detail in this review.

The understanding and investigation of the reasons for the recombination process in the perovskite layer and at the interface are imperative not only to control it but also to narrow the interface engineering schemes, which can be done with the help of a differential equation expressed as follows:

$$\frac{dq(t)}{dt} = \eta I_0 - \tau_1^{-1} q - \tau_2^{-1} q^2 - \tau_3^{-1} q \quad (3)$$

where p is the photo-induced charge carrier density, and τ_1 , τ_2 , and τ_3 are trap- (scinded) (monomolecular), interfacial (bimolecular), and layer recombination rate constants, respectively. The latter is negligible due to the wide bandgap nature of perovskite materials. The charge recombination in the perovskite is also significantly less for highly crystalline perovskite films. The dominant recombination is mainly due to the second-order, i.e., interfacial (bimolecular), recombination arising from (i) structural defects in the perovskite layer manifesting



Fig. 2 Schematic illustrating the importance of interfaces in PSCs.

from the lattice mismatch and thermal strain, (ii) energy offset between the perovskite and transport layers, (iii) surface defects present in the transport materials such as ZnO and SnO₂, (ETL) and NiO (HTL), and (iv) difference in the charge carrier mobility of perovskite and transport layers.²⁸

The charge dynamics, including extraction, transfer, and recombination of charge carriers, happens at the interface. Charge extraction is a very fast process and takes a few hundred picoseconds, which is significantly less than the lifetime of the charge carriers (around a few nanoseconds). Although the charge extraction process is hindered by the presence of Pb₂ at the surface of the perovskite, surface modification has become a prime requirement.^{28–30} Furthermore, the hole traps resulting from the under-coordinated halide anions on the crystalline surface of MAPbI₃ thin films can induce significant charge accumulation at the perovskite/HTL interface.³¹ These trap states existing at the interface can be eliminated by interface engineering to reduce the recombination rate and improve the charge transfer. Also, it has been perceived that the passivation of trap states can mitigate the hysteresis anomaly. Another obstruction for efficient charge extraction is the migration of ions present in the perovskite (MA⁺, Pb²⁺, and I⁻) towards the interface, which can also affect the device performance. These ions have low activation barriers and ionic diffusion coefficients to move within the perovskite, especially when the device is exposed to light illumination.³²

Another important feature is the energy level alignment at the interface, which is essential for smooth charge transportation. Generally, a band offset of -0.2 eV is required for efficient charge transfer at the perovskite/ETL interface. Further, the appropriate balancing in the energy level alignment allows smooth charge transportation, which results in a higher short circuit current density (J_{sc}) and FF factor (FF). Also, an increase in the open circuit voltage (V_{oc}) can be achieved by optimum tailoring of the band alignment.³³

Different approaches for interface engineering, including screening of alternative transport materials with different morphologies and surface modification to alter the charge carrier dynamics, have been attempted to improve the device performance, mainly V_{oc} , J_{sc} , and FF. Furthermore, the use of a mesoporous layer can affect the ion migration, producing a lower accumulation of charge carriers at the interface. The use of doped and composite transport materials, transport layer with different morphologies (one-dimensional and three-dimensional), and bi-layered mesoporous scaffolds can alter the mobility and band alignment of the transport layer, which will improve the device performance and stability. Additionally, different surface modifications and surface passivation techniques can and have been used to optimize the interface.

2.2 Charge carrier dynamics

The two main carrier characteristics of the transport layers that influence the performance of PSCs are mobility (μ) and conductivity (σ). The mobility of the carriers in the perovskite should be well-matched to that of the transport layers, i.e., the mobility of carriers in the transport layers should be greater than or equal to that of the perovskite absorbers for smooth extraction from the perovskite absorber at the interface of the perovskite and transport layer. Conversely, charge accumulation occurs at the perovskite/transport layer interface when the mobility of the carriers in the transport layers is lower than that in the perovskite light absorbers, leading to interfacial recombination. Practically, the carrier mobility of a material depends on its processing methods, microstructures, morphology, and defect characteristics. The electron mobility in a semiconductor can be expressed as follows:

$$\mu = \frac{r}{\tau} \quad (2)$$

where μ , m² and τ are the charge mobility (cm² V⁻¹ s⁻¹), effective mass, and characteristic time (s) of the charges in the transport layers, respectively.

Further, the charge conductivity of the transport layer should be comparable to that of the perovskite absorber to ensure lower charge recombination in the transport and achieve better performance in PSCs. The electrical conduction in a semiconductor is given by the following equation:

$$\sigma = qn\mu \quad (3)$$

where σ is the electrical conductivity (S m⁻¹), n is the free charge concentration based on the Boltzmann relation, q is the diffusion coefficient of charges, and E is the electric field (V m⁻¹). Thus, considering Einstein's equation, the electrical conductivities of the transport layers can be increased by either increasing the charge mobility (μ_n and μ_p for ETLs and HTLs, respectively) or concentration of free charges (n_n and n_p for ETLs and HTLs, respectively). Furthermore, the conductivity and mobility of the transport layers largely influence the series and shunt resistance of PSCs. Various reports suggest that the inclusion of low mobility transport layers at perovskite/transport layer interface results in dominant trap-assisted

recombination losses, delivering poor device performances. Therefore, various research groups have used the doping strategy to enhance the carrier mobility in the transport layers, but doping results in other undesirable issues such as parasitic absorption, dopant diffusion, and doping-induced degradation pathways. In addition, the concentration of dopants required to enhance the mobility in the semiconducting transport layers depends on their thickness and creates ambiguity in ascertaining the exact dopant that can work and its concentration. Le-Corre *et al.*²⁸ reported an alternative strategy to doping and found a different transport layer (with high mobility), namely, optimizing the thickness of the transport layers, which directly affected the fill factor (FF) of the PSCs. Further, to reduce the recombination of photo-generated charge carriers in the perovskite light absorbers, the mobility of electrons (μ_n) and holes (μ_p) should be balanced, i.e., the ratio of μ_n and μ_p should be equal to one. Thus, Chen *et al.*²⁹ used the space-charge-limited current (SCLC) method and demonstrated the importance of choosing and grading the transport layers to achieve a μ_n and μ_p ratio of 1, which enhanced the performance of PSCs.

In general, the carrier transport in the perovskite layer is discussed based on the ideal space charge region, but some studies have reported changes in the semiconducting state (p, i, or n) of the perovskite absorber depending on its ionic composition. Subsequently, Hyeon *et al.*³⁰ introduced the concept of dominant p-n junction depending on the type of ETL used. Electron-beam-induced current measurement (EBIC) and Kelvin probe force microscopy (KPFM) were used to analyse the electric field and charge densities. The EBIC measurements for devices based on a TiO₂ ETL showed a strong EBIC signal at the TiO₂/perovskite interface, unlike PSCs with a C₆₀ ETL, showing a strong EBIC signal at the perovskite/spiro interface, as shown in Fig. 4. Specifically, the generated charges dissociate at the dominant junction with a strong built-in potential and are transferred to the corresponding transport layers. Further, the E-field inside the junction was measured by local contact potential differences (LCPDs) with cross-sectional KPFM measurements. A strong E-field was observed at the TiO₂/perovskite interface for the TiO₂-based device, while the uniform distribution of a weak E-field was noticed at the MAPbI₃/spiro-MeOTAD interface and in the MAPbI₃ layer. On the contrary, a strong

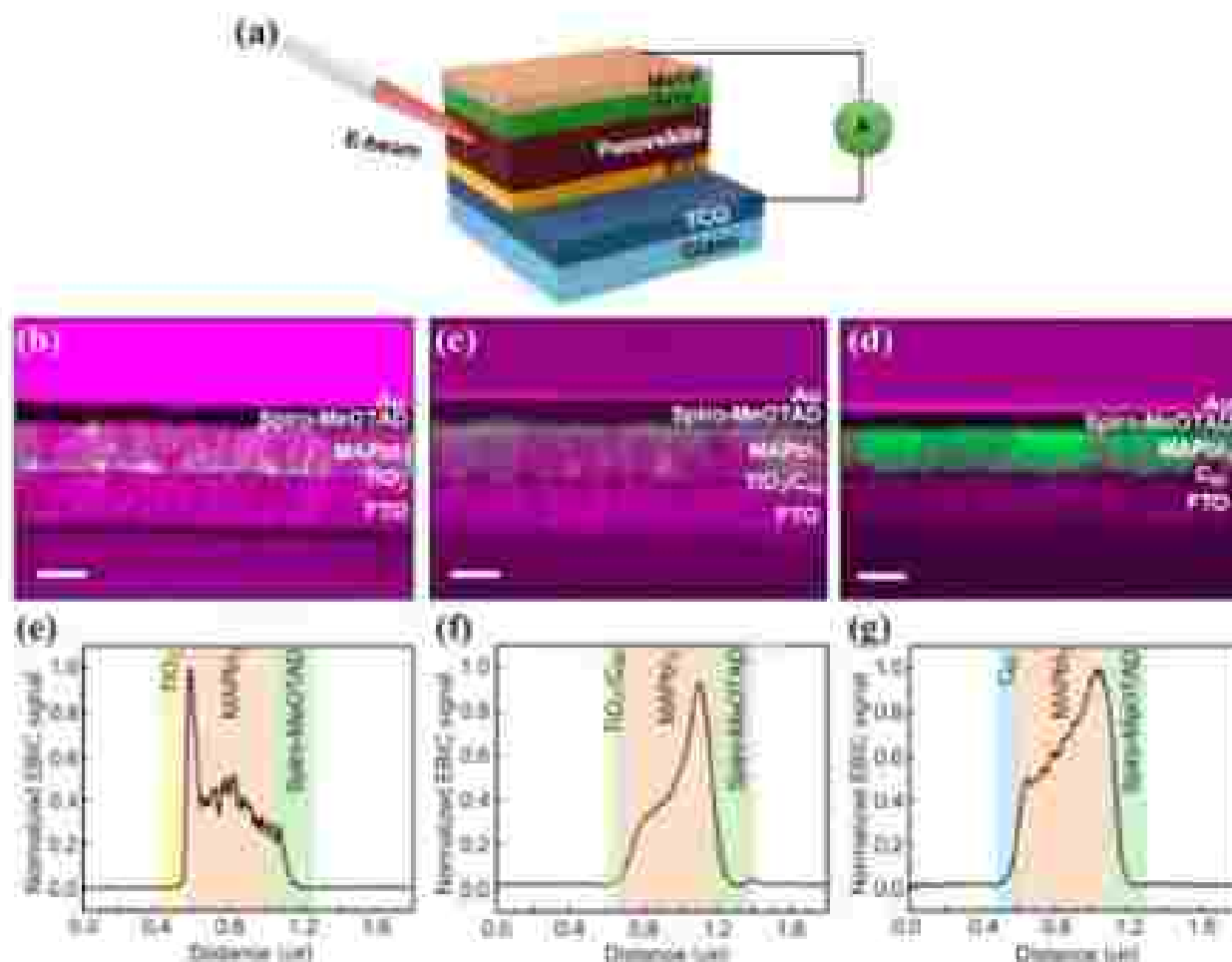


Fig. 4 (a) Schematics of electron beam induced current measurement setup. (b–d) Cross-sectional SEM images (representing the EBIC signal) (bright green color) and (e–g) their line profiles perpendicular to layers of TiO₂, TiO₂/C₆₀, and C₆₀, respectively. The scale-bars in SEM images are 500 nm. ³⁰ Reprinted with permission from JACS Energy (vol. 2005, 5, 2585). Copyright (2005) the American Chemical Society.

E-field developed at the MAPbI₃/spin-MeOFND interface instead of the C₆₀/MAPbI₃ interface in the C₆₀-based device. This again corroborates that the choice of ETL decides the location to form the dominant p-n junction. The carrier density profiles obtained showed that holes were extensively amassed at the TiO₂ interface, and therefore, the net charge of the perovskite layer was also positive for the TiO₂-based device. However, the C₆₀-based device mainly showed electron accumulation at the spin-MeOFND interface rather than C₆₀ (Fig. 5). The net charge of the entire perovskite layer was negative in the device comprised of C₆₀ than that of TiO₂. Thus, the actual devices were not an ideal p-n solar cell, indicating a localized E-field at the specific interface with distinct transport layers.

This further emphasizes the choice of transport layers as a key factor in controlling the carrier dynamics in the PSCs.

The semiconducting transport layers are vital components of high-performing PSCs, but these metal oxide transport layers usually possess inherent trap states. The UV active trap states in the semiconducting transport layers act as recombination centres, which directly impact the FF and short circuit current densities (J_{sc}) of the PSCs. Further, the recombination centres formed at the interface of the transport layer and perovskite absorber give rise to hysteresis in PSCs. Nirmala *et al.*⁴¹ emphasized that the fabrication method used to deposit the transport layers directly determines the trap density at the transport layer/perovskite interface. Further, besides the morphology of

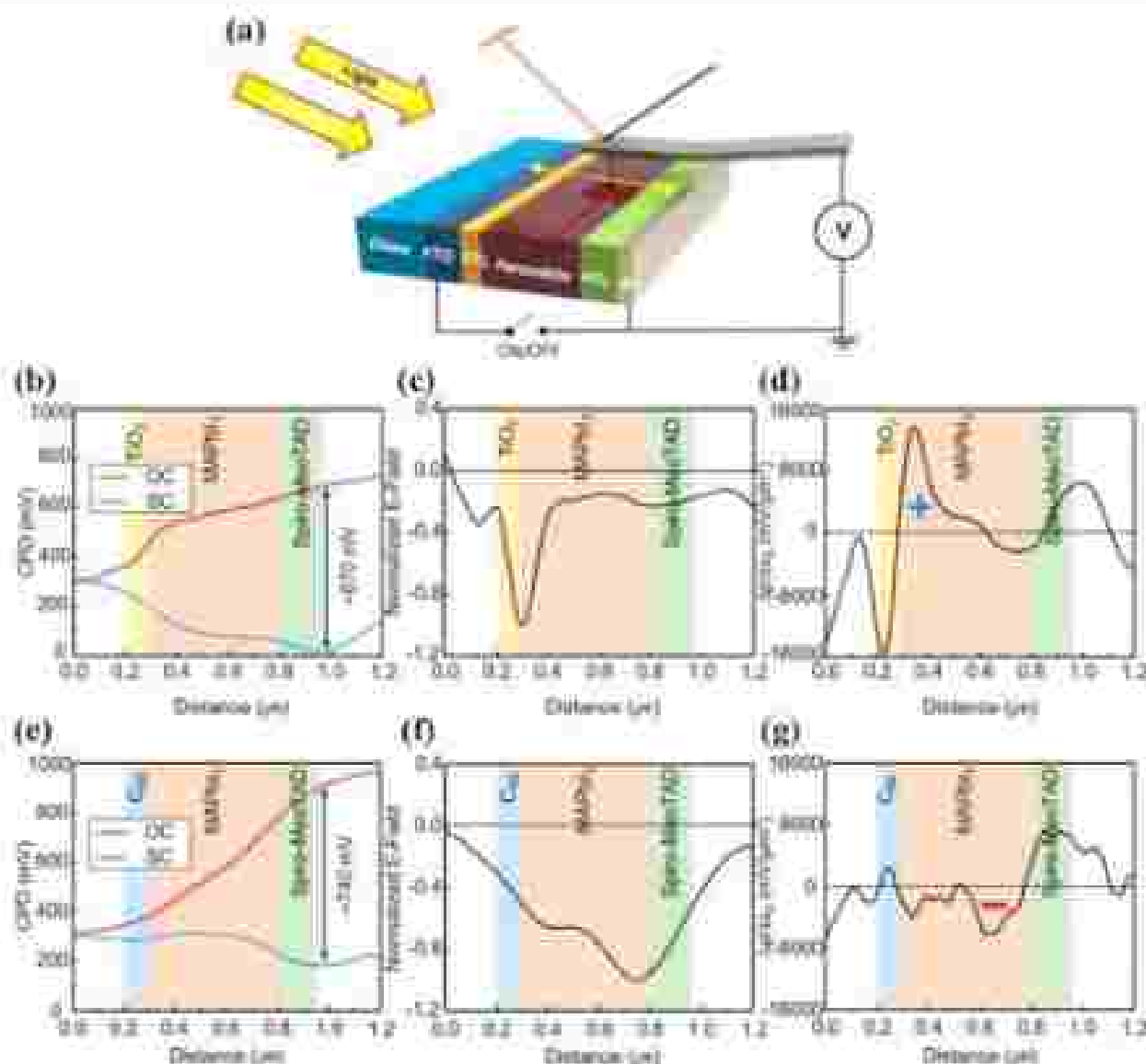


Fig. 5 (a) Schematic of cross-sectional device for the intensity-modulated photocurrent measurement scheme. (b) and (d) Distributions of contact potential differences in OC (red line) and SC (blue line) condition and V_{bc} and V_{sc} normalized E-field distribution and OC conditions under illumination and (c) and (g) charge density profile evaluated from (b) (c) potential difference between $V_{bc} = V_{oc}$ of TiO₂- and C₆₀-based PSCs, respectively. The arrows in (b) and (e) indicate the built-up V_{bc} , V_{oc} (open circuit), V_{sc} (short circuit), and V_{sc} (short circuit voltages).⁴¹ Reprinted with permission from ACS Energy Lett., 2020, 5 (256)–2568. Copyright ©2020, the American Chemical Society.

the transport layers or the perovskite absorber film, the trap density obtained due to the fabrication process of the transport layer greatly controls the performance of PSCs.

Overall, the charge transfer dynamics compete at different timescales. The lifetime of photogenerated carriers in polycrystalline perovskite film ranges from 10–100 ns. With driving forces such as concentration gradient and built-in potential, the photogenerated carriers diffuse to the transport layer/perovskite interface and are selectively separated in a timescale of ~ 10 ns. Subsequently, the free carriers get collected through the transport layers at a typical timescale of ~ 10 ps in the transport layers, before the carriers reach the electrode, the interfacial recombination competes with the carrier transport at the typical timescale of $1\text{--}1000$ ps depending on the concentration of interfacial traps arising from their synthesis protocol, resulting in photocurrent and photovoltage loss.^{42–44} Thus, by ensuring that the transport layers possess less traps at the transport layer/perovskite interface, the photovoltaic performance of PSCs can be significantly enhanced.

3.1 Density of states

The density of states (DOS) can help understand the distribution of the number of electron states per unit volume in the electronic band structure, which determines the optical properties and the V_{oc} of solar cells.^{45–48} Interestingly, the atomic and electronic structure at the interface is the result of the combined effects of the surface structures of the independent constituent layers, giving rise to the solitary electronic structure,

while forming the interface. Particularly, at the interface of the perovskite/transport layer, the atomic and electronic structure plays a pivotal role by affecting the lifetime and mobility of charge carriers.⁴⁹ Furthermore, the conduction band minimum and valence band maximum (mostly inorganic semiconductor) are analogous to the highest occupied molecular orbital (HOMO) and the lowest unoccupied molecular orbital (LUMO) (mostly organic/polymer semiconductor). Fig. 1(a) shows the electronic structure, which is comprised of the vacuum energy level (E_{vac}), work function (WF), Fermi energy (E_f), bandgap (E_g), electron affinity (EA), and ionization energy (IE) for all organic/inorganic semiconductors. The position of these energy levels and their alignment at the junction plays a key role in the overall performance of electronic devices.⁵⁰

The vacuum energy level is the energy of a stationary electron with zero kinetic energy located outside the surface of the material. The work function is the energy difference between the vacuum level and Fermi level ($WF = E_{vac} - E_f$), which depicts the energy barrier that restricts an electron from escaping the material. The Fermi energy represents the value of absolute zero temperature. The ionization energy (IE) refers to the energy difference between the vacuum level and valence band (VB) and depicts the minimum energy necessary to eliminate the electrons from the VB. Incidentally, the energy gained by dropping an electron from the vacuum level to the conduction band (CB) is known as the electron affinity (EA) of the semiconductor. The distribution of DOS in the energy band can be better understood by splitting semiconductors into

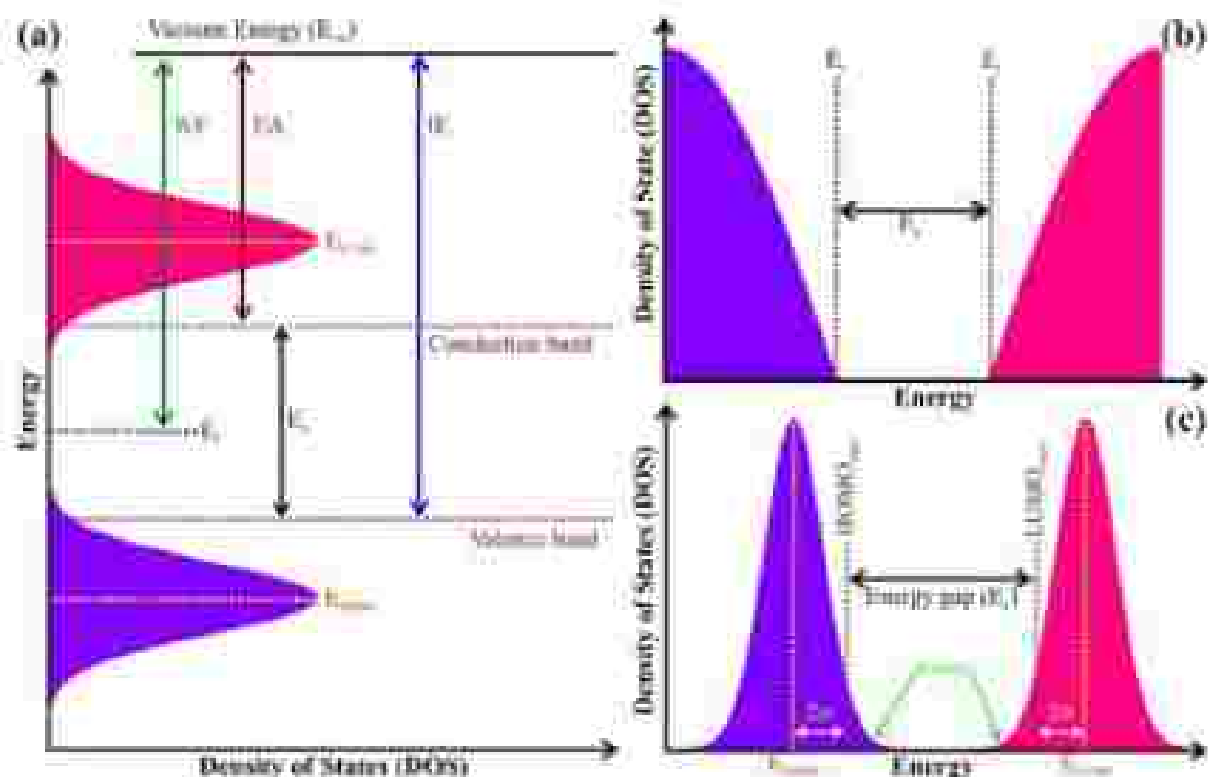


Fig. 6 Schematic of the electronic structure for (a) all-inorganic, (b) organic, and (c) semipolymer perovskite semiconductors.

two categories, i.e., ordered (single crystals and polycrystalline thin films) and disordered (amorphous materials) systems. In the case of ordered semiconductors, the localized charge carriers are at the band edges, and it shows a parabolic shape distribution of the DOS at the band edges, which can be represented as follows:²⁴

$$g(E) \propto \sqrt{E - E_c} \quad (4)$$

$$g(E) \propto \sqrt{E_v - E} \quad (5)$$

where E_c and E_v are the conduction and valence band edges, respectively. This infers that there are no gap states in the forbidden gap of the semiconductor or the DOS is reduced to zero in the energy gap $E_v < E < E_c$. This results in the formation of sharp conduction and valence band edges, as shown in Fig. 6(b).²⁴

In the case of disordered semiconductors such as amorphous and most organic semiconductors, the charge carriers have a poor degree of localization.²⁴ The weak localization at the band edges results in extended states, which progressively change to localized states, leading to the outgrowth of an extended state tail in the energy gap.²⁴ Therefore, the DOS is more appropriately described by the Gaussian or exponential distribution. Further, the Gaussian disorder model (GDM) was proposed to understand the charge carrier transport in disordered organic semiconductors, which gives the Gaussian density-of-state function, $g(E)$, as follows:

$$g(E) = \frac{N_0}{\sqrt{2\pi}\sigma} \exp\left\{-\frac{E^2}{2\sigma^2}\right\} \quad (6)$$

where N_0 is the density of states per unit volume, which is generally considered the density of the molecule, and σ is the width of the distribution. The extended states tailing from the

Gaussian distributed DOS are incapable of accurately defining clear bandgap and sharp band edges. Therefore, the energy gap is defined as the energy difference between HOMO_{max} and LUMO_{min} (Fig. 6(c)). Further details on determining the bandgap of disordered semiconductors can be found in previous studies.^{24,25,26}

In PSCs, to locate the band edges at the interface, Chatterjee *et al.* used scanning tunneling microscopy, i.e., they measured the tunnelling current versus tip voltage of ultra-thin films of layers of PSCs subsequently coated over n-type silicon substrates. The differential conductance (dI/dV) of the thin films was calculated from the obtained data, which corresponds to the DOS. The spectra in Fig. 7 show the positive and negative voltages, denoted as the CB and VB levels, respectively, obtained with respect to the Fermi level. Further, the difference in the valence and conduction band levels (transport gap) is slightly lower than the optical bandgap due to trap states, which contributes to the tunnelling current.²⁷ Moreover, the surface void states of the transport layer nanoparticles can be modified by ligands (silanes or thiols), which can alter the valence and conduction band edge levels by altering the density of states.²⁸

Photoelectron yield spectroscopy (PYS) can also be further used to determine the work function of the transport layers. Yao *et al.* tailored the work function of an NRA₂ layer with lanthanum doping, which could alter the density of states owing to changes in the valence and conduction band levels.²⁹ It should also be noted that the lattice mismatch at the transport layer/nanoparticle influences the charge dynamics. Liu *et al.*³⁰ conducted a first-principles study on the SnO₂/CuPb₂S₆ heterojunction and showed that the SnO₂(110) surface is well-matched with the CuPb₂S₆(100) surface due to their mismatch of 3.9%. The DOS at the interface was different from that in the bulk

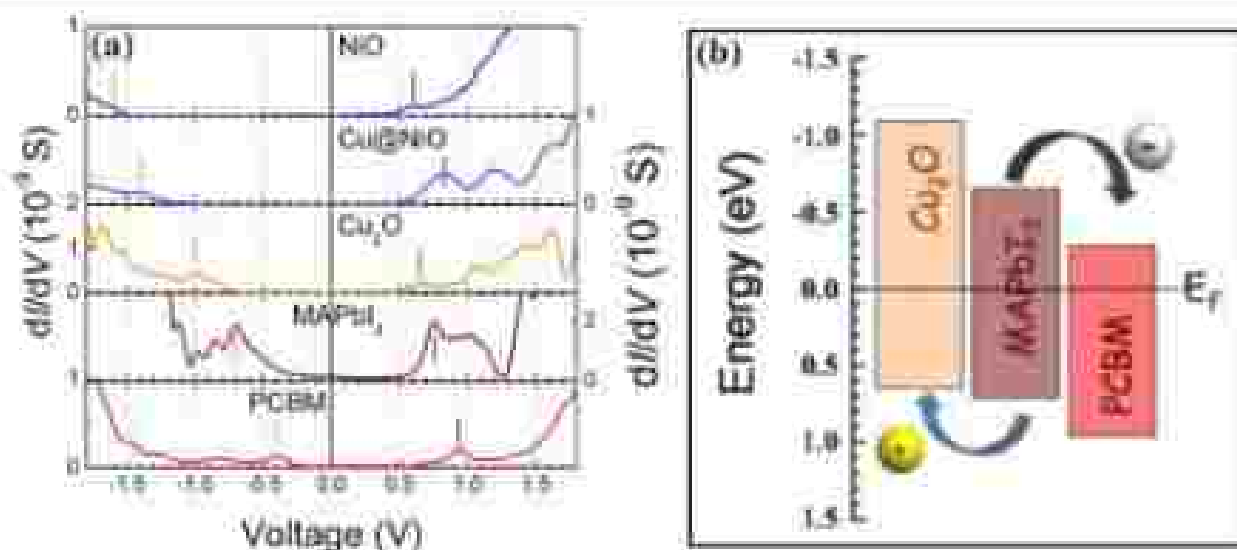


Fig. 7 (a) Experimental conductance (dI/dV) plots of NiO, Cu₂O, CuPb₂S₆, MAPbI₃, and PCBM thin films. VB and CB edges of the materials and HOMO and LUMO levels of PCBM with respect to the Fermi energy are marked with vertical dashed lines and broken straight bars in the positive and negative voltage regions, respectively. (b) Schematic energy level diagram of Cu₂O/MAPbI₃/PCBM heterojunction. The dashed line represents the Fermi energy after contact.²⁷ Reprinted with permission from J. Phys. Chem. C, 2012, 116, 1409–1411. Copyright 2012, the American Chemical Society.

because of the corresponding variation in electronic states at the interface. Therefore, it should be noted that the CBs in PSCs depends on not only the bulk of the inorganic layers but also the interface; however, it can be tuned by controlled doping to adjust the band offsets and achieve a high V_{oc} .

4. Electron transport layer (ETL)

The bandgap and band alignment of the ETLs control and guide the electron transfer at the ETL/perovskite interface. ETLs, in the form of wide bandgap *n*-type semiconductors transparent to visible light, absorb in the UV wavelength range.⁵⁴ Moreover, they allow full visible radiance to strike the perovskite absorber, but this may not be true in inverted device architectures where light strikes through the hole transport layer (HTL) and transparent conducting substrates.⁵⁵ Typically, the bandgap values of the ETLs are higher than the perovskite absorbers utilized to fabricate PSCs. Therefore, the CB edge of the ETL should be at a lower potential than that of the perovskite absorber to guide the electrons through the ETL and reduce the leakage of excited charges in the opposite direction. In the *n*-type structure, the Fermi levels of the ETLs are close to the CB; hence, the probability of the VB electron movement from the perovskite to ETL is close to zero, and hence negligible (Fig. 6). Therefore, variety of ETLs has been explored to control the recombination process and accelerate the charge carrier recombination dynamics in search of efficient and stable photovoltaic performances. In this section, we discuss the important characteristics of various inorganic ETLs and their outstanding development in delivering excellent PSCs when combined with perovskite absorbers.

4.1. Inorganic ETLs

Inorganic ETLs, which are engineered into nanostructures for exploiting the nano-scale physical properties, increase the

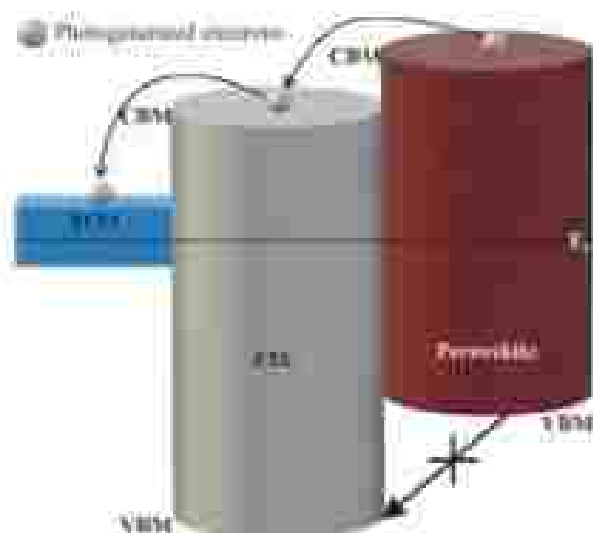


Fig. 6 Schematic structure the path of a photogenerated electron from the perovskite light absorber to the external circuit. CBM: conduction band minimum and VBM: valence band maximum.

junction interface. Therefore, oxides of various metals such as titanium (Ti), tin (Sn), zinc (Zn), tungsten (W), barium (Ba), strontium (Sr), aluminium (Al), iron (Fe), and indium (In) have been explored for their performance as ETLs in PSCs.^{56–60} The band structures of several perovskite inorganic ETLs are summarized in Fig. 9. The appearance of inorganic ETLs in various crystalline polymorphs and their ability to tailor the charge-transfer dynamics are of special interest to the PV community. The objective is to look for cost-effective inorganic ETLs processable under ambient conditions. Furthermore, the ETLs can act as a prominent template for the overlying perovskite layer in PSCs after engineering their phases and crystallinity. The synthesis, characterization, and significance of a few critical inorganic ETLs employed in PSCs are thoroughly discussed in this section.

4.1.1. Titanium dioxide (TiO₂). TiO₂ is one of the fascinating electron transport materials widely used in the fabrication of PSCs due to its low processing cost, chemical stability, and non-toxic nature. Titanium oxide has several allotropic forms categorized as TiO₂ and Ti₂O₃, with different crystal structures, namely, monoclinic, triclinic, tetragonal, orthorhombic, rhombohedral, and hexagonal.^{61–63} However, its most well-known forms are anatase (tetragonal structure, *P4*₂/mnm space group), brookite (orthorhombic structure, *Pbcn* space group), and rutile (tetragonal structure, *P4*₂/mnm space group), which are composed of a TiO₆ octahedral network through shared oxygen at the corners. The TiO₆ octahedra share both the corners and the edges to form the rutile and brookite-type crystal structures, but the sharing of only edges results in the formation of an anatase crystal structure. The chains of the edge-shared distorted TiO₆ octahedra run parallel to the *c*-axis and deliver the brookite phase. These distinct crystalline forms influence the electronic and electrochemical properties of TiO₂ nanostructures,^{64–67} and hence play a crucial role in the performance of PSCs. In the nanocrystalline form, the anatase, brookite, and rutile phases are the most thermodynamically stable at crystalline dimensions of <11 nm, between 11 to 51 nm, and ≥51 nm, respectively.⁶⁸ Nevertheless, the synthesis of the brookite phase is most challenging because of its metastable nature.^{69–71} Owing to the ease of processing of the anatase and rutile phases, they are more widely utilized than the brookite phase in solar cells.^{72–74}

The wide adaptability of TiO₂ as photoanodes in DSSCs has promoted it as an interesting ETL material in PSCs.^{75–80} TiO₂, which is an *n*-type wide bandgap semiconductor (i.e., $E_g = 2.3$ eV with CB edge level at -4.5 eV and VB edge level at -7.0 eV), is one of the most transparent materials to visible light and offers electronically favorable band edge alignment with most of the known perovskite absorbers. Usually, a compact TiO₂ film is used as the hole-blocking layer in PSCs. Various thin film growth techniques, namely, spin coating,²² air-spun-coated coating,⁸¹ electrospraying,⁸² sputtering,⁸³ atomic layer deposition (ALD),⁸⁴ hydrothermal growth,^{85–87} spray coating,⁸⁸ and template-based synthesis,⁸⁹ have been employed for the synthesis of good-quality TiO₂ transport layers. However, hydrothermal synthesis is an attractive process for obtaining hierarchical nanostructures such as nano-rod arrays,



Fig. 9 Schematic showing the band structures and the band alignment of various organic ETIs with a perovskite absorber

which offer dual functions of significant light trapping and efficient electron collection (Fig. 10).⁵⁸ The 3D morphology efficiently extracts the photoelectron from the perovskite absorber (i.e., MAPbI₃) and reduces the electron transport length in the matrix to surmount the obstacle of short electron diffusion length. Further, finite difference time domain (FDTD) simulations revealed that the electron transport pathway in PSCs consisting of branched nano-dendrites assists in the photoelectron collection near the spiro-MeOTAD layer due to absorption of long-wavelength light. Moreover, the surface passivation of the 1D TiO₂ nanorods by atomically deposited TiO₂ nanoparticles offers excellent charge separation, controlling the back-side reaction of the electrons excited from the perovskite absorber. This facilitates a low recombination rate with a conversion efficiency of 11.4%.⁵⁹ The secondary oxidation treatment at higher temperatures always contribute to the presence of defect/impurities (i.e., residual carbon) and changing the band alignment at the interface. The impurities serve as non-radiative quenching sites or charge recombination centres, effectively trapping the photo-generated electrons at the interface of the TiO₂, ETI and perovskite absorber, thereby curtailing the dramatically injected electron yield. However, the formation of defects or impurities was eliminated via UV/O₂ treatment without compromising the density of oxygen vacancies to gain competitive efficiency from the amorphous 3D-grown TiO₂ (i.e., 9.7%) and cupped TiO₂ (i.e., 18.9%) ETIs.^{60,61} Moreover, the uneven blocking layer of TiO₂ nanoparticles between the valleys and platform of F-doped (n-d), induced unidirectional electron transportation, and thereby the poor charge collection reduced the performance of the corresponding PSCs.⁶²

Chang et al.⁶³ introduced electrospun TiO₂ nanofibres as a photoanode, enabling a greater loading of perovskite materials and also lowering the trap-assisted recombination. Despite the

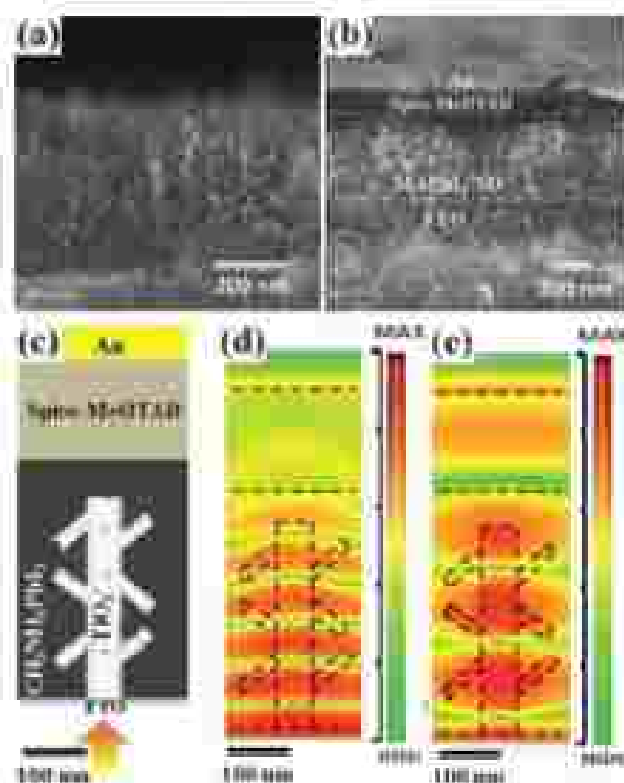


Fig. 10 Cross-sectional SEM images of 1D TiO₂ nanofibres (a) and (b) and collection devices composed of TiO₂ nanofibres (c) Schematic of the FDTD simulation cells for perovskite, TiO₂ nanofibres, FDTD-simulated TM energy density distribution (PSC after continuous electromagnetic wave passing through the perovskite-TiO₂ nanofibres with wavelength of 635 nm and (d) 635 nm.⁶³

more open structure and porous arrangement of the nanofibres, the poor PCE, conversion in CH₃NH₃PbI₃, was reported to

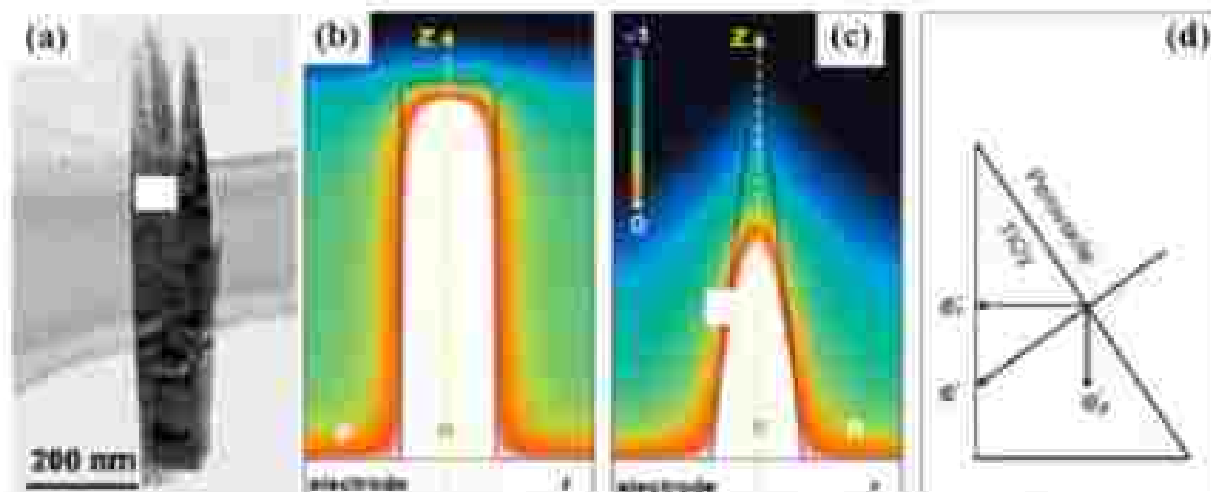


Fig. 11 (a) Low-magnification SEM image of TiO₂ nanowires, (b) schematic of electron injection from p-type TiO₂ and transport within TiO₂, (c) schematic of electron injection along the radial direction and e⁻ along the axial direction. Reprinted with permission from *Nano Energy*, 2015, 11, 409–418. Copyright 2015, Elsevier.

improve the device efficiency.¹⁰⁰ The tapered nanowires of rutile TiO₂, oriented in the [001] direction exhibited superior efficiency than nanowires, irrespective of the variation in their length (Fig. 11).¹⁰⁰ The suppressed charge recombination due to the faster electron injection rate of the TiO₂ nanowires was beneficial for the charge separation at their interfaces with CH_{3NH₃PS₄, resulting in an enhancement in the efficiency. The two possible factors responsible for the faster electron transfer from the perovskite to nanowires are as follows: (i) larger surface to volume ratio of the nanowires improving the charge separation and (ii) decreased distribution of electrostatic potential for p-n junction, generating an electric field along the axial direction, which enabled enhanced electron transportation, while minimizing its trapping. Specifically, the driving force for the injection of electrons into the TiO₂ nanowire ETL and transport along the axial direction for the nanowire/perovskite systems was absent in the nanowires (Fig. 11(d)), which led to faster electron transfer from the perovskite to TiO₂ nanowires, suppressing the charge recombination. Likewise, highly ordered anti-reflecting silica nanotubes served as nanocomposites and ETL in CH_{3NH₃PS₄ and facilitated efficient charge collection/extraction, delivering an efficiency of 14.8% despite the relatively lower loading of CH_{3NH₃PS₄.¹⁰¹}}}

It was shown by Xiao *et al.*¹⁰² that nanoporous submicron TiO₂ spheres with high specific surface area ensure higher light scattering effect and better contact with the perovskite through infiltration, which caused higher light absorption and faster charge transport, respectively, delivering excellent stability against atmospheric moisture when the PSCs with 14.7% efficiency were exposed to the air. Similarly, the smaller leakage current and reduced transport resistance of spool-like mesoscopic TiO₂ caused a high (18.3%) efficiency.¹⁰³ Further, as shown by Thambidurai *et al.*,¹⁰⁴ interface modification of a mesoporous TiO₂ ETL by (CO)₂ uplifted the conduction band of TiO₂, leading to better energy level alignment with the

perovskite, thereby enhancing the optical absorption, reducing the carrier recombination, and rendering excellent electron transportation. Together, they led to a high PCE of 17.2%. The passivation of the perovskite/TiO₂ interface using poly(vinyl carbazole) (PVC) and PCBM is a versatile and rational method to gain a PCE of around 21.1%. The PVC-assisted homogeneous dispersion of PCBM in the mesoporous TiO₂ layer also prevented shunt after the formation of the perovskite layer. The interface modification induced efficient charge transport to the TiO₂ ETL and efficiently reduced the carrier recombination at the ETL/perovskite interface.¹⁰⁵ Moreover, the introduction of a sodium sulfate (Na₂SO₄) passivation layer at the interface of the TiO₂ ETL and perovskite delivered an efficiency of 18.77%.¹⁰⁶

Recently, Wang *et al.*¹⁰⁷ introduced the interface modification of TiO₂/perovskite by CsAc to reduce the interface defect density and the related carrier recombination. Even though the CsAc improved the affinity of the perovskite precursor to form a compact and highly crystalline perovskite layer by decreasing the Gibbs free energy for heterogeneous nucleation, the carbon as an ETL may have restricted the efficiency to 13.8%. Likewise, a robust and simple acid-treatment strategy was introduced to produce an amorphous TiO₂ buffer layer above the anatase TiO₂ surface as an ETL.¹⁰⁸ The acid treatment weakened the bonding of the zigzag octahedral chains in TiO₂ and formed an amorphous buffer layer by deconstructing the staggered octahedron chains. This led to the formation of oxygen vacancies in the amorphous TiO₂ ETL, and hence increased electron density, efficiently transferring electrons from the perovskite to ETL layer. Modification of the interlayer between the TiO₂ and perovskite layers by introducing air-stable n-type DMOD-doped PCBM was shown to significantly diminish the energy level offset at the interface, thereby delivering an efficiency of 20.1%.¹⁰⁹

Nanocomposites of TiO₂ have also been explored to ensure the higher performance of PSCs based on them. Indeed, it was found that the PCE of 13% achieved using a TiO₂/graphene

nanocomposites¹⁰ further improved after replacing graphene with single-walled carbon nanotubes (SWCNTs).¹¹ However, the increased number of recombination sites due to higher loading of SWCNTs adversely affected the performance features. The composite of phosphotungstic acid (PW₆) and TiO₂ ETL down-shifted the conduction band edge and led to a well-aligned interface with the perovskite for excellent electron extraction.¹² Besides, metal oxides were also used as a substitute of carbon materials to form nanocomposites with TiO₂, but were found to be relatively inefficient as ETLs due to the inhibited recombination rate offered by impure phase formation.¹³ Therefore, Y,¹⁴ Ga,¹⁵ Zr,¹⁶ and Ba¹⁷ doped and ZrN¹⁸ and Er-Yb¹⁹ co-doped TiO₂ nanostructures have also been explored as ETLs to achieve longer carrier lifetimes and higher charge density at the ETL/perovskite interface. Moreover, hydrogen²⁰ and cadmium²¹ have been utilized to alter the recombination resistance and charge carrier density of TiO₂ to further increase the collection efficiency. An Nb-doped TiO₂ ETL covered with an over-layer of TiO₂ nanorods was shown to reduce the interface transport resistance and capacitance, thereby delivering an efficiency of 18.88% due to electron injection from the CB of perovskite to Nb-TiO₂.²²

Jiang et al.²³ doped a TiO₂ ETL with Na₂S in search of interface defect passivation and improved conductivity. The Na cations and S anions were observed to improve the conductivity and change the wettability of the TiO₂ layer, respectively. This was aimed to improve the crystallinity of the perovskite layer and passivate defects at the ETL/perovskite interface. Recently, various anions of TFSI⁻, Cl⁻, F⁻, and CO₃²⁻ of Li salts have been explored as ETLs for PSCs.²⁴ The first three anions of Li salts remain doped in TiO₂ to improve the electrical properties by one-octet enhancement in electron mobility and reduced electron trap density of Li-doped TiO₂ ETLs. Conversely, the stronger chemical bonding between Li₂CO₃ and TiO₂ exhibits the deepest conduction band and delivers the maximum efficiency of over 23%. The high temperature firing at ~300 °C required to gain the crystalline phase of pristine or doped TiO₂ nanostructures restricts the processing of the ETLs over plastic substrates. Alternatively, low-temperature processing to protect the plastic substrate, while gaining the desired crystalline phase of TiO₂, has been attempted to fabricate flexible PSCs. The plasma-enhanced atomic layer deposition of a compact TiO₂ layer at 80 °C on PED-coated PEN flexible substrates²⁵ and e-beam evaporation of TiO₂ on PET substrates²⁶ have been found to be effective to fabricate wearable power devices, achieving a PCE of 12%. However, physical deposition methods, such as ALD,²⁷ e-beam evaporation,²⁸ and sputtering,²⁹ are complex and demand high energy consumption to create a vacuum. Therefore, the use of solution methods such as spin coating³⁰ and solution dispersion³¹ on flexible substrates was also attempted, but the PCE was limited to 10%. Consequently, further optimization of the solution-based processes at low temperature to gain dense and compact TiO₂ ETLs is essential to improve the PCE.

4.1.2. Tin oxide (SnO₂). Tin oxide can be synthesized in various chemical forms [i.e., SnCl₂, SnCl₄, Sn₂O₃, and Sn₃O₄] and

crystalline phase forms [i.e., orthorhombic, tetragonal, cubic, and triclinic crystals].³² Most importantly, being chemically stable, UV-resistant, and low temperature processible (<200 °C), SnO₂ also supports high bulk electron mobility (i.e., 240 cm² V⁻¹ s⁻¹), wide bandgap [i.e., 3.6–3.9 eV], and visible transparency.³³ Thus, considering its higher charge mobility and excellent UV stability, it can potentially surpass the lower charge mobility ETLs such as TiO₂. Recently, SnO₂ nanocrystalline films have been identified as both technically stable ETLs and antireflection films.³⁴ Various synthetic techniques such as ALD,³⁵ chemical bath deposition,³² electrochemical deposition,³⁶ pulsed laser deposition (PLD),³⁷ e-beam evaporation,³⁸ and spray coating^{39,40} have also been used to synthesize compact, uniform, and self-defined morphologies of SnO₂ ETLs. However, the solution processing of salts such as SnCl₂, SnCl₄, SnCl₃, SnCl₂·2H₂O, and SnCl₂·4H₂O, followed by thermal decomposition,⁴¹ is the most widely employed technique due to its easy scalability as an industrial tool to render well-defined morphologies of ETLs for PSCs. Moreover, the uniform layer of SnO₂ nanoparticles easily realized by an automated spray coating technique at lower processing temperature over 25 cm² active area was shown to deliver an improved charge lifetime at the ETL/perovskite interface and stable performance under cell life test for 1000 h.⁴²

A thin layer of SnO₂ nanoparticles as the ETL delivered an efficiency of 21% in planar-structure PSCs,⁴³ but the development of PBL, a p-type material at the interface, led to a higher hole transfer rate than electron transfer rate. The reduced barrier at the perovskite/spiro-OMeTAD interface and passivation of the surface or grain boundary defects by PBL were found to control the device performance. Moreover, SnO₂ was also studied with ZnO nanostructures to improve the PCE performance, where a hollow (dimer) SnO₂ nanotube array was grown over ZnO nanorods as a sacrificial template (Fig. 1), but the PCE was still restricted to 12.1%, which could be due to sluggish electron transport from the hierarchical thicker shell layer of SnO₂ nanotubes, providing pinholes.⁴⁴ The pinholes caused surface current leakage and compromised the charge recombination processes at the interface. Therefore, the preparation of a smooth and compact bilayer structure of SnO₂ nanoparticles by filling the pinholes reduced the oxygen-deficient regions, improved crystallinity, and downshifted the dislocations, facilitating its efficacy as an ETL for PSCs. Indeed, the bilayer SnO₂ structure delivered a PCE of 18.84% due to the lowered electron trap density, continuously reduced contact resistance, and charge accumulation at the ETL/perovskite interface.⁴⁵

Surface treatments with aqueous solutions of salts such as TiCl₄ have been explored to significantly retard the recombination process of SnO₂.⁴⁶ However, the inclusion of conducting materials in SnO₂ ETLs provides a better interface with the perovskite and control over the recombination process, and thus more attractive in the search for improved PSCs. The addition of a small amount of graphene quantum dots was shown to enrich the electrode properties of SnO₂, thereby aiding the delivery of a steady-state PCE of 20.23% with very little hysteresis via controlled electron transfer from graphene.⁴⁷

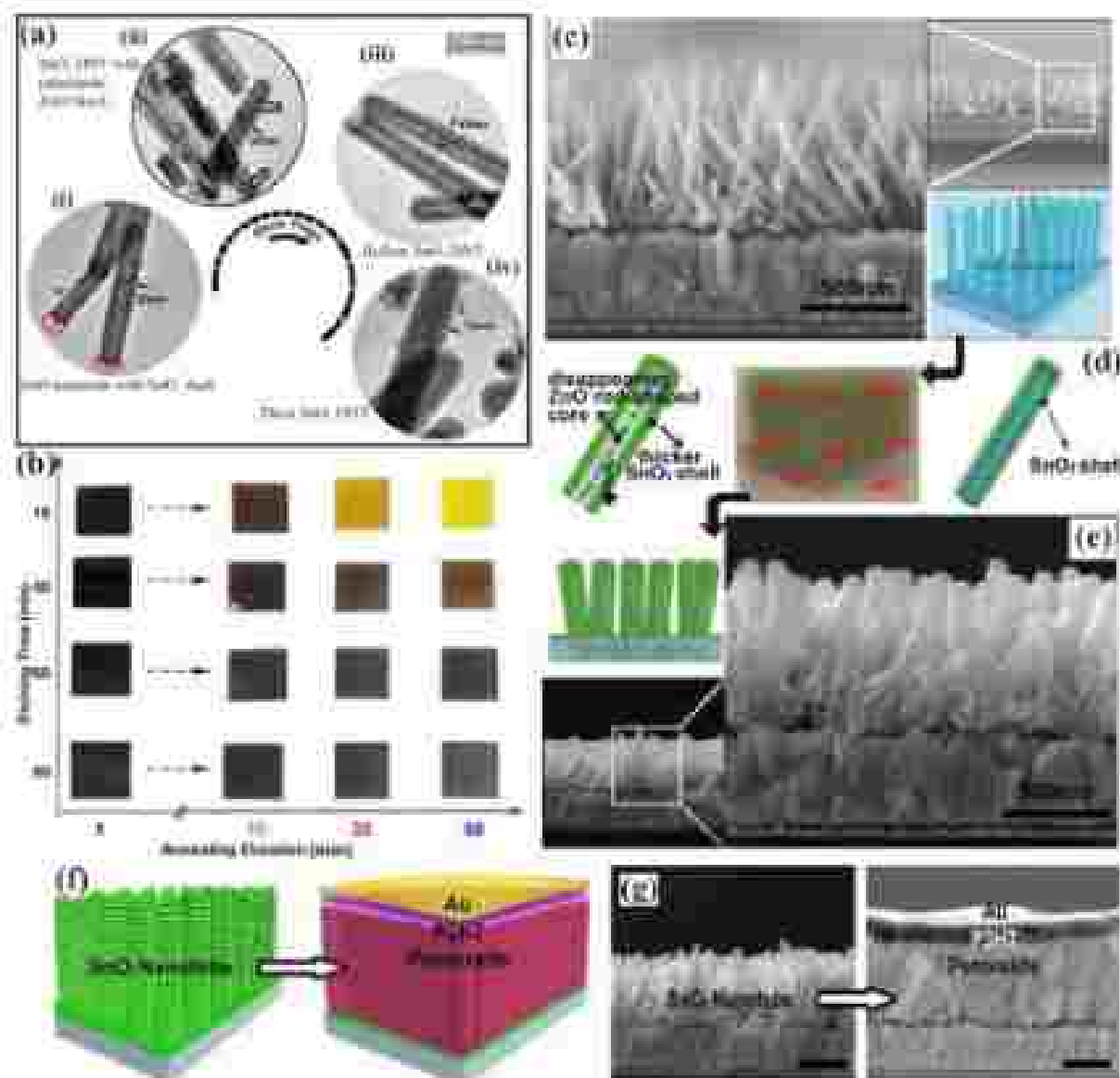


Fig. 12 (a) TEM images of time-dependent growth of SnO₂ (DNT) under reaction time of (i) 15, (ii) 20, (iii) 60, and (iv) 90 min; (b) layer-coated perovskite films over SnO₂ (DNT)/TiO₂/glass substrates at different reaction times; Schematic growth mechanism of (c) SnO₂ nanorods (covered with discontinuous SnO₂ nanoparticles); (d) OH⁻ ions as by-product of SnO₂ can etch the ZnO nanorods; and (e) SnO₂ (DNT)/ZnO nanorods; (f) fabrication scheme of PSCs and (g) corresponding cross section of SnO₂ (DNT)/ZnO/SnO₂ (DNT)/perovskite/PTBMA/Au device. The scale in black indicates 300 nm. ¹⁰⁰ Reprinted with permission from (Yan *et al.*, 2011, 325, 19–20). Copyright (2012) Elsevier.

The photo-generated electrons from graphene effectively fill the electron traps and improve the electron density in the conduction band (CB) of SnO₂, which collectively accounts for the reduced work function and improved conductivity of SnO₂. The reduced electron trap density and increased conductivity of the ETLs facilitated an enhancement in the electron extraction efficiency and reduced recombination at the ETL/perovskite interface. Further, the addition of graphene to mesoporous SnO₂ microspheres resulted in a relatively reduced charge transfer resistance (i.e., faster electron extraction) and larger recombination resistance than the pristine SnO₂, consequently leading to the least interface potential loss and PCE of 17.0%.¹⁰⁰ Likewise, the inclusion of carbon nanotubes substantially increased the

conductivity of the SnO₂ ETL by lowering the defect density, which improved the electron extraction and transport. This reduced the electron accumulation at the ETL/perovskite interface and significantly enhanced the PCE to 16.1%.¹⁰¹

Recently, Yoo *et al.*¹⁰² introduced a holistic approach to improve the performance of PSCs by virtue of charge carrier management. The SnO₂ ETL was developed with an ideal film coverage and thickness by tuning the chemical bath deposition process. Further, the decoupling of the passivation strategy between the bulk and the interface minimized the bandgap barrier and improved the charge carrier properties. Although control of the pH from most acidic (i.e., 1) to 6 delivered thin uniform films to a distinct tapered morphology, where the

layer film coverage at the most acidic pH caused interfacial recombination, and the oxygen site defects at pH > 3 reduced the carrier lifetime by increasing the non-radiative recombination. The magic reaction at pH 1.5 exhibited ideal film coverage, morphology, and chemical composition and delivered a certified PCE of 22.2%. A high FF of 84.8% was identified to be responsible for the enhanced PCE, which improved the carrier mobility in the Cs₂DBA/PTAC, active layer and excellent charge collection with the least parasitic losses from shunt/series resistances. Thus, the close association of charge carrier management with the FF and the V_{oc} can direct the improved performances of PSCs to reach the theoretical efficiency limit. Moreover, the resistance gradient across the edge and centre of the thin film influences the free carrier mobility to a considerable extent.¹³⁹ Hence, the realization of a uniform film with the controlled agglomeration of grains, which is feasible by adopting the rastering of multiple spray nozzles, can render an excellent ETL for PSCs.

Besides these efforts, doping strategies have been considered to improve the electron charge transfer, lower the charge recombination, and reduce the contact resistance at the SnO₂/perovskite interface. The downward shift of the CB or Fermi level and enhanced conductivity of the SnO₂ ETL after Li,¹⁴⁰ Mo,¹⁴¹ Mg,¹⁴² Cl,¹⁴³ Br,¹⁴⁴ KF,¹⁴⁵ Te,¹⁴⁶ ZnF,¹⁴⁷ and NH₄Cl¹⁴⁸ doping expedited the injection and transfer of electrons, increased the effects of the doped ETLs/perovskite layers, and inhibited the charge recombination at the interface. Yang *et al.*¹⁴⁹ explored a Y-doped SnO₂ ETL in search of efficient PSCs. The Y doping promoted the homogeneous distribution of well-aligned SnO₂ nanowires, which allowed better infiltration in and contact with the perovskite and improved electron transfer from the perovskite to SnO₂ nanowire ETL. Moreover, after Y-doping, the upshifted band levels resulted in better energy level alignment and reduced charge recombination at the Y-SnO₂/perovskite interface. Moreover, the optimized 5 mol% doping of Nb in SnO₂ created better surface coverage with perovskite and yielded a PCE of 20.5% due to the reduced recombination centres and enhanced electron extraction at the interfacial contact.¹⁵⁰ The Cl-capping upshifted the band levels of the SnO₂ nanowire ETL and suppressed the non-radiative recombination with faster transfer of charge carriers. Moreover, Cl-capping created a hydrophobic surface for SnO₂, which reduced the trap density and suppressed the interfacial recombination of charges by dramatically increasing the grain size and crystallinity of the perovskites, delivering the hysteresis-free PCE of 18.1%.¹⁵¹ In another study, nitrogen-doped graphene oxide (N-GO) was introduced as an oxidizing agent for SnO₂ to control the oxygen defects. The altered oxidation state from Sn²⁺ to Sn⁴⁺ reduced the oxygen vacancies in SnO₂ in the composite of SnO₂-GO, and efficiently extracted the charges and reduced the carrier recombination, thereby delivering a PCE of 18.5%.¹⁵² Likewise, diluted Gds quantum dots improved the carrier mobility of SnO₂ and delivered a PCE of 20.7% by accelerating the charge extraction at the modified interface.¹⁵³

Xia *et al.*¹⁵⁴ introduced the solution sulfuric acid (H₂SO₄) between the SnO₂ ETL and the perovskite layer, in which the interfacial chemical bridge formed through the coordination

bond via -SO₃⁻ anions and electrostatic interactions via -NH₄⁺, remedying the oxygen vacancies of SnO₂ and passivating the charged defects of the perovskites, respectively. This dipole alignment passivated the interfacial defects and offered barrier-free efficient charge transfer between SnO₂ and perovskites, leading to a PCE of 20.4%. Recently, the bi-directional functionalization via -NH₂ groups resulted in a PCE of 20.5%.¹⁵⁵ The chemical interface of -NH₂ groups expedited the charge transfer in the ETL and reduced the trap-state density in the perovskite.

To *et al.*¹⁵⁶ introduced the effect of molecular doping in an SnO₂ ETL on the overall performance of PSCs. The triphenylphosphine oxide (TPPO) molecule adopted n-type doping in SnO₂ to realize electron transfer from the P(=O)O⁻ σ bond to the peripheral Sn atoms (rather than the atoms directly interacting at the surface, which produced delocalized electrons at the surface, leading to a reduced work function and increased conductivity (Fig. 13). Moreover, the significantly reduced energy barrier (*i.e.*, 0.55 to 0.29 eV) after TPPO doping assisted the electron transfer and faded the charge accumulation at the interface, delivering a PCE of 20.6%. Similarly, graphdiyne doping in SnO₂ was employed to precisely engineer the interface due to heterogeneous perovskite nucleation, reducing the grain boundaries and defect density and leading to favourable C-O σ bond formation and band alignment. Consequently, this reduced the interfacial recombination and delivered a PCE of 20.7%.¹⁵⁷ In the future, molecular doping in the ETL can lead to achieving an excellent efficiency in PSCs, but the strong reducibility and stability under ambient conditions need to be inspected thoroughly. Similarly, modulation of the perovskite crystallization process needs to be explored deeply to gain a deeper understanding of the process of realizing highly stable and crystalline perovskite films. Recently, it was shown that a Ti₂O₃T₂ quantum dot modified SnO₂ ETL delivered a steady-state PCE of 21.3% with excellent charge extraction efficiency.¹⁵⁸

4.1.3. Zinc Oxide (ZnO). Zinc oxide, an n-type semiconductor, offers high crystallinity at low processing temperature and favourable band alignment with hybrid perovskites. A direct bandgap of 1.3 eV, electron mobility of 200–300 cm² V⁻¹ s⁻¹, and electron diffusion coefficient of 1.7×10^{-4} cm² s⁻¹ are the other major characteristics of ZnO, attracting researchers to explore it as a potential ETL to improve the performance of PSCs.^{159–161} Various methods have been widely explored to process and coat ZnO films under an ambient atmosphere, and each method provides a unique way of controlling the structure, electronic properties, and surface defects,^{159–161} which strongly affect the charge carrier transfer at the ZnO/perovskite interfaces. Furthermore, various morphologies (nanowires, nanosheets, nanodisks, and nano-flowers, etc.) of ZnO have been explored to improve the charge carrier collection efficiency at this interface. A simple and cost-effective approach to process the ZnO hole-blocking layer is repeated spin coating of a mixed solution of ethanol and zinc acetate as a precursor with intermediate drying to achieve the desired thickness. Sun *et al.*¹⁶² introduced the solution immersion method for the preparation of one-dimensional (1D) ZnO nanowires as an ETL in PSCs, which resulted in fast charge collection efficiency, leading to improved efficiency compared to that of TiO₂

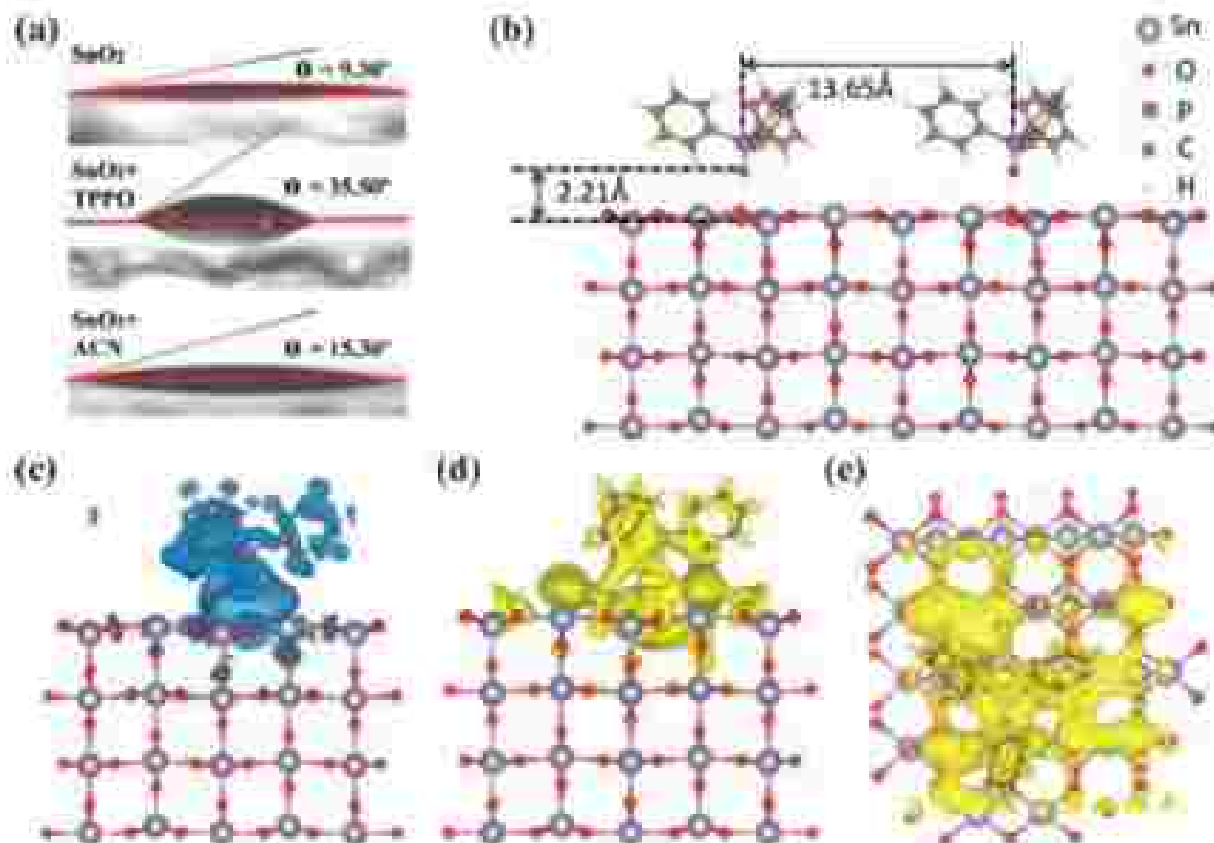


Fig. 11 (a) Surface contact angle of SnO₂, TFPO-coated SnO₂, and acetonitrile treated SnO₂ on ITO substrate; the oxygen atom of TFPO molecule coordinates with Sn atom, leaving other three ends facing upward (differed larger contact angle); (b) 3D ball-and-stick model of TFPO adsorbed SnO₂(110) surface; charge density difference (Δρ) of TFPO on SnO₂(110) surface was calculated at isosurface of 12 × 10⁻³ e|Δρ| Å⁻³; (c) blue indicates electron depletion, and (d) yellow indicates electron accumulation; (e) top view of charge density difference (Δρ) of TFPO adsorbed on SnO₂(110), electron gain is indicated by yellow.¹⁰⁴ Reprinted with permission from *Adv. Mater.*, 2015, **27**, 1805949. Copyright (2015) John Wiley & Sons.

nanowires as the ETL. The single-crystalline 1D ZnO nanowires offered smooth charge transfer across the ZnO/perovskite interface due to the internal electric field along the *c*-axis, i.e., common growth direction for ZnO nanowires and absence of grain boundaries.¹⁰⁸ The compact and uniform planar ZnO films induced delivered relatively high efficiency solar cells.

Tsang *et al.*¹⁰⁸ produced uniform ZnO films using RF sputtering under pure Ar and Ar + O₂ working gas to tune the surface electronic properties, which resulted in downshifting of the band structure, improving the electron injection and rendering an efficiency of ~16% combined with methylammonium lead iodide (i.e., MAPbI₃). However, given that the high-energy ions used during sputtering damage the substrate and deteriorate the ZnO film quality, ALD has been utilized to obtain high-quality ZnO films.¹⁰⁹ The optimized thickness of 10 nm for ALD-grown ZnO films attained a high *V_{oc}* (i.e., 0.97 V), FF (i.e., 40%), and *J_{sc}* (i.e., 14.15 mA cm⁻²) of the PSCs. This study revealed a better exciton dissociation rate at the ZnO/perovskite interface, owing to the enhanced lattice and photo-induced absorption strength. Nevertheless, an increase in thickness beyond 10 nm caused a high series resistance, and the performance of the PSCs decreased. Besides, the spray coating technique was also explored for the mass production of planar ZnO films over a larger

area.¹¹¹ Hydrothermally grown 1D hexagonal ZnO nanowires exhibited high charge conduction due to their sparsely populated conduction band and showed a good agreement between the experimentally measured *J_{sc}* and integrated current density (calculated from the external quantum efficiency).¹⁰²

The two major drawbacks of ZnO ETLs are the severe charge recombination at the ZnO/perovskite interface due to the high density of surface defect states and their poor chemical stability due to the presence of hydroxyl groups and organic residue on the surface of ZnO, which deteriorates cell efficiency. Notably, the presence of volatile organic residue on the surface of ZnO enables the penetration of atmospheric water/oxygen at the ZnO/perovskite interface and degrades the perovskite, leading to the operational instability of PSCs.¹¹² Thus, this has stimulated researchers to investigate other possibilities of ZnO surface control to overcome the interface stability. The chemical behavior of the ZnO surface, which is basic in nature, is responsible for the deprotonation of the methylammonium cation to form methylamine through an acid-base reaction, which causes the perovskite to undergo thermal decomposition even in the absence of hydroxyl groups and residual organic ligand at the ZnO surface.^{113,14} Density functional theory (DFT) calculations for the geometry optimization of the

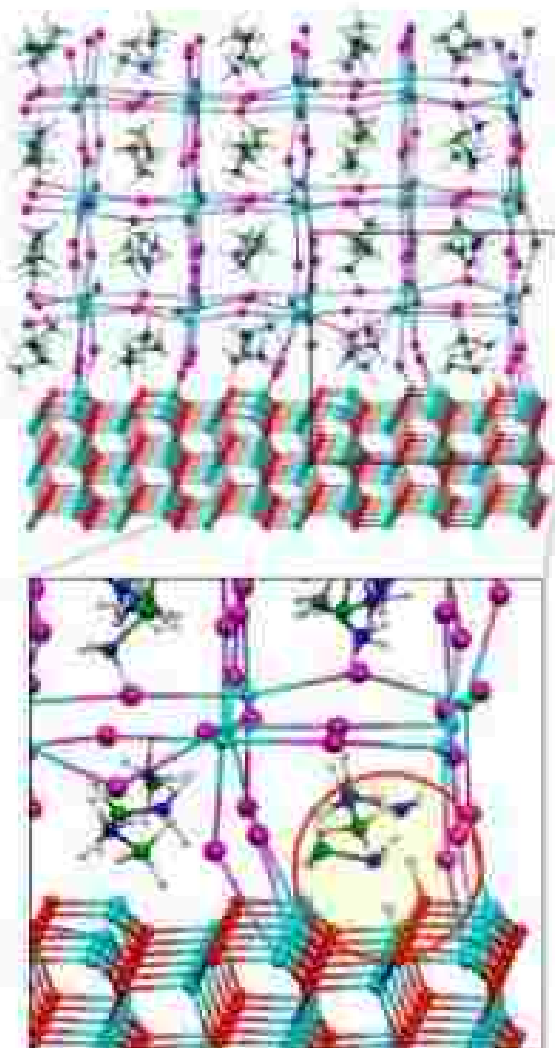


Fig. 14 Crystallographic structure of the ZnO ETLs and CH₃NH₃PbI₃ perovskite (upper panel). The magnified structure of disubstituted methylammonium cations (lower panel) from the portion marked in the upper panel.¹¹⁷ Reprinted with permission from (Chem. Mater., 2010, 22, 4229–4238). Copyright ©2010, the American Chemical Society.

ZnO/perovskite structure revealed that the deprotonation of the methylammonium ion (Fig. 14) is a constructive guide to develop PSCs capable of withstanding harsh temperature conditions.

Moreover, creative strategies such as doping and surface passivation of ZnO have been effectively used in search of its excellent performance as an ETL in PSCs. Both plane and nanostructured ZnO ETLs were doped with elements such as Mg²⁺,^{118–120} Al,^{121–123} Li,¹²⁴ and Sn²⁺ to develop low defect sites, larger surface area, and rapid electron extraction, which are some of the prerequisites for efficient ETLs. Besides, recently, the ZnO surface was modified with methylammonium chloride (MACl),¹²⁵ carbon nanotubes (CNTs),¹²⁶ and ethylenediamine tetraacetic acid (EDTA)¹²⁷ to eliminate the deprotonation ability and enhanced stability of the ZnO/perovskite interface was achieved.

Separately, the most widely studied optoelectronic material, aluminium-doped ZnO (i.e., AZO), has been proposed as an ETL and transparent conducting electrode in PSCs, which also improves the thermal stability by decreasing the Lewis acid–base chemical reaction at the ZnO/perovskite interface.¹²⁸

A monolayer of Cu and Li-doped ZnO on the ETL in a PSC delivered a PCE of 18%, which is comparable to that of the well-accepted TiO₂. This is attributed to the increased electron density due to the decrease in trap density by reducing the oxygen vacancies at the ZnO surface.¹²⁹ The doping of iodine facilitated the dense growth of ZnOx nanoparticles and led to a matching work function between the ETL and perovskite, which resulted in a PCE of around 18%.¹³⁰ The doping of ZnO¹³¹ is a common and effective approach to fine-tune the position of the Fermi level (E_F) and band structure and increase the conductivity to avoid interface charge recombination by achieving an optimized CB edge difference between ZnO and perovskite. Alternatively, the surface passivation strategy helps to enhance the thermal stability during annealing,¹³² improve the morphology of the perovskite layer,¹³³ and reduce the back electron transfer and charge recombination.¹³⁴ ZnO ETLs passivated with thin layers of MgO,¹³⁵ TiO₂,¹³⁶ Zn₂SnO₄,¹³⁷ Nb₂O₅,¹³⁸ SnO₂,¹³⁹ etc. were used to limit the degradation of the perovskite absorber due to the surface defects of ZnO at the perovskite/ZnO interface. The well-optimized passivation of ZnO with TiO₂ using the wet chemical approach of layer-by-layer absorption and reaction (LBLAR) method¹⁴⁰ achieved an efficiency of ~13.2% with better long-term stability compared to unpassivated ZnO nanowires (Fig. 15).¹⁴¹

Overall, the degradation and thermal decomposition of perovskite due to the ZnO surface hinder the long-term stability and outdoor applications of ZnO-based PSC devices. Therefore, more efforts by the broader research community are required to search for novel ways other than passivation that can stop the decomposition of methylammonium and also provide smooth charge transfer across the ZnO/perovskite interface.

3.1.4 Ternary metal oxides. Ternary metal oxides with the perovskite structures of ABO₃ and A₂B₂O₇ are gaining more attention than binary metal oxides, given that they allow better tunability of the bandgap, work function, and conductivity by adjusting the relative ratio of cations.^{142–144} BaSnO₃ (BSO) is a wide bandgap (i.e., 3.2 eV) *n*-type transparent semiconductor with a perovskite structure similar to the photoactive layer. High temperature processed BSO led to reduced charge recombination and charge transfer resistance at the BSO/perovskite interface, delivering PCEs close to 12%.^{145–147} Additionally, one-dimensional BSO nanowires showed better electron conduction subject to direct pathways and less grain boundaries than nanoparticles.¹⁴⁸ Further, to gain atomic insights into the BSO/perovskite interface, first principal DFT calculations were performed by Gao *et al.*,¹⁴⁹ revealing large interface binding energies, favouring robust interface and charge transfer capability, which were shown to further improve with the doping depth of La in BSO. Moreover, theoretical studies also predicted the easy bandgap tuning of BSO by substituting La³⁺ or Sr²⁺ to produce optimal band alignment for improved device

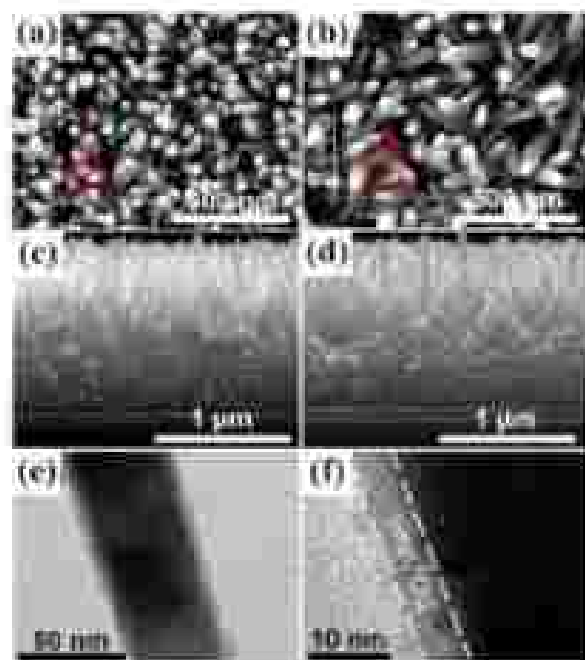


Fig. 15 SEM images of ZnO nanorods (a and c) without and (b and d) with TiO_2 passivation, depicting the top and cross-sectional views, respectively. (e) TEM and (f) HRTEM images of ZnO nanorods with TiO_2 passivation. The yellow dashed line in (f) HRTEM image marks the edge of the ZnO/TiO_2 interface.²²⁶

performance. Likewise, La-doping of TiO_2 via the aqueous colloidal solution route was shown to yield improved electron mobility and optimal bandgap of TiO_2 , which delivered an efficiency close to $\sim 21\%$ from the PSCs fabricated with a single cation lead trihalide. Recently, Zn doping also led to improved interfacial contact and reduced charge recombination at the interface of BSO .²²⁶

SnO_2 , NiO , having high electron mobility and a slightly higher conduction band than TiO_2 , has also been employed as the ETL for PSCs, giving a PCE of 10%.²²⁷ This striking device performance was ascribed to the SnO_2 /perovskite interface with reduced charge recombination due to the high dielectric constant of SnO_2 and formation of a uniform photoactive layer with large crystals on TiO_2 , allowing complete surface coverage.²²⁸ Unfortunately, the high-temperature processing, poor average J_{sc} and inadequately studied SnO_2 /perovskite interface were limitations in the initial stage. However, Neophytou *et al.*²²⁹ achieved a PCE of 19% from low temperature (150 °C)-processed SnO_2 as the ETL, which was attributed to the better optical transparency, reduced interfacial trap state density, improved electron transport, and efficient charge extraction. Despite the long term stability under UV light illumination, the conduction band edge of SnO_2 is unfavourable for the injection of electrons from the perovskite layers. Therefore, tuning of the CB position of SnO_2 by Ni doping, together with the removal of SnO_2 phase segregated on the surface of Ni-doped SnO_2 , was shown to enable fast charge transfer at the interface, which ultimately resulted in the highest PCE of 20.3%.²²⁸ In parallel attempts to use SnO_2 as the ETL of PSCs, a variety of

nanocomposites such as graphene/ TiO_2 ,²³⁰ 2-D self-healing of TiO_2 / SnO_2 nanoparticles,²³¹ and Al_2O_3 , graphene/ SnO_2 ²³² has been employed to achieve the highest PCE of close to 20.5%. Besides, BaTiO_3 (BTO), a ferroelectric material, has also been utilized as the ETL in PSCs owing to its spontaneous polarization, which drives the photo-generation of electrons to improve the transport and charge extraction.²³³ The use of a mesoporous double layer of TiO_2/BTO ²³⁴ and ultrathin layer of BTO to modify the mesoporous TiO_2 /perovskite interface²³⁵ resulted in boosted charge extraction and reduced charge recombination. Also, doped AlO_3 perovskites such as Y-doped SnO_2 ,²³⁶ and La-doped SnO_2 ,²³⁷ have helped to achieve an efficiency close to 19%.

Binary metal oxides besides the AlO_3 /perovskite structure such as Ag_2O , and Ag_2S have been scarcely studied as ETLs in PSCs. Among them, particularly, Zn_2SnO_4 (ZSO) is an up-and-coming alternative to TiO_2 in PSCs due to its comparable conduction band edge, higher electron mobility, much faster charge injection, and high electron diffusion efficiency, as observed by time and frequency-resolved spectroscopy.²³⁸ Moreover, it provides negligible hysteresis and extraordinary stability with acid/base and polar molecules, and also enhances the crystallization of the perovskite layer. Its refractive index close to TiO_2 permits high transmittance in the visible range. Furthermore, the use of ZSO as an ETL instead of SnO_2 plays a dual role by improving the crystallization of the perovskite without antisolvent treatment and providing increased stability without encapsulation.²³⁹ Also, the use of ZSO/ZnO and $\text{ZSO}/\text{Al}_2\text{O}_3$ nanocomposites as ETLs has resulted in better transmittance, electrical conductivity, and charge collection efficiency.^{238,237} Amorphous ZSO films with extreme surface uniformity delivered an efficiency close to 20% in the presence of the PAMAPM, perovskite light absorber.²⁴⁰ In an attempt to overcome the differences in charge diffusion lengths between the perovskite and transport layers, a bulk heterojunction (BHJ) of a composite of ZSO nanoparticles and perovskite was also explored as the photoactive layer (Fig. 16). The enhanced charge collection efficiency, improved morphology of the perovskite layer with large crystal size, balanced charge carrier mobility, and reduced trap density of BHJ films helped to achieve an efficiency close to 21%.²⁴¹ Finally, a mesoporous layer of the Zn_2SnO_4 /perovskite structure was employed as an ETL in a PSC, resulting in a PCE of 17.3%.²³⁸

4.1.5. Scaffolding technique. The scaffolding technique has attracted attention due to its ability to exploit the long charge diffusion length of the perovskite light absorbers. The dielectric scaffolds offer a higher level of conduction band edge than the perovskite absorbers and prohibit the reverse electron transport from the perovskite, increasing the V_{oc} of PSCs.^{238,237} Moreover, the implementation of insulating scaffold is possible due to the long range balanced electron and hole diffusion lengths of organic-inorganic perovskites. A mesoporous metal-oxide scaffold contributed to the electron-hole diffusion length of $\sim 1 \mu\text{m}$ in a mixed halide ($\text{CH}_3\text{NH}_3\text{PbI}_{2-x}\text{Cl}_x$) and $\sim 100 \text{ nm}$ in triiodide ($\text{CH}_3\text{NH}_3\text{PbI}_3$) perovskite absorbers.²²² Lee *et al.*²⁴² demonstrated the use of a mesostructured

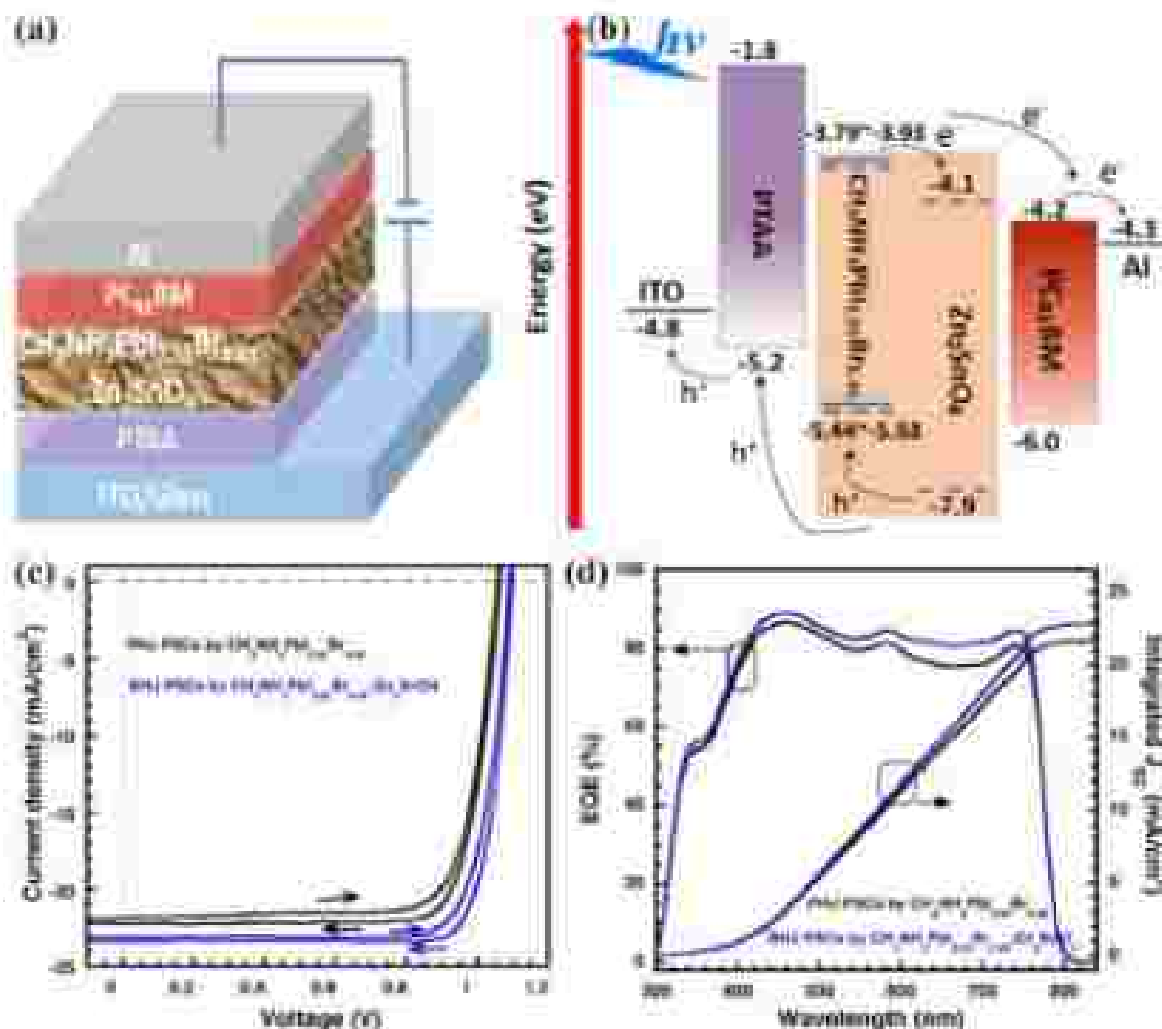


Fig. 18 Schematic of (a) device structure and (b) band diagram of bulk heterojunction (BHJ) PSCs. (c) J - V characteristics and (d) EQE spectra with integrated J_{sc} of planar heterojunction (PHJ) and BHJ PSCs, respectively. Reprinted with permission from *ACS Appl. Mater. Interfaces*, 2015, 7, 24070–24079. Copyright (2015) the American Chemical Society.

insulating scaffold to enhance the light absorption and photon management. The amnity of perovskite absorbers over the nanostructured scaffold forced the electrons to reside in and be transported through the perovskite, thereby being effective in providing a better PCE. The balance between series and shunt resistances was obtained by a thicker capping layer of less conductive spiro-OMeTAD (i.e., $\sim 10^{-3}$ S cm $^{-1}$). The self-connected percolating network of scaffold with a larger surface area infiltrated the perovskite and allowed better charge transport. In these scaffolds, the photo-generated electrons flow through the perovskite absorbers to the front electrodes rather than injecting into the oxide layer, and the holes inject into the organic hole conductor to flow through the back contact.

Hell et al.²²² systematically explored the effect of inorganic scaffolds on the performance of PSCs, which efficiently absorb light, generate charges, and transport electrons/holes with little recombination losses. This approach eliminates the use of discrete hole and electron transport media in interpenetrating composites by introducing an ambipolar material for the

conversion of absorbed photons into collected charges and transport of both electrons and holes. A porous Al $_2$ O $_3$ scaffold placed between TiO $_2$ and the perovskite absorber supported the charge separation and transport to deliver a PCE of 13.3%. Moreover, the ultraviolet light instability of TiO $_2$, due to the surface oxygen vacancies promoting the degradation of perovskite absorbers, was countered by introducing a mesostructured inert Al $_2$ O $_3$ scaffold in an organometal trihalide (PbI $_2$) to form a p-i-n heterojunction with spiro-OMeTAD HTL.²²²

For the efficient transfer of photo-generated electrons by the inorganic scaffolds, the infiltration of perovskites deep inside the scaffold is an important issue to be investigated. Hwang et al.²²³ controlled the size of meso-dispersed SiO $_2$ nanoparticles and observed an excellent performance at the diameter of 20 nm due to the optimized diameter size of the perovskites and strong optical absorption. The fragmentary infiltration of perovskites in the scaffold with a particle diameter <50 nm restricted the transport of electrons, whereas the needle-like growth of the perovskite grains over the particles with a size of >50 nm

Decreased the absorption of light due to the complex scattering behaviour, thereby impeding the performance of PSCs. However, the inclusion of SiO_2 nanoparticles in the matrix of TiO_2 formed a mesoporous composite scaffold, which led to an increase in photocurrent by affecting the optical properties of the mesoporous scaffold and altering the ion migration at the perovskite interface, providing a beneficial effect to render a PCE of 16.7%.²²² Zhou *et al.*²²³ replaced the Al_2O_3 scaffold with a hydroscopic polyethylene glycol (PEG) scaffold to control the PSC performance in a highly humid environment. Even though the hydroscopic PEG absorbs H_2O and presents the evolution of PbI_2 (i.e., degradation of perovskite) by forming a compact moisture barrier in the vicinity of the perovskite grain, the PCE did not exceed 15.4% for unknown reasons. Further, scaffold and transport layer combinations have been made to enhance the charge transport synergistically and suppress the charge recombination at the perovskite/transport layer interface. In these combinations of scaffolds, the ratio of scaffold to transport layer nanoparticles is controlled to optimize the transport processes.²²⁴ The TiO_2 ETL quickly transfers the electrons through a wide interface with the perovskite, but the insulating Al_2O_3 scaffold directs the electrons to transport entirely through the perovskite. Nevertheless, the heterogeneous combination of Al_2O_3 and TiO_2 directs the electrons to take easy pathways either through the ETL or the perovskite (Fig. 17) and render a good PCE by engineering the difference in charge carrier balance and ion migration. Moreover, a bilayer mesoporous scaffold of TiO_2 and Al_2O_3 was shown to enhance the

air-stability of ambient-processed PSCs with a PCE of 16.34%.²²⁵ The inclusion of the Al_2O_3 scaffold not only protected the infiltrated perovskite from degradation due to moisture attack but also offered stable light transmission, ensuring an adequate yield of photo-generated charge carriers, and mitigated the charge transportation property deterioration.

Keen *et al.*²²⁶ introduced parallelised nanogillar PSCs using anodised alumina oxide (AAO) as a scaffold. The AAO scaffold provided control over spatial distribution, relative volume fraction, and visible range transparency of the perovskite absorber. The vertically aligned perovskite pillars terminated the short currents and modulated the visible transmittance due to the vertical electronic transport and modulated the parasitic scattering because of the uneven deposition of the perovskite. The incorporation of an MoO_3 buffer layer and TiO_2 ETL together with the AAO scaffold controlled the ion migration at the perovskite interface and delivered a PCE of 21.6%.

Recently, Xu *et al.*²²⁷ introduced slot-dye coating for the mass production of PSCs consisting of a TiO_2 ETL and ZnO_2 scaffolds. Even though the infiltration mechanism in the scaffold was discussed based on the Lucas-Washburn model, further understanding of the coating parameters and their effect on the charge transport at the interface is recommended for the mass production of the PSCs. Qahary *et al.*²²⁸ explored an Al_2O_3 scaffold with Li-doped SnO_2 ETL to achieve an enhanced PCE. The Li-doped ETL and scaffold inhibited the charge recombination and prolonged the electron lifetime, but the PCE was restricted to 10.1% due to the unfavourable participation of the grain boundaries and bulk of the materials in the charge transfer process.

Overall, SiO_2 ,²²² Al_2O_3 ,²²³ AAO and ZnO_2 ²²⁷ scaffolds have been explored for the better infiltration of perovskites to gain high PCEs, but most of them delivered efficiencies in the range of 10% to 16%. Furthermore, they do not eliminate the need for a compact hole-blocking layer or ETL to fabricate efficient PSCs. The thickness, roughness, and porosity of the scaffolds need to be considered for controlling the charge transport, diffusion coefficient, and collection efficiency of PSCs.

3.1.4. Other inorganic ETLs. In addition to the well studied binary metal oxides such as TiO_2 , ZnO , and SnO_2 , many other metal oxides such as WO_3 ,²²⁹ CeO_2 ,²³⁰ In_2O_3 ,²³¹ Nb_2O_5 ,²³² and Fe_2O_3 ²³³ have been explored as ETLs for PSCs. Cerium oxide (CeO_2) offers several benefits including wide bandgap (i.e., 3.3 eV), high dielectric constant ($\epsilon = 26$),²³⁴ sufficient optical transparency (refractive index of 2.1–2.7),²³⁵ good ionic conductivity ($\sigma = 120 \text{ S cm}^{-1} \text{ K}^{-1}$),²³⁶ high thermal and chemical stability, ease of processing, low cost, and earth abundance, thereby qualifying as a highly promising ETL material.^{232–236}

The low temperature processing of CeO_2 ($\alpha = 181^\circ\text{C}$ at 100°C) with an inverted architecture and CeO_2 ($\alpha = 187^\circ\text{C}$ at 150°C) with a planar device architecture resulted in PCEs of 10.1% and 17.4%, respectively.^{232,233} Recently, lower temperature processed CeO_2 (at 80°C) as an ETL was shown to help realize a PCE of 18.6%.²³⁷ The dense CeO_2 layers not only protect the perovskite absorber from moisture but also act as a diffusion barrier to prevent corrosion.²³⁸ Additionally, CeO_2 nanocrystals

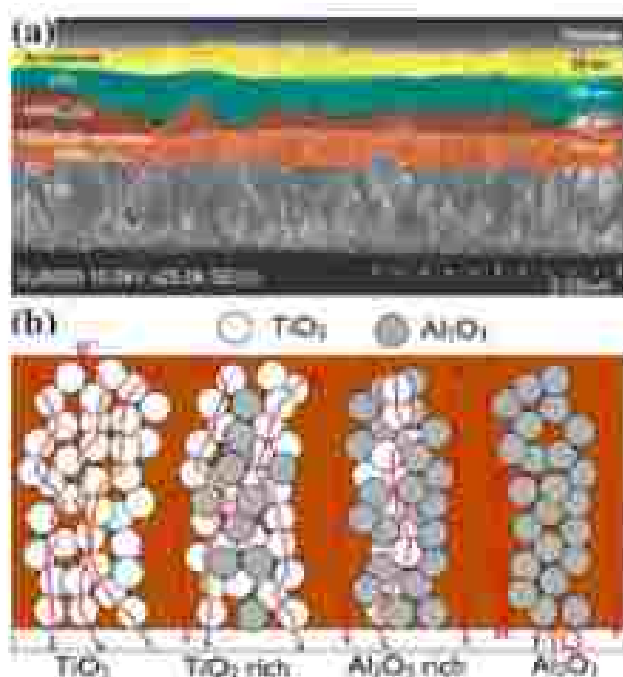


Fig. 17 (a) Scenic structure composed of mesoporous Al_2O_3 scaffold TiO_2 ETL and TPSC. (b) Schematic diagram of the charge transport mechanism. ²²³ Reproduced with permission from ACS Appl Mater Interfaces 2016, 8, 4408–4413. Copyright (2016) by the American Chemical Society.

were utilized as a double ETL with PCBM^{194–196} and ZnO¹⁹⁶ to achieve the best efficiency values of 17.3% and 19.5%, respectively. The improvement in PCE with double ETLs was possible due to the decreased series resistance for charge extraction.¹⁹⁶ CaO, when introduced with regular ETLs (ZnO), reduces the work function of the electron transport material (i.e., ETL) and eliminates the interfacial barrier. The rich discrete energy levels of CaO, also prevent the UV-induced degradation of the perovskite absorber.¹⁹⁴

Tungsten oxide (WO₃) is another crucial ETL possessing excellent chemical stability, wide bandgap [2 to 3 eV]^{197–201} and high electron mobility (10 to 20 cm² V⁻¹ s⁻¹).²⁰² Mahmood *et al.*²⁰¹ explored 0D, 1D, and 2D nanostructures of WO₃ as ETLs for PSCs. The 2D WO₃ nanosheets offered good perovskite infiltration and fast carrier charge dynamics, thereby performing well compared to the nanoparticle and nanorod morphologies. However, they suffered from recombination losses at the WO₃/perovskite interface, which had to be controlled by forming WO₃/TiO₂ core-shell structures. Amorphous WO₃ offered control over the conductivity and short circuit current, leading to an improved PCE (~13%) at the cost of lower transmittance (80% of TiO₂) and V_{oc} due to the inherent charge recombination.^{201,203} Conversely, a WO₃ film introduced with TiO₂ as a bilayer ETL served as an antireflection coating, rendering an enhanced J_{sc} ²⁰⁴ and improved non-viability, which led to better crystallization of the CH₃NH₃PbI₃ perovskite and resulted in a PCE of ~20%.²⁰⁵ The high-temperature processing of amorphous WO₃ incorporates defects, and subsequently deteriorates the performance of PSCs. On the contrary, ultra-low temperature (<50 °C) processing scales down the trap densities and offers high electron mobility, thereby yielding an efficiency of ~20%.²⁰⁶

The higher built-in potential achieved by the α -Fe₂O₃ ETL/perovskite interface led to more efficient charge extraction/transport, reduced charge accumulation, and less charge recombination than TiO₂ ETLs.²⁰⁷ The solution-processed Ni-doped (4%) α -Fe₂O₃ yielded an efficiency of ~13% with the CH₃NH₃PbI₃ perovskite owing to its enhanced electrical conductivity and lowered conduction band minimum, and also exhibited good stability upon exposure to ambient air and high-level UV irradiation.²⁰⁷ The effective approach of doping non-equilibrium Ti⁴⁺ in the lattice of Fe₂O₃ via the quenching process reduced the surficial oxygen vacancies and structural defects, which act as deep trap states. These states are responsible for the sluggish electron charge transfer and accumulation of charges at the ETL/perovskite interface, delivering a PCE of 17.6%.²⁰⁸ The quenching approach assisted with a uniform doping distribution and increased doping density in the bulk lattice of Fe₂O₃, by suppressing the segregation of TiO₂ on the surface (Fig. 10(a)). Likewise, 1D core-shell nanostructures were utilized to mitigate the absorber instability and increase the mobility and recombination resistance. The core-shell structures of ZnO/NiO,²⁰⁹ Al₂O₃/TiO₂,²¹⁰ WO₃/TiO₂,²¹¹ TiO₂/MgO,²¹² *etc.* have been explored to gain efficient electron injection and enhancing the recombination resistance at the ETL/perovskite interface. A thin MgO layer (large bandgap of ~3 eV) coating over

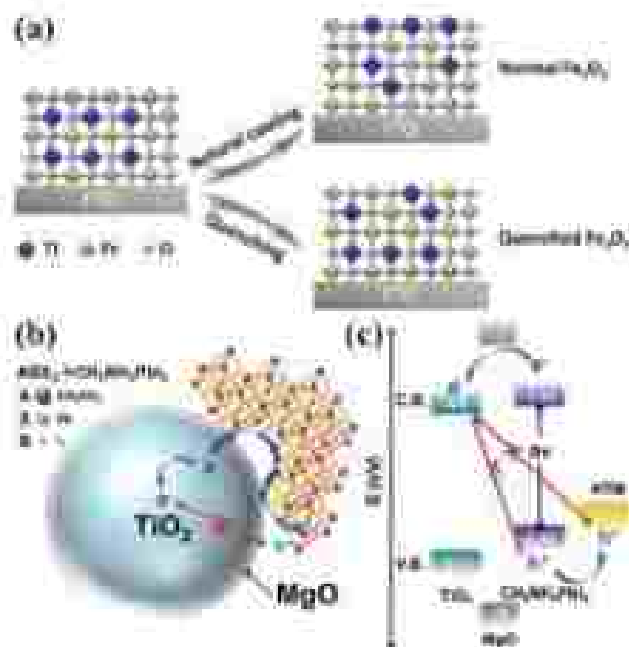


Fig. 10 Schematic representation of (a) structures for increased doping density in the bulk and suppressed segregation on the surface of Ti-Fe₂O₃,²⁰⁸ (b) charge transfer mechanism, and (c) band energy diagram of the MgO/TiO₂ core-shell nanoparticles based PSC.²⁰⁸

mesoporous TiO₂ particles increased the recombination resistance through an effective charge transfer mechanism (Fig. 10(b) and (c)), leading to a better V_{oc} and FF (i.e., 0.80 V and 67.1%) than that of the pristine TiO₂ (i.e., 0.85 V and 71.2%), respectively.

Moreover, the well-optimized In₂O₃, which satisfies the properties required for excellent ETLs such as wide bandgap (i.e., 3.8 eV), high electron mobility ($\mu = 10$ cm² V⁻¹ s⁻¹),²⁰⁴ high transparency, antireflection property, and thermal stability, offer efficient electron extraction and charge transfer, producing a stable efficiency of ~14% for 31 days when In³⁺ was stabilized by inhibiting hydrolysis using acrylamide.²⁰⁹ The PCE was further improved (i.e., up to 18.13%) by modifying the In₂O₃/perovskite interface with a PCBM interlayer.²¹⁰ The doping with Ce,²¹¹ Zr,²¹² and Sn²¹³ resulted in higher electron mobility and lower parasitic absorption in the NIR range than that of pristine In₂O₃, and resulted in a PCE of above 20%. Alternatively, Nb₂O₅ is a visibly transparent, air-stable, and water-insoluble material with extensive polymorphism, and its bandgap can be tuned by controlling the stoichiometry and crystallinity.^{214–217} Kaya *et al.*²¹⁸ first introduced Nb₂O₅ as an effective ETL with mesoporous Al₂O₃ perovskite-based PSCs and observed a higher V_{oc} (1.13 V) than that with TiO₂. However, the room-temperature processed amorphous Nb₂O₅ rendered a PCE of 17% and replaced the crystalline Nb₂O₅ as an ETL in flexible PSCs.²¹⁹ However, the direct *c*-beam-irradiated²²⁰ and spin-coated²²¹ pristine Nb₂O₅ were shown to offer smooth charge transfer by reducing the charge resistance and recombination at the interface, producing an efficiency of ~10%. Moreover, 5% Zn doping further assisted in faster charge extraction and reduced charge recombination at the Nb₂O₅ ETL/perovskite

interface.²⁰¹ The Nb_2O_5 , perovskite over-TiO₂ and ZnO was shown to improve the crystallinity of the perovskite overlayer, and thereby the stability of PSCs.^{163,162} Low-temperature processed CaSe ,²⁰² CaS ,²⁰³ and Bi_2S_3 nanocrystals are also appealing in the foregoing context due to their corresponding smaller interfacial barrier with suppressed charge trapping and smooth charge transfer without accumulation at the interface.²⁰⁴ Besides the above-mentioned developments to enhance the capabilities of inorganic ETLs, plasmonic nanoparticles [such as Au and Ag cores] have also been incorporated in inorganic ETLs to enhance their light absorption even further and reduce the exciton binding energy.^{14,163,162}

Even though several inorganic materials have been demonstrated as alternatives to the most common inorganic ETLs (i.e., TiO₂, ZnO, and SnO₂), various combinations of earth-abundant constituent elements in terms of doping, composites, core-shell structures, etc. need to be explored for controlled interfacial reactions, defining a higher PCE. Additionally, theoretical work on new inorganic ETL materials is essential to understand the electronic and structural properties of the interface, leading the way for a targeted experimental approach.

6.2. Organic ETLs

Organic n-type semiconductors are promising alternatives to metal-oxide-based ETLs due to their good thermodynamical stability, low-temperature processability, LUMO level matching with the conduction band of the perovskite, etc.^{128–130} Additionally, organic ETLs can mend the surface defects by coordination with lead ions and reduce the charge-trap related recombination at the ETL/perovskite interface.²⁰⁵ In contrast, low-temperature processed inorganic ETLs either require high-cost techniques or provide nonuniform film coverage.⁶⁶ Therefore, various researchers have replaced inorganic ETLs with organic counterparts to address these problems. Particularly, fullerenes and its derivatives, with excellent electron mobility and ability to passivate the trap state on the surface of the perovskite layer, have shown the promising possibility of utilization as ETMs.²⁰⁶

A [6,6]-phenyl- C_{60} -butyric acid methyl ester (PCBM) derivative of fullerene, a well-studied compound in organic solar cells, has been used in low-temperature-processed PSCs as an ETL, which efficiently blocks the holes at the perovskite/PCBM interface because of the higher VB of the perovskite than the HOMO level for PCBM, resulting in a PCE of ~12%.¹⁹⁷ Furthermore, graphene quantum dot/PCBM nano-composites²⁰⁷ was shown to improve the electrical conductivity compared to pristine PCBM. A blend of polystyrene/PCBM²⁰⁸ was shown to yield smooth films together with a uniform layer of organic ETL, which helped to enhance the charge collection. Moreover, a blend of organic and inorganic ETLs was also explored to govern the morphology and control the stability of the perovskite absorber and improve the device performance. Zeng et al.²⁰⁴ achieved a PCE of ~14% from a composite of CaSe quantum dots with PCBM as the ETL, increasing the built-in potential at the perovskite/ETL interface, which facilitated efficient electron-hole pair separation and enhancement of the photocurrent.

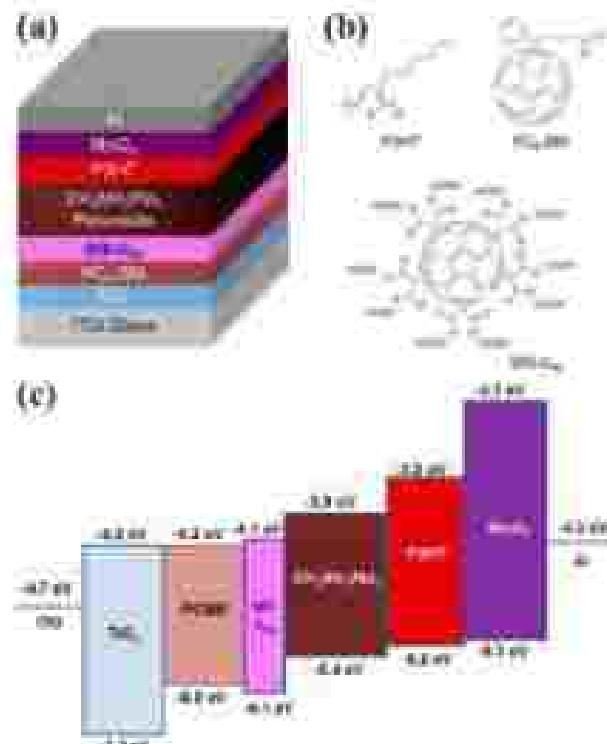


Fig. 19 (a) The device assembly of perovskite hybrid solar cells incorporating with PC₆₀BM the electron extraction layer. (b) Molecular structures of PC₆₀BM, water-soluble fullerene derivatives PC₇₀BM and PC₈₀BM. (c) LUMO and HOMO energy levels of the materials used in the perovskite hybrid solar cells.²⁰⁴ Reprinted with permission from *Prog Appl Mater Interface*, 2015, 7, 1221–1236. Copyright (2015) American Chemical Society.

Liu et al.¹⁹² explored thin films of organic PC₆₀BM over inorganic TiO₂ coupled with CaSe as the ETL and observed efficient charge extraction at the ETL/perovskite interface (Fig. 10).

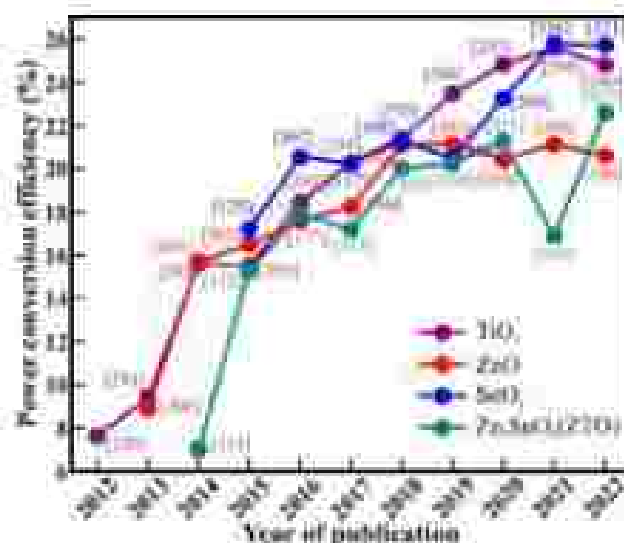


Fig. 20 Comparative study of the efficiency of ETLs developed by year to gain the best maximum efficiency in the list records (extracted from *ED Web of Knowledge* up to 10th August 2022).^{199,209,210,211,212,213,214,215,216,217,218,219,220,221,222,223,224,225,226,227,228,229,230,231,232,233,234,235,236,237,238,239,240,241,242,243,244,245,246,247,248,249,250,251,252,253,254,255,256,257,258,259,260,261,262,263,264,265,266,267,268,269,270,271,272,273,274,275,276,277,278,279,280,281,282,283,284,285,286,287,288,289,290,291,292,293,294,295,296,297,298,299,300,301,302,303,304,305,306,307,308,309,310,311,312,313,314,315,316,317,318,319,320,321,322,323,324,325,326,327,328,329,330,331,332,333,334,335,336,337,338,339,340,341,342,343,344,345,346,347,348,349,350,351,352,353,354,355,356,357,358,359,360,361,362,363,364,365,366,367,368,369,370,371,372,373,374,375,376,377,378,379,380,381,382,383,384,385,386,387,388,389,390,391,392,393,394,395,396,397,398,399,400,401,402,403,404,405,406,407,408,409,410,411,412,413,414,415,416,417,418,419,420,421,422,423,424,425,426,427,428,429,430,431,432,433,434,435,436,437,438,439,440,441,442,443,444,445,446,447,448,449,450,451,452,453,454,455,456,457,458,459,460,461,462,463,464,465,466,467,468,469,470,471,472,473,474,475,476,477,478,479,480,481,482,483,484,485,486,487,488,489,490,491,492,493,494,495,496,497,498,499,500,501,502,503,504,505,506,507,508,509,510,511,512,513,514,515,516,517,518,519,520,521,522,523,524,525,526,527,528,529,530,531,532,533,534,535,536,537,538,539,540,541,542,543,544,545,546,547,548,549,550,551,552,553,554,555,556,557,558,559,560,561,562,563,564,565,566,567,568,569,570,571,572,573,574,575,576,577,578,579,580,581,582,583,584,585,586,587,588,589,590,591,592,593,594,595,596,597,598,599,600,601,602,603,604,605,606,607,608,609,610,611,612,613,614,615,616,617,618,619,620,621,622,623,624,625,626,627,628,629,630,631,632,633,634,635,636,637,638,639,640,641,642,643,644,645,646,647,648,649,650,651,652,653,654,655,656,657,658,659,660,661,662,663,664,665,666,667,668,669,670,671,672,673,674,675,676,677,678,679,680,681,682,683,684,685,686,687,688,689,690,691,692,693,694,695,696,697,698,699,700,701,702,703,704,705,706,707,708,709,710,711,712,713,714,715,716,717,718,719,720,721,722,723,724,725,726,727,728,729,730,731,732,733,734,735,736,737,738,739,740,741,742,743,744,745,746,747,748,749,750,751,752,753,754,755,756,757,758,759,760,761,762,763,764,765,766,767,768,769,770,771,772,773,774,775,776,777,778,779,780,781,782,783,784,785,786,787,788,789,790,791,792,793,794,795,796,797,798,799,800,801,802,803,804,805,806,807,808,809,810,811,812,813,814,815,816,817,818,819,820,821,822,823,824,825,826,827,828,829,830,831,832,833,834,835,836,837,838,839,840,841,842,843,844,845,846,847,848,849,850,851,852,853,854,855,856,857,858,859,860,861,862,863,864,865,866,867,868,869,870,871,872,873,874,875,876,877,878,879,880,881,882,883,884,885,886,887,888,889,890,891,892,893,894,895,896,897,898,899,900,901,902,903,904,905,906,907,908,909,910,911,912,913,914,915,916,917,918,919,920,921,922,923,924,925,926,927,928,929,930,931,932,933,934,935,936,937,938,939,940,941,942,943,944,945,946,947,948,949,950,951,952,953,954,955,956,957,958,959,960,961,962,963,964,965,966,967,968,969,970,971,972,973,974,975,976,977,978,979,980,981,982,983,984,985,986,987,988,989,990,991,992,993,994,995,996,997,998,999,1000}

Table 1 A brief summary of isopropyl-TRiZ processed with various synthesis methods and their corresponding device performance parameters

S. no.	Device configuration	Material P	V_{oc} (V)	J_{sc} (mA cm ⁻²)	FF	PCE (%)	Year	Ref.
Thiophene based (TiO₂)								
1.	FTO/ITO/TiO ₂ /PA _{0.5} MA _{1.5} /TiO ₂ /C ₆₀ /spiro-OMeTAD/Ag	C60	1.174	25.43	0.691	24.01	2022	299
2.	FTO/SC(12%)/CH ₃ NH ₂ /TiO ₂ /spiro-OMeTAD/Ag	DC	1.11	23.14	0.667	20.75	2022	310
3.	FTO/FTO ₂ /TiO ₂ /C ₆₀ /PA _{0.5} MA _{1.5} /TiO ₂ /C ₆₀ /spiro-OMeTAD/Ag	SPM	1.094	22.94	0.701	20.40	2022	311
4.	FTO/TiO ₂ /TiO ₂ /NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC/MW	1.07	22.18	0.71	17.67	2022	320
5.	FTO/TiO ₂ /TiO ₂ /TiO ₂ /FAH ₂ /AMQ/spiro-OMeTAD/Ag	SP	1.109	22.20	0.617	22.8	2021	298
6.	FTO/TiO ₂ /TiO ₂ /TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	1.171	24.17	0.623	21.28	2021	118
7.	FTO/TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	Ag	1.06	22.92	0.71	18.05	2021	98
8.	FTO/TiO ₂ /spiro-OMeTAD/Ag	FTZS	1.16	24.24	0.688	22.99	2020	321
9.	FTO/Ni ₂ -TiO ₂ /PA _{0.5} MA _{1.5} /TiO ₂ /C ₆₀ /spiro-OMeTAD/Ag	SC	1.11	24.7	0.78	21.1	2020	322
10.	FTO/TiO ₂ /TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	HT	1.11	23.42	0.74	19.24	2020	323
11.	FTO/Ni ₂ -TiO ₂ /Ni ₂ S ₂ /TiO ₂ /MA _{1.5} PA _{0.5} /TiO ₂ /C ₆₀ /spiro-OMeTAD/Ag	SCS	1.28	23.15	0.707	23.33	2019	324
12.	FTO/TiO ₂ /C ₆₀ PA _{0.5} MA _{1.5} /spiro-OMeTAD/Ag	SC	1.05	24.94	0.72	18.81	2019	325
13.	FTO/TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	HP	1.04	23.55	0.75	18.22	2019	306
14.	FTO/TiO ₂ /TiO ₂ /Ni ₂ S ₂ /TiO ₂ /MA _{1.5} PA _{0.5} /TiO ₂ /C ₆₀ /spiro-OMeTAD/Ag	HT	1.025	22.91	0.71	17.2	2019	326
15.	FTO/TiO ₂ /spiro-OMeTAD/Ag	SC	1.09	22.91	0.70	21.1	2019	295
16.	FTO/NiO ₂ /TiO ₂ /NiO ₂ /NH ₂ PA _{0.5} spiro-OMeTAD/Ag	HT	1.01	22.95	0.77	18.08	2019	116
17.	FTO/TiO ₂ /TiO ₂ /PC ₆₁ BH ₂ Cl/PA _{0.5} spiro-OMeTAD/Ag	SC	1.10	23.11	0.662	20.1	2017	294
18.	FTO/TiO ₂ /PA _{0.5} MA _{1.5} spiro-OMeTAD/Ag	SC	1.075	22.38	0.769	18.42	2016	293
19.	FTO/TiO ₂ /TiO ₂ /PC ₆₁ BH ₂ Cl/PA _{0.5} spiro-OMeTAD/Ag	C60	0.985	22.8	0.72	15.71	2016	327
20.	FTO/TiO ₂ /TiO ₂ /NiO ₂ /NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	0.98	24.9	0.74	15.7	2015	302
21.	FTO/TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	Ag	0.979	24.3	0.723	13.08	2015	328
22.	FTO/graphene/TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	1.05	22.9	0.71	15.8	2011	29
23.	FTO/TiO ₂ /TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	YO	1.09	21.97	0.68	13.07	2011	84
24.	FTO/TiO ₂ /Ni ₂ S ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	0.933	11.6	0.62	7.1	2011	291
25.	FTO/TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	0.88	17.8	0.52	7.8	2011	329
Dye-sensitized (DSSC)								
26.	FTO/SnO ₂ /TA _{0.5} PA _{0.5} MA _{1.5} PA _{0.5} spiro-OMeTAD/Ag	SC	1.10	22.9	0.775	20.6	2021	309
27.	FTO/Ag ₂ O/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/TPSC/TPSA	Ag	1.05	23.18	0.74	18.09	2021	329
28.	FTO/Ag ₂ O/Ag ₂ O/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/TPSC/TPSA	ES	0.823	25.06	0.65	11.92	2021	328
29.	FTO/Ag ₂ O/Ag ₂ O/TPSC/TPSA/Ag ₂ O/PA _{0.5} MA _{1.5} spiro-OMeTAD/Ag	SC	1.14	22.88	0.707	21.15	2021	305
30.	FTO/Ag ₂ O/TPSC/TPSA/spiro-OMeTAD/Ag	HT	1.13	24.89	0.77	20.8	2021	304
31.	FTO/Ag ₂ O/Ag ₂ O/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	1.12	21.94	0.75	18.84	2020	322
32.	FTO/Ag ₂ O/Ag ₂ O/PA _{0.5} MA _{1.5} spiro-OMeTAD/Ag	SC/TPSC	1.15	23.42	0.781	21.01	2019	303
33.	FTO/Ag ₂ O/Ag ₂ O/CA ₂ TiO ₂ (C ₆₀ PMMA)/TiO ₂ /spiro-OMeTAD/Ag	SC	1.12	23.26	0.789	21.08	2019	62
34.	FTO/Ag ₂ O/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SCS	1.13	23.8	0.771	19.99	2018	311
35.	FTO/Ag ₂ O/TPSC/TPSA/PA _{0.5} spiro-OMeTAD/Ag	HT	1.13	22.42	0.719	18.24	2017	180
36.	FTO/Ag ₂ O/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	HTS	1.07	21.3	0.733	17.8	2016	177
37.	FTO/Ag ₂ O/TPSC/TPSA/PA _{0.5} spiro-OMeTAD/Ag	SC	1.07	20.9	0.745	16.3	2016	175
38.	FTO/TPSC/TPSA/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SP	1.10	19.7	0.75	15.8	2016	314
39.	FTO/TPSC/TPSA/TPSC/TPSA/Ag ₂ O/PA _{0.5} spiro-OMeTAD/Ag	Ag	1.02	20.73	0.764	16.2	2015	302
40.	FTO/Ag ₂ O/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	1.01	20.1	0.746	15.7	2014	301
41.	FTO/Ag ₂ O/TPSC/TPSA/PA _{0.5} spiro-OMeTAD/Ag	HT	0.991	20.08	0.76	14.13	2014	167
42.	FTO/Ag ₂ O/TPSC/TPSA/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	HT	0.991	20.08	0.76	14.13	2014	167
43.	FTO/Ag ₂ O/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	C60	1.02	16.98	0.611	8.5	2013	300
TiO₂ based (TiO₂)								
44.	FTO/TiO ₂ /PA _{0.5} QD/PA _{0.5} MA _{1.5} PA _{0.5} spiro-OMeTAD/Ag	SC	1.174	24.09	0.634	23.72	2022	313
45.	FTO/SnO ₂ /PA _{0.5} TPSC/PA _{0.5} MA _{1.5} PA _{0.5} spiro-OMeTAD/Ag	SC	1.149	23.16	0.611	21.25	2022	309
46.	FTO/TiO ₂ /TiO ₂ /PA _{0.5} MA _{1.5} spiro-OMeTAD/TPSC/TPSA	SC	1.15	24.20	0.762	21.71	2022	306
47.	FTO/Ag ₂ O/PA _{0.5} MA _{1.5} spiro-OMeTAD/TPSC/TPSA	SC/DC	1.07	24.25	0.75	18.94	2022	317
48.	FTO/Ag ₂ O/TPSC/TPSA/TPSC/TPSA/spiro-OMeTAD/Ag	SC	1.109	25.74	0.622	21.8	2021	310
49.	FTO/SnO ₂ /MA _{1.5} PA _{0.5} PC ₆₁ BH ₂ Cl/PA _{0.5} spiro-OMeTAD/Ag	C60	1.109	25.14	0.648	22.2	2021	319
50.	FTO/SnO ₂ /Ag ₂ O/TPSC/PA _{0.5} MA _{1.5} PA _{0.5} spiro-OMeTAD/TPSC/TPSA	SC	1.2	22.89	0.771	21.18	2021	318
51.	FTO/SnO ₂ /Ag ₂ O/TPSC/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	HT/DC	1.12	22.46	0.78	20.78	2021	153
52.	FTO/SnO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	1.14	22.38	0.76	20.24	2021	311
53.	FTO/SnO ₂ /TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	1.12	22.51	0.76	20.24	2021	152
54.	FTO/SnO ₂ /Ag ₂ O/TPSC/CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	SC	1.08	22.94	0.75	18.23	2021	188
55.	FTO/SnO ₂ /TiO ₂ /Ag ₂ O/TPSC/TPSA/spiro-OMeTAD/Ag	SC	1.18	19.79	0.79	19.26	2021	140
56.	FTO/SnO ₂ /TiO ₂ /CH ₃ NH ₂ PA _{0.5} spiro-OMeTAD/Ag	C60	1.13	22.01	0.78	20.14	2021	344
57.	FTO/SnO ₂ /TiO ₂ /Ag ₂ O/TPSC/TPSA/TPSA/spiro-OMeTAD/Ag	HT	1.13	22.45	0.78	21.25	2020	340
58.	FTO/SnO ₂ /Ag ₂ O/TPSC/TPSA/TPSA/TPSA/spiro-OMeTAD/Ag	SC	1.15	22.85	0.78	20.41	2020	324

Table 1 (continued)

C. no.	Device configuration	Method ^a	V _{on} (V)	I _{on} (mA cm ⁻²)	FF (%)	PCE (%)	Year	Ref.
59	FTO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.12	15.26	6.90	20.33	2020	188
60	FTO/SnO ₂ /MgO/CH ₃ COONH ₄ /spiro-OMeTAD/Au	SC	1.26	15.70	6.60	13.64	2020	191
61	FTO/SnO ₂ /TiO ₂ /CH ₃ COONH ₄ (MAI ₂ -PbI ₂)/spiro-OMeTAD/Au	SC	1.11	24.3	6.77	20.69	2019	196
62	FTO/SnO ₂ /TiO ₂ /PbMA ₂ /PbI ₂ /spiro-OMeTAD/Au	SC	1.10	24.2	6.77	20.5	2019	182
63	FTO/SnO ₂ /NH ₄ Cl/CdCl ₂ (PbMA ₂)/spiro-OMeTAD/Au	SC	1.19	22.2	6.75	20	2019	183
64	FTO/SnO ₂ /NH ₄ Cl/CdCl ₂ (PbMA ₂)/spiro-OMeTAD/Au	SC	1.17	18.67	6.33	16.54	2019	182
65	FTO/SnO ₂ /Cu ₂ CH ₃ NH ₂ /PbI ₂ /spiro-OMeTAD/Au	SC	1.12	22.8	6.99	21.2	2018	186
66	FTO/MgO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.12	23.00	6.70	19.21	2018	181
67	FTO/SnO ₂ /CdCl ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.12	23.01	6.79	20.25	2017	187
68	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	HT	1.019	23.62	6.70	19.21	2017	184
69	FTO/SnO ₂ /CH ₃ NH ₂ /PbI ₂ /spiro-OMeTAD/Au	ED	1.09	19.75	6.65	13.88	2017	189
70	FTO/SnO ₂ (FAI ₂) ₂ /(MAI ₂) ₂ /spiro-OMeTAD/Au	SC	1.10	23.38	6.73	20.28	2016	207
71	FTO/SnO ₂ /CH ₃ NH ₂ /PbI ₂ /spiro-OMeTAD/Au	SC	1.11	23.10	6.67	17.25	2015	185
Triaryl methyl cations								
72	FTO/SnO ₂ /PbI ₂ /MAI ₂ /MAI ₂ /PbI ₂ /spiro-OMeTAD/Au	Spray	1.119	18.18	6.66	21.78	2020	188
73	FTO/SnO ₂ /PbI ₂ /MAI ₂ /PbI ₂ /spiro-OMeTAD/Au	CHD	1.268	1.24	6.76	21.59	2020	187
74	FTO/TiO ₂ /NO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SP	0.91	23.04	6.68	14.77	2020	186
75	FTO/SnO ₂ /MAI ₂ /spiro-OMeTAD/Au	CHD	1.14	23.59	6.79	21.2	2020	185
76	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.12	22.3	6.710	19.7	2020	183
77	FTO/SnO ₂ /ZnO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	HT	1.05	18.78	6.794	18.22	2020	187
78	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	HT	0.98	21.2	6.69	14.2	2020	188
79	FTO/SnO ₂ /ZnO/SnO ₂ (MAI ₂ -PbI ₂)/spiro-OMeTAD/Au	SC	1.06	18.50	6.79	20.1	2019	189
80	FTO/SnO ₂ /ZnO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	PLD	1.12	22.40	6.796	20.69	2019	188
81	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.14	22.7	6.78	19.8	2019	182
82	FTO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.142	23.02	6.721	19.8	2019	180
83	FTO/SnO ₂ /PbI ₂ /spiro-OMeTAD/Au	SC	1.016	26.72	6.791	20.02	2018	61
84	FTO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	HTSC	1.12	23.4	6.81	21.2	2017	201
85	FTO/SnO ₂ /ZnO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	HT	1.048	23.71	6.662	17.33	2017	183
86	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SP	1.025	19.71	6.39	13.03	2017	184
87	FTO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	HT	0.998	17.66	6.627	18.96	2017	187
88	FTO/SnO ₂ /ZnO/SnO ₂ (MAI ₂)/spiro-OMeTAD/Au	SC	1.044	22.50	6.76	17.89	2016	187
89	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.02	18.8	6.71	17.3	2016	196
90	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	0.962	19.2	6.67	13.4	2016	190
91	FTO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.05	21.6	6.67	15.2	2015	182
92	FTO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	0.89	22.61	6.62	7.01	2014	181
Sulfides								
93	FTO/NiO ₂ /TiO ₂ /SnO ₂ (MAPbI ₃)/spiro-OMeTAD/Au	HT	1.11	22.4	6.76	20.2	2020	186
94	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC/UVT	1.069	22.31	6.782	19.46	2020	187
95	FTO/Nb ₂ O ₅ /Al ₂ O ₃ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.12	22.81	6.71	18.2	2015	186
96	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.00	18.4	6.65	11.49	2014	203
97	FTO/SnO ₂ /ZnO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.07	17.2	6.70	10.8	2012	213
98	FTO/SnO ₂ /Al ₂ O ₃ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.02	18.94	6.64	11.4	2012	21
99	FTO/SnO ₂ /Al ₂ O ₃ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	0.98	17.8	6.61	10.9	2012	220
Other inorganic ETAs								
100	FTO/TiO ₂ /CdTe/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.06	22.4	6.71	18.1	2020	182
101	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	TE	1.11	23.01	6.682	20.02	2019	188
102	FTO/SnO ₂ /SnO ₂ /spiro-OMeTAD/1,1,1,3,3,3-hexafluoro-2,2,2-trifluoroethane	CHD	1.09	7.79	6.629	5.29	2019	184
103	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.04	16.69	6.716	15.25	2018	185
104	FTO/SnO ₂ /SnO ₂ /ZnO/SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SLAR	1.02	19.05	6.754	14.9	2018	188
105	FTO/SnO ₂ /SnO ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	CHD	1.12	19.7	6.74	16.2	2018	187
106	FTO/SnO ₂ /MAI ₂ /spiro-OMeTAD/Au	P-LED	1.04	26.76	6.68	14.68	2017	189
107	FTO/SnO ₂ /MAI ₂ /CH ₃ COONH ₄ /PbI ₂ /spiro-OMeTAD/Au	SC	1.02	22.9	6.66	14.9	2015	189

^a SC – spin coating, P-LED – plasma enhanced chemical vapor deposition, CHD – chemical bath deposition, SLAR – successive ionic layer adsorption and reaction, TE – thermal evaporation, ALD – atomic layer deposition, SP – spray pyrolysis, SC – spin coating, ED – electrochemical deposition, HT – hot evaporation, GPCVD – low pressure chemical vapor deposition, TO – thermal oxidation, HT – hydrothermal synthesis, MIE – sol gel synthesis, HT – hydrothermal, ES – electro spinning, ST – sublimation, PV – perovskite precipitation, UVT – UV treatment, S-spray, and SPS – RF sputtering.

which was stimulated by the higher electrical conductivity of PC₆₁BM. Furthermore, an interlayer of organic molecules between the ETI/metal contact interface was introduced to passivate the defects, reducing the band bending and acting

as a permeation barrier for moisture to enhance the stability.¹⁸⁸

The inclusion of additives in PC₆₁BM decreases the film roughness and influences the morphology, which increases

the recombination resistance at the perovskite/PCBM interface. Also, these additives ease the exciton dissociation and promote fast charge transport.²⁸³ Recently, Song *et al.*²⁸⁴ used poly(3-benzothiothiophene) (P3BT) as an additive to dope PCBM to avoid aggregation, thereby enhancing the moisture and water resistance. This was shown to result in a retention of 12% of the initial PCE at 20% for 720 h. Similarly, after the modification of the PCBM/perovskite interface with poly(γ -vinylcarbazole) (PVK) doping in PCBM, it showed better anti-UV, moisture, and thermal stability.²⁸⁵ The other non-fullerene-based organic ETAs include tetraphthalate diimide derivatives, perylene diimide derivatives, naphthalene derivatives, indanocarbazole derivatives, and π -type conjugated polymers, which can be new alternatives to gain a better performance than various modifications of PCBM.²⁸⁶ Non-fullerene-based ETAs have unique advantages such as molecular structure diversity and adjustable frontier molecular orbitals.²⁸⁷ However, a detailed review of organic ETAs is beyond the scope of this review, which can be found in the literature.^{288–290}

Despite the promising properties of organic ETAs, they have only appeared in a small number of reports compared with inorganic ETAs. However, assuming that the superior electrical and optical properties can be harnessed from organic ETAs, a pathway for higher efficiency in PSCs can be visualized. Overall, matching the only energy levels at the ETL/perovskite interface is not sufficient, where matching the electron mobility is a prerequisite to avoid charge accumulation. A detailed study of the interface is required considering the defects on the perovskite surface, chemical reactions, and effect on perovskite morphology due to the presence of the ETL, charge trapping, and charge recombination.

Despite the differences in the electrical properties, synthesis process, and interface effects in the various observed materials used as ETAs, numerous ETL systems have delivered high PCEs. ETAs continue to exert a significant influence on the device performance and efficiency even after selecting distinguished perovskite materials as overlayers in PSCs. In the initial stage of research, only ~1% efficiency was observed with the PSCs utilizing oxides of Ti, Zn, Sn, etc. to form ETL/perovskite heterostructures. The higher efficiency reported each year for a decade from a variety of ETAs in the most prominent recent reports is shown in Fig. 20. Recently, the efficiency reached ~25% with the advancement of ETAs in interface engineering due to the doping, co-doping, compositing, decoration, etc. of ETAs. A brief summary of the inorganic ETAs processed using various synthetic methods and their corresponding device performance parameters are tabulated in Table 1. Thus, future developments of novel ETAs should not only focus on enhancing the power conversion efficiency but must be rationalized based on cost and sustainability.

5. Hole transport layer (HTL)

The HTL is equally essential to transport the acceptor or holes generated in the photoactive perovskite layer to the cathode. The HOMO of the hole transport material (HTM) under

consideration for PSCs is required to be located at a higher level than the valence band edge of the perovskite absorber (Fig. 21). The minimized energy barrier at the perovskite/HTL interface allows easy collection of the photogenerated holes. Moreover, the conductivity of the HTM, which plays a vital role in charge transfer and charge recombination at the perovskite/HTL interface, can be revamped by governing interface energies and defect densities. Besides, the thermal and chemical stability of HTMs continue to be a concern for the long-term and efficient photovoltaic performance. Thus far, various nano-structured, doped, and passivated HTAs have been explored in PSCs depending on the selected device architecture. In this section, we critically discuss the involvement of various inorganic HTAs in delivering a higher PCE.

5.1. Inorganic HTAs

Inorganic HTAs have gained importance in PSCs due to their ability to be downsized to nanostructures, increasing the junction interface. Given that PSCs are the resultant evolution of uncoated solar cells, though with conceptually newer foundations, main electrolytes have been replaced with metal salt electrolytes or HTAs in PSCs. However, the expensive solid-state organic spiro-OMeTAD when introduced in PSCs degrades the perovskite absorbers due to the use of hygroscopic dopants. Therefore, the low-cost inorganic HTAs with high chemical/thermal stability and scalability have attracted considerable attention from the scientific and industrial community as a replacement for spiro-OMeTAD. Various inorganic materials based on binary oxides, cyanates, and delafossite such as NiO, VO₂, CoO₂, CuO, Cu₂S, and Cu₂Se, have been investigated for their performance as HTAs in PSCs.^{291–293} The band structure positions of selected inorganic HTAs with reference to the perovskite absorber are summarized in Fig. 22. These HTMs are wisely engineered to alter the charge transfer dynamics and to efficiently extract holes. The significance and optoelectronic properties of these important inorganic HTAs employed in PSCs are discussed in this section.

5.1.1. Nickel oxide (NiO). NiO is one of the most widely studied HTAs for PSCs due to its chemical inertness, low processing cost, and earth-abundant nature. Nickel oxides with molecular formula of NiO, Ni₂O₃, and Ni₃O₄ can be engineered to obtain cubic, monoclinic, rhombohedral, and hexagonal crystalline phases.^{294–296} Mainly, p-type semiconducting stoichiometric NiO with a wide bandgap of 3.5–4 eV^{297,298} and deep valence band edge (i.e., 5.2 to 5.4 eV) provides excellent band alignment with the perovskite light absorber. The higher conduction band positioning of NiO than perovskite materials become advantageous to conduct holes very efficiently and serves as an excellent electron blocking layer.

Docampo *et al.*²⁹⁷ introduced NiO as an HTL in PSCs and gained an efficiency of <1% when utilized with a mixed halide perovskite absorber as the photoactive material. The low efficiency was attributed to the inadequate surface coverage and large number of pinholes in the perovskite films coated over the NiO HTL in the inverted device architecture. The possibility of improving the PCE after controlling the doping density

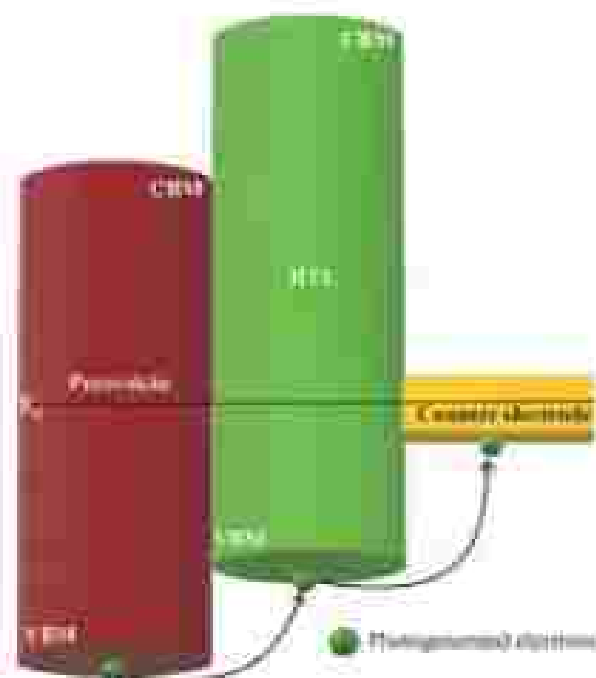


Fig. 21 Schematic depicting the path of the photo-generated hole from the perovskite/HTL absorber to the external circuit. CBM, conduction band minimum and VBM, valence band maximum.



Fig. 22 Schematic of band alignment of various inorganic HTLs with perovskite absorbers.

projected NiO as one of the forthcoming worthwhile HTL candidates. Therefore, various growth mechanisms and thin-film technologies have been explored for the synthesis and coating of NiO films in the ambient atmosphere, such as sputtering,⁴²⁴ atomic layer deposition (ALD),⁴²⁵ sublimation growth,⁴²⁶ sol-gel,⁴²⁷ e-beam evaporation,⁴²⁷ reactive e-beam evaporation,⁴²⁸ atmospheric pressure spatial atomic layer deposition (AP-SALD),⁴²⁹ and thermal evaporation followed by oxidation.⁴³⁰ Among them, repeated spin coating has been observed to be a simple and cost-effective method to gain precise control over the thickness and crystallinity of NiO nanostructures, although the

radical ligands reduce the coverage of the perovskite absorber, and hence the performance of PSCs. Moreover, the thickness of the faulted and corrupted NiO nanocrystalline films controls the hole extraction and transport competence at the HTL/perovskite interface⁴³¹ because a lower thickness presents a higher leakage current and a higher thickness offers higher series resistance. A precisely controlled ultra-thin NiO films with negligible absorption loss prepared by ALD showed no residuals and pinholes. The extremely thin NiO films with a thickness of 2–2.5 nm, less than the Debye length (i.e., 1–2 nm for NiO), increased the work function and hole concentration by overlapping of the space charge regions. Moreover, high-temperature treatment improved its interfacial properties by reducing the content of hydroxylate Ni(OH) and reducing the amount of surface defects related to C–N at the HTL/perovskite interface, achieving a PCE of 14.4%.⁴³² Subsequently, Liu et al.⁴³³ utilized a solution-coagulation based NiO HTL with the two-step-processed $\text{MA}_{0.9}\text{FA}_{0.1}\text{Pb}_{0.9}\text{I}_{0.9}\text{Cl}_0.1}$ perovskite to achieve a PCE 19.6%. Recently, the controlled island-like growth of NiO offered a lower absorption in the visible region, and also increased the effective interface with the perovskite absorber, while presenting the shunt resistance,⁴³⁴ knowing the fact that mesoporous structures provide a better interface between the HTL and perovskite, Yin et al.⁴³⁵ explored a mesoporous morphology of 1D NiO nanotube morphology. The hierarchical tube morphology offered a continuous conducting pathway for rapid hole extraction and less charge leakage due to the substantially passivated interfacial hole-trapping state density [i.e., $1.278 \times 10^{16} \text{ cm}^{-3}$], which yielded a PCE of 18.7% with quenched Shockley-Read-Hall recombination losses (Fig. 23).

The Ni^{2+} and Ni^{3+} variations govern the defect levels in NiO and inversely alter the conductivity and optical transmittance of the HTL. The spatial localization of the HOMO of the perovskite/HTL system on the NiO layer estimated by adopting the relativistic pseudopotential and pseudo-atomic orbitals predicted the transfer of holes from the perovskite in close proximity of the NiO surface connected by halogen and lead atoms (Fig. 24).⁴³⁶ Therefore, precise control of the $\text{Ni}^{2+}/\text{Ni}^{3+}$ ratio by the defect family aligns the VB of the HTL with the perovskite and provides faster hole extraction with lower energy losses, offering a PCE close to 10%.^{437–439} Nevertheless, the significantly reduced oxygen vacancies in self-doped Ni_2O_3 ⁴⁴⁰ and Ni(OH)_2 ⁴⁴¹ yielded a PCE close to 20%, gaining attention as alternative HTLs to replace NiO. The Ni^{2+} cation sites act as a Lewis electron acceptor and Brønsted proton acceptor by deprotonating cation anions and oxidizing iodide species. Therefore, different amounts of Ca^{2+} ,⁴⁴² Y^{3+} ,⁴⁴³ La^{3+} ,⁴⁴⁴ Fe^{2+} ,⁴⁴⁵ Cu^{2+} ,⁴⁴⁶ Sr^{2+} ,⁴⁴⁷ Ag^{+} ,⁴⁴⁸ Na^{+} ,⁴⁴⁹ and Zn^{2+} ⁴⁵⁰ metals and rare earth elements [i.e., Ba , Yb , Tb , Ce , and Nd]⁴⁵¹ were doped to enhance the intrinsic conductivity, charge extraction ability, hole mobility, energy level alignment, and optical transparency of NiO films by reducing the $\text{Ni}^{2+}/\text{Ni}^{3+}$ vacancy formation energy due to their replacement. Even though the segregation of alkali-cations such as Li^{+} ,⁴⁵² Cs^{+} ,⁴⁵³ and K^{+} ⁴⁵⁴ on the NiO surface improve the performance of PSCs due to their favorable interaction with perovskite, their time-dependent disparity

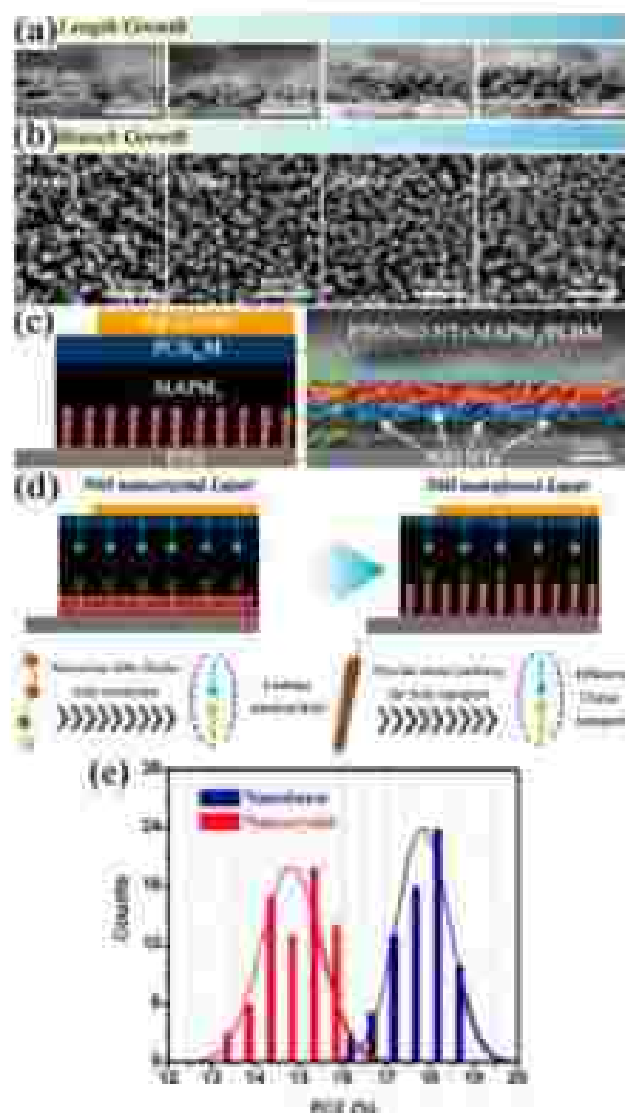


Fig. 2F (a) Cross-sectional and (b) top-view SEM images of the NiO nanorods synthesized with controlled length and branch growth. Schematic of (c) device architecture and corresponding cross-section SEM image and (d) charge transport in PSCs consisting of NiO nanocrystals and commercial HTL. (e) Comparison PCE distribution of nanocrystal and nanorods.²⁰⁷ Reprinted with permission from ACS Appl Mater Inter (2016) 11, 44388–44514. Copyright (2016) the American Chemical Society.

in the spatial distribution, modifies their performance and stability.

Al doping in the lattice of NiO, not only enhances the electrical conductivity of the HTL, but also improves the crystalline growth of the perovskite absorber, concurrently aligning its energy levels, which dramatically reduces the energetic non-radiative recombination losses and enables quicker hole transportation at the perovskite/HTL interface to deliver a PCE of 20.84%.²⁰² Mg doping has shown to downshift the VB maximum, matching it well with the perovskite and lowering the energy redundancy for hole injection. The reduced energy band offset benefited the efficient charge collection/transport

and curtailed the hysteresis, yielding a reproducible PCE of 18.2% from an ambient-stable commercial device with an active area of 10 cm² × 10 cm.²⁰⁸ Interestingly, embedding Au inside an NiO layer to form Au-NiO, as both an electrode and electrode interlayer for PSCs was attempted to replace the ITO electrode, but difficulties were encountered in the formation of a compact layer, reducing the film thickness to control the transparency, and loss of photoexcitation energy due to self-recombination of opposite charges at the electrode. This hampered the PSC device performance (i.e., PCE = 16.24%).²⁰⁹ The further addition of Cu on the top of Au-NiO film effectively reduced the resistance, but the device delivered a maximum PCE of 11.1% at a 1 nm Cu layer. This was reduced further with an increase in the thickness of Cu (i.e., >1 nm).²¹⁰ UV-titanium irradiation reduced the interface barrier between a Cu-doped NiO/HTL and MAPbI₃ perovskite by surface dipole formation and also increased the carrier concentration and charge-extraction efficiency.²¹¹ Recently, Zhou *et al.*²¹² improved the electrical conductivity of an NiO_x film by enhancing the Ni²⁺ content after N-doping and achieved a PCE of 17.02%. The reduced Gibbs free energy on the hydrophilic Ni-doped NiO_x surface led to a higher nucleation density, and thereby larger grain growth of the perovskite absorber with improved interfacial contact and passivation of the trap states in the perovskite layer, thereby suppressing nonradiative recombination.

Cobalt-doping exhibits a synergistic effect and endows the NiO_x film with a further improvement in its performance. As an HTL in PSCs, p-type Co-doping provides low transparency and high conductivity, whereas alkali and alkaline co-dopants result in high transparency with low conductivity. It was reported that 10% LiOAc/5% Co co-doping synergistically enhanced the PCE to 22.1% by providing a shorter carrier lifetime of 0.67 ps and a larger recombination lifetime of 2.34 ns, signifying efficient hole-charge recombination and suppressed charge carrier recombination, respectively.²¹³ The synergy between Ag and Li co-dopants with the +1 oxidation states was shown to tailor the optoelectronic properties of NiO. The smallest formation energy of Li and Ag among the related defects created shallower acceptor levels in NiO and enhanced the hole concentration, which effectively optimized the charge extraction/transport and reduced the charge accumulation at the interface, therefore boosting the PCE to 19.24%.²¹⁴ Mg²⁺ doping compensates the undesirable positive shift caused in the VB of NiO, due to the incorporation of Li and promotes the formation of an ohmic contact at the perovskite interface by reducing the barrier height via staircase energy level alignment with the MAPbI₃ perovskite.²¹⁵ However, the inclusion of Cu²⁺ in Mg-Li reduced the device performance severely (i.e., PCE = 12.32%) for unknown reasons.²¹¹ Besides, polymeric PDA, DEA, PBDI, and PEAL coatings^{144–146} introduced as an overlayer for the NiO_x HTL effectively modified the interfacial contact and boosted the interfacial charge transfer through favorable band alignment and reduced trap state density. The lone-paired functional groups on the polymer coordination with Ni and Pb ions form a quasi-2D polymeric-perovskite grain, which blocks the electron transport in the HTL and limits the carrier recombination at the interface.

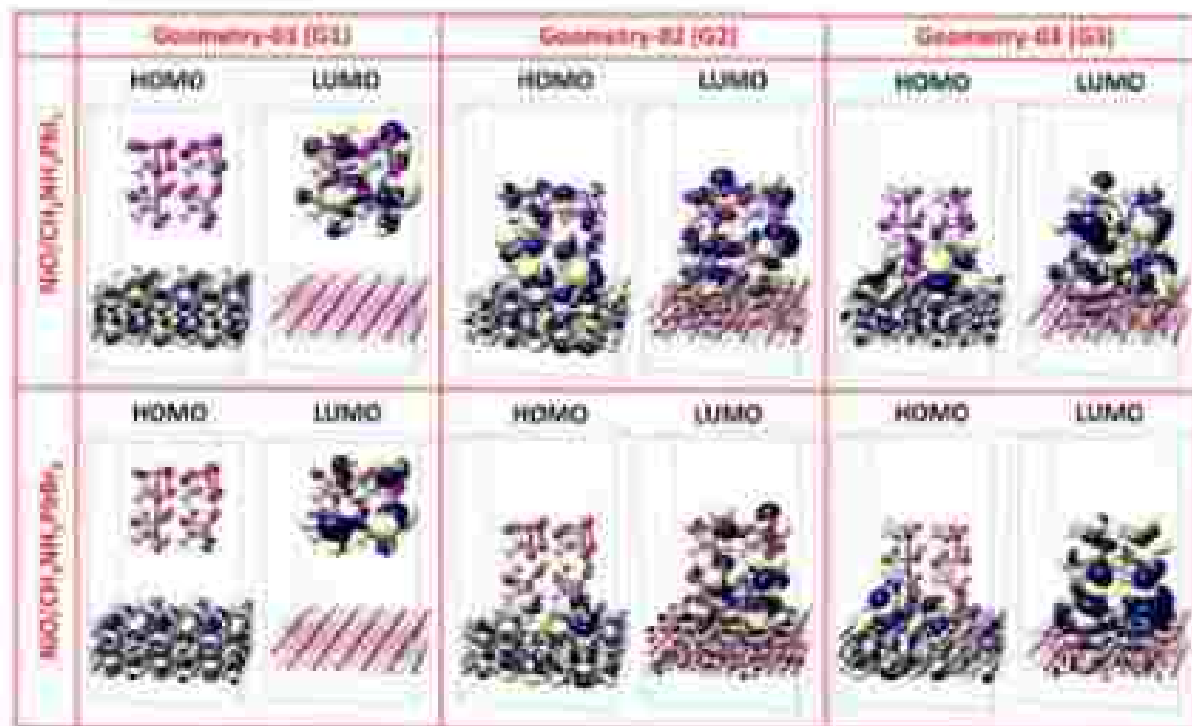


Fig. 24 Optimal structures showing the HOMO, LUMO and band structure for three initial orientations of an NiO (green) and perovskite (layer) interface region. The geometries G1 refer to the surface separation of ~ 1 nm between the perovskite and NiO, and G2 and G3 indicate the close proximity of <0.1 nm between the perovskite and NiO, but perovskite contact NiO(100) surface via the closest halogen atom and Ni atom and halogen atom and nickel atoms, respectively. The upper row shows the MPPM₁, and the lower row represents the MPPM₂, perovskite nanoparticles. In the NiO structure, the Ni and O atoms are represented by green and red spheres, respectively. In the perovskite structure, the Bi, I, and Pb atoms are identified in boxes.¹⁰⁰ Reprinted with permission from ACS Appl. Mater. Interfaces, 2019, 12, 11601–11610. Copyright (2019), the American Chemical Society.

3.1.2. Vanadium oxide (VO₂) Vanadium oxides composed of VO₄ square pyramids or distorted VO₄ octahedra with shared oxygen atoms appear in various chemical forms such as VO₂, V₂O₃, V₂O₄, V₃O₅, V₄O₇, V₅O₁₀, V₆O₁₃, V₆O₁₄, V₆O₁₅, and V₆O₁₆, of orthorhombic, cubic, triclinic, tetragonal, monoclinic, and rhombohedral crystalline phases.¹⁰¹ The existence of valence band levels and conduction band levels at ~ 2.16 eV and ~ 2.94 eV, respectively, and the bandgap of ~ 2.6 eV have projected VO₂ as another interesting HTL candidate material for PSCs. The low-temperature synthesis protocols have been shown to incorporate hydroxyl groups in vanadium oxides (i.e., VO₂), and the post-synthetic heat treatment results in oxygen vacancies by establishing V³⁺ (i.e., $\sim 65\%$ to 75%) and V⁴⁺ (i.e., ~ 35 – 25%) cations,^{102–104} which are protonium trap sites, restricting their use as HTL. Typically, the air-oxidation of VO₂ films during their synthesis naturally results in the formation of V₂O₅ on the top surface at the interface between the perovskite absorber and VO₂ HTL and controls the device performance by monitoring the band offset.¹⁰⁵ The large variation between the V³⁺ and V⁴⁺ cations results in the assembly of V₂O₅ films with higher roughness and unstable thickness, which typically yield a larger barrier to allow the tunnelling of charges in PSCs.¹⁰⁶ Therefore, a thin layer of hydrated V₂O₅ (i.e., VO₂) has been explored as an alternative HTL to minimize the catastrophic electrical and structural inhomogeneities in the

frequently explored PEDOT/PSS hole extraction layer, which adversely affect the device lifetime. Moreover, a compact layer of thermally stable VO₂ nanoparticles not only enhanced the light-harvesting but also delivered extremely high transmittance (i.e., $\geq 98\%$), higher quenching efficiency, and reduced internal resistance, which facilitated efficient charge transportation, offering a PCE close to 14% .^{107–109} Likewise, it also assisted in improving the stability of gradient heterojunction based PSCs exposed to solar radiation in N₂ (i.e., 25.8% PCE for 720 h) and ambient (14.1% PCE for 175 h) environments.¹¹⁰

The V₂O₅ additive, as an interface modification layer, is a good hole extraction layer, and this has been utilized to improve the quality of perovskite light absorbers (i.e., CH₃NH₃PbI₃-xCl_x).^{111–113} The hydrogen bonds and dangling bonds in the hydrated V₂O₅ additive produce larger perovskite grains. The optimized amount of additive produces a dense perovskite film of larger grains, which play a crucial role in reducing the trap charge density to improve the current injection, thereby concurrently limiting the leakage current. Although these modifications are performed to overcome the high recombination rate at the V₂O₅/perovskite interface, they also mitigate the migration of iodide ions into the crystal boundaries and retain a stable device performance beyond 1000 h. Besides, an ambient atmosphere-processed VO₂ interlayer in an unencapsulated n-i-p device showed excellent PCE retention (i.e., 71% of initial value) after

Illumination at the high temperature of 70 °C for 1100 h,⁴⁹³ but the slow ingress of oxygen and water in the unencapsulated device degraded the perovskite layer, despite a barrier layer being imposed to reduce the rate of vanadium ion diffusion. Therefore, the VO₂ thin film was further passivated with an aminopropionic acid (APPA) interfacial layer to control the effect of oxygen vacancies on the charge recombination at the perovskite/VO₂ HTL interface, which also enriched the perovskite crystallinity, reducing the content of charge-trapping pinholes.⁴⁹⁴

A copper phthalocyanine (CuPc)⁴⁹⁵ and thermally crosslinked triarylamine-based 2-DVPU⁴⁹⁶ buffer layer was introduced in the VO₂ matrix to limit the incorporation of moisture and realize excellent interfacial energy level alignment. The synergistic bilayer HTL was shown to reduce the charge carrier recombination, enhancing the charge extraction at the interface. Furthermore, VO₂ was also introduced over poly(triarylamine) to induce hydrophilicity to grow a high-quality perovskite absorber layer, thereby improving the PCE (i.e., 18.9%).⁴⁹⁷ A thin overlayer of VA₂ was shown to suppress the trap-assisted recombination, significantly improving the charge extraction and transport at the interface. However, owing to the limited improvement in

PCE to 19%, subsequent efforts were focused on increasing the conductivity of pristine VO₂ by doping rather than via additives or complex bilayer formation.

The improved conductivity of VO₂ (i.e., $1.05 \times 10^{-2} \text{ S cm}^{-1}$) and interfacial adhesion with the MAPbI₃ perovskite layer after Ca doping resulted in a 30% enhancement in the device efficiency.⁴⁹⁸ On the contrary, when dispersed in carbon, VO₂ facilitates the charge transfer at the perovskite/carbon interface due to the high work function without compromising the conductivity of carbon.⁴⁹⁹ Recently, PSCs with a top hybrid HTL composed of VO₂ incorporated p-type polytriarylamine (PTAA) polymer reached an efficiency of 20.1% and exhibited negligible degradation after 1000 h of light soaking due to the higher tolerance of VO₂ towards the perovskite absorber (Fig. 25).⁴⁹⁸ The donor-acceptor interactions between the electron-deficient VO₂ and electron-rich amine centers of polymer enable the impeccable fusion of VO₂ and PTAA layers, which provide improved charge transport, possibly similar to doping effects. The post-treatment strategy of vanadium oxides offers great flexibility to tailor the cation distribution, and hence the energy level alignment. The UV post-treatment of a few atomic layer thick (~1 nm) pristine VO₂ HTL film was shown to increase the

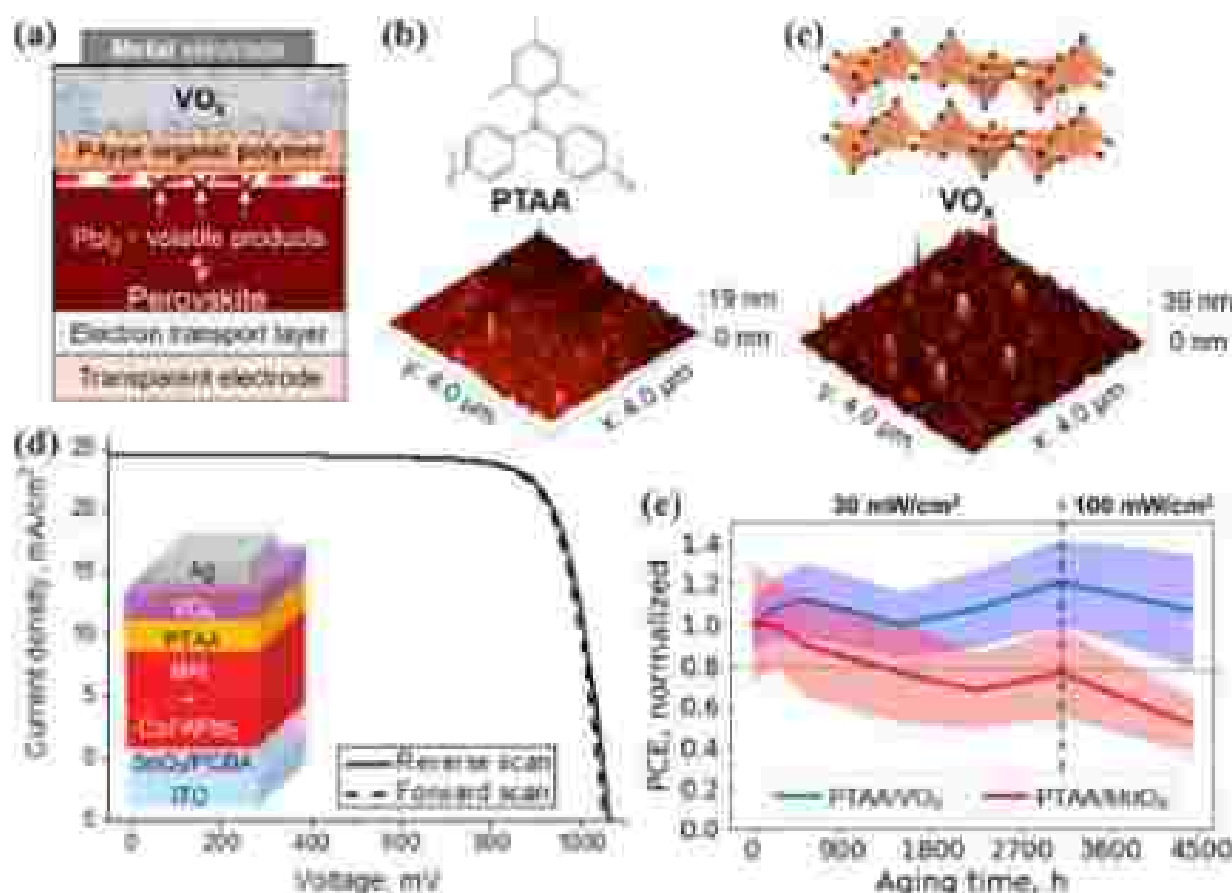


Fig. 25 (a) Schematic of n-i-p PSCs consisting of a hybrid HTL of PTAA and VO₂ with inert gas permeability and better barrier properties than the soluble polymeric decomposition products. Molecular structure, mixed pyramidal based structure and topography of 34 spin-coated p-type PTAA film and (c) evaporated 30-nm-thick VO₂ film on glass. (d) J-V characteristics of PSC consisting of VO₂ in bilayer hybrid HTL. (e) Stability of PSCs with bilayer hybrid HTL under illumination.⁴⁹⁸ Reprinted with permission from *J. Phys. Chem. Lett.*, 2020, **11**, 5553. (CC-BY) Copyright (2020), the American Chemical Society.

oxidation states from V^{4+} to V^{5+} , drawing the Fermi level close to the valence band, thereby enabling the hole quenching pathway for the transportation of holes to improve the device efficiency.⁴⁴ Even though VO_x has shown promise towards efficient and stable PSCs, further investigation of morphology controlled VO_x nanostructures, doped VO_x , and composites with other promising materials are required to explore its use as an HTL for reaching a milestone efficiency and the cost-effective mass production of PSCs.

The use of an Al-doped V_2O_5 buffer layer or barrier layer was shown to improve the long-term thermal stability of PSCs.⁴⁴⁵ Indeed, a precisely controlled stoichiometric V_2O_5 HTL enhanced the PCE from 11.24% to 13.07% when interfacial with PBDOT/PSO under ambient conditions.⁴⁴⁶ V_2O_5 curbs the formation of oxygen defects and also ensures hole transfer from the perovskite absorber ($CH_3NH_3PbI_3$) to V_2O_5 HTL by forming an excellent ohmic contact.⁴⁴⁷ Moreover, filling the pinholes of PBDOT/PSO by incorporating V_2O_5 nanoparticles improved the carrier mobility and increased the surface energy by exposing more PBDOT chains to the interface with the perovskite absorber.⁴⁴⁸ Further, V_2O_5 combined with nickel phthalocyanine (NiPC) effectively extracted holes from the perovskite by modifying the VB of both and rendered a 22% enhancement in the PCE (i.e., 13.0%).⁴⁴⁹ Basically, the VB of pristine V_2O_5 forms an electronically barrier-free cascading contact for hole transportation and extraction across the interface.

3.1.3. Cobalt oxide (CoO_x). Cobalt oxide is another HTM attracting attention due to its hole-quenching capability and low processing cost. Cobalt oxides with the molecular formula CoO , Co_2O_3 , and Co_3O_4 can be obtained in cubic and hexagonal spinel crystalline phases with a wide bandgap in the range of 1.3 to 2.4 eV.⁴⁵⁰ The much shorter hole extraction time of CoO_x (2.8 ns) relative to NiO_x (22.8 ns) and CuO_x (308.5 ns) has projected Co-oxides as possible competitor materials to other inorganic HTLs.⁴⁵⁰ In 2016, Shalin *et al.*⁴⁵¹ introduced ultrathin CoO_x films as an HTL in inverted PSCs, which was obtained via a simple spin-coating technique followed by high-temperature processing (400 °C). Besides the excellent light harvesting capability, it was mainly the phenomenal charge separation ability of the highly transparent CoO_x (i.e., 15 nm thick) achieved a PCE of 14.5% even with a single-cation single-halide perovskite. Despite the fact that an ultrathin HTL minimizes the incident photon loss induced by Co ion absorption and curtails the carrier losses by shortening the transport path, the introduction of a metal ion in the CoO_x lattice changes the conductivity of CoO_x and energy-level mismatch with the perovskite. The deeper VB position of CoO_x (~ 5.36 eV) than the HOMO of $CH_3NH_3PbI_3$ (- 5.1 eV) hinders the hole transport and causes reverse recombination. However, the incorporation of Cu in CoO_x uplifts the VB (- 5.34 eV) without altering the CB edge (- 2.2 eV), which is maintained much higher than that of $CH_3NH_3PbI_3$ (- 3.9 eV). This severely reduces the carrier transfer loss at the interface and energetically favours the electron injection.⁴⁵¹

Spinel Co_3O_4 with octahedral Co^{2+} is significantly tolerant to structural distortion or disorder, and hence excellent hole

transport materials for PSCs. Co_3O_4 assists with the issues of carrier transport and recombination process at the carbon/perovskite interface in carbon-based PSCs by reducing the charge transfer resistance from perovskite and suppressing interfacial recombination. Moreover, the interfacial layer of Co_3O_4 significantly promotes the separation and extraction of photo-generated carriers, as well as the hydration of perovskite, thereby providing a steady performance under ambient and light soaking conditions.^{445,446} Low-salinity doping reduces the density of defect states and enhances the hole mobility of Co_3O_4 by introducing acceptor energy levels on both the Co^{2+} and Co^{3+} sites of Co_3O_4 . Therefore, Li^+ doping in the lattice of Co_3O_4 improves the light absorption and boosts the hole mobility by forming an Li -enriched $LiCoO_2$ overlayer, which facilitates efficient hole transportation at the Li - Co_3O_4 /perovskite interface, delivering a PCE of ~ 14%.⁴⁴⁵ However, the super hydrophilicity induced in $LiCoO_2$ after UV/ozone treatment led to the formation of a highly dense MAPbI₃ film with an excellent interface, which was shown to enhance the PCE to 19%.⁴⁴⁶

Recently, the co-doping of Zn^{2+} in $LiCoO_2$ improved its conductivity and incrementally enhanced its hole mobility, which caused a 4-fold enhancement in the PCE compared to that of the pristine Co_3O_4 -HTL.⁴⁴⁵ The rock-salt CoO with octahedral high-spin Co^{2+} is another HTM from the CoO_x family that has the potential to improve the PCE. Recently, a CoO film was treated with pyridine to control the adverse effect of oxygenated molecules present on the CoO film on the growth of the perovskite film, and thereby the performance of PSCs. The ligand exchange process by pyridine not only improved the conductivity by influencing the defect states in CoO but also altered the HTL/perovskite interface for excellent charge extraction, showing a 2-fold improvement in the PCE.⁴⁴⁷ Recently, the decoration of CoO nanoplates in a discontinuous manner to fill the boundaries of crystalline perovskite grains yielded the highest PCE of 20.72% by improving the charge-transfer kinetics and hole extraction ability (Fig. 2b).⁴⁴⁸ The uncovered perovskite grains account uninterrupted hole transport from the perovskite to spinel- $OMeTAD$ HTL; moreover, the CoO nanoplates residing at the perovskite grain boundaries (where defect sites exist) reduced the trap state density ($3.771 \times 10^{17} \text{ cm}^{-3}$), suppressing the charge recombination. Overall, the best PCE is still to be realized from PSCs utilizing Co-oxide HTLs. In the future, the choice of precursor and reaction kinetics should be considered to obtain the best-quality nanostructures of Co-oxide HTLs to ensure maximum hole quenching and improved efficiency. Therefore, the research direction should be focused on improving the conductivity and mobility of CoO by proper choice of doping and the film quality by tuning the processing method to boost the interface between CoO -perovskite to reduce the recombination loss.

3.1.4. Copper oxide (CuO_x). The earth abundance oxides of copper with molecular formula of CuO (cupric oxide), Co_2O (cuprous oxide), and Cu_2O (cuprous sesquioxide, thermodynamically unstable) can be realized in cubic, monoclinic, and tetragonal structures, respectively.^{452–454} Cuprous oxides are primarily

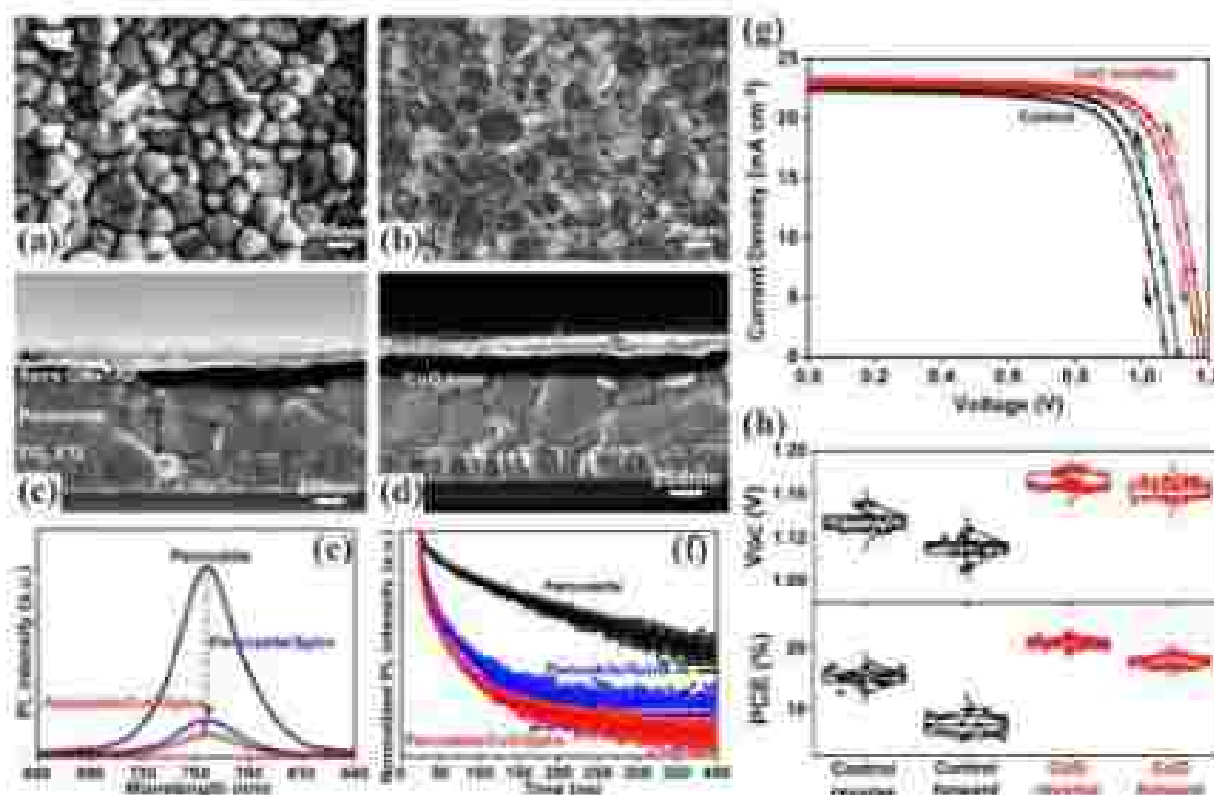


Fig. 26 Top-view TEM images of the perovskite layer (a) without and (b) with CaO nanoparticles (HTL), and their respective cross-sectional areas (c) without and (d) with CaO nanoparticles (HTL). (e) PL and (f) PPL spectra of the CaO nanoparticle HTL. (g) J-V curves of the PSCs with and without CaO nanoparticles (HTL) and the V_{OC} and PCE obtained by forward and reverse scan of J-V of these PSCs. The control was a PSC without CaO nanoparticles.³⁴⁴ Reprinted with permission from ACS Appl. Mater. Interfaces, 2015, 7, 32157–32165. Copyright (2015) the American Chemical Society.

utilized as buffer layers for the stable encapsulation of PSCs to maintain efficiency in adverse environmental conditions.³⁴⁴ The two-fold or magnitude higher mobility of pristine and modified Ca-oxides (i.e., $\sim 256 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$) than NiO (i.e., $1.8 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$) makes them an excellent choice as HTLs. Most importantly, the best-performing PSCs using copper oxide are prepared with ultrathin films of Cu_2O , but the ultra-thin nature of the film restricted the analysis of its crystallographic data for tailoring its interfacial properties. Therefore, X-ray photoelectron spectroscopy (XPS) studies have been given importance to understand the properties of the surface facing the interface. The existence of a Ca^{2+} content in the range of 45–60% (i.e., 17–23% of Ca^{2+}) confirmed the presence of both Ca_2O and CaO phases in CaO_x .^{345,346} Nevertheless, the $\text{Ca}^{1+}/\text{Ca}^{2+}$ ratio was controlled via the self-oxidation of independently prepared Ca_2O and CaO thin layers to govern the channels for charge carrier transport by lattice matching, and thereby the solar device efficiency.³⁴⁴ The equal existence of Ca^{1+} and Ca^{2+} delivered a Ca_2O phase with a bandgap of $<1.6 \text{ eV}$,^{345,346} which is lower for blocking the conduction electrons, and hence not explored much. However, the Ca_2O and CaO forms exhibit bandgaps (E_g) in the range of ~ 2.1 to 1.6 eV , with an approximately similar VB level of $\sim 5.3 \text{ eV}$, satisfying the primary requirement as HTLs in PSCs.

The conversion of spin-coated Ca into Ca_2O and CaO under controlled thermal treatment delivered a PCE close to 13% and

created excitement among the scientific community exploring solar materials.³⁴⁴ The mixture of $\text{Ca}^{1+}/\text{Ca}^{2+}$ with a ratio of 1:1 produced a PCE of 17.4% by improving the hole extraction and charge dissociation at the $\text{CaO}/\text{MAPbI}_3$ interface in the presence of a buffer layer.³⁴⁴ Further, in search of improved efficiency, Chen *et al.*³⁴⁷ transformed complex $\text{CaO}-\text{Ca}_2\text{O}$ uneven morphologies into stable CaO nanoparticles of uniform dimension, but this complex $\text{CaO}-\text{Ca}_2\text{O}$ structure delivered a maximum PCE of only $\sim 3\%$ for unknown reasons. Therefore, various synthesis techniques such as electrostatic spray deposition,³⁴⁷ magnetron sputtering,³⁴⁸ sputterless method,³⁴⁹ MBE,³⁵⁰ low beam sputtering,³⁵¹ thermal oxidation,³⁵² spin-coating,³⁵³ chemical vapor deposition,³⁵⁴ and electrospinning³⁵⁵ have been examined to control the Ca-oxide film thickness and its interface with the perovskite absorber layer, influencing the efficiency of PSCs. The CaO , employed in place of PEDOT:PSS HTL, exhibited a stable and higher PCE (15.1%) than that of the pure Ca_2O and CaO HTLs.^{352,356} Recently, it has been shown that a highly crystalline perovskite overlayer on CaO , quantum dots reduced the charge trap state density, leading to a higher carrier transfer efficiency and reduced charge recombination, delivering a PCE of 19.9%.³⁵² However, CaO suffers from a low transmittance in the visible range, and its further improvement by reducing thickness compromises the optical losses.

The nanoparticle-based interface modification concept provides a series of benefits in PSCs. Monolayered CaO

nanoparticles (3–10 nm) improve the light manipulation, suppress parasitic interfacial resistance, and induce higher hole-extraction ability, resulting in a V_{OC} of 1.09 V and an efficiency of 15.3%.⁵⁴ However, CuO nanowires introduced as an anodic buffer layer in the inverted planar device structure yielded a PCE of 15.27%, which originated from the higher hole mobility (or improved conductivity) of the HTL and its larger interfacial area with perovskite. Even though the diameter of nanowires plays a central role in improving the charge-extraction ability, unoptimized overlapping of the nanowires increases the hole-transport distance and degrades the crystallinity of the perovskite layer, thereby reducing the performance of PSCs.⁵⁵ Further, Ag nanoparticles doping in CuO nanowires increases the light trapping and suppresses the charge-recombination rate, but their high carrier mobility reduces the PCE (i.e., ~11%).⁵⁶ Besides, a reactively sputtered CuO thin film barely accompanied with Cu₂O, under controlled annealing conditions, had shown the highest efficiency of 22.86% due to the increased exciton-assisted band-to-band recombination.⁵⁷

The incorporation of Cu₂O in PSCs has been shown to reduce the recombination losses at the interface. Cu₂O forms type-II band alignment at both the p-i and i-n interfaces, enabling charge separation and uninterrupted-carrier transport from MAPbI₃.⁵⁸ The synergistic effect of Cu₂O nanocubes as the top HTL on the perovskite light absorber (CH₃AM/PI₃) in a planar n-i-p PSC demonstrated a highly stable PCE of ~17.28% at room temperature without encapsulation.⁵⁹ Further, the heterojunction of Cu₂O with SnO₂ enhanced the PCE to 18.6% by effectively preventing defects and pinholes, and also tailoring the recombination and collection of charge carriers at the interface with the perovskite absorber.⁶⁰ To further enhance the device performance, surface modification strategies using molecular solvents have been explored. Surface modification of Cu₂O quantum dots using silane molecules has been seen to increase the recombination resistance, affording faster and more efficient charge-carrier extraction to deliver a PCE of 18.9%.⁶¹ Moreover, a Cu/Cu₂O composite layer introduced as a p-type-modified layer between low-mobility hole-transport materials and the metal electrode acted as an electron-blocking buffer layer and effectively improved the PCE.^{62,63} Cu₂O was also blended with CuI/CN to avoid the formation of defects and impurities at the interface due to the reaction of halides migrated from organohalide perovskites into CuI/CN.⁶⁴ The existence of Cu₂O nanoparticles resulted in the faster extraction of charges generated in organohalide perovskites by their interaction with CuI/CN, thereby realizing a PCE of 19.2% by minimizing the detrimental interfacial degradation.

Device simulations have predicted that Cu₂O has the ability to improve the PCE to over to 25% by tuning the bandgap^{65–67} due to its high mobility despite the complication in its synthesis. However, control over the interface properties has become a key obstacle in this development. Due to the presence of Cu vacancies at the surface or termination in the oxygen planes, the reactive oxygen becomes the recombination centres to trap the conduction electrons. Therefore, the atomic model developed by Castellano-Aguila et al.⁶⁸ for the

Cu₂O(001) and MAPbI₃ interface showed that the formation of vacancies in the Cu₂O-terminating planes eliminates the dangling bonds and deep trap states, enabling the PSCs to exhibit excellent photoconversion efficiency (Fig. 2f). However, the diverse nanostructure morphologies and doping or co-doping of Cu₂O with promising elements are yet to be fully explored in-depth to understand their effect on the device performance.

5.1.3. Copper iodide (CuI). CuI crystallizes in zinc blende (<200 °C), wurtzite (>200 °C and <400 °C) and rock salt (>400 °C) structures,^{69,70} which is another promising HTL with a wide bandgap (i.e., ~2.1 eV), high hole mobility (i.e., 0.5–2 cm² V⁻¹ s⁻¹), high transparency, good chemical stability, and low production cost. Various solution-based and solid-gas reaction processes have been endorsed as facile methods to synthesize CuI.^{71–73} Systematic modelling based on a combination of DFT-based computational and group-theory methods has illustrated that among the intrinsic point defects, copper vacancies are the most prominent to govern the electronic and transport properties of CuI, resulting in an improvement in the PCE.⁴⁷ Initially, CuI was explored in conventional n-i-p PSCs, and then utilized in inverted planar PSCs to improve the PCE by avoiding iodide formation at the interface. The incorporation of an iodine atom expands the Cu (with lattice constant of 1.35 Å) structure of the film and results in the formation of a compact CuI crystal, removing the pinhole defects. Simultaneously, new species are formed at the interface of perovskite/CuI by loading Cu in the perovskite, resulting in stronger charge-extraction and noticeable short-circuit current density.⁷⁴ Nevertheless, the redundant iodine acts as an interfacial recombination centre.

Christians et al.⁴⁷ introduced CuI as a competitor to spin-coated HTL in PSCs, providing 3-orders of magnitude larger electrical conductivity; nevertheless, the high recombination in the CuI-based device restricted the PCE to 6% at a lower V_{OC} , suggesting a strong possibility for the achievement of its performance. Moreover, benefiting from the high transparency of CuI, with deep valence band, it showed a higher PCE than the acidic and hygroscopic PEDOT:PSS-based PSCs.⁷⁵ The smaller magnitude of charge separation at the perovskite/CuI interface leads to the generation of a smaller local electric field; therefore, the faster polarization relaxation down-sizes the hysteresis in $J-V$ measurement of CuI-based PSCs.⁷⁶ The larger roughness of a powder-pressed CuI HTL reduced the device performance by severely trapping the charge carriers at the numerous air voids generated deep inside the HTL layer.⁷⁷ The thermally evaporated ~40 nm-thick compact CuI HTL decreased the charge-carrier recombination losses at the interface and exhibited an air-stable PCE of 14.7%.⁷⁸ Later, an air-stable PCE of 16.8% was obtained by optimizing the morphology of the perovskite film coated on the CuI HTL to effectively reduce the energy loss at the interface.⁷⁹ Recently, the use of CuI-decorated Cu nanowires as a hybrid Cu₂O/CuI nanostructure enabled a PCE of 19.4% by efficient charge extraction from the outer CuI layer and rapid charge transfer from the inner Cu wires.⁸⁰ However, the synergistic effect of Na-doped TiO₂ HTL

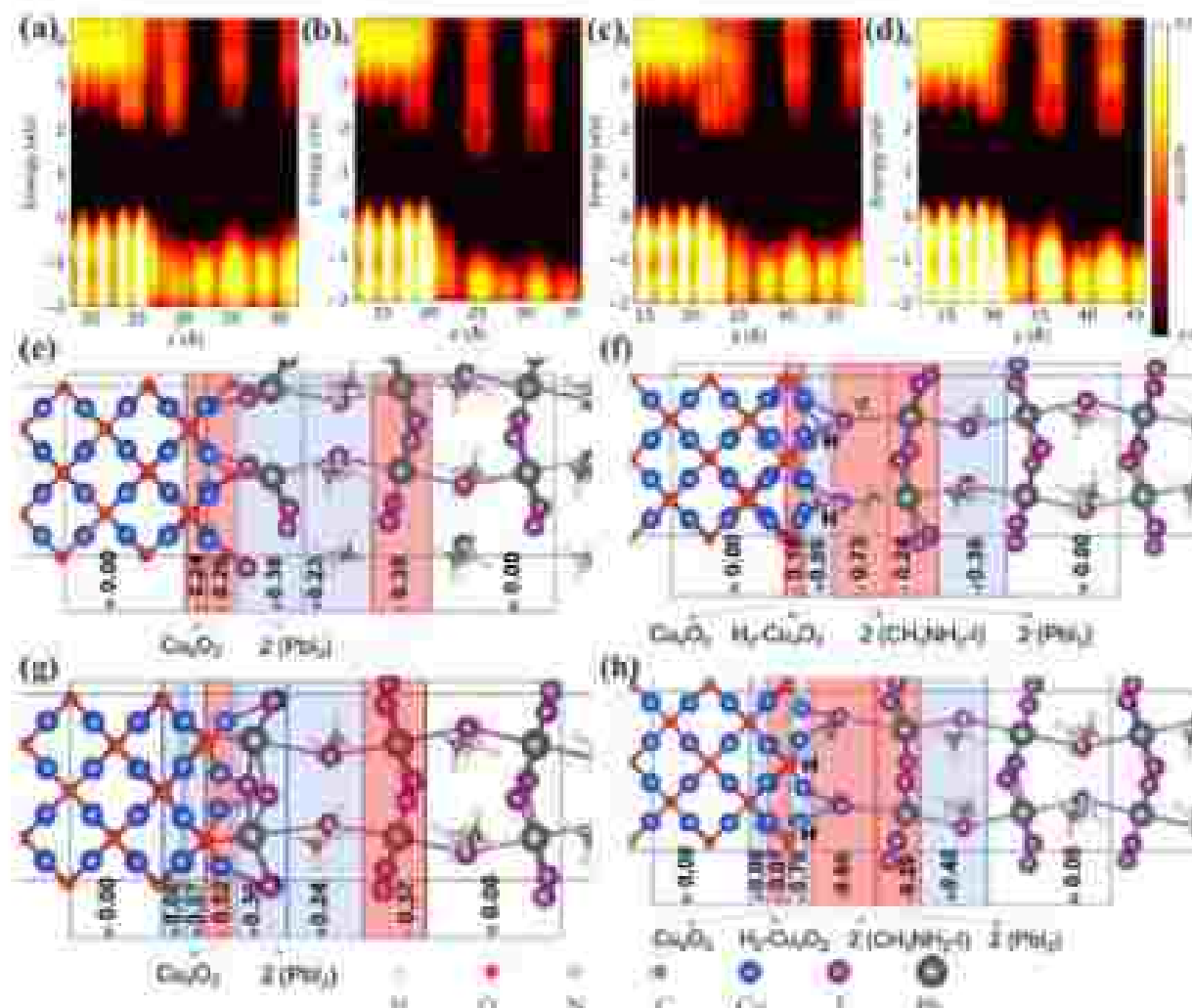


Fig. 27 (a–d) Topologies of LDOS $\times V_{bias}$ averaged in the xy plane calculated between the MAPT and Cu_2O interface and (e–h) their atomic structures for the four interface models: (a) and (f) CuPb, (b) and (g) CuPb, (c) and (d) CuPb, and (e) and (h) CuPb. The interface states are higher in energy than the MAPT/Cu₂O, allowing electrons to return to MAPT. Therefore, holes can be transferred from MAPT to Cu_2O without being trapped, although they can be attracted and recombine with electrons trapped at the CuPb and CuPb interfaces.²¹¹ Reprinted with permission from *Mater. Interfaces* 2020, 12, 44648–44655. Copyright 2020, for the American Chemical Society.

and CuI HTL, where Nb-doped TiO_2 enhanced the electron conductivity/mobility and CuI induced a higher recombination resistance, improved charge transport at both interfaces (i.e. HTL/perovskite and HTL/perovskite interface) and delivered an efficiency of 17.6%.²¹²

Despite its high mobility, the CuI HTL alone forms leakage paths, leading to carrier recombination at the CuI/perovskite interface. Therefore, $\text{Pb}(\text{CH}_3\text{NH}_2)_2$ was introduced as a middle layer for efficient carrier extraction through adequate energy level alignment, making the architecture more efficient with a thicker CuI overlayer.^{213,214} The further addition of CuI as a middle layer between PTAA and perovskite enhanced the charge extraction on both the sides and yielded a PCE of 19.34% by creating enhanced upward band bending (0.15 eV) at the CuI/perovskite interface with a large built-in potential (~ 1.28 V) all over the active layer.²¹⁵ Moreover, CuI is beneficial to reduce the trap-state concentration and parasitic charge

accumulation, limiting the flow of charges through the passivation of other HTLs. Sataishi *et al.*²¹⁶ observed that the passivation layer of CuI fills the pinholes and severely reduces the trap states of metal oxide, protecting the perovskite/HTL interface from degradation and promoting faster injection and relaxation processes in devices, yielding an impressive PCE of 15.2%.

Byungho *et al.*²¹⁷ introduced CuI islands on a TiO_2 ETL to pull the electrons at the perovskite/ TiO_2 interface and extract them via the dipole moments formed. The higher conduction band energy level of CuI (i.e., -2.1 eV) than the perovskite presents the formation of PbI_2 at the interface, facilitating superior electron extraction with a lower trap density, and the smaller Cu^+ and larger I^- ions mimicking PbI_2 (i.e., Pb^{2+} and I^-) inhibit the back recombination (Fig. 28(a and b)). Although a moderate number of CuI islands improved the PCE (i.e., 19%), a large number of CuI islands reduced it by blocking the electron pathways (Fig. 28(c)). Apparently, the

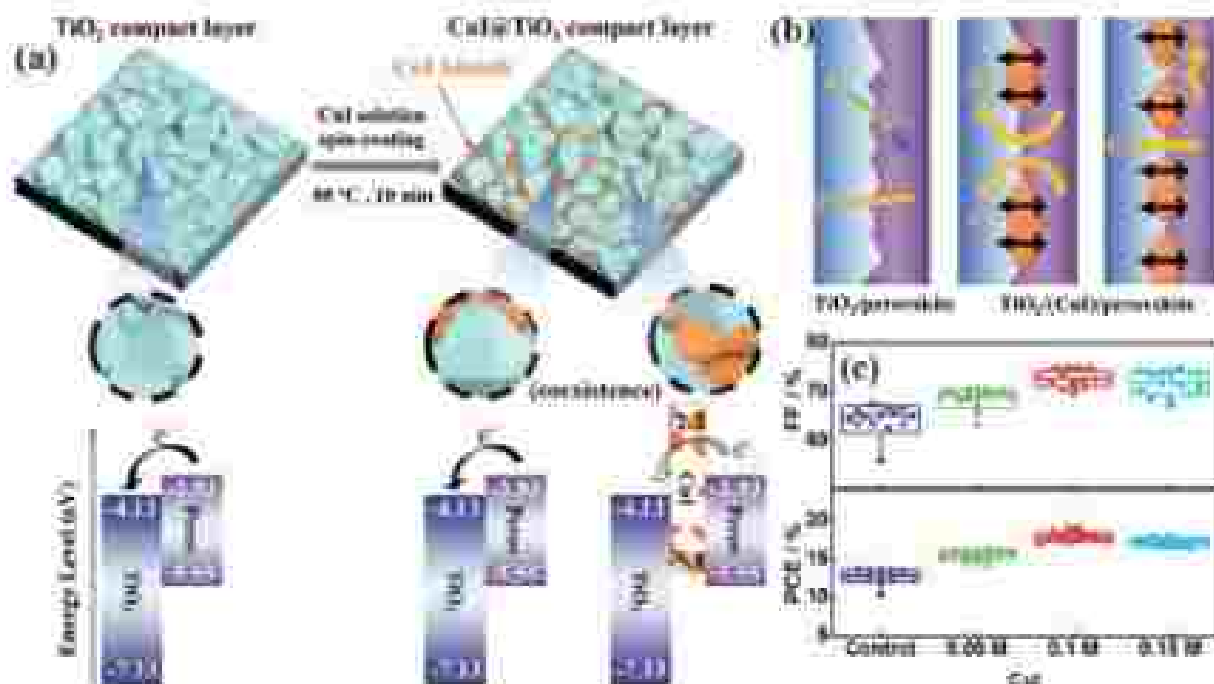


Fig. 28 (a) Schematic of CuI islands formed on TiO₂ compact layer and subsequent deposition of perovskite layer. (b) CuI modified TiO₂/CuI/perovskite based PSCs, electrical flow from the perovskite to the adjacent TiO₂ layer (b) instead of CuI islands because of its high conduction band energy level. (c) Efficiency with various amounts of CuI bands. J-V and PCE of devices with various concentrations of CuI⁺ deposited with perovskite from *Adv. Energy Mater.*, 2017, 8, 1702225. Copyright 2016, John Wiley & Sons.

incorporation of thionine in CuI (i.e., Cu(Tb)) operates by accelerating the hole transport and reducing the charge carrier recombination due to the increased depletion width (from 126 to 203 nm) as compared to the traditional CuI. Thus, Cu(Tb) exhibited a PCE of 19.9% by lowering the trap state energy level and eliminating the potential wells for hole transport at the interface.²⁹² This is why the doping or passivation strategies for further the modification of CuI endow it with potential to serve as magnificent HTLs for efficient PSCs.

Overall, CuI is one of the best HTMs to produce PSCs in the range of 10% to 20% after combining with TiO₂, CuI, ZnO, ZnS, ZnS, ZnO, ZnS, etc.,^{293–295} but a well-optimized thickness ratio of the ETL, perovskite, and HTL is highly demanded. The interplay of Pb and CuI restricts the (Pb-based) perovskite by the Cu-I chemical drain in the system and increases the CuI contact, and hence the charge carrier transport. CuI-based devices show suppressed hysteresis with a significant light soaking effect. The chemical potential gradient redistributes the I⁻ ions from CuI to the perovskite by diffusive movement (during aging, which can be tuned by controlling the distribution and morphology of CuI. The aging (instability) can be seen in any PSC that undergoes diffusive ion migration towards the interface, but it is relatively less for HTLs like CuI barely accumulating I⁻ ions.

3.1.6. Copper thiocyanate (CuSCN). CuSCN is one of the cost-effective hole selective contacts for the emerging organometal halide PSCs. The hole stability of 0.01–0.1 cm² V⁻¹ s⁻¹, E_{onset} level of 5.3 eV (E_{g,CuSCN} = 1.8 eV), and high thermal and chemical stability of CuSCN have gained attention as inorganic

HTLs in PSCs.²⁹⁶ CuSCN with an inherently wide bandgap (E_g = ~1.8 eV) transmits in the complete visible spectrum, facilitates photoactive materials to absorb more light, and generates higher photocurrents in solar cells. Ho et al.²⁹⁶ proposed the use of CuSCN as an HTL in PSCs for the first time to control the degradation of the CH_{3NH₃PbI₃} perovskite layer during the light exposure test without encapsulation. Later, various synthesis protocols such as drop-casting,²⁹⁷ electrodeposition,^{298–300} spin coating,³⁰¹ and spraying³⁰² were developed to obtain CuSCN in an ambient atmosphere with minimum damage to the underlying perovskite absorber, followed by annealing strategies to achieve a higher efficiency. Nevertheless, the texturized grain growth of CuSCN after recrystallization produces poor interaction with the perovskite absorber, thus inducing non-contacting sites as charge recombination centres, thereby reducing the device efficiency. The high-temperature treatment causes the SCN⁻ ions to diffuse near the perovskite/HTL interface, resulting in the degradation of the device performance, which can be impeded either by vacuum-assisted thermal treatment³⁰³ or EISN post-treatment.³⁰⁴

PSCs employing a CuSCN HTL exhibited a PCE of 11.3%, which degraded faster under elevated temperatures in ambient atmosphere. Therefore, the critical instability caused by the interfacial degradation of the heterojunction of CuSCN and perovskite in a dry N₂ environment was resolved with rudimentary on-cell encapsulation using an additional coating of insulating poly-methyl-methacrylate (PMMA).³⁰⁵ The mesoporous and rough surface of a 600–700 nm-thick CuSCN layer utilized in conventional and mesostructured PSCs attained a maximum

of PCIE of 12%.^{336,337} However, a very thin (40 nm) uniform and compact CaSCN film furnished a higher degree of transparency, resulting a PCIE of 16%, given that it efficiently generates a higher photocurrent and mitigates the recombination losses at the interface.³³⁸ The well-aligned junction geometries of the nanostructured arrays substantially increase the light trapping by reducing reflection losses, and also improve the carrier extraction by increasing the interfacial area at the perovskite/HTL interface. However, the hexagonal 10 prism, 10 pyramid, and 10 nanowire-like structures of the CaSCN HTL produced uncontrolled defect density and continued growth of perovskite, restricting the PCIE to <17%.³³⁹ Importantly, the incorporation of CaSCN in the mesoporous perovskite absorber layer resulted in the formation of a bulk heterojunction, which facilitated faster hole extraction with a resulting PCIE of >23%.³⁴⁰

The deposition of the CaSCN HTL overlayer causes damage to the perovskite absorber. Therefore, a protective buffer solvent layer of chlorobutane³⁴¹ and PDMO³⁴² was placed over the perovskite before the deposition of CaSCN, which not only hampered the formation and migration of defects but also promoted the crystallization of CaSCN to benefit the charge extraction at the interface (Fig. 29). However, the use of MA₂(aq) as a substitute to the commonly used diethyl sulfide solvent is seen to reduce the shunting pathways and interfacial current losses, resulting in a PCIE of 17.5%.³⁴³ Further, a fast solvent removal process facilitates the formation of a compact and conformal CaSCN layer, which serves towards rapid charge extraction and collection. The potential-induced degradation of the CaSCN/Au contact provided the operational instability of the PSCs with a PCIE exceeding 20%. Accordingly, the inclusion of a conductive PED spacer between CaSCN and Au avoids the electrical potential-induced reaction at their interface, forming an undesirable barrier and exceptionally improving the stability (i.e., >95% of the initial PCIE at 60 °C for 1000 h aging).³⁴⁴ However, PED has been seen to fail in improving the hole extraction and electron blocking, which cannot further enhance the PCIE. Therefore, the introduction of ultrathin polymer layers of P1H³⁴⁵ and P1H³⁴⁶ over CaSCN has gained attention.

These innovative alterations have enhanced the hole extraction efficiency by cascading energy levels and providing environmentally stable PCIEs of above 20% for over >1000 h of light illumination. Considering the dissimilarity against the defects structures, multi-component systems have been found to be helpful for the passivation of defects. The interfacial treatment of functional molecules such as Pt-DTC and Pb-DTC has been found to be effective in controlling the perovskite/CaSCN interface, resulting in a PCIE of 13.17% PCIE with an enhanced V_{oc} .³⁴⁷

Recently, Kim *et al.*³⁴² introduced CaSCN/P1HTL composite to address the instability of PSCs towards high-moisture conditions. The hole-extractive CaSCN, when combined with a p-type conductive polymer, initiated oxidative activities and triggered in-situ p-doping of polymers, thereby improving the interfacial charge transportation and device performance. Alternatively, the coordination strategy, where the coordination bond between CaSCN and ligands (e.g., pyridine derivative) forms a stable intermediate phase, has been found to be exceptionally good for realizing a compact CaSCN HTL by reducing the formation of intermediate adducts and enabling faster recrystallization. Consequently, it facilitated hole extraction and suppressed charge recombination at the interface, resulting in a PCIE of 13.1%.³⁴⁸ Besides, CaSCN is either doped or combined with organic HTLs such as P1TUNQ,³⁴⁹ P1DTC,³⁵⁰ P5S,³⁵¹ and spin-OMeTAU³⁵² to reduce the energy barrier and improve the charge extraction at the interface.

Overall, the theoretically predicted PCIE of 25%³⁵³ for the device utilizing CaSCN HTL, where Ca-T and Pb-T bonds form at the interface, inducing more significant electrostatic potential and electron-hole pair excitation, is highly encouraging. However, one should always consider that the molecular (atomic) adsorbates such as iodide and lead present in the perovskite absorber interact with CaSCN at the interface and form the Pb₂ moiety, leading to additional empty states in the bandgap of CaSCN and tailoring the corresponding optoelectronic properties. Therefore, theoretical studies on the passivation of CaSCN and interaction of solvent molecules (DMF or DMSO) with CaSCN need to be thoroughly devoted to the molecular interfacial engineering of CaSCN HTLs for realizing excellent PCIEs.

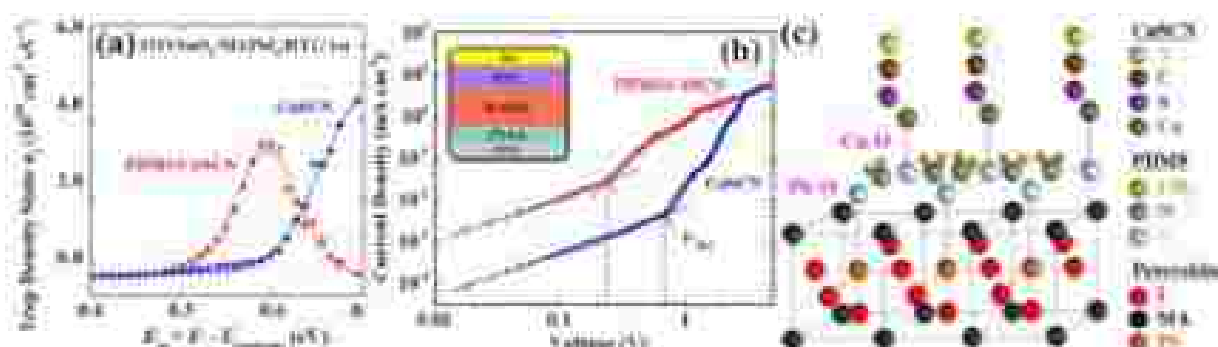


Fig. 29 (a) Trap distribution spectra and (b) J - V characteristics measured in the dark for the P1H/PSCs with and without the PDMO interlayer. (c) Schematic of the cross-section of the PDMO interlayer. The molecular and atomic features of the PSCs are estimated from the curves in (a) fitted with (a) lines. The arrows in (b) indicate the open-circuit (OC) voltages (V_{OC}).³⁴⁹ Reproduced with permission from [ACS Appl. Mater. Interfaces, 2016, 8, 4581B–4582B]. Copyright © 2016, the American Chemical Society.

3.1.7. Other inorganic HTLs. Delafossite materials with the general chemical formula of AB_2X_4 , where A ($=$ Cu), B ($=$ Al, Ga, Cr), and X bear $+1$, $+3$, and -2 states, respectively, have also attracted scientific attention to understand their photoactivity. These layers are composed of edge-sharing BO_4 octahedrons linked by triangular sheets of monovalent A^+ ions in the ABX_3 materials and possess high mobility, wide bandgap, and excellent stability. However, limited delafossite materials have been explored as HTLs for PSCs. $CuAlO_2$ (CAO) exhibiting a bandgap of ~ 3.75 eV and hole mobility of ~ 14 $cm^2 V^{-1} s^{-1}$ ²⁰⁸ is one of them. However, CAO, possessing decent optical transparency and thermochemical stability, has processing issues due to the need for high-temperature processing to gain pure polycrystalline delafossite form, and the complex Al chemistry prohibits the efficient synthesis of nanostructures. However, in amorphous phase, which provides a band gap of ~ 3.36 eV, has attracted attention due to its nonreactive behaviour with TiO₂ or other HTL materials during deposition. Therefore, Ighari et al.²⁰⁹ introduced magnetron sputtered CAO thin films below a PEDOT:PSS HTL in planar PSCs. The variation in the thickness of the CAO film tailored the energy level alignment and reduced the charge transfer resistance at the HTL/perovskite interface, which yielded an optimized PCE of $\sim 14.27\%$ and stable performance with efficiency retention of 90% over 250 h in the ambient atmosphere without encapsulation. Further, the incorporation of 12% CAO in the uniformly distributed CAO nanoparticles enhanced the electrical conductivity, which further reduced the interfacial charge recombination and induced faster charge collection to render a higher PCE of 16.3%. Recently, PAMI introduced during the electro-spray process to form a CAO/polyaniline (PANI) composite film delivered an $\sim 2\%$ larger efficiency for the optimized wts of CAO (i.e., 0.1%) than pure PANI film.²¹⁰ The addition of PANI improved the interconnectivity between the CAO nanoparticles, enabling the conformal film coating of a CAO HTL, and enhanced the hole conduction into the organic polymer. Nevertheless, the excessive aggregation of CAO induced high surface roughness and increased the series resistance by segregating the CAO and polymer.

$CuCrO_2$ (i.e., CCO) is another delafossite material with a hole mobility of 0.1 – 1 $cm^2 V^{-1} s^{-1}$, valence band maximum of ~ 5.3 eV w.r.t. the vacuum level, and a bandgap of 3.1 eV,²¹¹ which can offer the tuning of the energy levels by altering the phase composition. Low-temperature solution-processed CCO nanocrystals demonstrated a PCE of $\sim 19\%$ as HTLs in PSCs and acted as an excellent UV inhibitor, protecting the perovskite absorber from UV-induced degradation.²¹² Although DFT analysis proposed the formation of distinct hexagonal 2H (space group $P6_3/mmc$) and rhombohedral 3R (space group $R\bar{3}m$) polytypes of CCO, both are stable and deliver identical optoelectronic properties.²¹³ Besides the inverted device structure, CCO nanoparticles were utilized with a triple cation perovskite light absorber to form a highly stable n-i-p structure, exhibiting an efficiency of 16%.²¹⁴ A bigger VII offset does not favour hole transfer, whereas a lower electron affinity favours electron-blocking. Therefore,

Qin et al.²¹⁵ employed different Cu/Cr ratios to modulate the energy levels and phase composition of a CCO film to improve the hole-collection and electron-blocking ability. These Cr-terminated polar CCO films achieved a respectable PCE of 17.10% (Fig. 3H).

Yang et al.²⁰⁶ introduced an anisotropic-promoted doping approach for CCO to explore cost-effective commercialization aspects. The d-d excitation of the Cr^{3+} cations at the oxygen octahedrons of the delafossite structure causes the low transparency of CCO. The replacement of Cr^{3+} by In^{3+} (i.e., doping) decreases the absorption of d-d and improves the conductivity (i.e., carrier mobility) and transmittance of CCO, which are beneficial for solar-light harvesting and hole transport, and consequently an impressive PCE of 20.54% was achieved. Furthermore, considering the band alteration due to the doping of metallic elements, Mg has also been introduced in CCO. The smaller ionic radius of Mg than Cr overlaps the Cu d-orbitals by reducing the Cu–Cu bond distance, resulting in improved charge mobility and conductivity, which produces an efficiency close to 17%.²¹⁶

$CuGaO_2$ (i.e., CGO) is also a prominent HTL material with high carrier mobility ($\sim 10^{-1}$ $cm^2 V^{-1} s^{-1}$) and a bandgap of ~ 2.58 eV, furnishing a well-matched energy level with perovskite absorbers.²¹⁷ However, the aggregation of CGO results in a larger particle size, which is incapable of enabling the formation of a compact pinhole-free film, hindering its use as an HTL. Therefore, a surfactant such as Pluronic 123 was utilized to synthesize CGO nanoparticles with a diameter of ~ 10 nm.²¹⁸ Moreover, the use of CGO with Cu_2S improved the PCE to 16% by reducing the trap density of defects.²¹⁹ Besides the increased efficiency, a bilayer HTL was shown to offer high thermal stability, retaining 80% of the initial efficiency after exposure to a temperature of 30 °C and 80% relative humidity (RH) condition (encapsulated) for 100 h. Furthermore, 2s² doping (i.e., 5%) enhanced the hole mobility of pristine CGO (i.e., from 1.81×10^{-4} to 1.38×10^{-3} $cm^2 V^{-1} s^{-1}$), which yielded an efficiency of $\sim 20\%$ and high robustness to humidity and temperature.²²⁰ Chen et al.²²¹ reported the development of microscopic inverted device structures utilizing compact NO_2 and CCO mesoporous layers. The graded band alignment formed at the HTL with compact NO_2 and mesoporous CCO was shown to enable higher hole extraction, leading to an efficiency of $\sim 19\%$. Further, solution-processed CCO nanoplates were coated on the perovskite absorber to form an n-i-p device structure, effectively lowering the nonradiative Shockley-Read-Hall (SRH) recombination and providing a PCE of $\sim 18\%$.²²² Recently, a 3D hybrid HTL consisting of Cr-doped CCO nanoplates and NO_2 nanoparticles yielded a PCE of $\sim 20\%$. The nanoplates acted as expressways for hole extraction, whereas the ultrafine NO_2 nanoparticles modified the surface properties.²²³

Besides delafossite materials, various inorganic materials such as CuS , FeS , Cu_2S , and $CdTe$ have been investigated for their application as HTLs in PSCs. The use of Cu_2S nanoparticles uniformly deposited on TiO₂ without compromising the roughness and transmittance of the TiO₂ substrate resulted in an

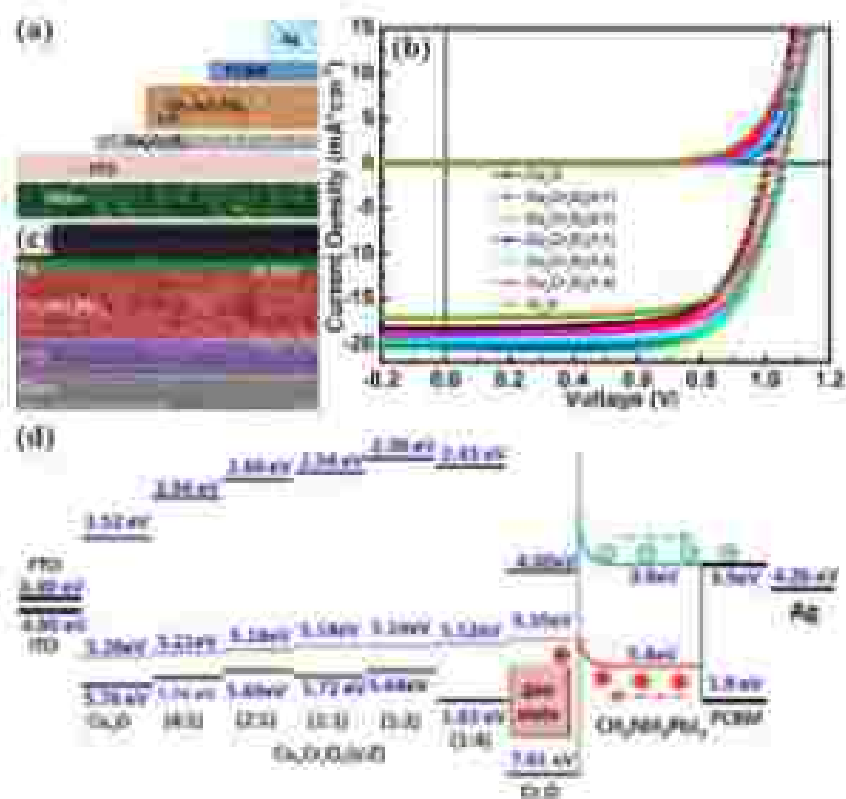


Fig. 10 (a) Schematic, (b) J - V characteristics under 1-sun illumination, and (c) a cross-sectional SEM image of PSCs consisting of Cu₂O/Cu₂FeSn₄ BHJ. (d) Band energy level diagram of PSCs composed of Cu₂O/Cu₂FeSn₄ HTL in various molar ratios of x : 2 = 1.0, 4:1.2, 1.1:1.1, 1:2, 1:4, and 0:1.¹⁰⁰ Reprinted with permission from (Scale 66, 2017, 1, 100000). Copyright (2017), John Wiley & Sons.

efficiency of ~10% with Cu₂FeSn₄/PbI₃ as the light absorber, although its V_{oc} was limited to ~0.8 V due to the considerable offsets in valence band levels at the Cu₂FeSn₄/perovskite interface.¹⁰⁰ High hole mobility Cu₂O nanoparticles have been incorporated in carbon to form a Cu₂O/C composite HTL and improved the hole mobility.¹⁰¹ Moreover, digenite Cu₂Te nanocrystals were formed by partially replacing Cu with Te in the aseltite Cu₂S structure and tested as HTLs in PSCs. The ternary Cu₂Te material showcased its potential as an HTL by yielding an efficiency of ~10%.¹⁰² High-purity kesterite Cu₂ZnSnS₄ (CZTS) nanocrystals as an inorganic HTM with Cu₂FeSn₄/PbI₃ perovskite achieved an efficiency of ~15% and remarkable FF of 81%.¹⁰³ Further, quantum dots of CZTS as HTLs were tested with all inorganic Cu₂Te, perovskite absorbers, showing a promising efficiency of ~5%.¹⁰⁴ The thickness of the light-absorbing CZTS HTLs in inverted PbI₂ plays a prominent role in controlling the irradiation over the perovskite light absorber.¹⁰⁵ Interestingly, numerical simulations have identified the plausible tunability of the Cu₂Te(Sn_{1-x}Te_x)₂ bandgap and band offsets at the perovskite/HTL interface through the partial replacement of Sn with Te (*i.e.*, $x = 0.8$) and predicted a theoretical efficiency of ~20% in combination with CH₃NH₃PbI₃ as a light absorber.¹⁰⁶ Kim *et al.*¹⁰⁷ observed an efficiency of ~17% with acetamidamine-capped FeS₂ nanoparticles, preventing moisture attack in the perovskite light absorber, thereby retaining stability for 3000 h. Further, the hole quenching capacity of

iron pyrite FeS₂ is comparable to that of the benchmark spin-coated Cu₂O, but its efficiency is not higher to the defect-mediated recombination at the FeS₂/perovskite interface, where low-energy photons are left largely unutilized with non-productive recombination events taking place.¹⁰⁸ Although FeS₂ is 100 times cheaper than spin-coated Cu₂O, its inefficient hole collection needs to be improved by using a capping ligand. Moreover, a wide bandgap *p*-type quaternary chalcogenide Cu₂TeS₂ semiconductor having favourable band alignment with a CH₃NH₃PbI₃ perovskite light absorber and high carrier mobility (~10 cm² V⁻¹ s⁻¹) was shown to exhibit an efficiency of 10% in inverted PSCs.¹⁰⁹ Similarly, spinel oxides of Ni, Co, Cu, etc. (such as NiCo₂O₄ and NiCu₂O₄) have been explored as HTLs in PSCs due to their high electrical conductivity, high optical transparency in the UV-Vis-NIR region, and well-matched energy levels to the perovskite absorber.^{110,111} The low-temperature solution-processable nanodispersed spinel NiCo₂O₄ oxide nanoparticles synthesized via a combustion method show high electrical conductivity (~1 S cm⁻¹) and low roughness (0.56 nm), delivering an efficiency of ~15% for the optimized film thickness of 15 nm with higher transmittance and better charge collection.¹¹² Likewise, various doping strategies¹¹³ have been explored to investigate the practicality of spinel NiCo₂O₄ as HTLs in PSCs. Thus, besides the traditional inorganic HTLs used in PSCs, various combinations of pristine novel *p*-type materials need to be tested for their hole quenching capabilities.

5.2. Organic HTLs

Several organic HTLs previously used in DSSCs and organic bulk heterojunction solar cells, which satisfy the requirements of PSCs, have been tested as HTLs to improve the performance. 2,2',2'',2'''-Tetrakis(*N,N*-di-4-methoxyphenylamino)-9,9'-spirofluorene (spiro-OMeTAD) is one of the widely used organic small molecule p-type semiconductors and dominant solid-state HTLs in PSCs. The large bandgap (about 3 eV) with a deep HOMO level of spiro-OMeTAD located at -5.2 eV eases the acceptor transport from most of the perovskite absorbers to the external contact.¹⁰⁶ Although spiro-OMeTAD has been proven to be the best HTL with good thermal stability owing to its high melting temperature, it suffers from poor conductivity ($\sigma \approx 10^{-10}$ mol cm⁻¹) and hole mobility ($\mu \approx 10^{-6}$ cm² V⁻¹ s⁻¹).¹⁴⁷ Thus, different strategies have been employed to deal with these issues, as follows: (a) doping to improve the conductivity together with hole mobility and to expedite the oxidation process; (b) designing novel synthesis processes to improve the film quality, coverage, and avoid pinholes; and (c) controlling the

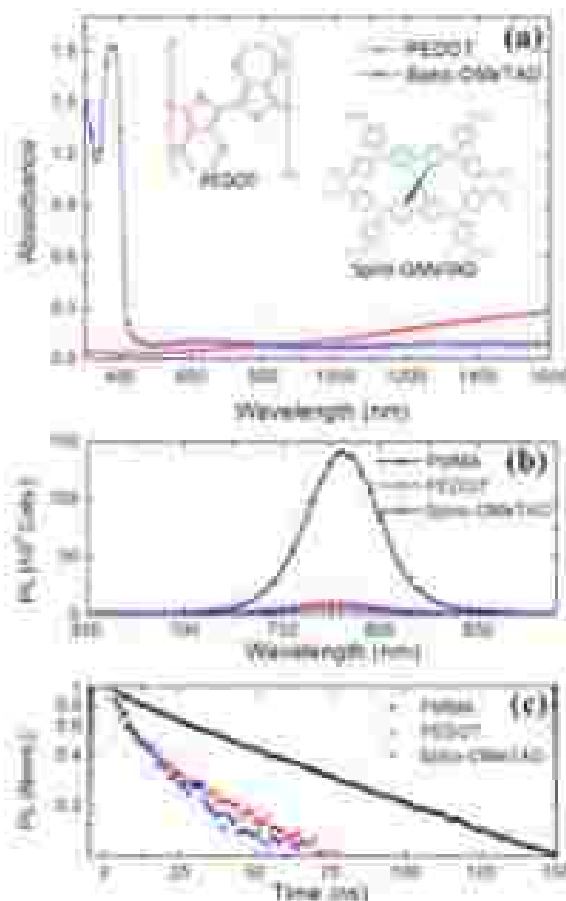


Fig. 3 (a) Absorbance spectra of ~250 nm-thick PEDOT films (red circles) and ~250 nm-thick spiro-OMeTAD films doped with Li-TFSI (blue triangles) deposited on glass. (b) Steady-state PL spectra and (c) time-resolved PL decay curves at 527 nm of perovskite films coated with PMMA (black squares), PEDOT (red circles), and spiro-OMeTAD (blue triangles) respectively.¹⁴⁸ Reprinted with permission from *J. Phys. Chem. Lett.*, 2015, 6, 3666–3672. Copyright (2015) the American Chemical Society.

defects and hydrophobic nature at the interface. Butyl pyridium (BTP) and lithium salt (LiTFSI) are the most common dopants that increase the hole mobility of spiro-OMeTAD,¹⁴⁹ but PSCs suffer from low stability with the introduction of the hygroscopic lithium. The doping of Cs₂CO₃ and CsI in spiro-OMeTAD reduced the amount of pinholes and improved its crystallinity, which protected the perovskite absorber from humidity and exhibited an efficiency of ~18%.¹⁵⁰ However, spiro-OMeTAD suffers from complicated synthesis and is ~20 times more expensive than p4d.¹⁵¹ Recently, a mixture of P66/spiro-OMeTAD and potassium persulfate (KPS)-doped spiro-OMeTAD HTLs exhibited a PCE of above 20%.^{152,153}

Likewise, poly(2,2'-ethylene dicyanophenyl)poly(styrenesulfonate) (PEDOT:PSS) is a typical choice as an HTL for inverted PSCs (p-i-n type), which shows high optical transparency in the visible region and exhibits the HOMO level of -5.3 eV, matching well with the perovskite. Unfortunately, PEDOT:PSS in its pristine form suffers from low conductivity (10^{-4} S cm⁻¹), poor hole mobility, and hygroscopic and acidic nature.^{154–156} Thus, to overcome these issues, PEDOT:PSS is either treated with a dimethylformamide (DMF)/methanol mixture or annealed with non-polar vapours of toluene, which improves its conductivity, reduces its trap state density, and facilitates smooth charge transfer at the PEDOT:PSS/perovskite interface, resulting in an improved PCE than the pristine HTL.^{157–159} Separately, the development of a PEDOT:PSS (ionium-based ink coated over the perovskite absorber in the conventional planar (n-i-p type) device architecture has attracted attention from the scientific and industrial community.¹⁶⁰ The absorbance of PEDOT films is very low in the UV-visible region, causing less parasitic losses during the second pass through the perovskite layer and resulting in an increased photocurrent with a PCE of 14.5% (Fig. 3). Further, the addition of island-like CeO₂ particles in PEDOT:PSS film served well as growth sites for perovskite absorbers with better crystallinity,¹⁶¹ resulting in a PCE of ~15%.

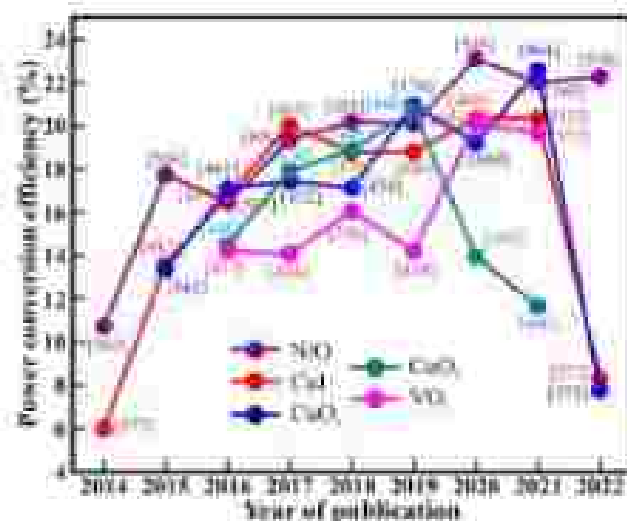


Fig. 5 Comparative study of the influential HTLs identified by year to gain the best maximum efficiency in the last decade (obtained from SC Web of Knowledge up to 22nd December 2022).¹⁶²

Table 2 (continued)

S. no.	Dye/sensitizer configuration	Method ^a	V_{oc} (V)	J_{sc} (mA cm ⁻²)	FF	PCE (%)	Year	Ref.
58	PTC/CuSCl ₂ /CH ₃ NH ₂ /PCBM/Ag	SC	1.06	13.31	0.261	16.89	2019	496
59	PTC/NiO/CH ₃ NH ₂ /PCBM/Ag	SC	1.07	20.00	0.45	15.26	2019	494
60	PTC/PTC ₂ /mp-TiO ₂ /CH ₃ NH ₂ /PCBM/Ag	PPT	0.67	14.25	0.58	8.1	2019	476
61	PTC/CuSCl ₂ /NH ₂ PC ₆₀ /PCBM/Ag	SC	1.05	10.05	0.69	14.53	2018	571
	PTC/CuSCl ₂ /NCH ₃ NH ₂ /PC ₆₀ /PCBM/Ag		1.11	22.23	0.76	18.76		
62	PTC/CuSCl ₂ /CH ₃ NH ₂ /PC ₆₀ /PCBM/Ag	SC	1.12	22.2	0.798	20.0	2017	491
63	PTC/NiO-TiO ₂ /CH ₃ NH ₂ /PCBM/Ag	S	1.01	22.78	0.75	17.6	2017	478
64	PTC/CuSCl ₂ /NH ₂ PC ₆₀ /PCBM/Ag	VI	1.20	10.5	0.68	14.7	2017	484
65	PTC/CuSCl ₂ /NH ₂ PC ₆₀ /PCBM/Ag	SC	1.01	22.5	0.719	16.4	2016	482
66	PTC/TiO ₂ /CH ₃ NH ₂ /PC ₆₀ /PCBM/Ag	SC	1.26	21.22	0.73	16.67	2016	341
67	PTC/TiO ₂ /CH ₃ NH ₂ /PC ₆₀ /Ag	TX	0.72	13.23	0.44	7.40	2016	481
68	PTC/CuSCl ₂ /NH ₂ PC ₆₀ /PCBM/Ag	SC	1.04	11.06	0.61	12.58	2015	482
69	PTC/TiO ₂ /mp-TiO ₂ /CH ₃ NH ₂ /PCBM/Ag	DC	0.82	17.8	0.62	6.0	2014	477
Copper thiocyanate (CuSCN)								
70	PTC/TiO ₂ /CH ₃ NH ₂ /PC ₆₀ /PCBM/Ag	SC	0.984	13.77	0.724	16.89	2022	586
71	PTC/TiO ₂ /CH ₃ NH ₂ /PC ₆₀ /PCBM/Ag	SC	0.92	17.2	0.63	9.1	2022	587
72	PTC/TiO ₂ /CuSCN/CuSCN/Ag	SC	1.05	12.1	0.78	9.96	2022	589
73	PTC/TiO ₂ /PC ₆₀ /MA/PC ₆₀ /PCBM/Ag	SC	1.15	23.21	0.786	21.7	2020	510
74	PTC/TiO ₂ /mp-TiO ₂ /CH ₃ NH ₂ /PC ₆₀ /PCBM/Ag	SC	0.81	13.25	0.67	11.03	2020	509
75	PTC/TiO ₂ /PC ₆₀ /MA/PC ₆₀ /PCBM/Ag	SPMP	1.074	13.37	0.756	18.74	2019	509
76	PTC/TiO ₂ /CH ₃ NH ₂ /PC ₆₀ /Ag	SC	1.068	13.85	0.763	18.57	2019	512
77	PTC/TiO ₂ /mp-TiO ₂ /PC ₆₀ /MA/PC ₆₀ /PCBM/Ag	SC	0.978	10.2	0.721	14.2	2019	504
78	PTC/CuSCN/CH ₃ NH ₂ /PC ₆₀ /PCBM/Ag	SC	1.01	18.21	0.764	14.28	2018	504
79	PTC/TiO ₂ /CH ₃ NH ₂ /PC ₆₀ /Ag	S	1.013	24.10	0.711	17.18	2017	501
80	PTC/CuSCN/CH ₃ NH ₂ /PC ₆₀ /PCBM/Ag	ED	0.92	19.43	0.68	11.89	2017	503
	PTC/CuSCN/CH ₃ NH ₂ /PC ₆₀ /PCBM/Ag		0.82	18.28	0.61	9.19		
Other inorganic HTLs								

^a SC – spin coating, CP – chemical co-precipitation method, PPT – RF sputtering, DCN – DC sputtering, SP – screen printing, ET – solvent evaporation, HT – hydrothermal, ED – electrochemical deposition, HB – ion beam sputtering, ES – electron spinning, LEP – liquid exchange process, TX – thermal evaporation, MPD – metal-organic chemical deposition, DC – drop casting, VI – vapour infiltration, PPT – powder past technique, DipC – dip coating, S – spray, and C – combustion.

Furthermore, different doping materials such as WO₃, PMR (1-ethyl-3-(3-dimethylammonium carbonyl) carbodiimide), CuSCN, and 3-(cyclohexylamino)-2-hydroxy-1-propane sulfonic acid (COPO) have been employed to achieve the required electronic and optical properties at the PTC/PTP/PCBM/perovskite interface.^{596,597,598,599}

Poly(1-hexylthiophene) (PHT) has been recommended as a promising organic HTL due to its larger-area solution processability, excellent optoelectronic properties, good hole mobility (0.1 cm² V⁻¹ s⁻¹)⁶⁰⁰ and hydrophobic surface (contact angle > 100°)⁶⁰¹ compared to other organic HTLs. Recently, Jung *et al.*⁶⁰² employed PHT as the HTL in PSCs and achieved a PCE of 23.7%, which retained 16% over a large area (25 cm²). The surface treatment of PHT using a gallium-based ligand, i.e., gallium(III) acetylacetonate (Ga(acac)₃), increased with the defects on the perovskite layer and modified the PHT/perovskite interface, resulting in PCE of 24%.⁶⁰² Moreover, the comparative performance of spiro-OMeTAD, PHT and 4-(diethylamino)benzaldehyde diethylhydrazone (DEH) as the HTL in

PSCs showed a better light absorption for PHT in the visible region compared to spiro-OMeTAD and DEH, besides, a negligible change in photon conversion efficiency.⁶⁰² In addition, other organic HTLs such as poly[10-(4-phenyl)[2,2,6,6-tetramethylpiperidinyl]amine] (PTAA),⁶⁰³ polyaniline doped with camphor sulfonic acid (PANI-CSA),⁶⁰⁴ and tetraphenyl benzenidine and MeO-triphenylamine (TPA-OMeTDA) have been employed in PSCs as alternative organic HTLs.

Although the overall efficiency of PSCs generally increases with the use of organic HTLs, their high cost, requirement of very high purity, complicated synthetic process in an inert atmosphere, hydrophilic nature of the surface, requirement of surface treatment, and long-term instability continue to be prime concerns. The stability of the devices is reduced drastically due to the use of hygroscopic dopants, which triggers the degradation of the perovskite layer. In the future, these drawbacks need to be targeted to develop effective strategies for easy processing in the ambient atmosphere.

Similar to ETAs, numerous HTAs have delivered high PCEs despite their distinct electrical, optical, and interfacial properties. HTAs have tailored the device performance and efficiency when utilized with different perovskite coating layers in PSCs. The highest efficiencies proclaimed in the most prominent recent reports from a variety of HTAs are shown in Fig. 27. The initial ~4% efficiency reported for PSCs utilizing oxides of Ni, Cu, Co, and V as HTAs to form an HTA/perovskite heterojunction has recently been boosted to ~23% (Fig. 21) with their advancement in terms of doping, co-doping, composite formation, decoupling, etc. A brief summary of the inorganic HTAs processed with various synthetic methods and their corresponding device performance parameters are provided in Table 1. Therefore, the future development of novel HTAs should be explored, focusing on enhanced PCE and sustainable and cost-effective device designs. Finally, the easy, quick, low cost and low-temperature processing of each of the layers of PSCs is an extremely important and decisive consideration for the commercialization of this technology. Therefore, alternative methods are desirable to explore for the cost-effective processing of various HTAs in the ambient atmosphere. Besides, a significant variation in the device performance can be observed when the devices are tested for a small area and scaled to large-area devices. The uniform interface over a larger area is a major concern, which affects the performance and stability of the device under testing. In this scenario, there is plenty space for investigation and finding new materials and processing methods for HTAs, to bring the commercialization of this technology one step closer.

6. Summary and outlook

The past few years have witnessed the significant role of the transport layers on the performance of PSCs and a notable uptick among the PSC devices. Some of the important features attracting researchers in this area are the cost-effective synthetic procedures, use of solar energy, engineering compatibility of ETAs and HTAs, altering the carrier mobility, band edge alignment, carrier concentration, conductivity, optical transparency, and other optoelectronic properties of the transport layers, effects of trap states, disjunct and defects on the device performance, charge transport and recombination at the HTA/perovskite interface, etc. Nevertheless, the most essential in the development of ideal transport layers.

Both organic and inorganic PSCs have shown promise to meet future energy demands. Unlike 3D perovskites predominantly suffering from instability, low-dimensional well-oriented perovskites may exhibit enhanced long-term stability. However, other supporting layers utilized with bulk and low-dimensional perovskites can alter the performance and stability of PSCs. Among the layers, the transport layers play a crucial role in maintaining and efficiently separating the photogenerated charge carriers and further boosting the solar efficiency and long-term stability. Engineering compatible transport layers with the perovskite light absorbers is essential given that the

ETAs and HTAs perform peculiar functionalities depending on the adopted device architecture. Therefore, understanding the intrinsic properties of the transport layers, namely, the electronic band edge alignment, optical transparency, charge conductivity, and charge mobility, is fundamental for developing efficient PSCs. Among the plethora of material systems that can be used as transport layers in PSCs, the ideal transport layers should also be cost-effective with easy processing. Consequently, the research trend reveals that self-organized approaches to develop distinct transport layers will complement the improvement in overall solar cell efficiency, but the search for ideal transport layers is a never-ending process.

In this review, we summarized the evolution of the transport layers analogous to the progress of PSCs based on the observations and discussions in the literature. Although the perovskite light absorbers have shown superior optoelectronic properties, the importance of the transport layers in PSCs was explained parallel to the photoanodes and electrolytes used in DSSCs. Additionally, the transport layers are distinguished based on the filled states as n-type (ETA) and p-type (HTA) to gain deeper insight. In the regular n-i-p device structures, besides the band edge and bandgap alignment with the perovskite light absorbers, the ETAs provide a template for perovskite deposition and blocking UV irradiation, which deteriorates the perovskite light absorber. The comparable electron mobilities of the ETA with perovskite absorbers and conductivity of electrons in ETAs have become the detrimental factor in avoiding charge accumulation and charge recombination at the ETA/perovskite interface. The techniques such as nanostructuring, doping, and fining used to tackle the charge accumulation and recombination were explained w.r.t. the majority reported inorganic ETAs. The role of cost-effective synthetic procedures used for developing efficient inorganic ETAs and their feasibility in large-scale production were correlated with the PCEs. Furthermore, different inorganic materials reported as ETAs for PSCs were scrutinized depending on their functionalities, synthetic procedures, and electrical and optical properties. The inorganic ETAs initially delivered an efficiency of ~1%, but reached the milestone of ~26%. Among the ETAs, employing doped TiO₂, ETAs has shown efficiencies of ~23% and created excitement among researchers. However, their application on plastic substrates is limited by their high processing temperature. Furthermore, the ZnO ETAs contribute to the deterioration of the perovskite light absorbers. Although SnO₂ ETAs have shown chemical stability and high efficiency with low-temperature processing, understanding their trap states will be beneficial to further tailor the properties towards ideal ETAs. Furthermore, ternary metal oxides need to be engineered as ETAs with better controllability over their optoelectronic properties. The scaffolding technique has been used to prevent shunting paths in PSCs, and thereby increase the V_{oc} . The diverse materials and their composites or combinations that can be used as ETAs in PSCs were discussed. Also, the extensively used organic ETAs in PSCs were compared for a comprehensive understanding. Overall, the ETAs have a direct influence on the efficiency of PSCs.

Conversely, there is an urgent need to replace the expensive hygroscopic organic HTLs employed in high-efficiency PSCs to increase their long-term stability and reduce their cost. Therefore, the importance of the HTL depending on the PSC device architecture was discussed in depth. Analogous to ETLs, HTLs perform similar functionalities w.r.t. the transport of photo-generated holes. Thus, the various techniques such as nanostructuring, doping, and forming composites used in PSCs were summarized. Inorganic HTLs such as NiO have achieved efficiency close to 22% in PSCs due to their well-aligned band edges and bandgap with perovskite light absorbers. Similarly, CoO_2 as an HTL has shown promise due to its high hole conductivity. The synthetic protocols, nanostructuring, and hole-quenching capabilities of multiple combinations of Cu-based HTLs such as CuO , Cu_2O , CuSCN , and CuI are yet to be explored for a deep understanding. Although there are several reports based on VO_2 as an HTL in PSCs, doped and nanostructured VO_2 are yet to be explored. Further, the class of materials known as delafinites was briefly presented for their controllability over hole conductivity and ease of processibility. Finally, the most commonly used organic HTLs and their influence on the efficiency and long-term stability of PSCs were compared.

Overall, all the materials reported as transport layers were scrutinized based on their optoelectronic properties, stability, durability, and charge separation at the perovskite interface with the transport layer. Furthermore, in this review, the efficiency of PSCs was comparatively evaluated based on only their transport layers. The ETLs and corresponding HTLs play a significant role in the overall performance of PSCs and vice versa. However, to gain better efficiency, the quality of the perovskite light absorber films used and the active device area should be considered during further studies. The systematic investigation of different transport layers and involved material systems interprets that an ideal HTL in the $n-i-p$ device structure should have a band-edged and bandgap alignment with the perovskite light absorbers, should possess compatible electron mobilities and conductivities with the perovskite light absorbers, and should be easily processible at low temperatures with no toxicity at a low cost. Moreover, the increased effective interface at nanostructured ETL/perovskite (mesoporous structure) can relatively enhance the free-electron transport. Further, the synthesized films should have no pinholes and be easily scaled up with high reproducibility. Conversely, ideal HTLs should perform similar functions as ETLs for hole transport depending on the device architecture.

The outlook for ideal transport layers is presented here.

(a) Tailoring the carrier mobility, band edge levels, and diffusion lengths is a promising approach to achieve ideal ETLs/HTLs.

(b) The physical vapor deposition techniques such as ALD, sputtering, and PLD are feasible for the industrial production of the transport layers. However, one should look for industrially scalable low-temperature processing techniques for the easy and reasonable deposition of ETL/HTL encompassing non-toxic and naturally abundant materials in the ambient

atmosphere. Posing low-temperature processing or synthesis can bring out uniform coating, leading to firm interfaces between different materials, which is necessary to avoid unfavourable effects at interfaces, defect sites, and interfacial losses such as light soaking effect and charge recombination.

(c) Precise engineering of the transport layer with minimum lattice mismatch, better chemical stability, excellent light management, and non-hygroscopic nature is mandatory to reduce defects and alterations in the intrinsic property of the perovskite active layer.

(d) The quest should be continued to explore new inorganic transport layers with higher p - and n -type conductivity and compatibility with the perovskite solution process deposition method. Moreover, the decoration, doping, coating, and incorporation of promising materials identified as ETL/HTL will assist in electron/hole mobility matching, enhancing the light absorption, and improving the recombination resistance, and therefore, enhance the charge extraction. Hence, various combinations of 3d transition metals, graphene, noble metal nanoparticles, organic molecules, etc. should be explored in line with further advancement.

(e) Numerical simulation and first-principles calculations can help to understand the density of states, charge accumulation, flow of charge carriers, defect density, optical transparency, optimized thickness, band edge, and photo/thermal stability of the transport layers, which will open up a new window for efficient charge separation, overcoming the issues of photo-reactivity and interface defects, and improving the sensitivity in the visible spectrum. The additional direction of theoretical work should focus on the intrinsic modification and electronic alterations at the transport layer/perovskite interface where experiments are complicated and require simulation-assisted experiments. Furthermore, theoretical methods such as first-principles calculations, DFT, and *ab initio* calculations are necessary to give directions towards less known families of materials that can be applied as transport layers of PSCs.

(f) The industrial focus is on the preparation of planar ETLs and HTLs using physical/chemical vapor deposition methods due to ease of reproducibility and commercial viability. However, mesoporous 3D nanostructures provide a larger surface area and better interface with the perovskite absorber layer, have secured a place in the best efficiency chart, and need to be explored for their utilization in the cost-effective mass production of PSCs.

(g) Among the explored nanostructures such as 0D, 1D, and 2D, 1D ETLs and HTLs provide a larger aspect ratio and deliver excellent light trapping deep inside the perovskite absorber and ensure relatively enhanced charge conduction, and hence enhanced efficiency. However, the large-area production of well-defined 1D nanostructures and their better interface with the perovskite absorber needs to be explored for pilot production.

Overall, the path for the finest optimization of the device structure and successful commercialization of PSCs entail the complete understanding of the transport layers and the charge extraction mechanism.

Author contributions

All authors contributed to conceptualization and writing of this review article.

Conflicts of interest

There are no conflicts to declare.

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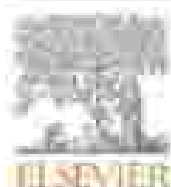
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TO WHOMSOEVER IT MAY CONCERN

Dr. Eshan Madhusudhan Desai, Assistant Professor, Department of Physics of A.P.J. Abdul Kalam University, Pune-411 004 is having a collaboration with me for carrying out research work in the Department of Physics, Savitribai Phule Pune University, Pune-411 004. I am pleased to use the research facilities such as 1.8 MeV Gamma Counter, Maximum 8 MeV electron-accelerator, Low energy electron facility, Radiation spectrometer system, Gamma ray spectrometry set in Department of Physics, Savitribai Phule Pune University for carrying out the research work. It is also confirmed by sharing the 10 MeV Gamma Counter and camera setup with Dr. Eshan Madhusudhan Desai for the better research work.


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Activation cross-section measurements and estimation of photon and neutron induced nuclear reactions for ytterbium isotopes with covariance analysis

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ABSTRACT

The cross sections of the $^{138}\text{Yb}(n,\gamma)^{139}\text{Yb}$, $^{139}\text{Yb}(n,\gamma)^{140}\text{Yb}$, $^{140}\text{Yb}(n,\gamma)^{141}\text{Yb}$, $^{141}\text{Yb}(n,\gamma)^{142}\text{Yb}$, $^{142}\text{Yb}(n,\gamma)^{143}\text{Yb}$, $^{143}\text{Yb}(n,\gamma)^{144}\text{Yb}$ and $^{144}\text{Yb}(n,\gamma)^{145}\text{Yb}$ nuclear reactions at 14.77 MeV neutron energy and the four-neighbored average cross sections of the $^{138}\text{Yb}(n,\gamma)^{139}\text{Yb}$, $^{139}\text{Yb}(n,\gamma)^{140}\text{Yb}$ and $^{140}\text{Yb}(n,\gamma)^{141}\text{Yb}$ nuclear reactions at 10 and 15 MeV bremsstrahlung endpoints energies are measured using active gamma spectroscopy. The bremsstrahlung photon-induced reactions are reported for the first time at these energies. The results are compared with the available neutron data from the EXFOR-3110, JEFF-3.3 and TENDL-2019 libraries. The theoretical model calculations are performed with the TALYS-1.95 nuclear code with parameters tuned to reproduce the measured data. The measured cross sections are in good agreement with the libraries and available data. The results are significant for the experimental nuclear medicine and reactor technology development.

1. Introduction

The cross sections of nuclear reactions are significant for nuclear technology and nuclear theory. Especially the cross sections of the neutron and photon-induced nuclear reactions are important for the development of fusion and fission reactor technology for structural, shielding, first wall and blanket materials (Cheng, 2006; Klinger et al., 2003). The cross sections are also useful for diagnostic work in the reactor environments (García et al., 2000). They are also used to probe into the nuclear structure studies, predictions of nuclear reactions and confirming the nuclear theory. Cross sections of specific reactions like (n,p) , (n,α) and (n,n) are required to estimate the neutron heating and gas formation in the reactor. The photon-induced nuclear reactions viz. (γ,n) , (γ,p) and (γ,α) are of astrophysical importance for studying the nucleosynthesis in stellar environments. Similar nucleosynthesis studies can be performed in laboratories with high flux gamma sources having energy >5 MeV. Unlike the strongly interacting particles, photons weakly interact with the nucleus. The photon-induced reactions are also used for the study of correlations of the nucleus inside heavy ($A > 50$) nuclei.

Ytterbium occurs naturally as 7 stable isotopes having mass numbers 168, 170–174 and 176 and abundances 0.123%, 1.962%, 14.016%, 21.49%, 24.103%, 22.025% and 15.962% respectively (Muller and Krauss, 2004). It has several practical applications such as doping in standard steel, laser, industrial analysis and memory devices. The isotopes ^{140}Yb and ^{141}Yb can be used as portable beta sources for medical imaging due to their relatively long half-lives of 22.019 and 4.185 days respectively (Gardner et al., 2001; Sahyoun et al., 2017). These isotopes are generally obtained from the nuclear reactors. The ^{140}Yb isotope is also known for its medical use as a high dose rate β source for brachytherapy. The medical isotope ^{140}Yb is used for targeted alpha therapy (Yamamoto et al., 2011). The ^{140}Yb isotope is produced by the β decay of ^{140}Lu isotope. The production yields of these important medical alpha-isotopes through a neutron generator and an electron accelerator can be estimated from the present work.

The cross sections of the neutron-induced nuclear reactions on ytterbium isotopes have been previously reported in the EXFOR database (Onaka et al., 2014) by few authors (Asano et al., 1972; Asano et al., 1975; Kim, 1977; Sato et al., 1981; Ishij et al., 1984; Iwamoto et al., 2012; Gajda and Makinon, 1997; Kuroda and Hara, 1991; Kim,

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et al., 1989; KUMAR et al., 1977; Liu et al., 2008; Liu et al., 2015; Pandey et al., 2014; Qaim, 2014; Sakuma et al., 1997; SATO et al., 2012; Srinivas, 1984; Vignani et al., 2015; Wills and Paul, 1990). Out of which, only four authors have reported measured cross sections in the last two decades. The reported cross sections have divergences due to the detection techniques used for measurement of gamma ray activity of the radioisotopes produced. While the (n,α) cross sections for ^{106}Ti and ^{107}Ti have been reported only by the authors (Vignani and Srinivas, 2015) and (n,α) cross sections for ^{109}Ti have been reported by only one author (Vignani and Srinivas, 2015) and (Kumar, 1977). In addition, a detailed covariance analysis is missing for these authors. The uncertainties along with the contributions of various experimental parameters are required by the data evaluators which is often missing in the existing literature. Therefore, it is necessary to measure the cross sections of these nuclear reactions more accurately with a detailed error analysis.

In the present work, we have reported the cross sections of new nuclear reactions on the titanium isotopes which comprises of (i) six nuclear reactions at 14.77 ± 0.17 MeV neutron energy and (ii) three nuclear reactions at 10 and 15 MeV bremsstrahlung neutron energies. The neutron-induced nuclear reactions are $^{106}\text{Ti}(n,\alpha)^{102}\text{Ti}$, $^{106}\text{Ti}(n,p)^{106}\text{V}$, $^{106}\text{Ti}(n,\alpha)^{102}\text{V}$, $^{106}\text{Ti}(n,\alpha)^{102}\text{Cr}$, $^{106}\text{Ti}(n,\alpha)^{102}\text{Mn}$, $^{106}\text{Ti}(n,\alpha)^{102}\text{Fe}$ and $^{106}\text{Ti}(n,\alpha)^{102}\text{Co}$, while the photon-induced nuclear reactions are $^{106}\text{Ti}(\gamma,p)^{105}\text{Ti}$, $^{106}\text{Ti}(\gamma,n)^{106}\text{Ti}$ and $^{106}\text{Ti}(\gamma,p)^{105}\text{V}$. A detailed covariance analysis has been performed for each reaction and the corresponding covariance matrix has been reported. The theoretical model calculations for these nuclear reactions are performed with the TALYS-1.95 code (Koning et al., 2007a). The results are compared with the literature data from the EXFOR database and with the evaluated nuclear data libraries ENDF/B-VII.0 (Madras et al., 2018), JEFF-3.3 (Gibson et al., 2018) and TENDL-2014 (Koning et al., 2018). The measured cross sections are in good agreement with the theoretical, evaluated and literature data.

3. Experimental details

3.1. Sample preparation

The samples of natural isotopic abundance of 99.99 pure TiO_2 in powdered form were used. A single sample consisted of 1 g of powder wrapped by a microbalance and wrapped in a polyethylene sheet. The size of each sample was 1 × 1 cm by size. Aluminium was used as a neutron flux monitor, as the samples used for neutron irradiation were covered in 99.99% pure aluminium foil of 1.8 g. Whereas, the samples used for photon-induced reactions were irradiated simultaneously with gold foils of 2.5 g each.

3.2. Neutron irradiation and measurement of γ ray activity

The neutron irradiation of the Ti sample covered in Al foil was performed at the 14 MeV Neutron Generator at Department of Physics, Central Board Secondary Education, Pune, India (Mishra, 1997). The neutrons are produced by bombarding a 175 keV deuterium ion beam on an D_2O titanium target. A typical 100 μA current of the deuterium ion beam was maintained during the irradiations. The neutron generator has a typical neutron flux of $\sim 10^{12}$ $\text{n}/\text{cm}^2/\text{sec}$. The sample was kept at 0° with respect to the incident deuterium ion beam, where the energy of the neutrons corresponds to 14.77 ± 0.17 MeV (Woodhead and Warner Activation Data, 1987). The gamma spectroscopy was performed with a tailcoated HPGe detector, having 1.5 MeV energy resolution at 1.38MeV gamma peak. The detector has a p-type Ge crystal of radius 5.18 cm and length 425 cm. The output of the detector was connected to an 88 multichannel analyser operated through a PC. The detector was shielded by lead bricks to reduce the background noise. The low-energy neutron flux having $E_n < 10$ MeV produced in the D-D reaction is about two orders of magnitude lower than the 14 MeV neutrons (Kumar et al., 2003). In, the contribution to the error is less than 2%. Similarly, the

effects of multiple scattering of neutrons and neutron flux fluctuations were neglected as the errors considered are negligibly small. The irradiation and counting was performed in following steps (i) The first sample was irradiated for a period 1500 s and then transferred within ~ 30 s to the counting room for gamma spectroscopy and counted for 1200 s (ii) The second sample was irradiated for a period 3600 s, then transferred to the counting room for gamma spectroscopy, cooled for ~ 3000 s and counted for 3600 s. The experimental details are summarized in Table 1 and the spectra of the neutron irradiated samples are shown Fig. 1(a) and (b).

3.3. Bremsstrahlung irradiation and measurement of γ ray activity

The bremsstrahlung irradiation of the Ti sample along with Au foil was performed with the medical linear accelerators at Dr. Yashwantrao Chavan Memorial Hospital, Ahmednagar, India. The Medical LINAC is generally used for medical applications, having a monoenergetic electron beam of current 5 μA and energy spread of less than 3% (A gold foil of 5 × 5 cm was set up the patient table situated 100 cm from the bremsstrahlung target). The samples were irradiated one by one for a period 1500 s by the bremsstrahlung beams of 10 MeV and 15 MeV endpoint energies. A constant dose rate of 850 ± 10 cGy/min for 10 MeV and 670 ± 10 cGy/min for 15 MeV was maintained during the irradiations. After the irradiation, the samples were brought to the control room for gamma spectroscopy with the HPGe detector. The thermal neutrons are generated around the LINAC due to photo-neutron reactions. The thermal neutron flux is lower by about four orders of magnitude than the photon flux (Vynnyk et al., 2000). Therefore the activity induced by the thermal neutrons due to the parasitic (n,γ) reactions was calculated and corresponding error was found to be less than 2%. The details of the irradiation, cooling and counting steps are given in Table 1, the spectra of 10 MeV photon irradiated Ti samples are shown in Fig. 2(a) and (b) and the spectra of 15 MeV photon irradiated Ti samples are shown in Fig. 2(a) and (b).

The nuclear spectroscopic data for the different radioisotopes produced during the neutron and bremsstrahlung irradiations, is given in Table 2 which is adopted from the EXFOR data library (Anglin, 2004, 2005; BACCH, 2002; Baratta, 2004; Brown, 1984; Furman, 2007; Kuznetsov's Group, 2001; Kuo, 1996; Koning, 2007). The gamma ray peaks used for data analysis are highlighted. The gamma ray lines used for analysis have the least consideration due to the other radioisotopes produced and are completely resolved.

3. Data analysis

3.1. Efficiency calibration and covariance analysis for HPGe detector

The HPGe detector was calibrated with a standard ^{137}Ba gamma source, before the gamma spectroscopy of the irradiated samples. The ^{137}Ba γ source has a half-life of 13.517 years (Morris, 2013) and an initial activity $A_0 = 4356.90$ Bq on 1 Oct 1999. The detection efficiency of the HPGe detector was calculated by the eq. (1)

$$\epsilon = \frac{C}{A_0 I_\gamma e^{-\lambda T}} \quad (1)$$

where, ϵ is the geometry dependent efficiency, C is the area under curve for a γ peak, A_0 is the initial activity, I_γ is the intensity of the gamma peak, λ is the decay constant, T is the time elapsed from the manufacturing of the source to the start of the counting time. As in the counting time 1600 s and λ is the correction factor for coincidence summing effect calculated with the EFFTRAN code (Vignani, 2015). The distance between the source and detector surface was 45 mm, which was incorporated in the EFFTRAN code along with other detector specifications given by the manufacturer. As the γ source has a finite geometry, the efficiency was transferred from point source geometry (ϵ_0) to the

Table 1

Experimental details of the irradiation, cooling and counting time for the reactions along with the threshold energy.

Reaction	Epitaxial Radiation	Irradiation Time (seconds)	Cooling Time (seconds)	Counting Time (seconds)	Threshold Energy E_{th} (MeV)
$^{139}\text{La}(n,\gamma)^{140}\text{La}$	24 MeV neutron source	1200	30	1200	0.11
$^{140}\text{La}(n,\gamma)^{141}\text{La}$		1200	30	1200	0.20
$^{141}\text{La}(n,\gamma)^{142}\text{La}$		3000	9000	3000	0.21
$^{142}\text{La}(n,\gamma)^{143}\text{La}$		3000	9000	3000	0
$^{143}\text{La}(n,\gamma)^{144}\text{La}$		3000	9000	3000	0.30
$^{144}\text{La}(n,\gamma)^{145}\text{La}$		3000	9000	3000	0.38
$^{139}\text{La}(n,\gamma)^{140}\text{La}$	Demarcating 20 MeV	1000	30	11	0.22
$^{140}\text{La}(n,\gamma)^{141}\text{La}$		1000	30001	3000	0.43
$^{141}\text{La}(n,\gamma)^{142}\text{La}$		1000	30001	3000	0.22
$^{142}\text{La}(n,\gamma)^{143}\text{La}$		1000	38500	3000	0.27
$^{139}\text{La}(n,\gamma)^{140}\text{La}$	Demarcating 25 MeV	1000	221	37	0.22
$^{140}\text{La}(n,\gamma)^{141}\text{La}$		1000	120403	3000	0.43
$^{141}\text{La}(n,\gamma)^{142}\text{La}$		1000	120403	3000	0.22
$^{142}\text{La}(n,\gamma)^{143}\text{La}$		1000	130003	3000	0.27

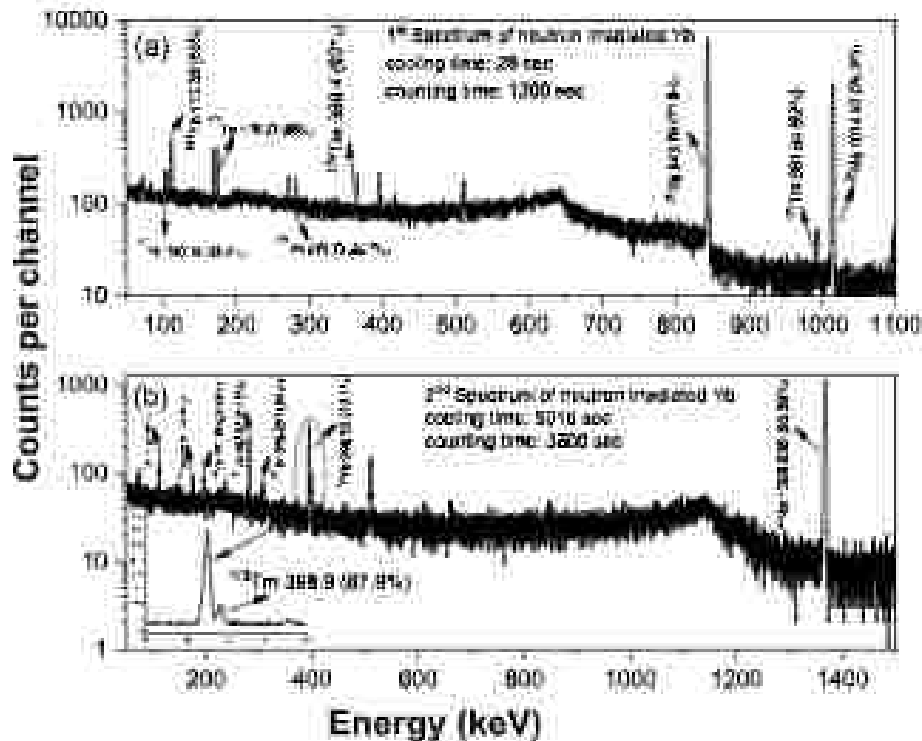


Fig. 1. (a) First gamma-ray spectrum of 24 MeV neutron irradiated Yb sample irradiated for 1200 s. (b) Second gamma-ray spectrum of 24 MeV neutron irradiated Yb sample irradiated for 3000 s.

Exit geometry (ix) with the EFFTRAN code, which reduces the efficiency approximately by 2%. The measured efficiencies at the corresponding γ energies are given in Table 3 and the calibration curve is shown in Fig. 4.

A detailed covariance analysis for the calibration efficiency of the HPGe detector was performed to determine the uncertainty in the detection efficiency, to understand the correlation between the different γ lines, to fit a polynomial curve for the efficiency and to determine the detection efficiency required for other energies of the produced isotopes. The covariance analysis was performed following the standard procedure (Gardner, 2011; Onda et al., 2017). The polynomial fit was obtained with the covariance matrix. The polynomial of the order $m - 1$ was found to be the best fit for the efficiency curve, and given by Eq. (2)

$$\text{Eff}(E) = \sum_{i=0}^{m-1} a_i E^i \quad (2)$$

where, a_i are coefficients, E_i are the energy parameters for the order m and E_i are the corresponding gamma energies in MeV. The fitting parameters for $m = 5$ are $a_0 = 0.0094$, 1.4275 , 0.2419 , 0.0799 , 0.1604 . The goodness of fit of the parameters was checked by the χ^2 test with the value of $\chi^2/(n-m) = 0.01 < 1$, for $m = 5$ and $n = 8$ (number of gamma lines used). The efficiencies for the characteristic γ energies of the radioisotopes produced were calculated, with the polynomial curve equation. The uncertainties were determined by the same technique of covariance analysis.

3.3. Calculation of correction factors for induced activity

The area under the gamma peak of the radioisotopes produced was corrected for (a) the self-absorption of the gamma rays and (b) the coincidence summing effect due to the cascade gammas. The coincidence summing factor S_c was calculated by the TrueCoinc code (Gardner, 2011). The self-absorption coefficient S_a was calculated by Eq. (3)

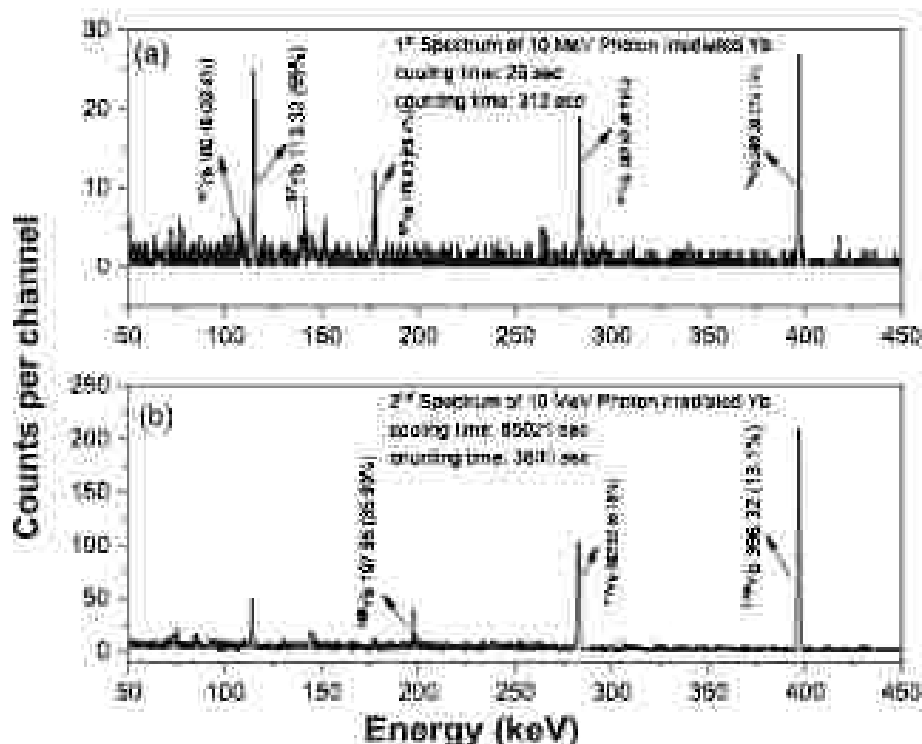


Fig. 2. (a) First gamma-ray spectrum of 10 MeV photon irradiated Yb sample irradiated for 1500 s and counted for 312 s. (b) Second gamma-ray spectrum of 10 MeV photon irradiated Yb sample irradiated for 1500 s and counted for 3611 s.

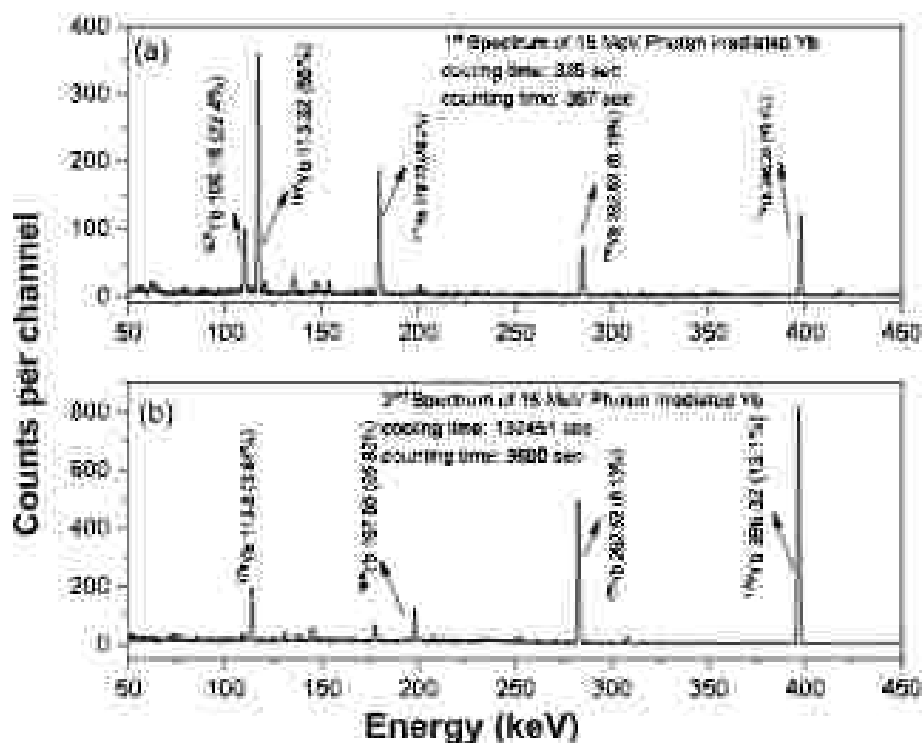


Fig. 3. (a) First gamma-ray spectrum of 15 MeV photon irradiated Yb sample irradiated for 1500 s and counted for 367 s. (b) Second gamma-ray spectrum of 15 MeV photon irradiated Yb sample irradiated for 1500 s and counted for 3600 s.

$$F = \frac{\mu}{\mu - \mu_{\text{air}}} \quad (4)$$

where μ is the linear attenuation coefficient in cm^{-1} for the sample and μ_{air} is the thickness of the sample in cm. The mass attenuation coefficient (μ/ρ)

for the constituent elements were obtained by interpolating the data from the NIST Standard Reference Database (Hubbell and Seltzer, 2004). The mass attenuation coefficient (μ/ρ) of a compound can be calculated by adding with the atomic weights of the constituent elements. The total correction factor is denoted as F , which is the product of

Table 3
The nuclear spectroscopic data for the different radioisotopes produced in the present work.

Isotope	Half-life	Decay mode	E_{γ} (keV)	I_{γ} (%)
^{176}Lu	37.3 ± 0.2 d	α (100%)	113.30	53 ± 2
			202.16	33.4 ± 0.3
			173.22	33.4 ± 0.3
^{177}Lu	6.4 ± 0.2 d	β (100%)	388.4	83 ± 4
			301.84	87 ± 4
			371.75	83.7 ± 0.3
^{178}Lu	2.4 ± 0.1 h	β (100%)	173.31	58 ± 3
			494.11	11.4 ± 0.7
			398.9	87.0 ± 0.2
^{179}Lu	7.302 ± 0.0028 d	β (100%)	461.4	5.9 ± 0.3
			300.393	84.3 ± 2
			390.901	30.9 ± 1.3
^{180}Lu	51.008 ± 0.0008 d	β (100%)	113.821	33.9 ± 1
			174.317	3.1 ± 0.3
			113.830	33.3 ± 0.30
^{180}Yb	4.200 ± 0.0013 d	β (100%)	187.8207	30.03 ± 0.03
			177.213	33.38 ± 0.11
			108.773	17.38 ± 0.09
^{181}Yb	4.200 ± 0.0013 d	β (100%)	180.123	11.38 ± 0.09
			286.328	13.1 ± 0.3
			303.123	8.13 ± 0.08
^{182}Yb	4.200 ± 0.0013 d	β (100%)	113.803	3.87 ± 0.08
			194.313	3.872 ± 0.003
			Decay scheme	
^{176}Lu	3.432 ± 0.011 d	β (100%)	842.78	71.8 ± 0.02
			514.42	33.3 ± 0.02
			171.82	0.30 ± 0.02
^{177}Lu	14.987 ± 0.011 d	β (100%)	1288.830	26.9638 ± 0.0015
			530.15	0.3015
			1734.127	26.9205 ± 0.0018
^{180}Lu	2.1005 ± 0.0008 d	β (99.9999%) (7%)	150.73	87 ± 2
			323.29	33.9 ± 1.3
			433.1	3.6 ± 0.2

Table 4
Measured detector efficiency at the corresponding gamma energies and intensities from the ^{176}Lu source and the coincidence summing correction factor.

E_{γ} (keV)	I_{γ} (%)	ϵ_{d} (%)	ϵ_{c}	ϵ_{sc} (%)
113.75	28.53	0.34	1.00	0.02 ± 0.12
346.71	1.23	0.04	1.00	0.73 ± 0.19
401.13	0.24	0.010	1.00	0.43 ± 0.18
576.20	12.09	0.00	0.99	0.47 ± 0.03
664.58	14.51	0.07	0.94	0.00 ± 0.03
1133.08	10.47	0.00	0.99	0.10 ± 0.03
1208.14	1.83	0.001	0.99	0.40 ± 0.04
1408.31	0.087	0.00	0.99	0.38 ± 0.03

ϵ_{d} -absorption coefficient ϵ_{c} and coincidence summing factor ϵ_{sc} . The self-absorption coefficient ϵ_{a} and coincidence summing factor ϵ_{c} for the produced radioisotopes are given in Table 5.

2.2. Cross section measurements and data analysis

2.2.1. Measurement of ^{176}Lu neutron-induced fission cross sections and covariance analysis

In the present work, we have measured the cross sections of six nuclear reactions at 14.77 \pm 0.17 MeV neutron energy. The cross sections of the nuclear reactions $^{176}\text{Lu}(n,\text{f})^{176}\text{Lu}$ and $^{176}\text{Lu}(n,\text{f})^{176}\text{Yb}$ were measured relative to the $^{235}\text{U}(n,\text{f})^{235}\text{U}$ monitor reaction. The 543.76 keV (71.830) peak of ^{176}Lu was used for the analysis. The cross sections of the $^{176}\text{Lu}(n,\text{f})^{176}\text{Lu}$, $^{176}\text{Lu}(n,\text{f})^{176}\text{Yb}$, $^{177}\text{Lu}(n,\text{f})^{177}\text{Lu}$ and $^{177}\text{Lu}(n,\text{f})^{177}\text{Yb}$ nuclear reactions were measured relative to the $^{235}\text{U}(n,\text{f})^{235}\text{U}$ monitor reaction. The 1163.428 keV (99.9999%) peak of ^{235}U was used for the analysis. The cross section data for the monitor reaction was adopted from the IAEA-ILibrary (Dierckx et al., 2010). The nuclear spectroscopic data of the reaction products is given in Table 3.

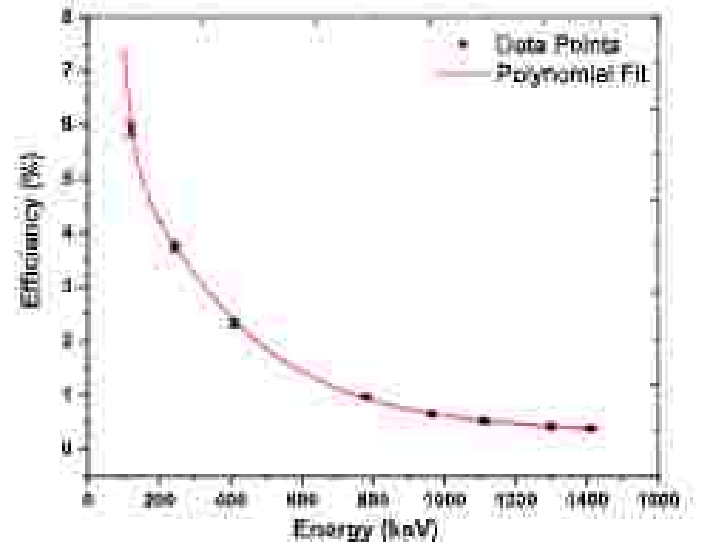


Fig. 4. The efficiency-energy calibration curve for the HPGe detector.

Table 5
Calculated values of the self-absorption coefficient ϵ_{a} and coincidence summing factor ϵ_{c} for gamma energies corresponding to the produced radioisotopes.

Isotope	E_{γ} (keV)	ϵ_{a}	ϵ_{c}	ϵ_{sc} (%)
^{176}Lu	113.30	1.8794	1.0011	0.9730
	388.4	1.0900	1.0000	1.0000
	301.8	1.0760	0.9999	1.0001
^{177}Lu	300.393	1.1223	1.0004	1.0000
	371.75075	1.0183	1	1.0158
	390.918	1.0760	0.999	1.0167
Decay scheme				
^{180}Lu	842.78	1.0000	1.0001	1.0004
	1088.830	1.0071	1	1.0073
	300.73	1.1287	1.0043	1.0044

The linear sections were estimated with the extraction eq. (4).

$$\ln \left(\frac{I_{\text{f}}(n, \text{f})^{176}\text{Lu}}{I_{\text{f}}(n, \text{f})^{235}\text{U}} \right) = \ln \left(\frac{\sigma_{\text{f}}^{176}\text{Lu}}{\sigma_{\text{f}}^{235}\text{U}} \right) + \ln \left(\frac{\epsilon_{\text{d}}^{176}\text{Lu}}{\epsilon_{\text{d}}^{235}\text{U}} \right) + \ln \left(\frac{I_{\text{f}}^{235}\text{U}}{I_{\text{f}}^{176}\text{Lu}} \right) \quad (4)$$

where, the subscripts Lu and U correspond to the parameters belonging to lutetium and uranium elements respectively. θ is the reaction cross section, F is the particle correction factor mentioned in Table 6, G is the true outer gamma peak, M is the mass of the sample, w is the isotopic abundance, A is the atomic mass, ϵ is the detector efficiency at corresponding gamma energy, I_{f} is the gamma peak intensity and t_{c} is the counting time given in eq. (3).

$$\ln \left(\frac{I_{\text{f}}(n, \text{f})^{176}\text{Lu}}{I_{\text{f}}(n, \text{f})^{235}\text{U}} \right) = \ln \left(\frac{\sigma_{\text{f}}^{176}\text{Lu}}{\sigma_{\text{f}}^{235}\text{U}} \right) + \ln \left(\frac{\epsilon_{\text{d}}^{176}\text{Lu}}{\epsilon_{\text{d}}^{235}\text{U}} \right) + \ln \left(\frac{I_{\text{f}}^{235}\text{U}}{I_{\text{f}}^{176}\text{Lu}} \right) \quad (5)$$

where, k is the decay constant and τ_1 , τ_2 and τ_3 are the irradiation, cooling and counting time respectively.

The total uncertainty in the measured cross sections is the root of sum of squares of the partial uncertainties due to each attribute in the equation (4). The partial uncertainty in the cross sections can be calculated by differentiating the eq. (4) with respect to each attribute. The partial uncertainty due to the τ_1 , τ_2 and τ_3 are negligible, as the uncertainty in t_{c} can be calculated by differentiating eq. (3) with k . The partial uncertainties due to each attribute in the eq. (4) are given in Table 7, where $\theta = \sigma_{\text{f}}^{176}\text{Lu} / \sigma_{\text{f}}^{235}\text{U}$, the ratio of the efficiencies. The correlations between every attribute is also given in the same table. This correlation (ρ or -1) is used to establish the micro-correlation matrix for calculating the correlation coefficients of the measured cross sections of

Table 6

The hypothetical combination (H) due to various the parameters used to calculate the weighted average cross sections for photon-induced reactions.

Reaction	E _γ	σ _{tot}	σ _n	σ _p	σ _α	σ _γ	σ _{np}	σ _{pp}	σ _{pn}	σ _{αn}	σ _{αp}	σ _{αα}	σ _{αγ}	σ _{αn}	σ _{αp}	Total
¹⁸⁷ Re(γ,n) ¹⁸⁶ Re	14.77MeV	0.99	11.24	0.00	0.40	0.40	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	14.73
¹⁸⁷ Re(γ,p) ¹⁸⁶ Re		0.99	14.20	1.85	0.00	0.40	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	16.29
¹⁸⁷ Re(γ,α) ¹⁸³ Re		0.40	4.00	1.80	2.27	1.40	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	7.27
¹⁸⁷ Re(γ,γ) ¹⁸⁷ Re		0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00
¹⁸⁷ Re(γ,n) ¹⁸⁶ Re	13.16MeV	0.88	1.20	0.10	0.40	1.40	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	3.28
¹⁸⁷ Re(γ,p) ¹⁸⁶ Re		0.88	0.00	0.00	0.00	1.40	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.88
¹⁸⁷ Re(γ,α) ¹⁸³ Re		0.00	1.40	0.00	0.00	1.40	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	0.00	2.80
GM(1,2)		0	0	0	0	1	0	0	0	0	0	0	0	0	0	1
GM(1,3)		0	0	0	0	1	0	0	0	0	0	0	0	0	0	1
GM(1,4)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,5)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,6)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,7)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,8)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,9)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,10)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,11)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,12)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,13)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,14)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,15)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,16)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,17)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,18)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,19)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
GM(1,20)		0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

nucleus (specific level optical model) (KJ 18600007) (Ewing and DeLeonis, 2013), the two-component matrix model (Loring and Dujovnie, 2014) for calculating pre-equilibrium contribution and the Feynman transition coefficients for EI transition are given by the Kapotek-Gil generalized Lorentian (Kapotek and Gil, 1993). Moreover, TEMPLE-2019 calculations incorporate the Sack-shifted Fermi Gas model (Sack et al., 1973) for nucleus level densities and other default parameters.

In this work, we have performed the calculations for all the 304 possible combinations for 5 nucleus level density models, 2 nuclear-nucleus optical model potentials, 4 pre-equilibrium models and 8 gamma-ray strength functions. The input parameters were optimized for the theoretical calculations to closely match the current measured cross sections. The nuclear parameter used in present work for the calculations of the neutron-induced reactions are given in Table 7. The different parameters given in Table 7 refer to the following models:

- (Model 1: Sack-shifted Fermi Gas model (Sack et al., 1973)
- loring2 = Global optical model of Loring and DeLeonis (2013)
- loring3 = Level optical model of Ewing and DeLeonis (2013)
- preequilib 1 = Exciton Model: Analytical Transition rates (Loring and Dujovnie, 2014)
- preequilib 2 = Exciton Model: Numerical Transition rates (Ewing and DeLeonis, 2013)
- preequilib 3 = Exciton Model + optical model (Loring and Dujovnie, 2014)

The following eight gamma strength functions are available in the TALYS-1.95 code:

- GSF 1: Generalized Lorentian of Ewing and Gil (1993)

Table 7

Input parameters of the TALYS-1.95 code used for neutron-induced reactions

Reaction	TALYS-1.95 Default Parameters used			
	Nucleus Level Density	Pre-equilibrium GSF	Pre-equilibrium	Gamma Ray Strength Function
¹⁸⁷ Re(γ,n) ¹⁸⁶ Re	Model 3	loring3	preequilib 1	GSF 1
¹⁸⁷ Re(γ,p) ¹⁸⁶ Re		loring3	preequilib 2	GSF 1
¹⁸⁷ Re(γ,α) ¹⁸³ Re		loring3	preequilib 3	GSF 1
¹⁸⁷ Re(γ,γ) ¹⁸⁷ Re		loring3	preequilib 3	GSF 1
¹⁸⁷ Re(γ,n) ¹⁸⁶ Re		loring3	preequilib 1	GSF 1
¹⁸⁷ Re(γ,p) ¹⁸⁶ Re		loring3	preequilib 2	GSF 1

- GSF 2: Generalized Lorentian of Sack and Aust (Aust, 1962; Ewing, 1971)
- GSF 3: Hauser-Feshbach-Spempin random-phase approximation (Hauser et al., 2009)
- GSF 4: Hauser-Feshbach-Spempin random-phase approximation (Ewing et al., 2010)
- GSF 5: Hybrid model of Gemely (1998)
- GSF 6: Gemely Independent NPE (Gemely, 1997)
- GSF 7: T-dependent NPE (Gemely, 1994)
- GSF 8: Gogny D1K NPE + GSA Gemely (1998)

The reaction barriers for the ¹⁸⁷Re(γ,n)¹⁸⁶Re, ¹⁸⁷Re(γ,p)¹⁸⁶Re and ¹⁸⁷Re(γ,α)¹⁸³Re nuclear reactions induced by photons from threshold to 20 MeV are calculated by the TALYS-1.95 code. In addition, the cross section data for the ¹⁸⁷Re(γ,n)¹⁸⁶Re nuclear reaction was calculated with the default set of parameters in TALYS-1.95. The cross section calculations for the photon-induced reactions were performed with the default constant temperature model and the Fermi gas model for nucleus level densities, the Hauser-Feshbach mechanism for compound nucleus reactions, level optical model for the nucleus-nucleus optical potentials and eight gamma strength functions (GSF) available in the TALYS-1.95 code. There is negligible variance in the cross sections due to the choice of the parameters other than GSFs. The results of the calculations with eight GSFs are compared with the TEMPLE-2019 data.

4. Results and discussion:

We have measured the cross sections of six nuclear reactions for the Re isotopes induced by 14.77 MeV neutrons. The measured cross sections of neutron-induced reactions are compared with the experimental data from the ECFE database (Dain et al., 2010) and the evaluated

evaluate data libraries ENDF-B-VIII.0 (Brown et al., 2018), JEFF-3.3 (Chang et al., 2017) and TENDL-2019 (Koning et al., 2019). We have normalized the earlier reported cross sections from ENDF, with the data from JEFF-3.3 (Chang). The normalization was performed to avoid unreasonable comparison of the data points. Due to normalization, the cross sections vary from 1 to 10%. The details about the normalizations of every author are discussed in the following sub-sections. For the authors whose monitor information is not available, no normalization was performed.

We have measured the cross sections of three nuclear reactions for the γ -rays induced by 10 MeV and 15 MeV bremsstrahlung photons, relative to the $^{27}\text{Al}(n,\gamma)^{28}\text{Al}$ reaction. The measured average cross sections of bremsstrahlung photon-induced reactions or photofission reactions are compared with the cross sections calculated with TALYS-1.95 code. The TALYS-1.95 calculations were performed for eight gamma strength functions. Theoretical flux-weighted average cross section was calculated for all the gamma strength functions. The theoretical flux-weighted average cross sections are compared with the evaluated data available only from the TENDL 2019 library. The experimental data reported in the ENDF database for $^{249}\text{Pu}(n,\gamma)^{250}\text{Pu}$, $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ and $^{253}\text{Cf}(n,\gamma)^{254}\text{Cf}$ reactions is available only from two authors (Krauss, 2014; Yagusa and Sudo, 2018), at 14 MeV and 15 MeV bremsstrahlung endpoint energies.

The measured cross sections of the neutron and bremsstrahlung photon-induced reactions for the photofission isotopes are given in the Table 8 and Table 9 respectively. The cross sections in these tables are presented along with their uncertainties and correlation coefficients. The correlation matrix describes the degree to which the different cross sections are correlated. There exists a correlation in the measured cross sections, due to the models and parameters used to estimate the identification, gamma flux and monitor reactions used. The cross sections are fully correlated through the efficiencies at the same detector was used for the measurements. The correlation between the first two and the rest four neutron induced reactions and first three and the rest three photon induced reactions is very low as they correlated through very few parameters. The correlation between the different neutron induced reactions varies from 1% to -7 %. Whereas, the correlation between the different photon induced reactions varies from 11% to -50 %, because of more uncertainty contribution due to the correlated parameters.

In the following subsections we have discussed each neutron and bremsstrahlung photon-induced reaction in detail.

4.1 Neutron-induced reactions

4.1.1 The $^{249}\text{Pu}(n,\gamma)^{250}\text{Pu}$ reaction

In Fig. 6 we have shown the measured cross section for the $^{249}\text{Pu}(n,\gamma)^{250}\text{Pu}$ reaction relative to the $^{27}\text{Al}(n,\gamma)^{28}\text{Al}$ reaction, at 14.77 MeV neutron energy. The data is given along with the literature data from the ENDF database, the evaluated cross sections from the

Table 8
Measured cross sections of the neutron-induced reactions for photofission isotopes along with uncertainties and correlation coefficients

Reaction	Cross section (mb)	Correlation Coefficients					
$^{249}\text{Pu}(n,\gamma)^{250}\text{Pu}$	1002.0 ± 141.79	1					
	278 ± 0.28	0.94	1				
	433 ± 0.42	0.908	0.997	1			
	112 ± 0.28	0.908	0.998	0.91	1		
	1002.0 ± 121.59	0.91	0.998	0.99	0.91		
$^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$	1241.04 ± 128.08	0.98	0.998	0.94	0.94	0.97	1

ENDF-B-VIII.0, JEFF-3.3, TENDL-2019 libraries and evaluated TALYS-1.95 data.

The reported cross sections agree with the evaluated data at 14.77 MeV energy within the given uncertainty. It also agrees with the cross sections of the authors (Bau, 1971; Giam, 1974; Chang et al., 1988; Yagusa et al., 2020) and (Lee et al., 2013). Whereas, the data for the authors (Bau et al., 1991) disagrees with our work and the evaluated cross sections.

The cross sections of the authors (Bau, 1971; Giam et al., 1991) and (Giam, 1974) have been normalized with monitor reaction cross section data from the JEFF-3.3 data for the $^{27}\text{Al}(n,\gamma)^{28}\text{Al}$ reaction and for the authors (Krauss et al., 2014) the cross section is normalized for the $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ reaction. For the authors (Lee et al., 2013) cross section is normalized for both $^{27}\text{Al}(n,\gamma)^{28}\text{Al}$ and $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ reactions. After normalization the values vary from 4 to 7 % for (Bau, 1971; Giam, 1974) and (Krauss et al., 2014), for others it varies less than 1%. The normalization is performed for authors (Chang et al., 1988) as no monitor details are available.

We have reported the cross section of 1002.0 ± 141.79 mb for this reaction. Where, the total uncertainty is 7.43%, major uncertainty contribution is from the monitor reaction cross section 1.48%, counting statistics 0.87%, gamma peak intensity 0.45%, 1-3% due to less abundant energy ^{248}Pu and detector efficiency 1.58% as it is a low energy 112.55 keV gamma peak.

4.1.2 The $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ reaction

In Fig. 7 we have shown the measured cross section for the $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ nuclear reaction relative to the $^{27}\text{Al}(n,\gamma)^{28}\text{Al}$ reaction, at 14.77 MeV energy, along with the literature data and evaluated data from the ENDF-B-VIII.0, JEFF-3.3 and TENDL-2019 libraries.

The cross section data does not agree with the evaluated data from the ENDF-B-VIII.0, JEFF-3.3 and TENDL-2019 data libraries for most of the authors along with us. The TALYS-1.95 calculations with the modified parameters agree with the literature and our data. The cross sections of the authors (Giam and Muller, 1967; Sauer et al., 1987; Lee et al., 2006; Giam et al., 2017) and Lee et al., 2013) agree with our work. Whereas, the authors Bau (1971), Andon et al. (1982), Giam et al., 1988, Chang et al., 1990) and (Fang et al., 2014) slightly disagree with the current work.

The authors (Bau, 1971; Giam et al., 1987) and Chang et al., 1988) have used the $^{27}\text{Al}(n,\gamma)^{28}\text{Al}$ monitor reaction, which has been normalized with the JEFF-3.3 data. Other authors (Giam and Muller, 1967) have used the $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ reaction, the authors (Andon et al., 1982) have used the $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ reaction, the authors (Sauer et al., 1988) have used the $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ reaction, the authors (Giam et al., 2017) have used the $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$ reaction, which have been normalized. The data of the authors (Lee et al., 2013) have been normalized with respect to both reactions $^{27}\text{Al}(n,\gamma)^{28}\text{Al}$ and $^{252}\text{Cf}(n,\gamma)^{253}\text{Cf}$. Normalization is not performed for (Fang et al., 2014) as they have used long counters for flux monitoring and no monitor details are available for (Chang et al., 1990) and (Lee et al., 2006).

We have reported 1241.0 ± 128.08 mb cross section for this reaction. The major uncertainties or uncertainty are the monitor cross section 1.45%, counting statistics 1.36%, gamma peak intensity 0.34% and k_p factor of sample 1.29% due to their half-life of product. The total uncertainty is 12.21%.

4.1.3 The $^{253}\text{Cf}(n,\gamma)^{254}\text{Cf}$ reaction

In Fig. 8 we have shown the measured cross section for the $^{253}\text{Cf}(n,\gamma)^{254}\text{Cf}$ nuclear reaction relative to the $^{27}\text{Al}(n,\gamma)^{28}\text{Al}$ reaction, at 14.77 MeV energy, along with the literature data and the evaluated data from the ENDF-B-VIII.0, JEFF-3.3 and TENDL-2019 libraries.

The measured cross sections do not agree with any of the evaluated data and agrees only with the TALYS-1.95 calculations performed with the modified input parameters. Data of the authors (GATO et al., 1983) agrees with the JEFF-3.3 and TENDL-2019 calculations. Other authors

Table 9

Measured cross sections of the bombarding photon-induced reactions for various energies along with uncertainty and reaction coefficients

Reaction	Energy (MeV)	Measured Cross section (mb)	Reaction Coefficients					
$^{174}\text{Yb}(\gamma,n)$	0.20 to 30	40.00 ± 0.40	1					
$^{174}\text{Yb}(\gamma,p)$	0.40 to 30	20.00 ± 0.60	0.11	0				
$^{174}\text{Yb}(\gamma,\alpha)$	0.20 to 30	40.00 ± 0.20	0.03	0.00	1			
$^{174}\text{Yb}(\gamma,n,2n)$	0.20 to 30	104.70 ± 11.07	0.0000	0.0000	1.0000	1		
$^{174}\text{Yb}(\gamma,n,p)$	0.40 to 30	102.00 ± 10.00	0.0000	0.0000	1.0000	0.00	1	
$^{174}\text{Yb}(\gamma,n,\alpha)$	0.20 to 30	102.00 ± 0.00	1.0000	1.0000	0.0000	0.00	0.00	1

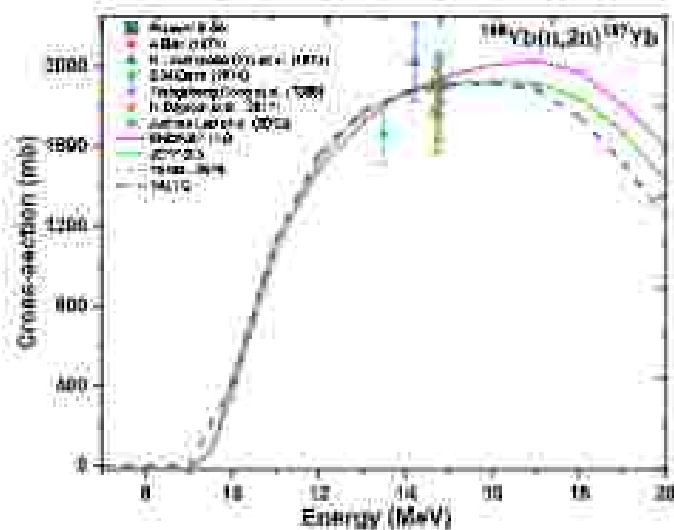


Fig. 4. Comparison of present experimental $^{174}\text{Yb}(n,2n)^{173}\text{Yb}$ reaction cross section with literature data, evaluated data and TALYS-1.95 calculations.

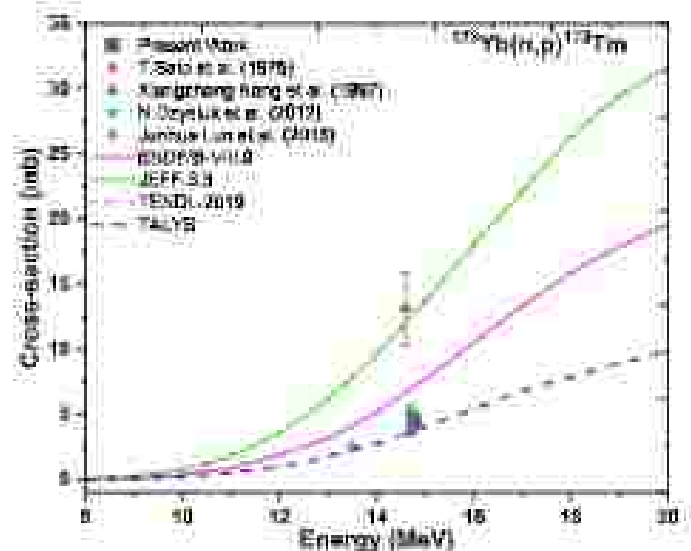


Fig. 5. Comparison of present experimental $^{174}\text{Yb}(n,p)^{173}\text{Tm}$ reaction cross section with literature data, evaluated data and TALYS-1.95 calculations.

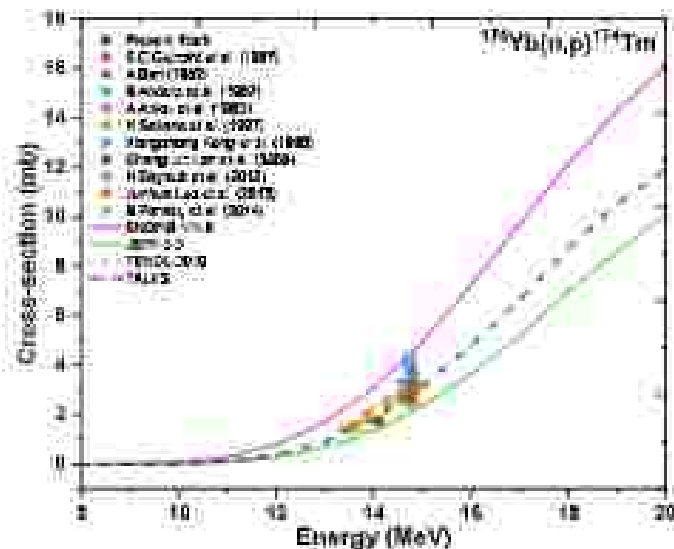


Fig. 6. Comparison of present experimental $^{174}\text{Yb}(n,p)^{173}\text{Tm}$ reaction cross section with literature data, evaluated data and TALYS-1.95 calculations.

(Yang et al., 1990), (Dewald et al., 2017) and (Sun et al., 2019) agree with the present data point and the TALYS-1.95 calculated curve. Disagreement observation is visible for all the authors mentioned in the 4.1.1 and 4.1.2 sections except for the authors (Sato et al., 1978) have used $^{174}\text{Yb}(n,\alpha)^{173}\text{Er}$ reaction and we have normalized it with the ENDF-V data.

Our cross section for this reaction is $4 \pm 0.3 \pm 0.1$ mb, which is 20% total uncertainty. The major uncertainty is identified due to the counting

reactant (3.47%), as the gamma peak of product ^{173}Tm (208.6 keV) is very close to gamma peak of ^{173}Yb (204.320 keV) produced in (n,2n) reaction with ^{174}Yb isotope.

4.1.4 The $^{174}\text{Yb}(n,\alpha)^{173}\text{Er}$ reaction

The Fig. 7 shows the cross section of the $^{174}\text{Yb}(n,\alpha)^{173}\text{Er}$ reaction along with the literature data from the ENDF database and the evaluated data from the ENDF, B-VII.0, JEFF-3.3 and TENDL-2019 libraries.

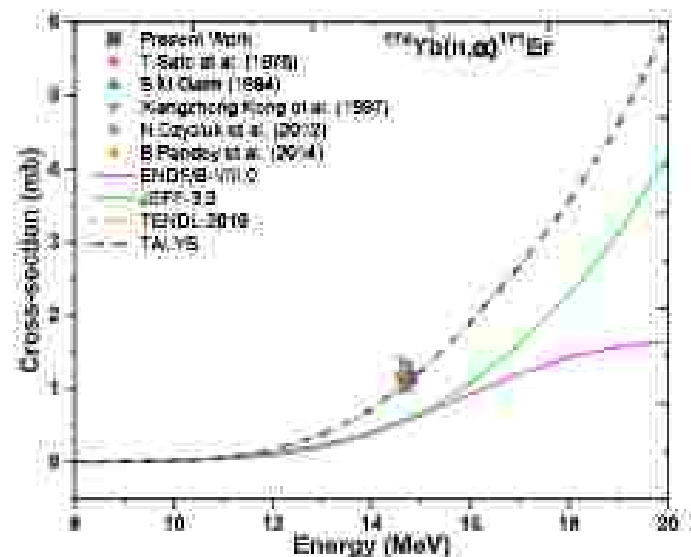


Fig. 7. Comparison of present experimental $^{174}\text{Yb}(n,\alpha)^{173}\text{Er}$ reaction cross section with literature data, evaluated data and TALYS-1.95 calculations.

The literature data and our data do not agree with the ENDF B-VIII.0 and JEFF-3.1 evaluations. The literature data along with our data agree with the TENDL-2019 and TALYS-1.95 calculations. The cross sections of the authors (GATO *et al.*, 1973), (Qaim, 1974), (Gang *et al.*, 1990), (Sharma *et al.*, 2012) and (Sinha *et al.*, 2014) agree with our data within the uncertainties. The normalization information is similar to the 4.1.1 and 4.1.2 sections for all the authors.

We have reported cross section value of 1.15 ± 0.08 mb for this reaction with 15.6% uncertainty. The major part of uncertainty comes from counting statistics (4.8%) as the reaction is less probable and gamma peak intensity of product is low.

4.1.5. The $^{177}\text{Yb}(n,2n)^{176}\text{Yb}$ reaction

Fig. 11 shows the cross section of the $^{177}\text{Yb}(n,2n)^{176}\text{Yb}$ reaction along with the literature data from the EXFOR and the evaluated data from the ENDF B-VIII.0, JEFF-3.1 and TENDL-2019 libraries.

Our cross section matches with the ENDF B-VIII.0 data and TALYS-1.95 data with modified input parameters and disagrees with the JEFF-3.1 and TENDL-2019 evaluations. The data also agrees with the cross sections of authors (Gang *et al.*, 1990), (Qaim, 1974), (Gang *et al.*, 1990) and (Lee *et al.*, 2002), slightly disagrees with the authors (Qaim, 1974) and (Sharma *et al.*, 2012) and strongly disagrees with cross sections of the authors (Singh *et al.*, 2018). The normalization information is similar for all the authors as mentioned in 4.1.1 and 4.1.2 sections except for the authors (Gang *et al.*, 1990) have used the $^{241}\text{Am}(n,\alpha)^{237}\text{Np}$ monitor reaction and (Singh *et al.*, 2018) have used the $^{241}\text{Am}(n,\alpha)^{237}\text{Np}$ reaction which has been corrected with the ENDF-B data.

We have reported cross section value of 2163.81 ± 135.54 mb of this reaction with 6.3% total uncertainty. The major contribution to uncertainty are counting statistics 5.1% and detector efficiency 0.55% due to the 147.95 keV peak.

4.1.6. The $^{177}\text{Yb}(n,2n)^{176}\text{Yb}$ reaction

In Fig. 12 we have shown the cross section of the $^{177}\text{Yb}(n,2n)^{176}\text{Yb}$ reaction with the experimental cross sections from the EXFOR database and the evaluated data from the ENDF B-VIII.0, JEFF-3.1 and TENDL-2019 libraries.

Our reported cross section along with most of the literature data does not match with the evaluated data from the ENDF B-VIII.0, JEFF-3.1 or TENDL-2019 evaluations. Moreover, the measured cross section and the literature data does not match with any of the model calculations for TALYS-1.95 code. We have plotted the measured cross section data with the closest fitting curve.

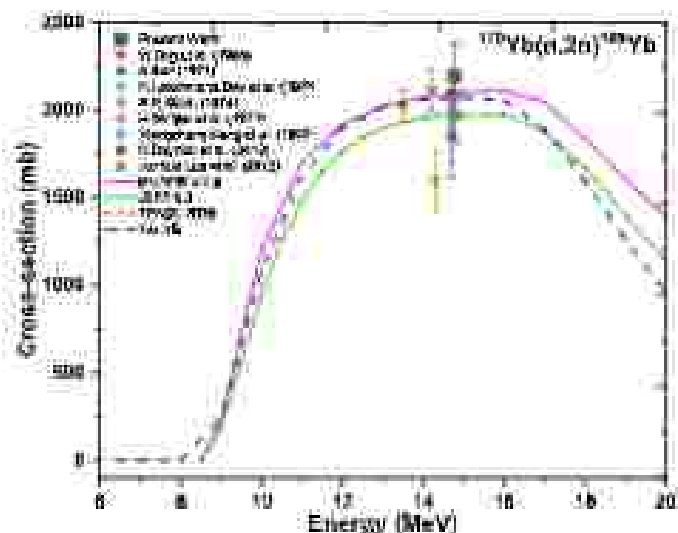


Fig. 10. Comparison of present experimental $^{177}\text{Yb}(n,2n)^{176}\text{Yb}$ reaction cross section with literature data, evaluated data and TALYS-1.95 calculations.

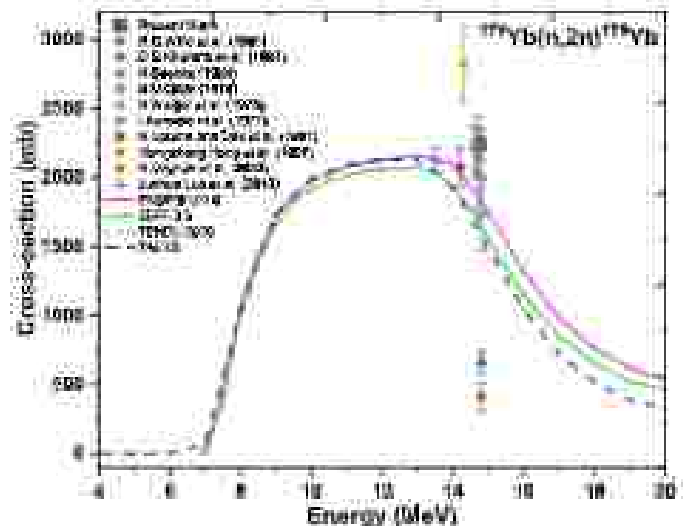


Fig. 11. Comparison of present experimental $^{177}\text{Yb}(n,2n)^{176}\text{Yb}$ reaction cross section with literature data, evaluated data and TALYS-1.95 calculations.

The cross section data of the authors (Qaim, 1974), (Qaim *et al.*, 1977), (Gang *et al.*, 1990), (Sharma *et al.*, 2012) and (Lee *et al.*, 2002) agree with our value. The cross sections of (Singh and Park, 1982), (Qaim and Nara, 1981), (Qaim, 1994) and (Singh *et al.*, 1978) strongly disagree with our value. The negative cross section data reported in last 20–20 years for all the authors disagree with the evaluated cross sections from all the data libraries and nuclear model calculations with the TALYS-1.95 code. This calls for some refinement in the nuclear model calculation of cross sections for this reaction.

The normalization data is same as 4.1.1 and 4.1.2 sections for all the authors except for the authors (Singh and Park, 1982) have used the $^{241}\text{Am}(n,\alpha)^{237}\text{Np}$ reaction (Qaim and Nara, 1981), have used the $^{241}\text{Am}(n,\alpha)^{237}\text{Np}$ reaction (Gang *et al.*, 1990) and (Singh *et al.*, 1977) have used the $^{241}\text{Am}(n,\alpha)^{237}\text{Np}$ reaction. The cross sections for all the authors have been normalized with the ENDF-B data library.

We have reported the cross section value of 2241.04 ± 100.48 mb for this reaction with 4.5% total uncertainty, where the major contribution is coming from only counting statistics 5.5%.

4.2. Bremsstrahlung photon-induced reactions at 10 and 55 MeV bremsstrahlung endpoint energy

The Figs. 13–14 show the cross section data for the $^{177}\text{Yb}(\gamma, n)^{176}\text{Yb}$, $^{177}\text{Yb}(\gamma, p)^{176}\text{Yb}$ and $^{177}\text{Yb}(\gamma, \alpha)^{174}\text{Yb}$ nuclear reaction for monoenergetic photons from reaction threshold to 55 MeV energy calculated with the TALYS-1.95 code and the evaluated data from the TENDL-2019 library. The TALYS-1.95 calculations are performed for eight Gamow-Teller Functions (GSF) available in the code, named as GSF1 to GSF8. The effective cross section is calculated for all the eight gamow strength functions and is given in Table 2. No literature data is available for these reactions at 10 and 55 MeV bremsstrahlung endpoint energies to compare. The calculated effective cross sections cannot be graphically compared with the TALYS-1.95 curves because TALYS-1.95 evaluates the cross sections for monoenergetic photons, while, we have calculated the flux weighted average cross sections.

4.2.1. The $^{177}\text{Yb}(\gamma, n)^{176}\text{Yb}$ reaction

Fig. 13 shows the cross section for the $^{177}\text{Yb}(\gamma, n)^{176}\text{Yb}$ reaction for GSF1 to GSF8 along with the TENDL-2019 data. Only the authors (Yagnik and Sinha, 2018) have reported the cross section for this reaction at 14 MeV bremsstrahlung endpoint energy. They have reported 105 ± 21 mb cross section at 14 MeV bremsstrahlung endpoint energy.

We have reported the average cross section value of 43.99 ± 8.45 mb

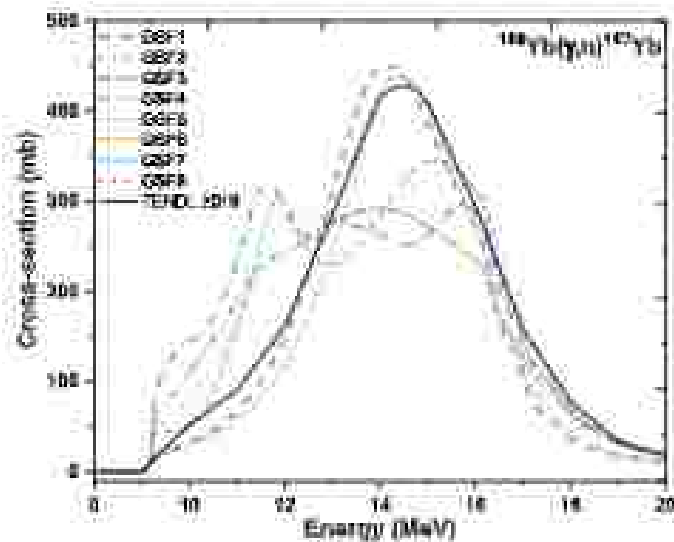


Fig. 11. Comparison of the $^{176}\text{Yb}(p,n)^{176}\text{Yb}$ reaction cross section with the TENDL 2015 data and TALYS-1.05 simulation for eight gamma strength functions.

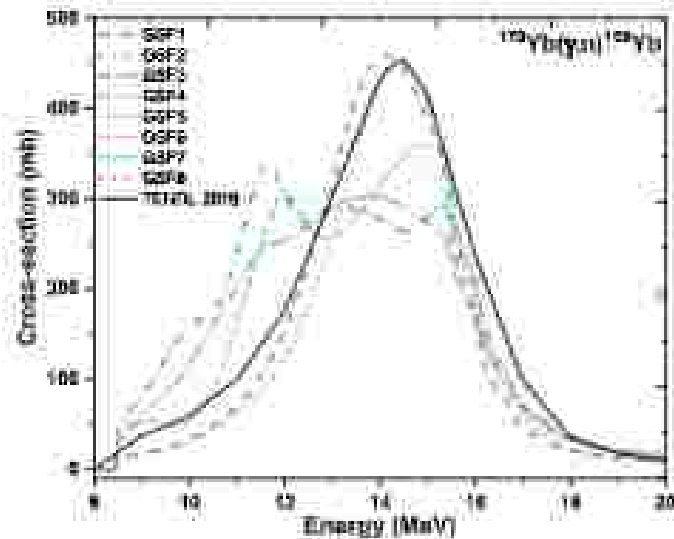


Fig. 12. Comparison of the $^{176}\text{Yb}(p,n)^{176}\text{Yb}$ reaction cross section with the TENDL 2015 data and TALYS-1.05 simulation for eight gamma strength functions.

and 154.73 ± 11.57 mb for 10 and 15 MeV bremsstrahlung endpoint energies respectively. The major contribution to the uncertainty is due to the counting statistics (11.00% and 2.5%) of sample counting of reaction (5.91% and 2.00%) respectively for 10 and 15 MeV energies and due to the gamma peak intensity (3.40%) and abundance of the sample (2.43%). The theoretical effective cross section calculated from TALYS-1.05 varies from 27.23 to 181.05 mb for 10 MeV and 113.16 to 206.07 mb for 15 MeV energy.

4.2.2. The $^{176}\text{Yb}(p,n)^{176}\text{Yb}$ reaction

Fig. 13 shows the cross section for the $^{176}\text{Yb}(p,n)^{176}\text{Yb}$ reaction for GSF1 to GSF8 along with the TENDL 2015 data. Only the authors (Vijaya and Sathya, 2020) have reported the cross section of 117 ± 11 mb for the reaction at 14 MeV bremsstrahlung endpoint energy.

We have reported the average cross section of 25.31 ± 3.86 mb and 152.82 ± 15.25 mb at 10 and 15 MeV bremsstrahlung endpoint energies respectively. The major contribution to the uncertainty is due to the

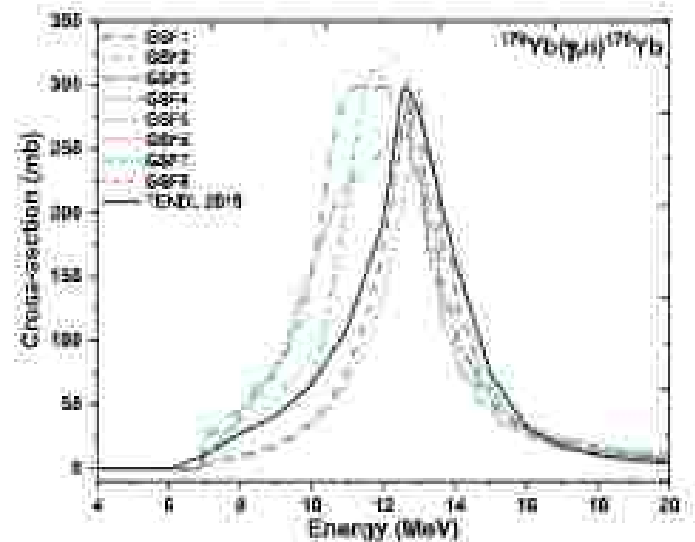


Fig. 14. Comparison of the $^{176}\text{Yb}(p,n)^{176}\text{Yb}$ reaction cross section with the TENDL 2015 data and the TALYS-1.05 simulation for eight gamma strength functions.

counting statistics (4.00% and 8.00% of sample for 10 and 15 MeV energies respectively). The theoretical effective cross section calculated from the TALYS-1.05 varies from 24.87 to 34.22 mb for 10 MeV and 101.94 to 249.49 mb for 15 MeV energy.

4.2.3. The $^{176}\text{Yb}(p,n)^{176}\text{Yb}$ reaction

Fig. 14 shows the cross section for the $^{176}\text{Yb}(p,n)^{176}\text{Yb}$ reaction for GSF1 to GSF8 along with TENDL 2015 data. Only the authors (Vijaya and Sathya, 2020) have reported the cross section of 113 ± 34 mb for the reaction at 14 MeV bremsstrahlung endpoint energy and the author (Sathya, 2021) has given the (1.0) fold ratios for 22 MeV bremsstrahlung endpoint energy.

We have reported the average cross section of 45.61 ± 5.11 mb and 152.63 ± 8.21 mb at 10 and 15 MeV bremsstrahlung endpoint energies respectively. The major contribution to the uncertainty is due to the counting statistics (4.00% and 2.45% of sample for 10 and 15 MeV energies respectively). The theoretical effective cross section calculated from the TALYS-1.05 varies from 11.45 to 46.66 mb for 10 MeV and 54.02 to 121.76 mb for 15 MeV energy.

5. Conclusions

We have reported the cross sections of six neutron-induced reactions and the five weighted average cross sections of six bremsstrahlung photon-induced reactions in the present work. The uncertainties in the measured data have been determined by a detailed covariance analysis. The uncertainties for the data vary from 4 to 16% depending on various factors for each reaction. We have discussed in detail the partial uncertainties due to various attributes and reported them separately, which is recommended by the data evaluator. We have also reported the cross section of the less probable (n,p) and (n,d) reactions, with good accuracy. Two isotopes ^{176}Yb and ^{177}Yb are medically important. The current study of production cross sections of these isotopes, points out the alternative ways of producing these isotopes with compact systems such as Neutron Generators and Medical LINAC. We have correlated the cross sections from the literature with respect to the IAEA-II data in order to avoid unfair comparison. The reported cross sections are compared with the evaluated data from the EXFOR B-7023, JEFF-3.2 and TENDL-2015 libraries. Except for the $^{176}\text{Yb}(p,n)^{176}\text{Yb}$ reaction, the cross sections for all the reactions agree with the evaluated data. All of our measured cross sections agree with the recent literature data. The bremsstrahlung photon-induced reaction cross sections are the first and

Table 10
 The Transcendental function weighted average cross sections for *E* gamma strength functions (*GDF*) weighted with measured cross sections.

Reaction	Energy (MeV)	Measured Cross-section (mb)	GS01	GS02	GS03	GS04	GS05	GS06	GS07	GS08
²⁰⁸ Pb(γ,γ) ²⁰⁸ Pb	0.20 to 10	49.08 ± 3.48	17.00	28.20	31.03	31.00	14.40	30.00	21.00	42.28
²⁰⁸ Pb(γ,γ) ²⁰⁸ Pb	0.40 to 10	25.28 ± 1.99	10.88	26.20	34.22	31.28	17.80	31.28	44.20	30.20
²⁰⁸ Pb(γ,γ) ²⁰⁸ Pb	0.80 to 10	45.82 ± 2.22	10.48	27.18	49.58	45.81	11.90	48.81	41.72	39.72
²⁰⁸ Pb(γ,γ) ²⁰⁸ Pb	0.20 to 10	124.71 ± 11.27	132.13	139.78	130.00	170.49	132.17	170.49	180.24	173.43
²⁰⁸ Pb(γ,γ) ²⁰⁸ Pb	0.40 to 10	120.89 ± 11.20	118.84	122.89	138.70	148.99	121.89	148.99	148.24	161.73
²⁰⁸ Pb(γ,γ) ²⁰⁸ Pb	0.80 to 10	122.82 ± 9.97	81.87	82.87	121.70	113.81	94.90	113.82	137.67	124.89

very important addition to the nuclear database at 22 and 12 MeV endpoint energies.

CRediT author statement

E.T. Shcherbak: Methodology, Data curation, Writing - original draft, Software, Investigation, Formal analysis, Validation, T.S. Gerasimov: Data curation, Software, Validation, Formal analysis, A.B. Pionov: Visualization, Validation, I.M.D. Anis: Formal analysis, S.S. Delivanis: Resources, Funding acquisition, S.T. Sarayev: Data Curation, Validation, Funding acquisition, V.H. Eberstein: Conceptualization, Project administration, Supervision, Investigation, S.D. Dzhuk: Funding acquisition, Project administration, Resources, Writing - review & editing, Supervision, Investigation.

Declaration of competing interest

The authors declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper.

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Measurements of neutron and photon induced cross sections for the production of medical isotopes of strontium

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Abstract

The direct reaction of the $^{235}\text{U}(n,f)^{87}\text{Sr}$, $^{235}\text{U}(n,f)^{88}\text{Sr}$, $^{235}\text{U}(n,f)^{89}\text{Sr}$, $^{235}\text{U}(n,f)^{90}\text{Sr}$, $^{235}\text{U}(n,f)^{91}\text{Sr}$, $^{235}\text{U}(n,f)^{92}\text{Sr}$ and $^{235}\text{U}(n,f)^{93}\text{Sr}$ nuclear reactions at 14.77–20.01 MeV neutron energy and the average cross sections of the $^{235}\text{U}(n,f)^{87}\text{Sr}$ and $^{235}\text{U}(n,f)^{90}\text{Sr}$ nuclear reactions at bombardment of 15 MeV endpoint energy were measured with the activation method and offline gamma-ray spectroscopy. The measured cross sections were repaired with a detailed covariance analysis for uncertainty and correlation coefficients. The experimental results were compared with the previously reported experimental data from the EXFOR database and the calculated data from the TENDL-2019 library. Statistical model calculations were performed with the latest TALYS-1.95 code with optimized upper parameters to better reproduce reported experimental data. The measured cross sections were found to be in good agreement with the literature and theoretical calculations. These studies highlight the alternate production routes for the medical radioisotopes of ^{87}Sr and ^{90}Sr .

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1. Introduction

The radioisotopes of strontium (^{84}Sr , ^{87}Sr , ^{89}Sr and ^{90}Sr) are used in nuclear medicine for diagnostic imaging [1–3] and treatment. The radioisotope ^{89}Sr is shown to lessen the pain in bones for patients having metastatic carcinoma [4]. ^{89}Sr having a short half-life 2.915 h [5] decays by internal transition emitting 158.131 keV gamma-ray without any beta particles and this makes it ideal for imaging malignant metastatic bone lesions [6]. ^{89}Sr is used to study calcium intake in bones [7] due to its similar chemistry. ^{89}Sr is used to generate ^{89}Rb , an important positron emitter tomography isotope.

^{89}Sr is indirectly produced from ^{89}Y which has a half-life of 19.37 h [5] by bombarding rubidium targets with alpha particles [8]. ^{89}Sr can also be directly produced by protons [9] or deuterium ions [1] induced reactions on natural rubidium (^{85}Rb) target or by bombarding natural krypton (^{84}Kr) targets with alpha particles [10]. ^{89}Sr can be indirectly produced from ^{89}Y by the $^{89}\text{Sr}(p,\text{In})^{89}\text{Y}$ reaction [11]. Direct production routes for ^{89}Sr are i) $^{85}\text{Rb}(p,\text{nn})^{89}\text{Sr}$ [12] ii) $^{85}\text{Rb}(d,\text{nn})^{89}\text{Sr}$ [1] and $^{84}\text{Kr}(\alpha,\text{n})^{89}\text{Sr}$ [13]. Alternatively ^{89}Sr , ^{90}Sr can be directly produced by bombarding natural strontium targets with 14 MeV neutrons through $^{88}\text{Sr}(n,\text{In})^{89}\text{Sr}$, $^{90}\text{Sr}(n,\text{In})^{90}\text{Sr}$ reactions [14] or 15 MeV photons [15].

Neutron-induced reaction cross sections on natural strontium target have been studied by a few authors [14,16–19] in the neutron energy range 12.5–15 MeV. The uncertainties reported by Guechi et al. [14] is 6%, by Rao et al. [16] is 10%, by Hussain et al. [17] is 10%, by Borhane et al. [18] is 3% and Srehal et al. [19] is 7%. The cross sections reported by the authors at 13.5–14.9 MeV have uncertainties from 3% to 19%. Photo-nuclear cross sections on strontium by 85 MeV bremsstrahlung reported by [20] do not include $^{89}\text{Sr}(\gamma,\text{n})^{88}\text{Sr}$ results. There are discrepancies in reported literature in neutron-induced reactions on strontium and there is scarce availability of literature on photo-neutron data at 15 MeV. Therefore, there is a need for experimental measurements in both the above cases.

In the present work the cross sections for $^{88}\text{Sr}(n,\text{In})^{89}\text{Sr}$, $^{90}\text{Sr}(n,p)^{89}\text{Rb}$, $^{90}\text{Sr}(n,\alpha)^{87}\text{Kr}$, $^{90}\text{Sr}(\alpha,\text{In})^{89}\text{Sr}$, $^{88}\text{Sr}(\alpha,\text{In})^{89}\text{Sr}$ and $^{88}\text{Sr}(\alpha,\text{In})^{89}\text{Sr}$ reactions are measured at 14.77 ± 0.17 [21] MeV neutron energy with $^{25}\text{Al}(n,p)^{25}\text{Mg}$ and $^{197}\text{Au}(n,\alpha)^{194}\text{Au}$ as monitor reactions, and the average cross sections for $^{89}\text{Sr}(\gamma,\text{n})^{88}\text{Sr}$ and $^{90}\text{Sr}(\gamma,\text{n})^{89}\text{Sr}$ reactions are measured with 15 MeV bremsstrahlung photons with $^{197}\text{Au}(\gamma,\text{n})^{196}\text{Au}$ as a monitor reaction using the activation technique and off-line gamma-ray spectroscopy. Statistical model calculations for neutron-induced reactions on strontium from reaction threshold to 20 MeV with the TALYS-1.95 [22] nuclear code is compared with the evaluated cross section data files of the JENDL-2019 [23] library and experimental data from the EXFOR database [24].

2. Experimental details

2.1. Measurement of 14.77 MeV neutron-induced reaction cross sections on strontium

Samples of pure SrO (99.99%) powder of natural isotopic abundance were prepared and wrapped in pure aluminium foil as a monitor element. A known weight of the sample was packed in a polythene bag and sandwiched between two aluminium foils and the sample size was made to be 10 mm \times 10 mm. Neutron irradiation of the samples was carried out at the 14 MeV neutron generator facility [24], Department of Physics, Savitribai Phule Pune University, Pune, India. The 14 MeV neutron generator is a 150 kW DC electrostatic accelerator. Deuterium ions are produced by an RF ion source [26]. The 14 MeV neutron beam was produced by bombarding ~ 150 keV

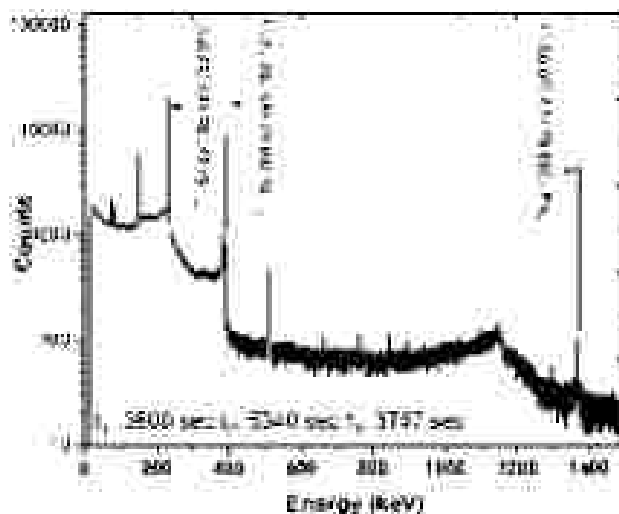


Fig. 1. The typically recorded spectrum for the Sr sample and Al control element irradiated by 14.77 MeV neutrons.

deuteron beam on an ^3C tritium target. The neutron flux was determined with the $^{22}\text{Al}(n,\alpha)^{19}\text{Ne}$ reference monitor reaction [27]. The calculated neutron flux was $\sim 10^6$ n/cm² sec. The strontium sample was mounted at 90° with respect to the incident deuteron beam where the neutron energy corresponds to 14.77 ± 0.15 MeV [28]. The deuteron ion beam current on the tritium target was ~ 40 μA at 175 kV accelerating voltage. The sample was irradiated with neutrons for an hour and then immediately transferred to the counting room where it was cooled.

The gamma-ray activity of the irradiated samples were measured with a coaxial HPGe (30%) detector cooled by a liquid nitrogen cryostat. The energy resolution of the detector was measured as 1.49 keV at the 1332.5 keV peak of ^{60}Co gamma source. The detector was connected to an Ortec EASY-MCA-1K Multichannel Analyzer through an amplifier. The Ortec-mks Maestro software was used for the data acquisition and the dead time was maintained below 2%. Eu-152 standard source was used for energy calibration of the HPGe detector. The calibration source was kept at 50 mm from the central area of the detector surface. The gamma-ray activity of the neutron irradiated samples was measured by mounting the sample at the marked position in front of the pre-calibrated HPGe detector. Typical recorded gamma-ray spectrum for Sr and Al samples irradiated by 14.77 MeV neutrons are shown in Fig. 1, along with the timing details where t_i is the irradiation time, t_c is the cooling time and t_s is the counting time. The details of the irradiation time, cooling time and counting time are given in Table 1. The nuclear data used for the reactions are given in Table 2.

2.1. Measurement of 15 MeV bremsstrahlung induced nuclear reaction cross sections for Sr and Al

Samples of pure SrO_2 (99.99%) powder of known weight and natural isotopic abundance were prepared. An foil (0.5 gm), of the same size as the samples was placed along with the samples for monitoring the bremsstrahlung flux. The bremsstrahlung irradiation experiment of the samples was carried out with the medical linear electron accelerator at Dr. Vikram Sarabhai Memorial Hospital, Ahmednagar, India. The Medical LINAC is capable of delivering a monochromatic electron

Table 1
Timing details of the samples irradiated with 14.77 MeV electrons.

Reaction	Irradiation time (sec)	Cooling time (sec)	Counting time (sec)
$^{88}\text{Sr}(e, n)^{87}\text{Sr}$	300	150	174
$^{88}\text{Sr}(e, p)^{88}\text{Y}$	300	30	150
$^{88}\text{Sr}(e, p)^{87}\text{Y}$	300	1700	732
$^{88}\text{Sr}(e, n)^{87}\text{Rb}$	300	100	100
$^{88}\text{Sr}(e, n)^{87}\text{Sr}$	300	1700	732
$^{88}\text{Sr}(e, n)^{87}\text{Sr}$	300	1700	732

Table 2
Decay data adopted for the present work [1,29,31] along with threshold energy.

Reaction	Threshold (MeV)	Q_{β}	Decay mode	$T_{1/2}$ (s)	β_{β} (%)
$^{88}\text{Sr}(e, n)^{87}\text{Sr}$	1.620	2.957 ± 0.017 e	$\beta^{-} (99.7\%)$	386.51	92.79 ± 0.11
$^{88}\text{Sr}(e, p)^{88}\text{Y}$	4.362	17.775 ± 0.016 e	$\beta^{-} (100\%)$	449.01	100 ± 0.24
$^{88}\text{Sr}(e, p)^{87}\text{Y}$	4.664	4.666 ± 0.006 e	$\beta^{-} (100\%)$	133.19	100 ± 0.3
$^{88}\text{Sr}(e, n)^{87}\text{Rb}$	11.879	67.61 ± 0.006 e	$\beta^{-} (100\%)$	211.66	100 ± 0.4
$^{88}\text{Sr}(e, n)^{87}\text{Sr}$	11.821	44.344 ± 0.007 e	$\beta^{-} (100\%)$	1.43448	99 ± 4
$^{88}\text{Sr}(e, n)^{87}\text{Sr}$	12.067	72.41 ± 0.013	$\beta^{-} (100\%)$	762.57	100 ± 0.3

Table 3
Timing details of the samples irradiated with bremsstrahlung of 15 MeV and pure gamma.

Reaction	Irradiation time (sec)	Cooling time (sec)	Counting time (sec)
$^{88}\text{Sr}(e, n)^{87}\text{Sr}$	100	10	60
$^{88}\text{Sr}(e, n)^{87}\text{Sr}$	100	10	60

beam of current 5 μA with an energy spread of less than 0.5%. The bremsstrahlung radiation was generated by bombarding the high energy electron beam on a tungsten target. A field size of 5 cm \times 5 cm was setup by the operators at the patient table 100 cm from the source. The samples were placed in this field on the patient table. Both the Sr sample and Au monitor were irradiated simultaneously with bremsstrahlung of 15 MeV endpoint energies of dose rate 0.70 ± 10 cGy/min for 1500 seconds. Samples were taken to the control room after irradiation for counting. The gamma-ray activity of the irradiated samples was measured with a pre-calibrated HPGe (30%) detector one after the other. Typical recorded gamma-ray spectrum for Sr sample irradiated with bremsstrahlung of 15 MeV end point energy is shown in Fig. 2, along with the fitting details. The timing details of the present experiment are given in Table 1. The nuclear data used for the reactions are given in Table 2.

3. Data analysis

3.1. Calibration and estimation of the efficiency of the HPGe detector

The calibration of the HPGe detector was carried out with a standard ^{137}Cs source of known activity ($A_0 = 4336.93 \pm 36.74$ Bq as on 1 Oct. 1995). The absolute efficiency ϵ for the point

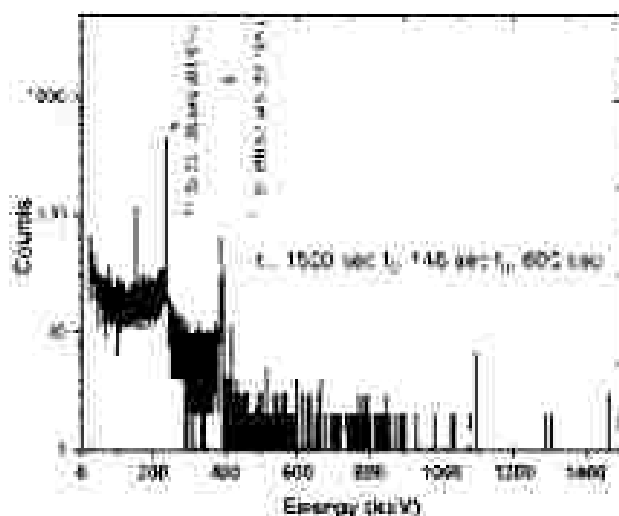


Fig. 2. Theoretically corrected spectrum for the 15 source evaluated by deconvoluting of 27 MeV end-point energy.

Table 4
Efficiency and efficiency calibration with ^{228}Ac standard source.

E_p (keV)	I_p (%)	C	K_C	$\epsilon(E_p)$
121.78	23.73 ± 0.09	7343 ± 236	1.4461	1.031 ± 0.034
164.29	26.75 ± 0.26	6662 ± 297	1.4277	2.341 ± 0.076
212.9	22.91 ± 0.46	4764 ± 114	1.3711	1.213 ± 0.042
264.68	14.25 ± 0.07	3193 ± 103	1.3409	1.997 ± 0.027
311.37	11.67 ± 0.08	4948 ± 147	1.3145	4.498 ± 0.028
403.97	20.17 ± 0.49	4475 ± 97	1.4267	3.654 ± 0.077

source placed at a distance of 53 mm from the end-cap of the detector is given by the expression

$$C = \frac{K_C}{A_0 e^{-\lambda T} I_p \Delta t} \quad (1)$$

where C is the count obtained for a counting time ($\Delta t = 3500$ seconds) for a particular gamma-line of ^{228}Ac having a decay intensity I_p , A_0 is the activity of ^{228}Ac source at the time of manufacture, T is the time between date of manufacture to the beginning of counting and K_C is the correction factor for the coincidence summing effect. Absolute efficiency was obtained from EFFTRAN code [37]. Efficiency $\epsilon(E_p)$ at each of the six identified γ -rays of Eu-152 are presented in Table 4. The uncertainty in efficiency was calculated with the Taylor series expansion of detector efficiency (equation (1)) from Ref. [33]. The interpolated detector efficiency fitting curve and measured detector efficiency is plotted in Fig. 3.

The efficiencies of the detector at required points of energies were generated with a linear parametric function [34]

$$\ln \epsilon = \sum_{n=1}^6 \mu_n (\ln E_p)^{n-1} \quad (2) \quad 1 \leq n \leq 6$$

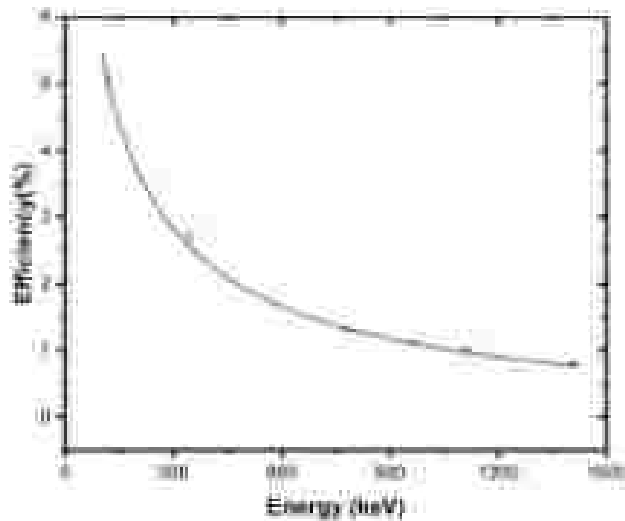


Fig. 3. Measured relative efficiency, with interpolation, versus E_{γ} (keV) (solid).

Table 5

Interpolated energy efficiencies $\epsilon(E)$ (relative) and correlation matrix for the employed 10 monitor reactions.

E_{γ} (keV)	Efficiency	Correlation matrix								
111.204	$4.5(1) \pm 0.009$	1.000								
131.56	3.639 ± 0.004	0.977	1.000							
146.37	3.233 ± 0.005	0.957	0.956	1.000						
174.0646	1.821 ± 0.002	0.847	-0.220	0.367	1.000					
182.63	1.78 ± 0.01	0.748	-0.689	0.446	0.171	1.000				
185.74	1.244 ± 0.028	0.739	0.482	0.471	0.162	0.099	1.000			
198.05	1.178 ± 0.026	0.728	0.627	0.472	0.159	0.091	0.099	1.000		
208.026	0.828 ± 0.009	0.376	0.009	0.197	0.261	0.161	0.294	0.009	1.000	

The best quality of fit was achieved for $m = 4$, with $\chi^2_{red} = 1.06 \approx 1$. In order to estimate the efficiencies corresponding to γ -rays emitted from the decay of the reaction products $^{88}\text{Sr}^m$, ^{90}Zr , ^{92}Kr , $^{94}\text{Sr}^m$, $^{96}\text{Sr}^m$, ^{98}Sr , ^{100}Sr , ^{102}Ne and ^{104}Mg , the following linear parametric model was used

$$\ln \epsilon = -4.534403 - 0.036434 \ln E + 0.067139 \ln E^2 + 0.039392 \ln E^3 \quad (3)$$

The interpolated efficiencies and the corresponding correlation matrix for characteristic γ lines for the sample and the monitor reaction are given in Table 5.

3.2. Measurements of $(n,2n)$, (n,p) and (n,α) reaction cross sections on natural chromium targets

The cross sections of $^{52}\text{Cr}(n,2n)^{51}\text{Cr}^m$, $^{52}\text{Cr}(n,p)^{52}\text{V}$, $^{52}\text{Cr}(n,\alpha)^{49}\text{Ca}$, $^{54}\text{Cr}(n,2n)^{53}\text{Cr}^m$, $^{54}\text{Cr}(n,2n)^{55}\text{Cr}^m$ and $^{54}\text{Cr}(n,\alpha)^{51}\text{V}$ reactions were measured at 14.77 ± 0.17 MeV neutron energy relative to $^{27}\text{Al}(n,\alpha)^{24}\text{Na}$ monitor reaction. The cross section was determined with the neutron activation equation [35]

$$\sigma_x = \sigma_m \frac{c_m C_{100} A_1 I_{\gamma 1} M_m \lambda_m \ln 2 P_1}{I_1 C_{100} A_2 A_2 I_{\gamma 2} M_x \lambda_x \ln 2 P_2} \quad (4)$$

Table 5
Coincidence Factor (CF) for self-attenuation and coincidence summing for sample and monitor.

Product nuclei	λ_p (s ⁻¹)	Sample	CF
^{87}Sr	386.33	Sr	1.023
^{203}Tl	984.07	Tl	1.017
^{207}Pb	221	Pb	1.013
^{209}Bi	211.26	Bi	1.001
^{210}Po	1.14 (96d)	Po	1.011
^{210}Bi	762.07	Bi	1.021
^{210}Po	1.16 (138d)	Po	1.001
^{210}Pb	340.79	Pb	1.003
^{210}Bi	715.71	Bi	1.013

where, the subscript *s* denotes sample reaction parameters and subscript *m* denotes the monitor reaction parameters. Here $\sigma_{\text{th}} = 111.5 \pm 0.42$ mb is taken from the IRLFF-II evaluated data file at 14.77 MeV, ϵ is the detector efficiency, C is the photo peak counts, w is the isotopic abundance, A atomic mass, λ_p is the branching ratio of γ -ray taken from [35], M is the mass, f is the timing factor, and CF is the correction factor due to coincidence summing effects and gamma ray self-attenuation. The timing factor f is given by

$$f = \frac{(1 - e^{-\lambda t_i})(1 - e^{-\lambda t_c})(1 - e^{-\lambda t_s})}{\lambda} \quad (5)$$

where, λ is the decay constant, t_i is the irradiation time, t_c is the cooling time and t_s is the counting time. The Coincidence summing correction factor f_c was calculated by the TrueCoinc code [17]. The total efficiency curve for the HPGe detector was obtained from the TrueCoinc code. The self-attenuation coefficient, f_a due to interactions of gamma rays within the sample thickness is given by

$$f_a = \frac{\mu x}{1 - e^{-\mu x}} \quad (6)$$

where μ is the linear attenuation coefficient in cm⁻¹ for the irradiated sample and x is the thickness of the sample in cm. The mass attenuation coefficient μ/ρ for individual elements (Strontium, Oxygen, Aluminium and Gold) was obtained by interpolating the curves from the NIST Standard Reference Database [38]. The μ/ρ for the compound SrO₂ was calculated using

$$(\mu/\rho)_{\text{SrO}_2} = \sum_i W_i (\mu/\rho)_i \quad (7)$$

where W_i is fraction of the *i*th element by weight in the compound SrO₂ and $(\mu/\rho)_i$ is the mass attenuation coefficient of the *i*th element. CF for induced activity in sample is given by

$$CF = f_c \times f_a \quad (8)$$

The calculated self-attenuation coefficients f_a and coincidence summing correction factor f_c are given in Table 5 for SrO₂ sample, Al and Au monitor.

The measured cross section calculated with equation (4) contains uncertainty [35] contributed by parameters observed with uncertainty. The partial uncertainties for each parameter of equation (4) and their correlations are given in Table 7 following Sec. 4.1.4 of Ref. [35]. The fractional uncertainties in atomic mass for sample and monitor are negligible.

Table 7

Continuity parameter α for each channel obtained with the present measurements (α) (previous publications)

Reaction	C_1	C_2	I_{γ_1}	I_{γ_2}	$I_{m,1}$	$I_{m,2}$	$I_{m,3}$	M_1	M_2	α_1	α_2
1) $^{197}\text{Au}(\gamma,n)^{196}\text{Au}$	1.124	0.2143	0.2477	0.0011	0.1271	0.168	0.2764	0.20	0.1000	0.4111	0.1
2) $^{197}\text{Au}(\gamma,p)^{196}\text{Au}$	2.5195	0.2155	2.0007	0.0011	0.0019	0.0153	0.0761	0.05	0.1000	0.0027	0.1
3) $^{197}\text{Au}(\gamma,p)^{196}\text{Au}$	0.2214	0.4044	0.0040	0.0011	0.0014	0.0023	0.0044	0.00	0.1000	0.0021	0.1
4) $^{197}\text{Au}(\gamma,p)^{196}\text{Au}$	1.4019	0.0010	0.4760	0.0011	0.1040	0.0007	0.0771	0.10	0.1000	0.1010	0.1
5) $^{197}\text{Au}(\gamma,p)^{196}\text{Au}$	1.0021	0.4018	0.4167	0.0011	0.0754	0.0107	0.0044	0.00	0.1000	0.1014	0.1
6) $^{197}\text{Au}(\gamma,p)^{196}\text{Au}$	1.7059	0.4018	0.2707	0.0011	0.0011	0.0171	0.0044	0.00	0.1000	0.7007	0.1
$\text{Cu}(0,0)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(0,1)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(1,4)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(2,1)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(0,0)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(0,1)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(1,4)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(2,1)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(0,0)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(1,4)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(2,1)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(0,0)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(1,4)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(2,1)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(0,0)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(1,4)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(2,1)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(0,0)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(1,4)$	0	1	0	1	1	1	1	1	1	0	1
$\text{Cu}(2,1)$	0	1	0	1	1	1	1	1	1	0	1

Table 8

Continuity factor (CF_p) and the threshold energy for various end-nuclei reactions

Reaction	Threshold energy (MeV)	CF_p
$^{197}\text{Au}(\gamma,p)^{196}\text{Au}$	0.071	
$^{197}\text{Au}(\gamma,p)^{196}\text{Au}$	1.111	0.24
$^{197}\text{Au}(\gamma,p)^{196}\text{Au}$	1.070	0.29

3.3. Measurement of (γ,n) reaction cross sections for natural isotopic targets

The average cross sections of $^{197}\text{Au}(\gamma,n)^{196}\text{Au}$ and $^{197}\text{Au}(\gamma,p)^{196}\text{Au}$ reactions were measured using the ratio method [39] at bremsstrahlung of 15 MeV end-point energy with $^{197}\text{Au}(\gamma,n)^{196}\text{Au}$ as the monitor reaction. Here, the cross section was determined with the equation

$$\sigma_x = \left[\sigma_m \right] \frac{CF_{2m} C_{1,m} \lambda_{1,m} I_{\gamma,m} M_{m,1}}{CF_{1x} C_{1,x} \sigma_{1,x} \lambda_{1,x} I_{\gamma,x} M_{1,x} f_x CF_p} \quad (9)$$

where the parameters have the same meaning as in equation (4) and I_{γ} is the branching ratio of γ -ray taken from Refs. [5,30,44]. CF_p is the flux ratio used to normalize the cross sections due to the monitor and targets having different threshold energies and is given in Table 8.

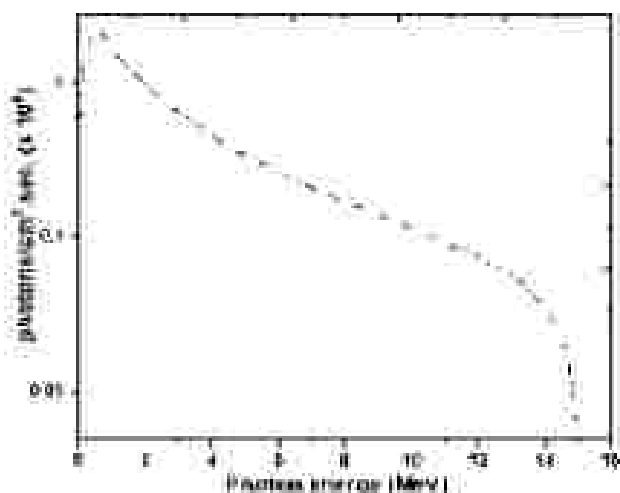


Fig. 4. GRANT4 simulated bremsstrahlung spectrum of 11 MeV x-rays source.

The flux ratio is given as

$$CF_{\gamma} = \frac{\int_{E_{th}}^{E_{st}} \varphi(E)dE}{\int_{E_{th}}^{E_{st}} \sigma(E)dE} \quad (10)$$

where $E_{th} = 15$ MeV, E_{st} is the threshold energy for the sample and E_{st} is the threshold energy for the sample. $\varphi(E)$ was taken from the bremsstrahlung spectrum Fig. 4 simulated using Monte Carlo based GRANT4 code [41]. The Geant4 simulations were performed by default physics models with EMStandardPhysics physics list. The bremsstrahlung photons incident on the sample surface was simulated by adopting the LINAC geometry of the experiment. The dose deposited on the patient table was correlated with the simulated dose deposit to obtain the photon flux as in Ref. [42,43].

$$\langle \sigma_{m} \rangle = \frac{\int_{E_{th}}^{E_{st}} \sigma(E)\varphi(E)dE}{\int_{E_{th}}^{E_{st}} \varphi(E)dE} \quad (11)$$

$\langle \sigma_{m} \rangle$ in equation (9) is the average value of the cross section for the monitor reaction from threshold energy to 11 MeV and $\varphi(E)$ is taken from the simulated bremsstrahlung spectrum Fig. 4 and $\sigma(E)$ is taken from interpolated cross section of $^{89}\text{Au}(\gamma, n)^{88}\text{Au}$ reaction in Ref. [44] from threshold energy for the monitor reaction to 15 MeV bremsstrahlung stop point energy.

Here $\langle \sigma_{m} \rangle = 153.93 \pm 4.78$ mb is calculated from equation (11). The partial uncertainties for each parameter of equation (9) and their correlations are given in Table 9. The fractional uncertainties in atomic ratio for sample and scaling factor for monitor are negligible. The fractional uncertainties of the measured cross sections were calculated as the quadratic sum of the fractional uncertainties.

4. Nuclear model calculations

The excitation functions for $^{88}\text{Sr}(n, \text{In})^{87}\text{Sr}$, $^{88}\text{Sr}(n, p)^{87}\text{Rb}$, $^{88}\text{Sr}(n, \alpha)^{84}\text{Kr}$, $^{88}\text{Sr}(n, \text{In})^{87}\text{Sr}$, $^{88}\text{Sr}(\alpha, 2n)^{87}\text{Sr}$ and $^{88}\text{Sr}(n, \text{In})^{87}\text{Sr}$ reactions were simulated from reaction threshold to 20 MeV

Table 4

Optimized parameters (%) of various parameters used in TALYS-1.95 software.

Reaction	C_V	C_M	$f_{p,n}$	$f_{p,m}$	$S_{n,r}$	$I_{n,r}$	M_V	M_M	A_V	A_M	C_{γ}
1. $^{88}\text{Sr}(p,\alpha)^{85}\text{Sr}$	0.9932	2.4719	0.2477	1.4493	0.0621	0.2991	0.00	0.1	0.1012	0.0001	1
2. $^{88}\text{Sr}(p,\alpha)^{86}\text{Sr}$	2.3386	2.4719	0.4768	1.4493	0.2701	0.4491	0.00	0.1	0.1012	0.0001	1
Code(1,2)	1	1	1	1	1	1	1	1	1	1	1

with the TALYS-1.95 statistical model code [11]. The TALYS-1.95 code can be used for nuclear reactions that involve incident projectiles such as gammas, neutrons, protons, deuterons and α -particles in the incident energy range from 1 keV to 100 MeV. The TALYS-1.95 calculations of the present work are based on the contributions of the compound nucleus theory, direct reactions, optical model potentials and pre-equilibrium processes. An elaborate description of the TALYS-1.95 code can be found in Ref. [10]. Inelastic scattering for 14 MeV neutrons has both compound and direct-like components. The latter is described by the Distorted Wave Born Approximation (DWBA). At energies above the threshold of the (n,n') channel, the direct-like component's contribution to the inelastic scattering dominates the former. There are 334 model combinations in TALYS-1.95 code. These correspond to the combinations of six level density models [45–50], two nucleus-nucleus optical model potentials [51], four pre-equilibrium models [52] and eight γ -ray strength functions [53–59]. Chi-squared validation of calculated cross sections with experimental data from the EXFOR database was done to determine a consistent parameter set [60]. The uncertainty band in the optimised parameter set was studied based on Refs. [61,62]. Here, parameters of the level density model and optical model potential were assigned an uncertainty based on the above. 1000 calculations were performed to determine the uncertainty in the excitation functions by randomly varying the value of the aforementioned parameters within the optimised parameter set between $\pm 1\%$ of its central value. The neutron energies were binned at intervals of 1 MeV. The statistical mean corresponding to 1000 values of cross section and the standard deviation (SD) for each energy bin was calculated. The uncertainty in theoretical calculations was expressed as the percentage SD per unit calculated cross-section per bin multiplied by 1.95 to determine the 95% confidence interval. The direct-like component was accounted for by DWBA calculations. The pre-equilibrium contributions were accounted for by the two-component exciter model [52]. The default local optical model parameters in the present work are the parameterisation of Koning and Delaroche [31]. The level densities are described by the generalised superfluid model [49]. The gamma-ray transmission coefficients are calculated through the energy-dependent gamma-ray strength function given by Brink-Axel [54,55].

The excitation functions for $^{88}\text{Sr}(p,\alpha)^{85}\text{Sr}$ and $^{88}\text{Sr}(p,\alpha)^{86}\text{Sr}$ were calculated for photon energies from reaction threshold to 20 MeV using TALYS-1.95 code with the default constant temperature model for calculating nuclear level densities, with the eight available gamma-ray strength functions as given below:

- (1) GSF-1: Generalised-Lorentzian of Kopecky and Uhl [33]
- (2) GSF-2: Generalised Lorentzian of Brink and Axel [54,55]
- (3) GSF-3: Hartree-Fock-BCS tables [56]
- (4) GSF-4: Hartree-Fock-Bogolyubov tables [57]
- (5) GSF-5: Hybrid model of Goriely [54]
- (6) GSF-6: Goriely TDHFB [58]

Table 10

Measured cross-sections σ_{exp} by present work, and cross-sections σ_{eval} .

Reaction	σ_{exp} (present work)	Coverage factor ($\sigma_{\text{exp}}/\sigma_{\text{eval}}$)	Confidence limits
$^{88}\text{Sr}(n,\gamma)^{89}\text{Sr}$	0.172 ± 0.010	1.00	1
$^{88}\text{Sr}(n,\gamma)^{89\text{m}}\text{Sr}$	0.0348 ± 0.0004	0.61–0.66	0.1–1
$^{88}\text{Sr}(n,\gamma)^{88\text{m}}\text{Sr}$	0.00127 ± 0.00002	0.41–0.4	0.00–0.01
$^{88}\text{Sr}(n,\gamma)^{88}\text{Sr}$	0.201 ± 0.001	0.69–0.67	0.75–1.00
$^{88}\text{Sr}(n,\gamma)^{87}\text{Sr}$	0.7427 ± 0.0074	0.1–0.33	0.02–0.6
$^{88}\text{Sr}(n,\gamma)^{87\text{m}}\text{Sr}$	0.0152 ± 0.0010	0.1–0.33	0.01–0.47

Table 11

Measured cross-sections at 1471 ± 3 keV energy energy compared with the evaluated data of the TENDL-2019 [25] (blue) and TALYS-1.95 [53] (red) calculations.

Reaction	Present work (red)	TALYS-1.95 (red)	TENDL-2019 (blue)
$^{88}\text{Sr}(n,\gamma)^{89}\text{Sr}$	0.172 ± 0.010	0.2167 ± 0.0020	0.146
$^{88}\text{Sr}(n,\gamma)^{89\text{m}}\text{Sr}$	0.0348 ± 0.0004	0.0132 ± 0.0014	0.0001
$^{88}\text{Sr}(n,\gamma)^{88\text{m}}\text{Sr}$	0.00127 ± 0.00002	0.00077 ± 0.00004	0.00022
$^{88}\text{Sr}(n,\gamma)^{88}\text{Sr}$	0.201 ± 0.001	0.2041 ± 0.0009	0.0107
$^{88}\text{Sr}(n,\gamma)^{87}\text{Sr}$	0.7427 ± 0.0074	0.7060 ± 0.0023	0.7101
$^{88}\text{Sr}(n,\gamma)^{87\text{m}}\text{Sr}$	0.0152 ± 0.0010	0.0102 ± 0.0003	0.0144

(7) GSF-7: T-Dependent relativistic mean field [54]

(8) GSF-8: Gogny D1M HF + quasi-random-phase approximation [55]

5. Results and discussion

The covariance matrix and the correlation matrix of the measured neutron-induced reaction cross sections for strontium are presented in Table 10. Normalisation is carried out for earlier reported experimental data with respect to the recent evaluated cross section data for monitor cross section from the IRRDF-II [27] database. The measured cross sections for $^{88}\text{Sr}(n,\gamma)^{89}\text{Sr}$, $^{88}\text{Sr}(n,\gamma)^{89\text{m}}\text{Sr}$, $^{88}\text{Sr}(n,\gamma)^{88\text{m}}\text{Sr}$, $^{88}\text{Sr}(n,\gamma)^{88}\text{Sr}$, $^{88}\text{Sr}(n,\gamma)^{87}\text{Sr}$ and $^{88}\text{Sr}(n,\gamma)^{87\text{m}}\text{Sr}$ reactions are compared with the normalised experimental data from the EXFOR database. The measured data is also compared with the cross section reported by evaluated cross section data from the TENDL-2019 [25] library and statistical model calculations with the TALYS-1.95 nuclear code in Table 11. For all the reactions in the present study, the TALYS-1.95 calculations were done with generalised the superfluid model for level densities (lfmodel 3), the exciton model for pre-equilibrium contributions (premode 2), the generalised lorentzian of Brink and Axel (strength 2) and the local nuclear nucleus potential of Koning and Delaroche (localamp y). The optimised TALYS-1.95, the cross sections from the TENDL-2019 evaluation are represented by a thin black solid line, ENDF-B-VIII.0 evaluation by a black dotted line, TALYS-1.95 95% upper confidence level by a red dotted, TALYS-1.95 95% lower confidence level by a black dashed line and the region between the above two dashed lines is filled in Fig. 3 to Fig. 8. For experimental data where monitor cross section is not available on the EXFOR database, normalisation is not performed and compared with the present work.

The covariance matrix and the correlation matrix for measured photon-induced reaction cross sections of strontium are presented in Table 12. The TENDL-2019 evaluated data is compared

Table 12
Comparison matrix and probability matrix for reported prior values.

Reaction	Correlation matrix	Correlation matrix ($\times 10^{-2}$)	Correlation matrix
$^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$	0.0100 0.000000	0.274	1
$^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$	0.0114 0.000000	27.071	11.074

Table 13
Measured average cross section (σ) for $^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$ and $^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$ reactions at 14.77 MeV (normalised) and prior values.

Reaction	Present work (barn)	TALYS-1.95 calculated values							
		00F.1	00F.2	00F.3	04F.4	04F.5	04F.6	05F.7	05F.8
$^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$	0.0100 \pm 0.0000	0.0046	0.0141	0.0407	0.0106	0.0010	0.0014	0.0040	0.0007
$^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$	0.0114 \pm 0.0000	0.0038	0.0176	0.0164	0.0171	0.0210	0.0075	0.0100	0.0044

with TALYS-1.95 calculations for eight different gamma strength functions (G5F-1 to G5F-8) and the present work is presented in Table 13.

5.1. The $^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$ reaction

In Fig. 5 the measured cross section for $^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$ reaction at 14.77 \pm 0.17 MeV neutron energy is plotted along with reported experimental data from the EXFOR database and evaluated data from the TENDL-2019 library. For this reaction, Filatenkov et al. [60], Murao et al. [64], Molla et al. [65], Dabek et al. [66], Rao et al. [67], Holub et al. [68], Hussain et al. [17] and Strahel et al. [18] adopted $^{27}\text{Al}(n,\alpha)^{24}\text{Na}$ reaction as monitor reaction. He et al. [14] and Komro et al. [69] adopted $^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$ reaction as a monitor reaction, while Minetti et al. [70] adopted $^{63}\text{Cu}(n,\alpha)^{60}\text{Ni}$ reaction as a monitor reaction. Pao et al. [16] adopted $^{56}\text{Fe}(n,p)^{56}\text{Mn}$ reaction as monitor reaction. Reported cross section data are normalised at respective neutron energies with respect to IRRFF-II data for respective monitor reactions.

As shown in the Fig. 5, cross sections reported by Dabek et al. [66], Molla et al. [65], Komro et al. [69], Guadalu et al. [10] and Filatenkov et al. [71] whose neutron energies overlap with the present value are in good agreement with the present result within reported experimental uncertainty. Our measured cross section does not correspond with those reported by Zhou et al. [64], Hussain et al. [17] and Minetti et al. [70]. The measured cross section is in good agreement with TALYS-1.95 calculations and the TENDL-2019 evaluation within the error bar.

5.2. The $^{88}\text{Sr}(n,p)^{88}\text{Rb}$ reaction

Fig. 6 shows the measured cross section for $^{88}\text{Sr}(n,p)^{88}\text{Rb}$ reaction at 14.77 \pm 0.17 MeV neutron energy along with reported experimental data from the EXFOR database and evaluated data from the TENDL-2019 library. For this reaction, Kitagami et al. [72], Dabek et al. [66], Molla et al. [65], Itaku et al. [73], Hama et al. [17] and Strahel et al. [18] adopted $^{27}\text{Al}(n,\alpha)^{24}\text{Na}$ reaction as a monitor reaction. Guadalu-He et al. [74] adopted $^{88}\text{Sr}(n,\alpha)^{84}\text{Kr}$ reaction as monitor reaction, whereas Leskoviński et al. [4,75] adopted $^{63}\text{Cu}(n,\alpha)^{60}\text{Ni}$ reaction as monitor reaction. Gupta et al. [76], Drexler et al. [77], Rao et al. [16] and Prasad et al. [78] adopted $^{56}\text{Fe}(n,p)^{56}\text{Mn}$

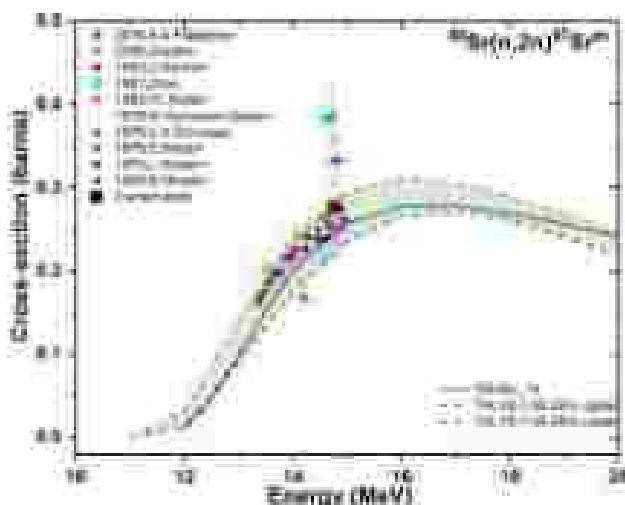


Fig. 3. Comparison of the experimental $^{238}\text{Pu}(n,2n)^{237}\text{Pu}$ reaction cross sections with the evaluated ENDF/B-VI data and theoretical values calculated with TALYS-1.02. (For interpretation of the references to this figure, the reader is referred to the web version of this article.)

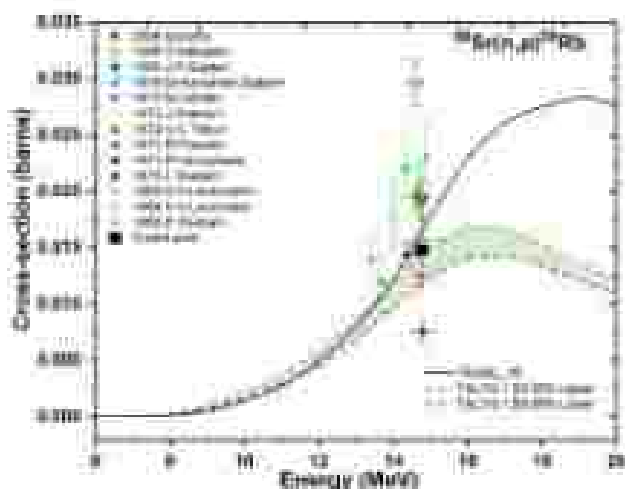


Fig. 4. Comparison of $^{238}\text{Pu}(n,p)^{237}\text{Po}$ reaction experimental cross sections with the evaluated ENDF/B-VI data and theoretical values using TALYS-1.02.

reaction as a monitor reaction. Reported cross section data are normalized at respective neutron energies with respect to IRDFF-II data for respective monitor reactions.

As shown in the Fig. 4, cross sections for $^{238}\text{Pu}(n,p)^{237}\text{Po}$ reaction reported by Gupta et al. [6] and Leykovskii et al. [3], whose neutron energies overlap with the present value are in good agreement with the present result. The measured cross section shows a large deviation with those reported by Guanais-He et al. [14], Kasugai et al. [2], Dobek et al. [66], Molle et al. [63], Dresler et al. [77], Tikki et al. [33], Prasad et al. [78], Hussain et al. [17] and Strohal et al. [19]. However,

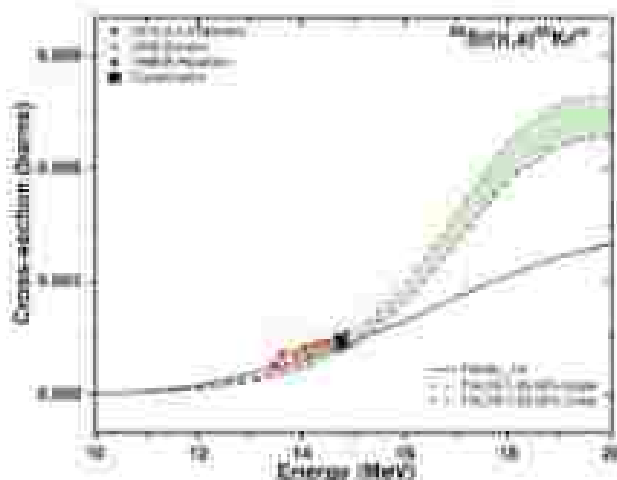


Fig. 2. Comparison of experimental $^{45}\text{Sr}(n,\alpha)^{41}\text{Kr}$ reaction cross section with the present TENDL-2019 data and theoretical values using TALYS-1.95.

the measured cross section is in good agreement with TALYS-1.95 calculations and the TENDL-2019 evaluation within the error bar.

1.2. The $^{45}\text{Sr}(n,\alpha)^{41}\text{Kr}$ reaction

In Fig. 2 the measured cross section for $^{45}\text{Sr}(n,\alpha)^{41}\text{Kr}$ reaction at 14.77 ± 0.17 MeV neutron energy is plotted along with reported experimental data from the EXFOR database and evaluated data from the TENDL-2019 library. For this reaction, Filatenkov et al. [63], Pepelnik et al. [79] and Strohal et al. [19] adopted $^{27}\text{Al}(n,\alpha)^{24}\text{Na}$ reaction as a monitor reaction. He et al. [14] adopted $^{93}\text{Nb}(n,\text{In})^{93}\text{Nb}$ reaction as a monitor reaction. Reported cross section data are normalized at respective neutron energies with respect to IRR97-II data for respective monitor reactions.

The present results for $^{45}\text{Sr}(n,\alpha)^{41}\text{Kr}$ reaction are in good agreement with the reported experimental cross sections of Filatenkov et al. [63], Guesho-He et al. [14] and Pepelnik et al. [79]. Moreover, the measured cross section matches with TALYS-1.95 calculations and the TENDL-2019 evaluation within the error bar.

1.4. The $^{45}\text{Sr}(n,\text{In})^{45}\text{Sr}$ reaction

Fig. 3 shows our measured cross section for $^{45}\text{Sr}(n,\text{In})^{45}\text{Sr}$ reaction at 14.77 ± 0.17 MeV neutron energy along with reported experimental data from the EXFOR database and evaluated data from the TENDL-2019 library. For this reaction, Ma Rui-Fang et al. [60], Labeyrie et al. [66], Rao et al. [67], Hahné et al. [68], Husain et al. [17], Riader et al. [12] and Strohal et al. [19] adopted $^{27}\text{Al}(n,\alpha)^{24}\text{Na}$ reaction as a monitor reaction. Luo et al. [13], Guesho-He et al. [14] and Kouno et al. [69] adopted $^{93}\text{Nb}(n,\text{In})^{93}\text{Nb}$ reaction as a monitor reaction. Rao et al. [16] adopted $^{56}\text{Fe}(n,p)^{56}\text{Mn}$ reaction as monitor reaction. Reported cross section data are normalized at respective neutron energies with respect to IRR97-II data for respective monitor reactions.

As shown in the Fig. 3, cross sections for $^{45}\text{Sr}(n,\text{In})^{45}\text{Sr}$ reaction reported by Hahné et al. [68] and Strohal et al. [19], whose neutron energies overlap with the present value are in good

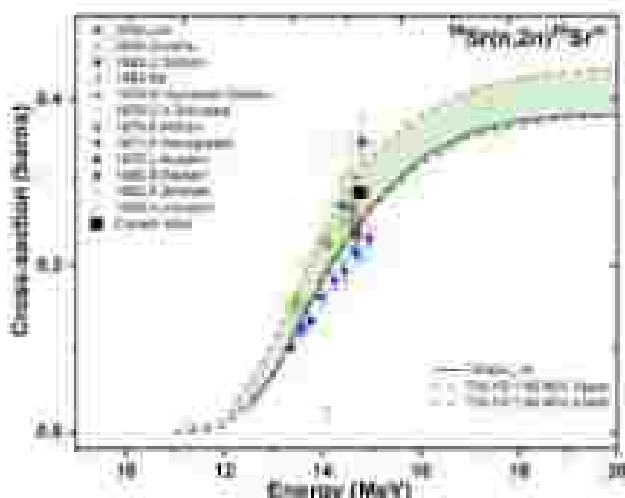


Fig. 6. Comparison of experimental $^{86}\text{Sr}(n,2n)^{85}\text{Sr}$ reaction cross sections with the evaluated TENDL-2019 data and theoretical values using TENDL-1.0.

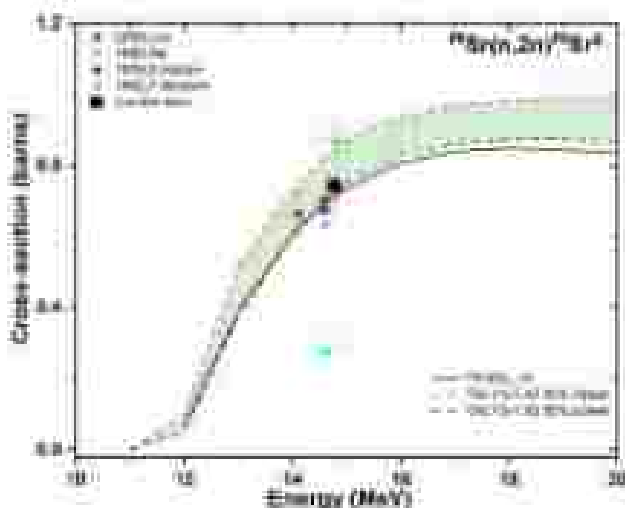


Fig. 7. Comparison of experimental $^{86}\text{Sr}(n,2n)^{85}\text{Sr}$ reaction cross sections with the evaluated TENDL-2019 data and theoretical values using TENDL-1.0.

agreement with the present result. Our measured cross section shows a large deviation with those reported by Luo *et al.* [33], Gonnim-Ha *et al.* [14], Kohns *et al.* [59], Ma Hui-Fang *et al.* [20], Dabek *et al.* [66], Rao *et al.* [31], Rao *et al.* [36], Huzain *et al.* [17] and Röscher *et al.* [83]. The measured cross section is in good agreement with TENDL-1.0 calculations within the error bar, however they are higher than the evaluated excitation function by the TENDL-2019 library.

3.3. The $^{86}\text{Sr}(n,2n)^{85}\text{Sr}$ reaction

Fig. 7 shows the measured cross section for $^{86}\text{Sr}(n,2n)^{85}\text{Sr}$ reaction at 14.77 ± 0.17 MeV neutron energy along with reported experimental data from the ENDF-database and evaluated

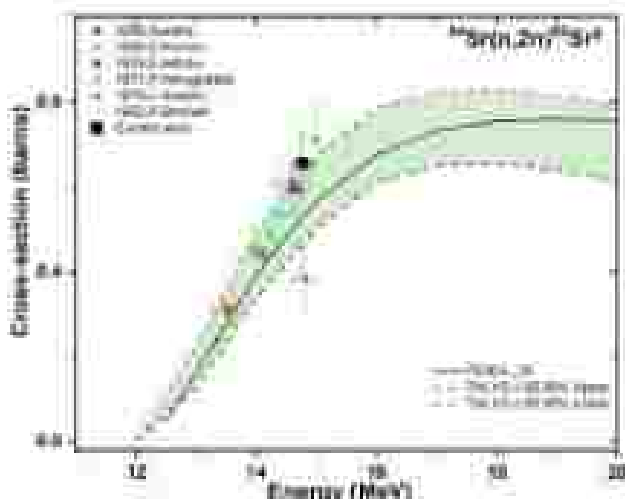


Fig. 9. Comparison of experimental $^{89}\text{Sr}(n,2n)^{88}\text{Sr}$ reaction cross section with the evaluated TENDL-2019 data and the present work using TALYS-1.95.

data from the TENDL-2019 library. For this reaction, Hui-Fung et al. [40], Holub et al. [68] and Strohal et al. [19] adopted $^{27}\text{Al}(n,\alpha)^{24}\text{Na}$ reaction as a monitor reaction. Liu et al. [33] adopted $^{93}\text{Nb}(n,2n)^{92}\text{Nb}$ reaction as a monitor reaction. Reported cross section data are normalized at respective neutron energies with respect to IRRFF-II data for respective monitor reactions.

The present results for $^{89}\text{Sr}(n,2n)^{88}\text{Sr}$ reaction are in good agreement with the reported experimental cross sections of Liu et al. [33]. However, the experimental results reported by Ma et al. [30], Holub et al. [68] and Strohal et al. [19] show large deviations from our results. TALYS-1.95 calculations agree with the present results within the error bar, while the evaluated excitation function by the TENDL-2019 library predicts a lower cross section for 14.77 MeV neutron energy for the $^{89}\text{Sr}(n,2n)^{88}\text{Sr}$ reaction.

5.4. $^{84}\text{Sr}(n,2n)^{82}\text{Sr}$ reaction

Fig. 10 shows our measured cross section for $^{84}\text{Sr}(n,2n)^{82}\text{Sr}$ reaction at 14.77 ± 0.17 MeV neutron energy along with reported experimental data from the EXFOR database and evaluated data from the TENDL-2019 library. For this reaction, He et al. [14] and Kanno et al. [49] adopted $^{93}\text{Nb}(n,2n)^{92}\text{Nb}$ reaction as a monitor reaction. Rao et al. [16] adopted $^{56}\text{Fe}(n,p)^{56}\text{Mn}$ reaction as a monitor reaction. Holub et al. [68], Hossain et al. [17] and Strohal et al. [19] adopted $^{27}\text{Al}(n,\alpha)^{24}\text{Na}$ reaction as a monitor reaction. Reported cross section data are normalized at respective neutron energies with respect to IRRFF-II data for respective monitor reactions.

For $^{84}\text{Sr}(n,2n)^{82}\text{Sr}$ reaction, the present results are in good agreement with Gharib-He et al. [14], Kanno et al. [49] and Holub et al. [68]. However, the present results do not agree the reported data of Hussain et al. [17] and Strohal et al. [19]. The above two reported data do not follow the TENDL-2019 evaluation for the same reaction. The present results match with the general trend of the excitation function for the $^{84}\text{Sr}(n,2n)^{82}\text{Sr}$ reaction and the TALYS-1.95 calculations. The TENDL-2019 evaluation is lower than most normalized experimental data above 14 MeV neutron energy.

1.7. The $^{86}\text{Sr}(\gamma, n)^{85}\text{Sr}^m$ and $^{86}\text{Sr}(\gamma, n)^{86}\text{Sr}^m$ reactions

The average cross sections of $^{86}\text{Sr}(\gamma, n)^{85}\text{Sr}^m$ and $^{86}\text{Sr}(\gamma, n)^{86}\text{Sr}^m$ reactions have been measured relative to the cross section of $^{197}\text{Au}(\gamma, n)^{196}\text{Au}^m$ monitor reaction at 15 MeV bremsstrahlung endpoint energy. The total uncertainties in the measured cross sections of $^{86}\text{Sr}(\gamma, n)^{85}\text{Sr}^m$ and $^{86}\text{Sr}(\gamma, n)^{86}\text{Sr}^m$ reactions are 5.37% and 5.81%, respectively with a detailed covariance analysis. The energy dependent cross sections from the TENDL-2019 library and TALYS-1.95 calculations with eight different gamma-ray strength functions have been converted to the average cross section for bremsstrahlung with end point energy of 15 MeV by using equation (1.1) and compared with the present result in Table 1. It is observed from the present work that for both $^{86}\text{Sr}(\gamma, n)^{85}\text{Sr}^m$ and $^{86}\text{Sr}(\gamma, n)^{86}\text{Sr}^m$ reactions, the measured average cross section is not in agreement with the TENDL-2019 evaluation and GSF-1 to GSF-3 although they are of the same order of magnitude of the present results.

6. Conclusions

Cross sections for $^{86}\text{Sr}(n, \alpha)^{82}\text{Sr}^m$, $^{86}\text{Sr}(n, p)^{86}\text{Rb}$, $^{86}\text{Sr}(n, \alpha)^{82}\text{Kr}$, $^{86}\text{Sr}(n, \alpha)^{84}\text{Sr}^m$, $^{86}\text{Sr}(n, \alpha)^{84}\text{Sr}^m$ and $^{86}\text{Sr}(n, \alpha)^{84}\text{Sr}^m$ Sr reactions have been measured at 14.77 ± 0.17 MeV neutron energy with $^{27}\text{Al}(n, \alpha)^{24}\text{Na}$ and $^{27}\text{Al}(n, p)^{27}\text{Mg}$ as monitor reactions. In addition, the average cross sections for $^{86}\text{Sr}(\gamma, n)^{85}\text{Sr}^m$ and $^{86}\text{Sr}(\gamma, n)^{86}\text{Sr}^m$ reactions have been measured using 15 MeV bremsstrahlung photons from a medical LINAC with $^{197}\text{Au}(\gamma, n)^{196}\text{Au}^m$ as a monitor reaction with Activation Technique and off-line gamma-ray spectroscopy. Uncertainty in measured cross section is determined with a detailed covariance analysis. The results from the present work were compared with available normalized EXFOR experimental data and evaluated nuclear data from the TENDL-2019 library. The measured cross sections are found to be in good agreement with certain literature and statistical model calculations with the TALYS-1.95 code. The results of the present study validate nuclear model approaches with increased predictive power. The photoneuclear reaction cross sections are reported for the first time at 15 MeV bremsstrahlung end point energy. The present results highlight alternative production routes for $^{85}\text{Sr}^m$ and $^{86}\text{Sr}^m$.

CRediT authorship contribution statement

E.S. Ganesapathy: Data curation, Formal analysis, Investigation, Methodology, Software, Validation, Writing – original draft. G.T. Bhalerao: Data curation, Formal analysis, Software, Validation. A.B. Phatangare: Resources, Visualization, F.M.D. Attar: Formal analysis. S.S. Dabivale: Funding acquisition, Resources. S.V. Suryanarayana: Conceptualization, Funding acquisition. V.N. Bhorekar: Conceptualization, Project administration, Supervision. S.D. Dhule: Funding acquisition, Investigation, Project administration, Resources, Supervision, Writing – review & editing.

Declaration of competing interest

The authors declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper.

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Isomeric cross sections of the (n, α) reactions on the ^{90}Zr , ^{93}Nb and ^{92}Mo isotopes measured for 13.73 MeV–14.77 MeV and estimated for 10 MeV–20 MeV neutron energies

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ABSTRACT

Isomeric cross sections for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$, $^{93}\text{Nb}(n, \alpha)^{90}\text{Nb}$ and $^{92}\text{Mo}(n, \alpha)^{89}\text{Mo}$ reactions were measured at five neutron energies over the range 13.73 MeV–14.77 MeV using the activation technique in combination with high-resolution γ -ray spectrometry. In the present work, the cross sections are measured for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ and $^{93}\text{Nb}(n, \alpha)^{90}\text{Nb}$ reactions are referenced to the $^{235}\text{U}(n, f)$ standard reaction cross section whereas those measured for $^{92}\text{Mo}(n, \alpha)^{89}\text{Mo}$ reaction are referenced to the $^{235}\text{U}(n, f)$ standard reaction cross section. The cross sections for these reactions were also theoretically estimated using the ENDF-5.2 and TENDL 2.0 codes over the neutron energy range of 10 MeV–20 MeV and compared with the experimental cross sections by making a proper choice of the model parameters. A minimum tight different set of these statistical model calculations were performed by using the consistent set of model parameters along with the pre-equilibrium mechanism in addition to the direct reaction and the statistical Hauser-Feshbach (HF) compound nucleus model. The measured cross sections for these three reactions increase with the increase in neutron energy from 13.73 MeV to 14.77 MeV. As the neutron number increased by one when we go from zirconium to niobium or from niobium to molybdenum, the probability of alpha particle emission also increases at each corresponding neutron energy. The present results indicate that the measured cross section at each neutron energy for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ reaction is found to be the highest as compared to the other two reactions whereas, for the $^{92}\text{Mo}(n, \alpha)^{89}\text{Mo}$ reaction, the measured cross section is found to be the lowest as compared to the other two reactions studied. The results obtained from the present measurement are found to be in good agreement with the calculated reaction cross section based on theoretical models and also with the ones reported by earlier authors.

1. Introduction

The measurement of isomeric cross sections in the neutron-induced reactions with the use of the activation technique is an effective method for knowing mainly the details of (n, α) reactions. This work is also of importance for both the basic and applied research including nuclear technology, and most of these cross sections are given in the ENDF database (Shiba *et al.*, 2014). The cross sections for different nuclear reactions such as (n, p) , (n, α) , (n, d) , (n, t) , (n, sg) have remained a field of interest for the past few decades (Jain *et al.*, 2008, 2014; Arriaga *et al.*, 2006; Sankaranarayanan *et al.*, 2011). ENDF compilation shows that several measurements are available over 14 MeV neutron energy,

however the available cross-section data is literature within the neutron energy range of 13.73 MeV–14.77 MeV are very much scattered.

Measurements of cross sections for the emission of α particles in reactions induced by fast neutrons for neutron-rich nuclei with $N > 83$ in the mass region around 90 are of considerable interest in testing the nuclear models. At higher neutron energies up to 20 MeV this data is important in several fields of applications such as Accelerator-Driven Systems (ADS) for energy production and transmutation of nuclear waste, for medical therapy and in many other fields. Moreover, knowledge of these cross sections for the emission of α particles is also important for assessing the radiation damage in fusion reactors as deuterium, tritium and polonium are used as constituents of structural

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materials in fusion reactors (Jadhav and Basky, 2006). For example, zirconium is used in cladding of nuclear fuel elements and also as a hardening agent in alloys required for nuclear reactors. Niobium is an excellent structural metal particularly when the operations are to be made at elevated temperatures. Moreover, it is also used for aerospace applications, such as controlled nuclear fusion devices. The niobium is used as a first wall and structural material in the experimental fusion reactors. This acts as an efficient microalloying element for steel. Similarly, zirconium metal can maintain the toughness, strength, formability and weldability of the alloys alloyed steel. The alloy of zirconium-niobium is also used for fabricating fuel element claddings of the pressurized water reactors. As these elements are used in reactor technology, the cross-sections for neutron induced reactions are important. Neutron induced reaction cross sections provide the data for the evaluation of generators in these materials under irradiation in reactor and is also of particular importance in the hydrogen and helium gas production through (n, p) and (n, α) reactions.

In the present work, the activation technique has been used to measure the cross sections for the $^{90}\text{Zr}(n, p)^{89}\text{Zr}$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Y}$ and $^{90}\text{Zr}(n, p)^{90}\text{Nb}$ reactions at 11.73 MeV, 14.07 MeV, 14.43 MeV, 14.62 MeV and 14.77 MeV neutron energies. All the three reactions studied have positive Q values and zero threshold energies (IAEA Nuclear Data Centre). These three target nuclei in the mass region $A \leq 90$ constitute excellent test cases for nuclear models in the neutron energy range from 10 MeV to 20 MeV.

Since many reaction channels are opened in the neutron energy range above 14 MeV, the experimental results are compared with the theoretically calculated cross-sections up to the neutron energy of 20 MeV by using global and local-parameter approaches, which take into account direct reactions, pre-equilibration emission (PE), and statistical Hauser-Feshbach (HF) model comprised various contributions. The previous databases obtained by global optimization within the computer codes ELEGANT-2.0 (Wang et al., 2007) and TALYS 1.2 (Koning et al., 2008a) and have been used over the neutron energy range from 10 MeV to 20 MeV.

Attempts were also made to use different values of the parameters like nuclear potential namely neutron and alpha particle, level density, level density parameters and nuclear models, etc., to match the theoretically estimated cross sections with the cross sections measured in the present work as well as those reported literature data compiled in ELEGANT (Wang et al., 2007). The comparison of various calculations including their sensitivity to model approaches and parameters will be complemented by an analysis of recent data measurements.

2. Experiment

2.1. Neutron irradiation

The neutron irradiation work was carried out at the 14 MeV neutron generator laboratory (Mishra, 2003), Department of Physics, Scientific Staff College University, Raun, India. The 14 MeV neutrons were produced by bombarding deuterium ions having an energy of 173 keV on an Li_6 tritium target. On the tritium target, the deuterium beam had a diameter of about 4 mm and current of about 100 μA . For the study of $^{90}\text{Zr}(n, p)^{89}\text{Zr}$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Y}$, $^{90}\text{Nb}(n, p)^{90}\text{Nb}$ and $^{90}\text{Zr}(n, p)^{90}\text{Nb}$ reactions, the samples were made from natural ZrO_2 (99.999%) powder, Nb_2O_5 (99.999%) powder and the molybdenum (1.424%) target foil in the form of a metal foil respectively. For the study of all the three reactions, the samples were prepared for neutron irradiation by packing in a polyethylene bag. The polyethylene bag was folded in such a way that the size of the sample was close to 10 mm \times 10 mm. Following this procedure three sets of samples were made in which each set had five samples. In each experiment performed for each reaction, the samples were irradiated with neutrons by placing them at 0°, 30°, 60°, 90° and 120° angular positions at a distance of 85 mm from the tritium target (Ghoshal et al., 2012).

For the measurement of $^{90}\text{Zr}(n, p)^{89}\text{Zr}$ and $^{90}\text{Zr}(n, \alpha)^{87}\text{Y}$ reaction cross-sections, aluminum in the form of γ -metal foil (99.99%) was used as monitor element and the $^{24}\text{Al}(n, \alpha)^{21}\text{Na}$ reaction was chosen as a standard reaction. Each respective sample (ZrO_2 and Nb_2O_5) was made by sandwiching 2 gm of mixture powder between two aluminum foils with total weight 0.2 gm measured with a microbalance at an accuracy of 1.0 μg . For the $^{90}\text{Zr}(n, p)^{90}\text{Nb}$ reaction the molybdenum samples in the form of metal foils were used and the $^{90}\text{Zr}(n, p)^{90}\text{Nb}$ reaction was chosen as a monitor reaction. Each sample was prepared by taking 0.8 gm of molybdenum foil and 0.2 gm of Fe powder in a polyethylene bag. Five such samples for each element were placed at 0°, 30°, 60°, 90° and 120° angular positions relative to deuterium ion beam direction. The energy of neutrons at these positions correspond to 14.77 MeV, 14.62 MeV, 14.43 MeV, 14.07 MeV and 11.73 MeV (IAEA TECDOC, 2002). These samples of Zr, Nb and Mo were irradiated for a period of 3600 s, 3600 s and 600 s respectively. The same set of irradiations were carried out for each sample following the same procedure. After the irradiation the samples were immediately transferred to the counting room.

2.2. Measurement of the γ -ray activity

The induced γ -ray activities of the irradiated samples were measured with a HPGe detector. The γ -ray detector efficiency and energy calibration of this detector was performed with a Canberra make Multi Channel Standard MCA-3 γ -ray source. Initially the γ -ray activity of the sample irradiated at 0° was measured. Later on, the γ -ray activities of the samples irradiated at 30°, 60°, 90° and 120° were measured in sequence. A total period of 10 s was kept between the end of counting the γ -ray activity of first sample and the start of counting the γ -ray activity of second sample. Accordingly, the total cooling time for each sample was accounted while estimating the actual induced γ -ray activity. The decay data of the radioisotopes ^{89}Zr , ^{87}Y , ^{90}Zr , ^{90}Nb and ^{90}Mo produced via the $^{90}\text{Zr}(n, p)^{89}\text{Zr}$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Y}$, $^{90}\text{Nb}(n, p)^{90}\text{Nb}$, $^{90}\text{Zr}(n, p)^{90}\text{Nb}$ and $^{90}\text{Zr}(n, p)^{90}\text{Nb}$ reactions respectively are given in Table 1 (National Nuclear Data Centre, 2004).

The induced photo-peak activity of 0.588 MeV γ -ray from ^{89}Zr and 1.260 MeV γ -ray from ^{87}Y was measured for a period of 1800 s. The induced photo-peak activity of 0.46 MeV γ -ray from ^{90}Zr and 1.260 MeV γ -ray from ^{90}Nb was measured for a period of 1800 s. Similarly, the induced photo-peak activity of 0.588 MeV γ -ray from ^{90}Zr and 0.847 MeV γ -ray from ^{90}Mo was measured for a period of 60 s.

3. Data analysis

Figs. 1, Fig. 2 and Fig. 3 show the gamma-ray spectrum of ^{89}Zr and ^{87}Y , ^{90}Zr and ^{90}Nb and ^{90}Zr and ^{90}Mo respectively, produced via neutron induced reactions. The spectra shown in these figures are background subtracted and therefore the area under each photo peak is proportional to the negative γ -ray activity induced in the sample. The activation cross sections for the $^{90}\text{Zr}(n, p)^{89}\text{Zr}$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Y}$ and $^{90}\text{Zr}(n, p)^{90}\text{Nb}$ reactions

Table 1
The decay data of the radioisotopes produced in neutron induced reactions (National Nuclear Data Centre, 2004).

Parent Reaction	Abundance (%)	Half-life	$T_{1/2}(\text{h})$	$\lambda(\text{h}^{-1})$
^{89}Zr , ^{89}Zr	14.43 \pm 0.40	1.523 \pm 0.020	0.398	0.127 \pm 0.005
^{87}Y , ^{87}Y	100	1.22 \pm 0.03 s	0.49	0.02 \pm 0.001
^{90}Zr , ^{90}Zr	14.62 \pm 0.10	4.51 \pm 0.03 s	0.322	0.021 \pm 0.001
^{90}Nb , ^{90}Nb	100	14.887 \pm 0.011 s	1.388	0.072
^{90}Mo , ^{90}Mo	0.724 \pm 0.006	2.0739 \pm 0.0008 s	0.247	0.002 \pm 0.0001

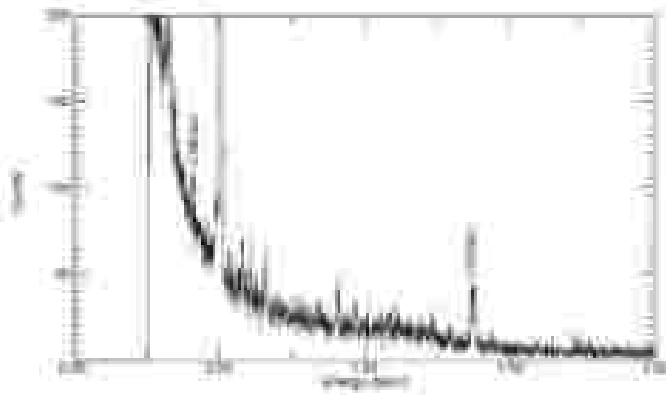


Fig. 1. γ -ray spectra of ^{228}Ac and ^{228}Th radio nuclei produced by irradiating ^{223}Rn and ^{223}Ac respectively with 13.73 MeV neutrons.

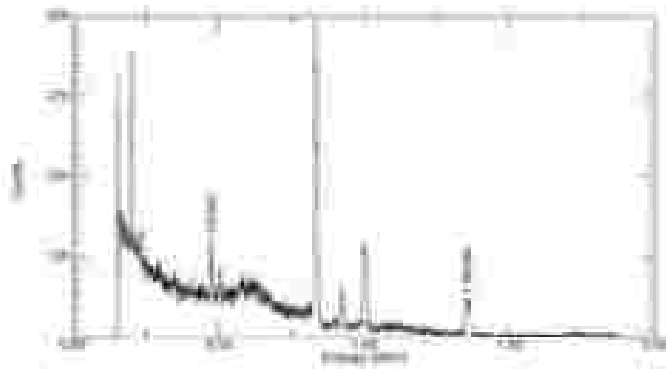


Fig. 2. γ -ray spectra of ^{228}Fr and ^{228}Ra radio nuclei produced by irradiating ^{223}Rn and ^{223}Ac respectively with 13.73 MeV neutrons.

^{223}Rn and ^{223}Ac reactions were obtained at 13.73–14.77 MeV neutron energies using the activation formula given by the following activation equation (1).

$$N_p = \frac{\sigma_{th}(A-1) N_0 \left(1 - e^{-\lambda_p t}\right) e^{-\lambda_p t_p} \left(1 - e^{-\lambda_p t_d}\right)}{\lambda_p \left(1 - e^{-\lambda_p t}\right) e^{-\lambda_p t_p} \left(1 - e^{-\lambda_p t_d}\right)} \quad (1)$$

where σ_{th} is the thermal neutron cross section, A is the number of atoms under the photopeak, λ_p is the photopeak disintegration possibility, ϵ is the detector efficiency, θ_{sp} is the cross section for spallation reaction, t is the decay constant, N is the number of grams of the sample of the element, t_p is the irradiation time, t_d is the cooling time, and t_c is the period for which the activity is measured. The quantity with the subscript d stands for the measuring period.

By considering the uncertainties involved in the measurement of each parameter, the error analysis was carried out using the quadratic method (Taylor, 1997). The flux of the low energy neutrons ($E_n < 10$ MeV) in the D-T reaction is about one order of magnitude lower than that at 14 MeV (Tavakoli et al., 2002). In the present work, the contributions of the low energy neutrons in the cross sections of all the three reactions studied are negligible and were therefore not taken into account. Similarly, the effects of the multiple scattering of neutrons and the inhomogeneities were also not taken into account as the errors induced by these processes are negligibly small. For different parameters, the estimated errors are satisfactory: (i) detector efficiency ($\sim 1.5\%$) (ii) self-absorption of gamma-rays ($< 2.5\%$) (Hatchell and Sinton, 1994) (iii) neutron energy distribution ($< 1\%$) (iv) absolute gamma-ray intensity ($< 1.1\%$) and (v) reference reaction cross section of ^{223}Ac , ^{223}Fr ($< 1.1\%$) (Zayadeh et al., 1995) and reference reaction cross section of ^{223}Rn , ^{223}Ac ($2.8-7\%$) (Tavakoli et al., 2002).

4. Nuclear model based reaction cross section calculations

The theoretical intrinsic cross sections for the ^{223}Rn , ^{223}Ac , ^{223}Fr , ^{223}Th , ^{223}Pa , ^{223}U and ^{223}Np , ^{223}Pu reactions were estimated over 10 MeV–20 MeV neutron energies by using statistical nuclear reaction models using the EMUCEL-3.2 (Morris et al., 2007) and TALYS-1.9 codes (Young et al., 2006a) to investigate if a consistent description can be obtained by the use of these codes. The calculations were performed in the framework of the direct-reaction, PE and statistical Hauser-Feshbach (HF) models in which a mixture of eight different sets of calculations of cross sections for these three reactions were performed by considering the pre-equilibrium mechanism, namely the neutron

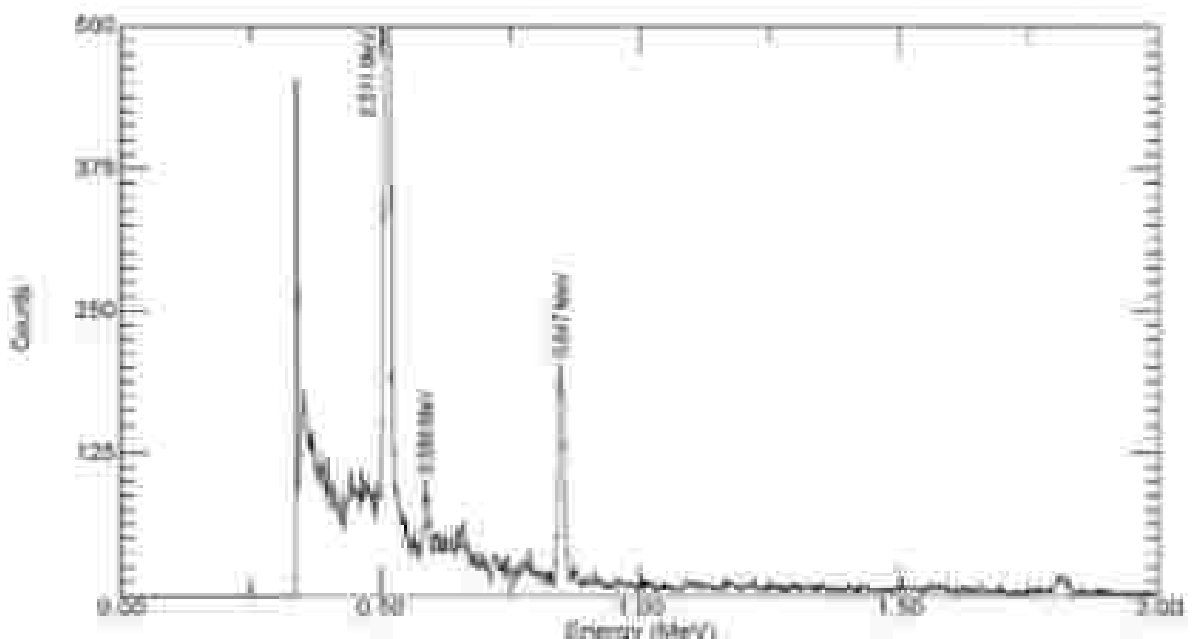


Fig. 3. γ -ray spectra of ^{228}Ac and ^{228}Th radio nuclei produced by irradiating ^{223}Rn and ^{223}Ac respectively with 13.73 MeV neutrons.

model PCROSS code (Gommes and Morada, 1983) of EMPIRE-3.3 and the two-component neutron model (Fensky and Doytshova, 2004) of TALYS-1.8. The first four sets of calculations were performed by means of the computer code EMPIRE-3.3 and the other four sets of calculations were performed by using the TALYS-1.8 code. In three codes, a number of options are available mainly for the nuclear level density, the nuclear potentials etc. Initially, the choice of the parameters was made to obtain a good matching between the theoretical cross sections with those measured in the present work for neutron beam energies between 13.73 MeV and 14.77 MeV by considering the possible neutron channels depending on the compound nucleus excitation energy. Using these consistent sets of input parameter options, the theoretical cross sections of these reactions were estimated between 10 MeV and 20 MeV by the EMPIRE-3.3 and TALYS-1.8 codes, as these models make use of structure and model parameters.

4.1. The EMPIRE-3.3 code

The cross-sections of the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ and $^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$, $\alpha^{87}\text{Zr}^*$ reactions were estimated using the EMPIRE-3.3 code over the neutron energy range of 10 MeV–20 MeV in which all the transmission coefficients for the incident neutron reactions were calculated within the coupled channel approach using ECIS-98 (Krauss, 1994). The calculations of cross sections were carried out using the microscopic combinatorial level density by (Gommes et al., 2007) obtained from the Hauser-Fock-Bergelson method and considering the pre-equilibrium mechanism as defined in the neutron model (Gommes, 1983) as implemented in PCROSS code (Gommes and Morada, 1983). While employing the neutron model, the calculations were performed by choosing the values 1.5 (default) and 3 for the mean free path multiplier namely the MFP parameter. Moreover, in these calculations, for each MFP parameter value, the optical potentials for incident neutrons given by Koning (Koning and Delaroche, 2000) and by Koning (Koning, 1981) were respectively used along with the alpha potential given by Arriaga (Arriaga et al., 1994) for the outgoing alpha particle. Hence there are two sets for each MFP value chosen in PCROSS code and each set of model parameters was used for estimating the cross sections over the neutron energy range of 13.73 MeV–14.77 MeV. Moreover for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$ reaction, the calculations were also performed by considering multiple compound model (Platenke et al., 1988) along with the MFP parameter values 1.5 and 3 in the PCROSS code.

A comparison between the estimated cross sections with those measured in the present work provided important information about the best option of the input parameters available. Using all these four options of the input parameters and their combinations, the cross sections for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ and $^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$, $\alpha^{87}\text{Zr}^*$ reactions were successfully reproduced from 10 MeV to 20 MeV neutron energy using the EMPIRE-3.3 code.

4.2. The TALYS-1.8 code

The TALYS-1.8 code was also used for estimating the cross sections for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ and $^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$, $\alpha^{87}\text{Zr}^*$ reactions over the neutron energy range of 10 MeV–20 MeV in which all the optical model calculations were performed by ECIS-98 (Krauss, 1994). The calculations of the cross sections for these reactions were carried out using the level density model by (Niine et al., 2012), which uses temperature dependent combinatorial level densities with the Hill-Gözeper finite given by Hauser-Fock-Bergelson calculations. Moreover these calculations were performed implementing the pre-equilibrium mechanism via the neutron model (Fensky and Doytshova, 2004) and by using the local, global optical model parameters of neutrons as given by Koning (Koning and Delaroche, 2000) and for the alpha particle as given by Arriaga (Arriaga et al., 1994). For all three reactions, the calculations were performed using a sensitive parameter for the alpha particle reaction namely C_{ang} (Krauss, 2000) with the assigned

values of 1.0 and 1.5. For each value of C_{ang} , two sets of calculations were performed, one by using the neutron local potential and the other set by using the neutron global potential. Moreover for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$ reaction, the calculations were also performed by considering the additional parameters of Gandy (Gandy et al., 2012; Fensky et al., 2006) and complex (Gandy and Gammess, 1983) along with a C_{ang} value of 0.04.

Initially, the calculations were carried out using all the input parameters mentioned above to find out the consistent best option set. The parameters that produced theoretical cross sections close to those measured over 13.73 MeV–14.77 MeV were used for estimating the cross sections for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ and $^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$, $\alpha^{87}\text{Zr}^*$ reactions from 10 MeV to 20 MeV neutron energy.

5. Results and discussion

The experimental cross sections for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$, $\alpha^{87}\text{Zr}^*$ and $^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$, $\alpha^{87}\text{Zr}^*$ reactions were obtained over the neutron energies of 13.73 MeV–14.77 MeV by substituting the values of all the experimental parameters and constants in the activation equation (1) and the values of the cross sections for each reaction under study are given in Table 2. It is evident from Table 2 that, the cross sections of (i) $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$, $\alpha^{87}\text{Zr}^*$ reaction varies from 3 mb to 4.1 mb, (ii) $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ reaction varies from 5 mb to 7 mb and (iii) $^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$ reaction varies from 3.4 mb to 8 mb.

The theoretical cross sections for the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ and $^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$, $\alpha^{87}\text{Zr}^*$ reactions obtained using EMPIRE-3.3 and TALYS-1.8 are given in Table 3, Table 4 (a and b) and Table 5 respectively. In the present work, most of the theoretically estimated cross sections for the three reactions studied are close to the measured cross sections within the experimental error bar.

On comparing the theoretically estimated isotropic cross sections with the respective measured isotropic cross sections given in Table 2, it is observed that the cross sections estimated by the EMPIRE-3.3 code using the MFP parameter value 3 and that estimated by the TALYS-1.8 code using the C_{ang} parameter with a value of 1.5 are in good agreement with the corresponding present cross sections measured in the present work from 13.73 MeV to 14.77 MeV as compared to the other sets of input parameter options used. Using the consistent set of input parameters given in Table 3, the cross sections of the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$ reaction were also estimated using EMPIRE-3.3 and TALYS-1.8 codes and the results are given in Fig. 4. In addition, the cross sections measured in the present work and those reported in literature (Bornerfeldt and Siegel, 1982; Steier et al., 1975; Steier and Siegel, 1983; Kelly et al., 1955; Steier et al., 1968; Flanagan, 2014; Fensky et al., 1977; Gammess et al., 1987; Gammess et al., 1990; Steier et al., 1976; de Meijer et al., 2001; Gode et al., 1980; Moushinski et al., 2006; Meier et al., 1991; Haxelmueller and Seifert, 1985; Haxel, 1971; Haxel, 1994; Steier et al., 1971; Siegel, 1980; Kelly et al., 1957; Sieber et al., 2013; Siegel and Siegel, 1976; Steier and Siegel, 1970) are also plotted in Fig. 4. The plots in Fig. 4 show that, the theoretical cross sections obtained using almost all the best options of input model parameters of the EMPIRE-3.3 and TALYS-1.8 codes mentioned in Table 3 are in good agreement with the cross sections measured in the

Table 2
Measured cross sections of the $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$, $^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$ and $^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$, $\alpha^{87}\text{Zr}^*$ reactions over 13.73 MeV–14.77 MeV neutron energies.

Neutron energy (MeV)	Reported isotropic cross section (mb)		
	$^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}^*$	$^{90}\text{Zr}(n, \alpha)^{87}\text{Zr}$	$^{90}\text{Zr}(n, \alpha)^{86}\text{Zr}$, $\alpha^{87}\text{Zr}^*$
13.73 ± 0.11	3.0 ± 0.3	3.2 ± 0.4	3.8 ± 0.3
14.27 ± 0.11	2.9 ± 0.3	3.2 ± 0.3	3.3 ± 0.3
14.42 ± 0.13	2.7 ± 0.3	3.8 ± 0.3	3.8 ± 0.4
14.68 ± 0.08	4.0 ± 0.3	5.1 ± 0.3	7.0 ± 0.4
14.77 ± 0.08	4.2 ± 0.4	7.0 ± 0.3	8.0 ± 0.4

Table 3
Cross sections for $^{235}\text{U}(n, f)^{235}\text{U}$ reaction estimated over 13.73 MeV–14.77 MeV neutron energies using EMRE-3.2 and TALL-1.8 cells along with cross sections measured in the present work.

Neutron energy (MeV)	Measured fission cross section (mb)	Theoretical fission cross section (mb)							
		EMRE-3.2				TALL-1.8			
		1373.0		1477.0		Only 1.8		Only 1.8	
		neutron potential (eV)	neutron global potential by fitting	neutron potential (eV)	neutron global potential by fitting	neutron total potential by fitting	neutron global potential by fitting	neutron total potential by fitting	neutron global potential by fitting
13.73	3.0 ± 0.3	3.13	3.73	3.23	3.83	3.49	3.57	3.49	3.73
14.07	3.4 ± 0.3	3.35	3.93	3.35	3.94	3.54	3.63	3.53	3.73
14.42	3.7 ± 0.3	3.57	4.14	3.54	4.13	3.69	3.80	3.45	3.85
14.82	4.0 ± 0.3	3.83	4.33	3.83	4.43	3.95	4.03	3.81	4.32
14.77	4.2 ± 0.3	3.93	4.43	3.93	4.53	4.04	4.08	4.07	4.37

Table 4a
Cross sections for $^{235}\text{U}(n, f)^{235}\text{U}$ reaction estimated over 13.73 MeV–14.77 MeV neutron energies using EMRE-3.2 cells along with cross sections measured in the present work.

Neutron energy (MeV)	Measured fission cross section (mb)	Theoretical fission cross section (mb) using EMRE-3.2 cells							
		1373.0				1477.0			
		1373.0		1477.0		1373.0		1477.0	
		neutron potential (eV)	neutron global potential by fitting	neutron potential (eV)	neutron global potential by fitting	neutron potential (eV)	neutron global potential by fitting	neutron potential (eV)	neutron global potential by fitting
13.73	3.0 ± 0.4	4.17	3.59	4.33	3.73	4.17	3.59	3.53	4.45
14.07	3.3 ± 0.3	4.35	3.85	4.43	3.84	4.35	3.85	3.35	4.35
14.42	3.6 ± 0.3	4.51	4.04	4.42	4.01	4.51	4.04	3.35	4.34
14.82	3.9 ± 0.3	4.33	4.23	4.42	4.23	4.33	4.23	3.35	4.35
14.77	4.0 ± 0.3	4.33	4.33	4.42	4.33	4.33	4.33	3.37	4.73

Table 4b
Cross sections for $^{235}\text{U}(n, f)^{235}\text{U}$ reaction estimated over 13.73 MeV–14.77 MeV neutron energies using TALL-1.8 cells along with cross sections measured in the present work.

Neutron energy (MeV)	Measured fission cross section (mb)	Theoretical fission cross section (mb) using TALL-1.8 cells					
		Only 1.8 + colliding + completed		Only 1.8 + colliding + completed		Only 1.8 + colliding + completed	
		neutron total potential by fitting	neutron global potential by fitting	neutron total potential by fitting	neutron global potential by fitting	neutron total potential by fitting	neutron global potential by fitting
		13.73	3.0 ± 0.4	8.33	8.33	21.33	21.33
14.07	3.3 ± 0.3	8.33	8.37	27.33	28.33	30.73	30.87
14.42	3.6 ± 0.3	8.74	8.43	30.82	30.84	33.42	33.82
14.82	3.9 ± 0.3	7.34	7.48	30.22	30.33	32.52	33.84
14.77	4.0 ± 0.3	7.09	7.32	30.22	30.33	33.82	33.24

Table 5
Cross sections for $^{235}\text{U}(n, f)^{235}\text{U}$ reaction estimated over 13.73 MeV–14.77 MeV neutron energies using EMRE-3.2 and TALL-1.8 cells along with cross sections measured in the present work.

Neutron energy (MeV)	Measured fission cross section (mb)	Theoretical fission cross section (mb)							
		EMRE-3.2				TALL-1.8			
		1373.0		1477.0		Only 1.8		Only 1.8	
		neutron potential (eV)	neutron global potential by fitting	neutron potential (eV)	neutron global potential by fitting	neutron total potential	neutron global potential by fitting	neutron total potential	neutron global potential by fitting
13.73	3.0 ± 0.3	3.13	3.43	3.23	3.83	3.49	3.68	3.53	3.73
14.07	3.3 ± 0.3	3.35	3.73	3.35	3.94	3.54	3.63	3.53	3.73
14.42	3.6 ± 0.3	3.57	4.03	3.54	4.13	3.69	3.80	3.45	3.85
14.82	3.9 ± 0.3	3.83	4.33	3.83	4.43	3.95	4.03	3.81	4.32
14.77	4.0 ± 0.3	3.93	4.43	3.93	4.53	4.04	4.08	4.07	4.37

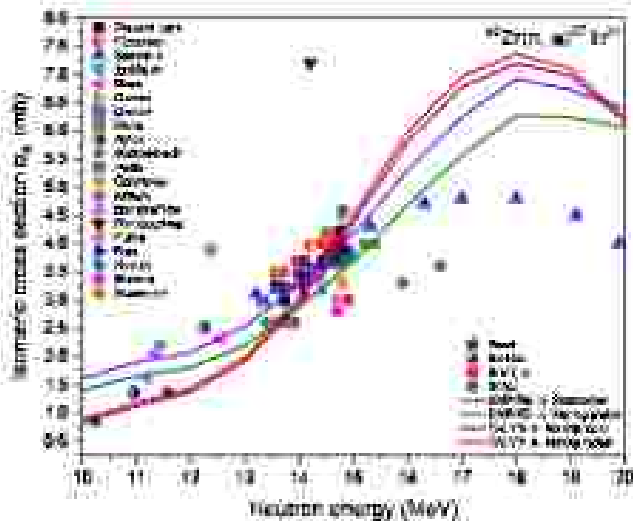


Fig. 4. Cross sections for $^{238}\text{U}(n, \alpha)^{234}\text{Th}$ reaction at different neutron energies (a) measured in the present work and (b) estimated from (c) 10 MeV–20 MeV neutron energies using consistent set of input model parameters of EMPIRE-3.2 and TALYS-1.8 codes in the present work. A few literature cross sections are plotted for comparison.

present work as well as with those reported in literature (Chadwick et al., 1988; Serizawa and Toppo, 1992; Serizawa et al., 1993; Fiksel, 2004; Farris et al., 1977; Gopalakrishnan, 1989; Gellera et al., 1973; Hansen et al., 1973; De March et al., 2000; Sachs et al., 1949; Martakowicz et al., 1990; Motta et al., 1991; Mahalingam and Reddy, 1983; Ganes, K.T., Rajkumar, 1996; Sureshbabu, 1998; Reed, 1960; Saha et al., 1973; Sankaranarayanan, 2010; Egg and Fritzsche, 1978) between 10 MeV and 18.5 MeV.

The cross sections measured by Serizawa *Serizawa et al., 1993* above 16.8 MeV are found to be lower than those estimated theoretically using both codes, whereas the cross sections measured by DeMarch *De March et al., 2000* at 12.17 MeV and by Irinichian *Irinichian et al., 1970* at 14.2 MeV are found to be higher than the theoretically estimated cross sections. Moreover, the cross sections measured by Martakowicz *Martakowicz et al., 1990* at 15.9 MeV and at 18.6 MeV, by Saha *Saha and Fiksel, 1993* and by Saha *Saha et al., 1973* are found to be lower as compared to the theoretically estimated values. The overall picture shows a well determined production cross section of the ^{234}Th isomer for the (n, α) reaction on ^{238}U .

The cross sections for the $^{238}\text{U}(n, \alpha)^{234}\text{Th}$ reaction were calculated using some additional parameters available in both codes as compared to the set of input parameters which were used for the other two (n, α) reactions of the present study. This is mainly because the theoretical cross sections for the reaction obtained using EMPIRE-3.2 or TALYS-1.8 are found to be much lower or much higher than the presently measured cross sections respectively.

Table 4–6 gives a summary of the cross sections for the $^{238}\text{U}(n, \alpha)^{234}\text{Th}$ reaction measured in the present work and estimated using the EMPIRE-3.2 code. It is observed from Table 4–6 that the variation in the obtained theoretical cross sections is very small using all the options of the input parameters used in the theoretical calculations as compared to the variation in the measured (average) cross sections, which is 2 mb over the whole neutron energy range. In the present work, out of all the input parameter options used in the theoretical calculations, only the option with MS3-3 and MS3-1 reduces the theoretical cross-section values close to the measured ones at 12.73 MeV and 14.97 MeV. For the remaining used higher neutron energies, the theoretical cross sections are found to be lower than the corresponding measured ones. Similarly, Table 4–6 gives a summary of the cross sections for the $^{238}\text{U}(n, \alpha)^{234}\text{Th}$ reaction measured in the present work and estimated using the TALYS-1.8 code

by substituting the different values for the Cauchy parameter along with adjusting, singlet and the square local as well as global potentials by Hamann. It is observed from Table 4–6 that the cross-sections obtained using the Cauchy parameter value 3.04 are close to the one measured in the present work as compared to any other set of input parameters options which resulted very large values at each neutron energy.

Similarly, using the consistent set of the input parameters given in Table 4–6 and Table 4–8, the cross sections of the $^{238}\text{U}(n, \alpha)^{234}\text{Th}$ reaction were estimated using EMPIRE-3.2 and TALYS-1.8 codes and the results are shown in Fig. 5. In addition, the cross sections measured in the present work and those reported in literature (Chadwick et al., 1988; Serizawa et al., 1993; Serizawa and Fiksel, 1993; Serizawa et al., 1993; Farris et al., 1977; Gopalakrishnan, 1989; Gellera et al., 1973; Gellera et al., 1973; Hansen et al., 1973; Mahalingam and Reddy, 1983; Motta et al., 1991; Mahalingam and Reddy, 1983; Ganes, K.T., Rajkumar, 1996; Sureshbabu, 1998; Reed, 1960; Saha et al., 1973; Sankaranarayanan, 2010; Egg and Fritzsche, 1978) between 10 MeV and 19 MeV. The plots in Fig. 5 show that the theoretical cross sections obtained using almost all the four options of input model parameters of EMPIRE-3.2 and TALYS-1.8 codes mentioned in Table 4–6 and Table 4–8 are close to the cross sections measured in the present work within the uncertainties as well as to those reported in literature (Chadwick et al., 1988; Serizawa et al., 1993; Serizawa and Fiksel, 1993; Serizawa et al., 1993; Farris et al., 1977; Gopalakrishnan, 1989; Gellera et al., 1973; Gellera et al., 1973; Hansen et al., 1973; Mahalingam and Reddy, 1983; Motta et al., 1991; Mahalingam and Reddy, 1983; Ganes, K.T., Rajkumar, 1996; Sureshbabu, 1998; Reed, 1960; Saha et al., 1973; Sankaranarayanan, 2010; Egg and Fritzsche, 1978) between 10 MeV and 19 MeV. The cross sections measured by Weidhaas *Weidhaas et al., 1988* between 11.65 MeV and 13.15 MeV and above 18.5 MeV are found to be higher than those estimated theoretically using both codes. However, the cross sections measured by Weidhaas between 15.8 MeV and 17 MeV lies between the theoretical cross sections estimated using both codes. Moreover, the cross sections measured by Lankarani *Lankarani et al., 1971* are found to be lower than the theoretically estimated cross sections. The overall picture shows a well determined production cross section of the ^{234}Th isomer for the (n, α) reaction on ^{238}U .

Table 7 gives a summary of the cross sections for $^{238}\text{U}(n, \alpha)^{234}\text{Th}$ reaction measured in the present work and estimated theoretically. On comparing the theoretically estimated cross sections with the respective

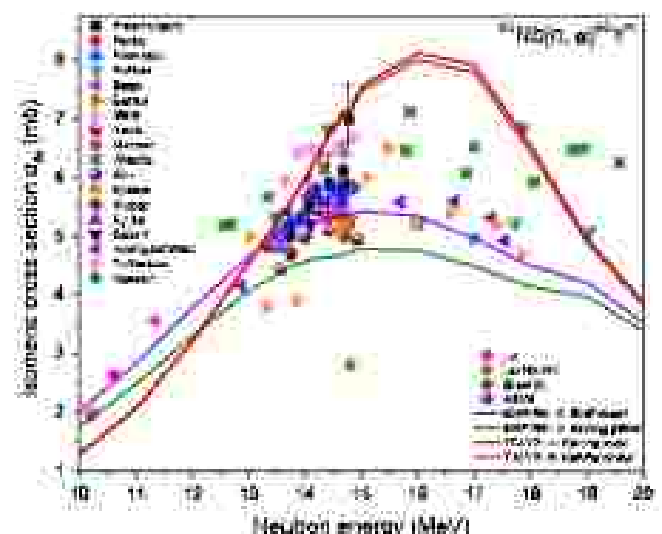


Fig. 5. Cross sections for $^{238}\text{U}(n, \alpha)^{234}\text{Th}$ reaction at different neutron energies (a) measured in the present work and (b) estimated from 10 MeV–20 MeV neutron energies using consistent set of input model parameters of EMPIRE-3.2 and TALYS-1.8 codes in the present work. A few literature cross sections are plotted for comparison.

measured ones given in Table 3, it is observed that the agreement is quite satisfactory as compared to any other set of input parameter options used.

Using the smallest set of input parameters given in Table 3, the theoretical cross sections of the $^{235}\text{U}(n, \alpha)^{231}\text{Th}$ reaction are shown in Fig. 5. In addition, the cross sections measured in the present work and those reported in literature (Gammie et al., 1982; Filimonov, 2014; Fujino et al., 1977; Garcia et al., 1992; Hauer et al., 1972; Isidor et al., 1982; Kanda, 1972; Lu et al., 1970; Moshchukova et al., 1988; Quinn et al., 1974; Rao et al., 1981; Saitoh et al., 2002; Ugg and Kanda, 1975) are also plotted in Fig. 6. The plots in Fig. 6 show that, the theoretical cross sections obtained using almost all the best options of input model parameters of EMRE-3.3 and TALYS-1.8 codes mentioned in Table 3 are also in good agreement with most of those reported in literature (Gammie et al., 1982; Filimonov, 2014; Kanda et al., 1982; Moshchukova et al., 1988; Ugg and Kanda, 1975) between 13 MeV and 15.9 MeV. The cross sections measured by Isidor (Isidor et al., 2002), Garcia (Garcia et al., 1992), Intaravarak (Jee et al., 2001), Fujino (Fujino et al., 1977), most of the measured cross sections by Kanda (Kanda, 1972), Hauer (Hauer et al., 1972) and Quinn (Quinn et al., 1974) are found to be lower than those estimated theoretically using both codes as well as other works mainly. In addition, the cross section measured by Lu (Lu et al., 1970) is found to be higher than those estimated theoretically using both codes. The overall picture shows a well determined production cross section of the ^{231}Th isomer for the α_n reaction on ^{235}U .

From the results shown in Figs. 4–6, it can be observed that the theoretical cross sections for all the three reactions studied are found to decrease around and above 17 MeV as other reaction channels are beginning to emerge.

The measured cross sections for these three reactions increase with the increase in neutron energy. Moreover, from the results of Table 1 it is quite interesting to know that, as the proton number increased by one when we go from protium to carbon or from sodium to molybdenum, the probability of alpha particle emission also increased with the neutron energy. The present results indicate that the measured cross section at each neutron energy for the $^{235}\text{U}(n, \alpha)^{231}\text{Th}$ reaction is found to be the highest as compared to the other two reactions whereas, for the $^{235}\text{U}(n, \alpha)^{231}\text{Th}$ reaction it is found to be the lowest as compared to the other two reactions studied. This is mainly due to the increase in Coulomb repulsion between the proton as we go from aluminum to molybdenum nucleus, because the percentage increase in the proton number is quite large as compared to percentage increase in the number of neutrons in a target nuclear which are responsible for compensating the Coulomb repulsion between the proton. Therefore, these cross sections for the emission of 6 particles in these three reactions reduced by fast neutrons for oxygen-rich nuclei with $Z > 20$ as the mass region > 20 are found to be useful in testing the nuclear models. The results obtained from the measurements are compared with our model calculations and also with works by other authors and good agreement was found to exist between the experimental data and the our model calculations.

4. Conclusions

The isotopic cross sections for the $^{235}\text{U}(n, \alpha)^{231}\text{Th}$, $^{235}\text{U}(n, \alpha)^{231}\text{Th}$ and $^{235}\text{U}(n, \alpha)^{231}\text{Th}$ reactions were measured at five neutron energies over the range of 13.73 MeV–14.77 MeV, using the neutron activation technique. The results obtained were compared with our model based calculated values and also with earlier works reported by other authors and were found to be in good agreement. The measured cross sections increase with the neutron energy from 13.73 MeV to 14.77 MeV. From the results of the present study, it can be concluded that as the proton number increases by one, from aluminium to nickel, or from sodium to molybdenum, the probability of alpha particle emission also increases at each corresponding neutron energy. Moreover, the theoretical cross

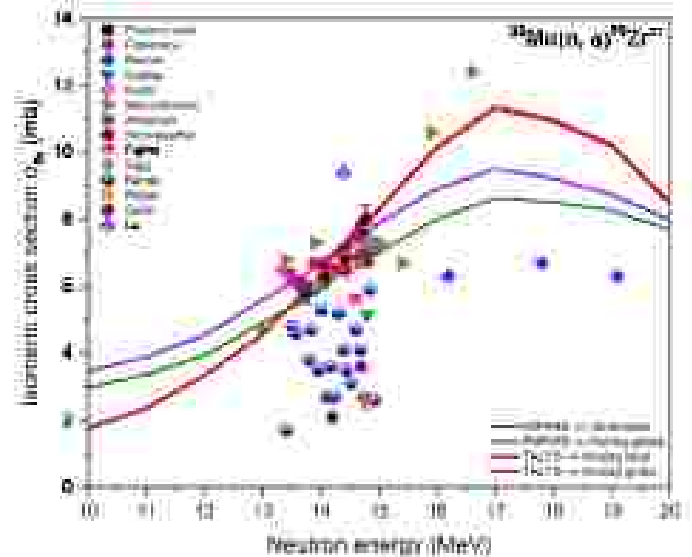


Fig. 6. Cross sections for $^{235}\text{U}(n, \alpha)^{231}\text{Th}$ reaction at different neutron energies (a) measured in the present work and (b) estimated over 10 MeV–20 MeV neutron energies using smallest set of input model parameters of EMRE-3.3 and TALYS-1.8 codes in the present work. A few literature cross sections are plotted for comparison.

sections obtained using the mean free path multiplier namely MFP for EMRE-3.3 and those obtained using a sensitive parameter for alpha particle emission, namely Calpha for TALYS-1.8, plays an important role in getting the cross-section values close to the measured ones in the present work. These experimental results are important for reactor technology applications and constitute an addition to the ENDF database.

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Declaration of competing interest

The authors declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper.

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We do not have any objection about him for getting M.Phil. Ph.D. studies in our Institute.

Have signed this No Objection Certificate on behalf of our Institute and Kamini V. Desai College, K. J. Somaiya Institute of Technical Education.

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Effect of low energy argon ion irradiation on work function of AISI 304L stainless steel

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Abstract

The effect of low-energy Ar⁺ ion irradiation on the work function of stainless steel AISI 304L (SS-304L) was studied by varying energy and fluence of Ar⁺ ion. The irradiation of Ar⁺ ions on stainless steel creates several vacancies in the target material which resulted a change in work function. The retarding field diode method was used for the measurement of work function. Results reveal work function decreases with an increase in ion energy (for fixed ion fluence) of irradiated Ar⁺ ion. Furthermore, it was observed that at varying ion fluence (for fixed ion energy) the decrease in work function value was more prominently, but at higher fluence, it again increases. In both (energy and fluence) cases of irradiation, the displacement per atom (DPA) in the material has been estimated with the stopping range using the SRIM 2013 (0) program and is correlated with the experimental observation. Overall, the maximum work function was observed to be decreased by ~ 7.28% relative to the pristine sample in the case of fluence variation keeping the energy constant at 30 keV. The results indicate that low-energy ion irradiation can be utilized for work function modulation of materials and can be optimized by controlling ion fluence. The results are useful for further understanding of corrosion rate of materials and the data are extremely important for various nuclear reactors, where these materials are used.

Keywords Low energy ion irradiation · DPA · Work function · SS-304L

1 Introduction

Stainless Steel is an important material for many decades due to its good stability, specific material properties, easy fabrication, broad applicability in critical parts, etc. Due to the long durability and stability of stainless steel, it has a very high demand in metallurgical processes, construction,

various engineering applications, etc. [1, 2]. However, Stainless steel is a corrosive metal when it comes in contact with a humid environment. M. Struettmann et al. investigated the kinetics of corrosion rate and corrosion potential of the metals, such as iron and steel, during drying of wetted metal surfaces. They have shown if the surface kept in humid environment the voltage drop across the oxide scale formed on top of the iron surface is small as a result corrosion rate changes [3]. M. Briceau et al. reported ion irradiation on 304 stainless steel which forms defects on the mobility of dislocations, dislocation sources and newly generated dislocations. In this work they have reported that mobility of dislocations is altered due to ion irradiation and in depth analysis is given for the same [4]. The content of Chromium (Cr) and Nickel (Ni) in stainless steel is responsible for its superior corrosion resistance [5]. Austenitic stainless steel used in biomaterials engineering application. Reports are available on the measurements made for the corrosion resistance with electropolishing methods for austenitic stainless steel [6, 7]. To protect from corrosion of austenitic stainless

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steel, electrochemical treatment was also been used [8]. Earlier, Akon Horsuth et al. investigated the behaviour of work function for the stainless steel material by H^+ and Ar^+ ions irradiation. It was found that the stability of corrosion depends on the work function of the material as well as on the projectile ion species [9]. Controlling the corrosion rate is of prime importance from the application point of view.

The metal or semiconductors when exposed to high energy radiation leads to the formation of lattice defects, such as vacancies as well as dislocation loops near the interface. As a result of which materials properties may get altered [10–12]. G. D. Tolstoukhov et al. studied the nano hardness and microstructural changes in SS-316 martensitic stainless steel by influence of different gaseous (hydrogen, helium, argon) ion irradiation. They found that regardless of the type of incident energetic ions, the formation of radiation-induced dislocation structure is responsible for hardening of the steel [13]. They further extended their work for the swelling behavior of 18Cr10NiTi austenitic stainless steel irradiated with energetic Ar^+ ions which shows changing behavior of microstructure and swelling occur after 0.7–1.4 MeV Ar^+ irradiations in the temperature range of 550–700 °C to doses between of 40 and 105 DPA. He revealed that microstructure strongly based on Ar^+ concentration, implantation temperature and level of displacements per atom [14]. The heavy ion irradiation causes a change in the magnetic properties of the soft magnetic alloys as a result of a reduction in coercivity and removal of anisotropy [15]. Stainless steel is an important material for accelerators as well as nuclear reactors. In the accelerators or nuclear reactors, the material gets exposed to various radiation, such as the proton, neutron, or ions. Exposure to such radiation causes activations and deteriorations in the physical and chemical properties of the materials [16]. Very recently 247 MeV Ar ions irradiation on martensitic steel (SIMP) material was reported by Canteng Yao et al. They reported that due to ion irradiation thickness of surface oxides increases with modification in microstructure of oxides [17]. Austenitic stainless steel (ASS) was irradiated with 1.1 MeV Nitrogen ions which show a hardening behavior after irradiation reported by Chuanliang Xu et al. [18]. Thus, as mentioned above, there is a massive scope of the stainless-steel material in various fields, such as construction, metallurgy, biomedical, nuclear reactors, electronic, etc. However, stainless-steel material has tendency that they easily gets corroded due to various reasons and thus their properties gets degraded. Various physical and chemical approaches are used to reduce the corrosion of this material. In this work also, our aim is to explore the effect of ion irradiation on SS-304L work function, which is related to corrosion property.

A very few reports are available for Ar^+ ions irradiation on stainless steel. In the present work, we report the effect of

Ar^+ ion irradiation on the SS-304L material. The Paper is divided into two part. In first part, study on Ar^+ ion irradiation on the work function of SS-304L, at different ion energy Ar^+ ion (keeping the ion fluence fix) was carried out and in second part of study on Ar^+ ion irradiation on the work function of SS-304L, at different ion fluences (keeping ion energy fix at 30 keV) was carried out. For both the cases, we studied the variation in work function along with the calculations of DPA. The observed variation in work function is implied to change the corrosion property.

2 Experimental method

2.1 Sample preparation

In the present work, a piece of SS-304L material of size 10 mm × 10 mm × 0.5 mm was cut and taken directly for experiments. The cleansing of samples was done with soap water, ethanol, and ultra-sonication for 5 min at room temperature. The sample was further sputtered for 60 min in isopropanol at room temperature. After that, the samples were left for drying overnight under ambient conditions.

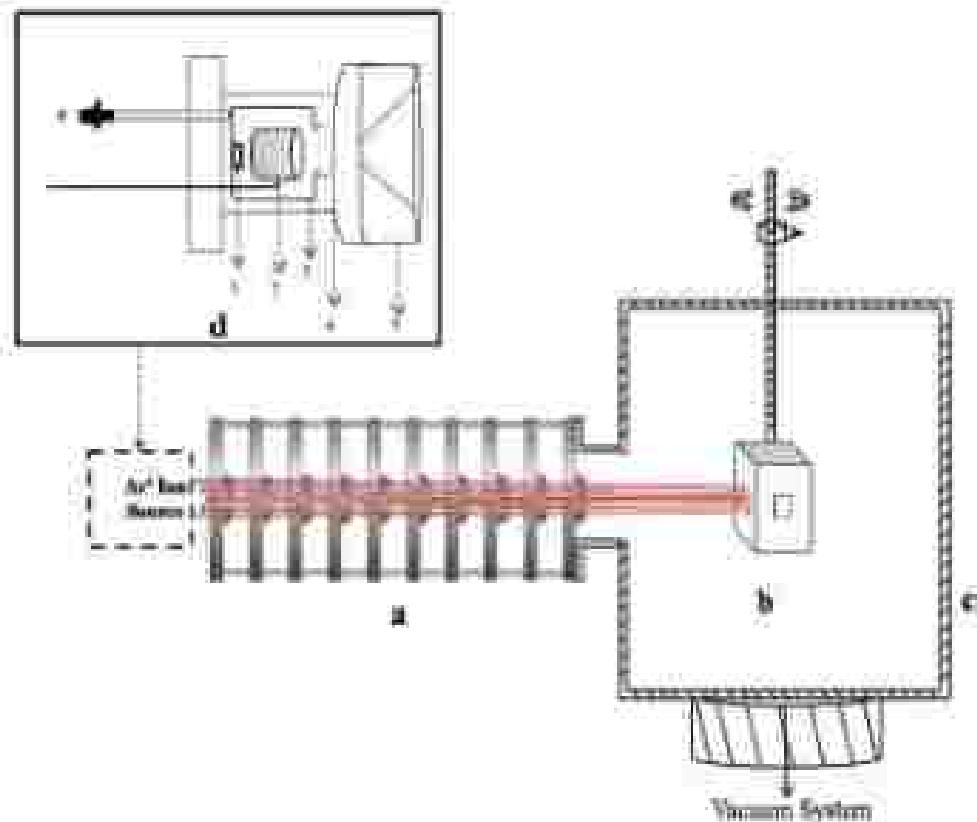
2.2 Ion irradiation

The indigenously developed low energy (5–100 keV) ion irradiation facility at the Department of Physics, Savitribai Phule Pune University was used for ion irradiation purpose. Figure 1 shows a schematic view of the ion irradiation facility. In this system, the penning ionization gauge (PIG) type gaseous ion source is used to get the ion species.

Gaseous ion sources primarily consist of cylindrical anodes and cathodes. It is a cold cathode discharge type ion source. In the cathode region, the gas to be ionized is injected through a gas needle valve. The cathode is a hollow cylinder made from mild steel (MS). Inside the cathode cylinder, a hollow thin anode cylinder is placed. A Neodymium permanent magnet (NdFeB) is placed at the center of the cathode bottom face. The detailed schematic of the ion source is shown in inset of Fig. 1a.

Potential difference of about 3 kV is applied between the cathode and anode. When gas is fed into the cathode region, the stray electrons gets accelerated and collide with neutral gas atoms while traveling toward the anode, thereby creating electric discharge. Electrons from first ionization further get accelerated and gain enough energy to knock out electrons from other neutral atoms. This continuous process creates a plasma at the central part of anode. The permanent magnet helps in increasing the density and sustaining the plasma. Finally, the ions are extracted from the plasma by applying suitable potential to extraction electrode.

Fig. 1 Schematic view of ion irradiation facility of energy ranging 5–100 keV. **a** Ion acceleration tube with ion source, **b** Sample holder cube, **c** Experimental Chamber placed on the vacuum system, **d** Schematic of the pressure indication gauge (DGD type) gauges ion source: 1—Magnet, 2—Anode, 3—Cathode, 4—Nylon Case, 5—Filtration, 6—Gas Inlet



The total potential drops due to resistor chain across anode and fast electrodes of accelerator from where ions are extracted and falls on the sample holder results in the total ion energy, which is the kinetic energy of ions. The ion energy can be varied by increasing the high-voltage between anode and fast extraction electrode. The ion fluence can be varied by varying ion irradiation time.

The SS-304L sample was placed on the copper sample holder and it was suspended with Wilson port. The desired Ar^+ ion energy was used for the sample irradiation. The ion current density was $3.53 \mu A cm^{-2} \pm 0.015\%$ and it was kept constant throughout the experiment under the vacuum pressure of 4×10^{-4} Pa. Before irradiation, the base pressure in the chamber was maintained at 1×10^{-4} Pa. At a time four samples were placed on a hollow cubical sample holder, one sample placed on each face of the cube (leaving the top and bottom face empty). One by one each sample was exposed to the Ar^+ ion beam by rotating the sample holder by 90° without breaking vacuum pressure. These irradiated samples were then used for further analysis.

2.3 DPA calculations

Estimation of ion distribution in the target material was computed using the Monte Carlo simulation Code with SRIM-13.00 Software. The dislocation of the target atoms

in the total phase of a material by bombarding ions creates vacancies. The vacancies created per ion per unit length give the displacement per ion per unit length. The SRIM-13.00 also estimates stopping energy and projected range of ions in the matter along with vacancies created per ion per unit length [19–22]. The total number of displaced atoms in a unit volume over a total number of atoms in the material gives a DPA [9, 23, 24].

The ion energy, angle of incidence of ions, elemental composition, and atomic density of target material are the required parameters to find out the full cascade of ion distribution in the target material which was used as input for SRIM-13.00. The angle of incidence for ion was kept at 0° and atomic density input for SS-304L, was $7.78 g/cm^3$. All the results recorded from SRIM-13.00 were the average of 9999 ion trajectories. The required calculation of DPA was done by following Eq. 1 given by Akos Horvath et al [18]

$$\text{Peak Area} = \int_{x_1}^{x_2} DPA(x) dx \quad (1)$$

Here, x_2 is the projectile depth, where we get a maximum of $DPA(x)$, full-width half maxima (FWHM) have been computed in the region which is denoted by $x_1 + x_2$ for the $DPA(x)$ distribution.

2.4 Measurement of work function

Work function measurement for SS-304L samples was carried out using retarding field diode method with the help of a low energy electron beam. The design of the electron gun is similar to that as discussed by Kläuner and Bau [25]. Work function measurement of a variety of samples viz. metals, semiconductors are well known and reported earlier, and [26, 27] almost similar method applies to insulators too.

In the present work, work function measurement system used consists of an electron gun and sample manipulator assembly enclosed in the Stainless Steel high vacuum chamber. The polycrystalline gold sample was used as a reference sample which was placed on the sample manipulator along with other samples. The work function of gold ($\phi = 4.9 \text{ eV}$) was taken as a reference for calculating the work function of the pristine and irradiated SS-304L samples. In the retarding field diode method, the sample was kept at a negative potential relative to cathode, i.e., filament of the electron gun. When the sample and filament are at the same potential, the sample sees the electron above its vacuum level, with a kinetic energy (Eq. 2) equal to

$$K.E. = eV - \phi_s \quad (2)$$

where eV is the kinetic energy of electrons (in eV) ejected from the electron gun and ϕ_s is sample's work function.

However, if we apply a retarding potential (V_R) to a sample, the sample current will reduce in magnitude, and approach a zero value when the vacuum level approaches the electron kinetic energy. Prior to this same measurement is done for reference sample. Using the plot of sample current vs retarding potential on a semi-logarithmic scale one obtains the value of the work function by measuring the slope of the linear region of the graph compared to a reference sample. The work function of SS-304L samples were measured before and after Ar^+ ions irradiation for two different conditions, (i) at varying ion energy keeping ion fluence constant and (ii) at varying ion fluence keeping the ion energy constant. These work function measurements were carried out at vacuum pressure of $3 \times 10^{-4} \text{ Pa}$.

2.5 Electrochemical measurement

The AUTOLAB PGSTAT302N was used for the corrosion I - V test using three-electrode cell measurement. Platinum (Pt) foil was used as a counter electrode, a Silver/Silver Chloride (Ag/AgCl) was used as a reference electrode, and a stainless-steel specimen (surface area of $1 \times 1 \text{ cm}^2$) was used as the working electrode. Potentiodynamic polarization was used to investigate the corrosion stability of AISI 304L stainless steel in the range of -0.5 to 0.5 V at a scan

rate of 1 mV/s vs Ag/AgCl at ambient temperature. Tafel extrapolation method was used for the corrosion rate analysis. The corrosion behavior of AISI 304L stainless steel was studied with polarization experiments in an aqueous solution of 0.05 M NaCl [28–31].

3 Results and discussion

3.1 Work function analysis

To calculate the work function using the retarding field diode method (described in Sect. 2.4), initially sample current (I_s) was measured as a function of retarding potential (V_R). Graph of sample current as a function of retarding potential is shown in Fig. 2A.

As the retarding potential was increased the sample current was decreased for all the samples, as it was expected. However, it was observed that with increase in the ion irradiation energy, the change in sample current increased with respect to pristine sample. Furthermore, no significant difference in sample current within the irradiated samples (for all the irradiated samples) was observed at any energy. To understand the effect more clearly, a log plot of sample current vs retarding potential was plotted and is shown in Fig. 2B.

It can be seen from the graph that there is a change in values of current for pristine sample compared to irradiation samples at any typical value of retarding potential. By taking the linear and parallel part of the low current region, considering gold sample as reference, we estimated the work function values. From the estimated values, variation in work-function (ϕ) was plotted as a function of ion energy and is shown in Fig. 3A.

As evident from the figure, it can be clearly seen that there is substantial change in work function value between pristine and first irradiated sample (i.e., 10 keV); however, no significant change in the work-function values was observed as we increase ion energy (within the irradiated samples). This may be because, the energy and the fluence we are using here are only able to sputter the top surface of the SS-304L, and further change in energy does not affect the work-function values. The maximum depth for 40 keV argon ion in SS-304L sample is $\sim 19 \text{ nm}$. As fluence is constant for all the energies used for irradiation, the major damage or defects per unit length is not changing substantially. The defects are mainly created by number of ions falling per unit area of the sample. Therefore, even if we change the energy from 10 to 40 keV it is not affecting work function values as a result we observe almost constant work function within irradiated samples. To verify our argument, we made DPA calculations using SRIM 13.00 software. We performed the calculations for displacement damage as a function of depth

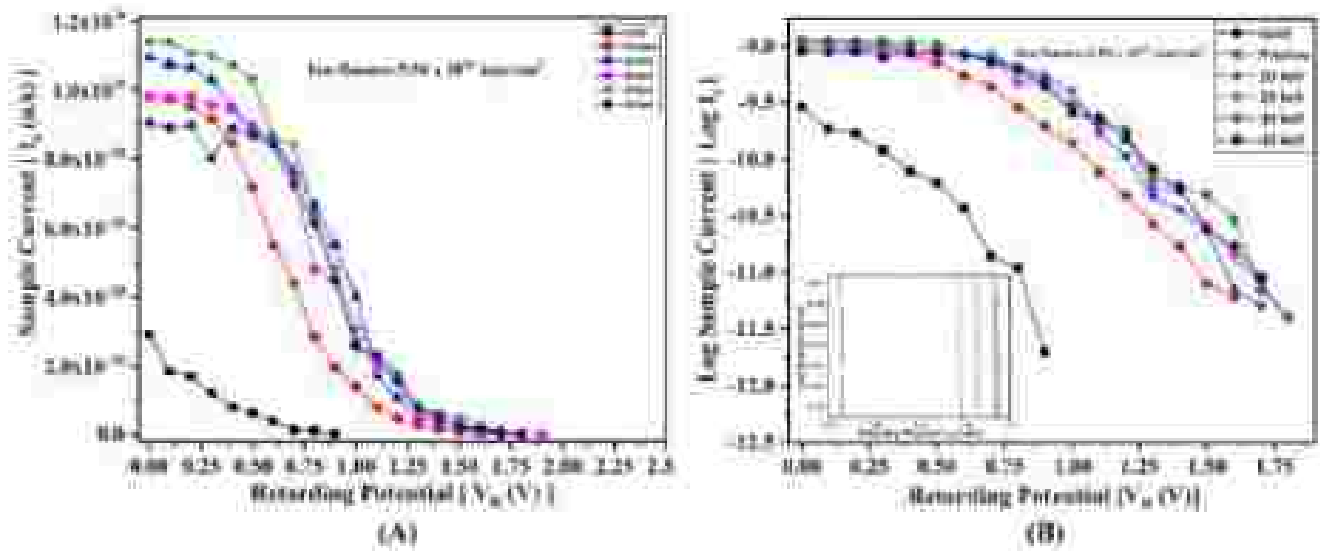
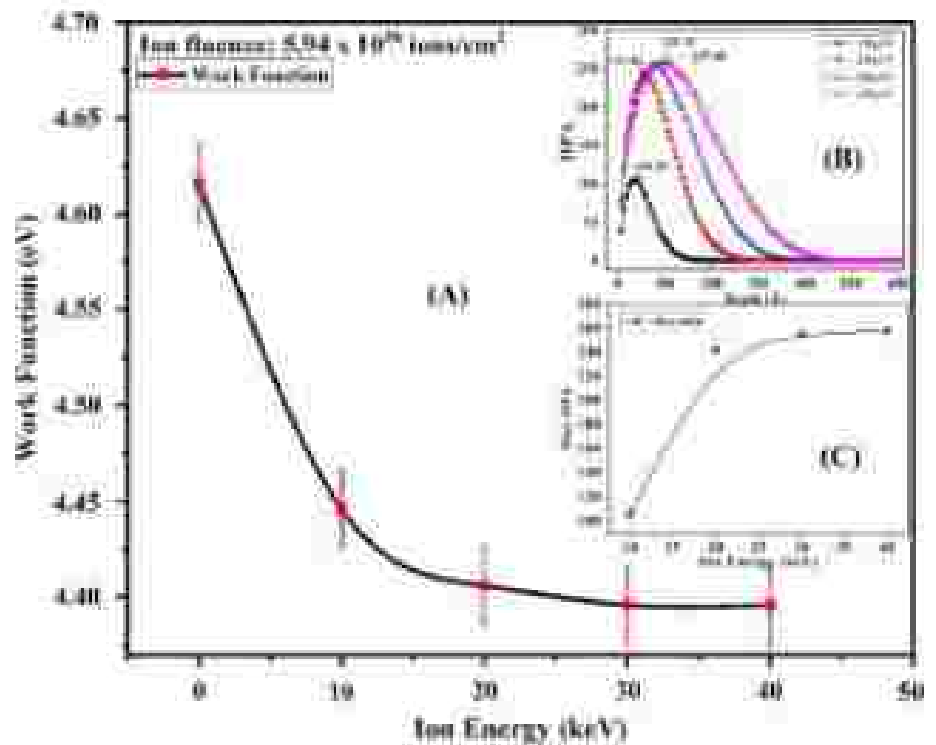


Fig. 2 Graph of A sample current I_s (mA) as a function of scanning potential V_s (V), B $\log I_s$ as a function of scanning potential V_s for various ion energies keeping the flux constant

Fig. 3 Graph of A work function as a function of ion energy, B distribution of DPA as a function of depth, and C Max DPA as a function of ion energy at constant ion fluence 5.94×10^{16} ions/cm²



for Ar^+ ion in SS-304L samples at varying ion energy (keeping fluence constant).

In this specific case, ion energy was varied and fluence was kept constant (5.94×10^{16} ions/cm²). With increasing ion energy from 20 to 40 keV, the DPA value has changed from 241.82 to 257.8, i.e. only 6% change has been observed. DPA is correlated with damage in the surface of the material, which in turn changes the Wigner Seitz

radius thereby affecting the work function value. Because of the lower damage, the change in the Wigner Seitz radius is smaller, which results in an insignificant change in the work function values, as can be seen in Fig. 3A. The sputtering yield estimated from SRIM for the ion energy 10 keV was obtained to be 5.17 atoms/ion, whereas for ion energy 40 keV it is 4.80 atoms/ion. Change in sputtering

yield is also not significant, which may be the other reason behind insignificant change in the work function values.

Figure 3B shows that as the Ar^+ ion energy is increased the penetration depth increases and the peak of DPA curve also increases. For 40 keV the peak of DPA curve is obtain at 100Å. Furthermore, we checked the total DPA as a function of increasing ion energy, as shown in Fig. 3C. From the graph it is observed that the maximum DPA saturates at higher energies.

Both calculation results agree with our experimentally observed work-function values. It can be correlated as follows, since the displacement damage created by 10 keV and 40 keV ions is almost same, the change in work function which is related to displacement damage also remains constant. Now, the work function (Φ) is also related to electrostatic potential ($\delta\phi$) of the metal surface and the electron Fermi energy (ϵ_f) by the relation given in Eq. 3.

$$\Phi = \delta\phi - \epsilon_f \quad (3)$$

$\delta\phi$, ϵ_f both are related to Wigner-Seitz radius (r_s) for given metal, as a decreasing exponential function [9, 28–30]. In general, r_s defined as a radius of sphere, whose volume is equal to mean volume per atom in a solid. Now, if r_s increases, $\delta\phi$, ϵ_f both may decrease and depending upon whether your $\delta\phi$ or ϵ_f is dominating work function will change. In our experimental observation, among the irradiated sample the work-function (Φ) is not changing. This may be because, as we increase the energy, the damage/displacements are neither affecting $\delta\phi$ nor ϵ_f (within the irradiated samples) as ion fluence is constant. However, as compare

to pristine sample, certainly some defects/displacement has been created on the surface of the SS-304L due to irradiation, which has increased r_s , which resulted in decrease in $\delta\phi$ and ϵ_f eventually showing reduction in work function (Φ).

To verify our above argument, we further performed second set of experiment in which ion energy was kept constant and ion fluence was varied.

In this set of experiment, ion energy was kept constant at 30 keV and the ion fluence from varied from 9.9×10^{14} ions/cm² to 1.18×10^{17} ions/cm². Figure 4A shows measured sample current as a function of retarding potential. It was observed that there was a gradual increase and then a decrease in the sample current values to make it close to zero with individual retarding potential values for individual ion fluences. To get more clarity at low current region (close to zero) a log plot was plotted. Figure 4B shows samples Log current as a function of retarding potential. It is observed that irradiated samples current were retarded for higher values as a result the differences in retarding potential were higher.

From both the graphs, it is not very clear how much it has affected the surface, so we estimated the work-function values as a function of fluence, at constant ion energy of 30 keV. The graph is shown in Fig. 5A. We can clearly observe that with increase in ion fluence the work-function value has decreased lowest up to 4.27 eV for the ion fluence of 5.94×10^{16} ions/cm² and then gradually increased back up to 4.45 eV for the ion fluence of 1.18×10^{17} ions/cm².

These results clearly indicate the definite effect of ion fluence on the surface and subsurface region of the material, which resulted in the work function change. As it was

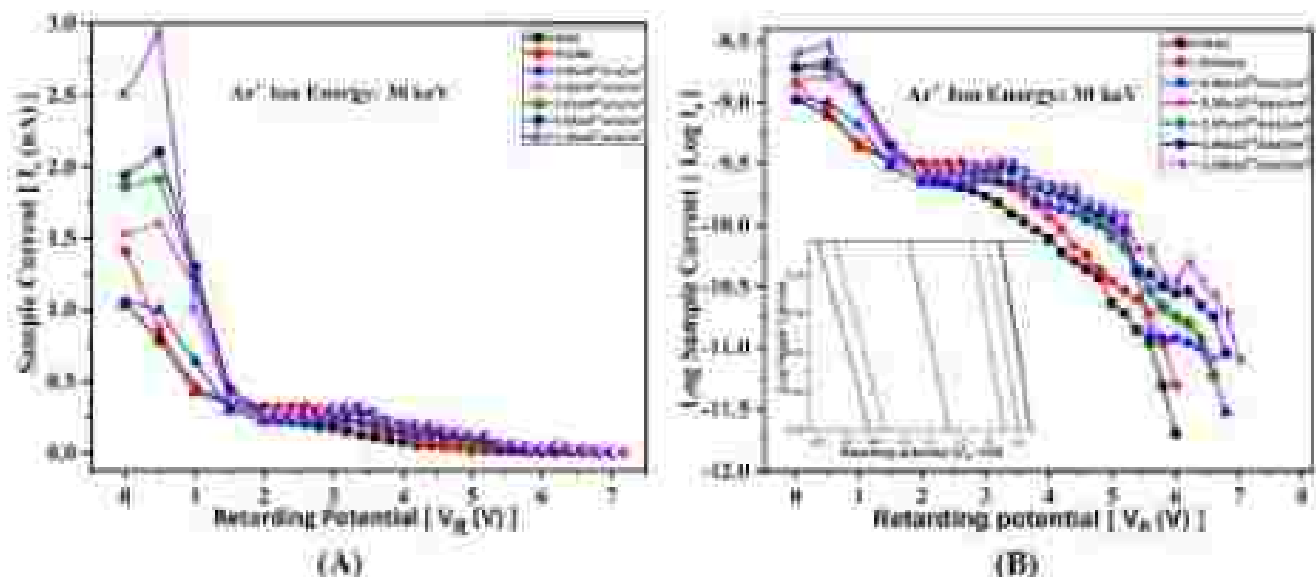
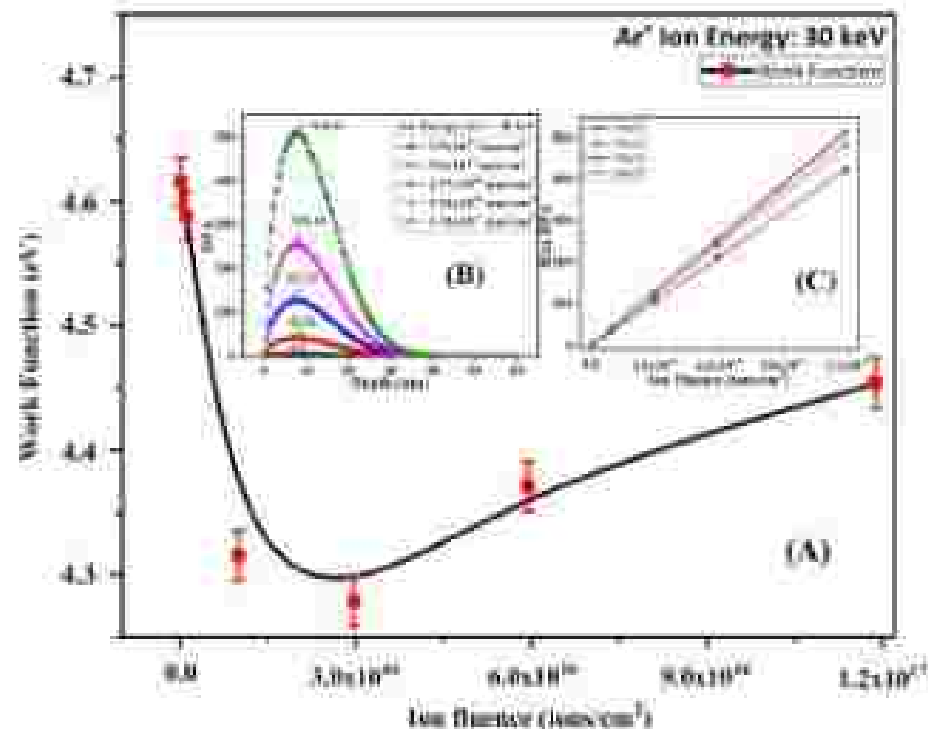


Fig. 4 Graph of A sample current I_s (nA) as a function of retarding potential V_R ; B log (I_s) as a function of retarding potential V_R for various ion fluences at constant ion energy 30 keV

Fig. 5 Graph of A work function as a function of ion fluence, B Distribution of DPA determined for 30 keV Ar^+ ion irradiation, and C Max DPA as a function of ion fluence at constant ion energy 30 keV



argument in previous section that the fluence, i.e., number of ions falling per unit area plays a role in creating defect/displacement which might result in change in work-function values seems to be true. However, it is showing a non-linear behaviour of initial decrease and then increase in the work-function with increase in the ion fluence, which needs to be understood.

For this purpose, we again plotted the DPA values as a function of depth and ion fluence, and is shown in Fig. 5B, C, respectively. Figure 5B shows the area under the curve keeps on increasing with increase in the ion fluence without change in the depth value. In addition, from Fig. 5C, we can see that, as the fluence increases the DPA increases linearly. Thus, both the results indicate that, the number of displacements increases with increase in the ion fluences. This increase in the defects have resulted in decrease in the work-function. However, this is not following, what we have observed experimentally. Experimentally we observe that initially there is decrease in work function up to certain fluence and then it increases with fluence. This decrease and increasing trend of work-function can be again be explained on the basis of Wigner-Seitz radius following the relation given by Eq. 3. As the fluence is increasing at initial stages, i.e., at low fluence, change in r_s is due to both ϕ_0 and c_0 (where both are competing). After certain threshold of fluence ϕ_0 dominates as compare to change in c_0 , which results in increase in work function (4) [32].

In contrast with previous observations for change of work function as function of ion energy, when ion fluence is varied

(keeping ion energy constant 30 keV), the DPA change is 91.67%. Which resulted in change in Wigner-Seitz radius in a significant way causing change in work function values. These results indicate that ion fluence variations dominate modification of work function. Similar results are also been observed by Akos Horvath et al. [9] and are in agreement with these experimental findings.

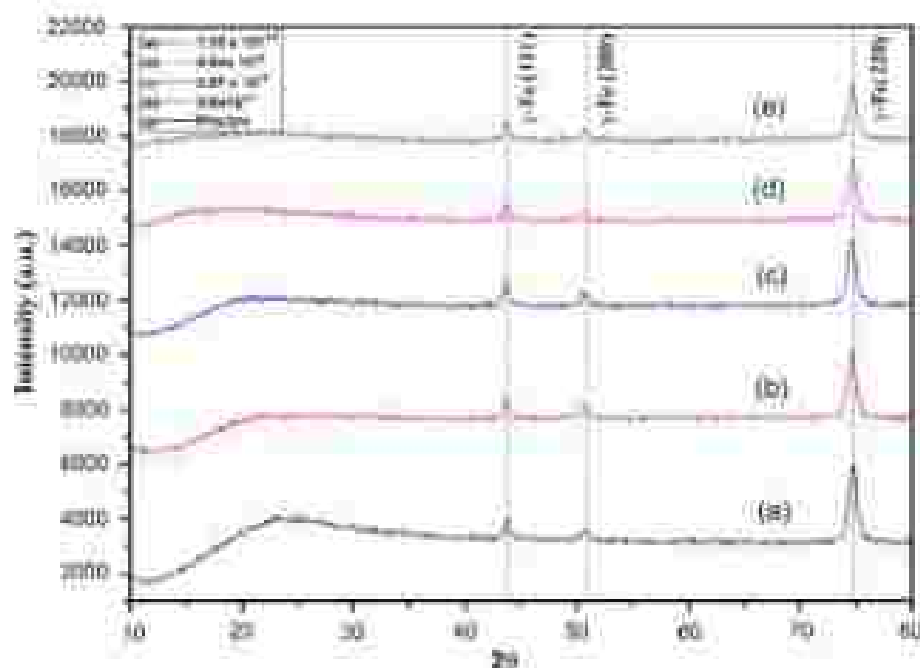
3.2 XRD analysis

Figure 6 shows the XRD pattern for pristine and irradiated AISI 304L SS samples with different ion fluences pristine (a), 9.9×10^{15} ions/cm² (b), 2.97×10^{16} ions/cm² (c), 5.94×10^{16} ions/cm² (d), and 1.18×10^{17} ions/cm² (e), respectively. XRD peaks observed at 2θ values 43.7° , 50.7° , 74.8° corresponds to (111), (200), (220) planes indicating austenitic γ -Fe phase accordance with the JCPDS card No: (00-003-0397) [33–38]. It has been observed that with increase in ion fluence, the peak intensities are decreasing. The peak intensity of highest fluence decreased up to 32% compared with pristine sample.

3.3 SEM Analysis

Figure 7 shows SEM (Surface morphology) of pristine and irradiated AISI 304L stainless steel samples for Fig. 7A Pristine (B) 9.9×10^{15} ions/cm² (C) 2.97×10^{16} ions/cm², (D) 5.94×10^{16} ions/cm² and (E) 1.18×10^{17} ions/cm², respectively. Figure 7A of pristine and Fig. 7B of 9.9×10^{15} ions/cm²

Fig. 6 X-ray diffraction patterns of AISI 304L SS material before and after Ar^+ ion irradiation at various ion fluences



cm^2 irradiated sample shows a smooth surface. Figure 7C of 2.97×10^{18} ions/ cm^2 irradiated sample shows little rough surface with line formation. Further increase in ion fluence, Fig. 7D, shows highest roughness with line formation and the highest fluence sample, Fig. 7E, shows quite smooth surface, however, as we increase the ion fluence the roughness goes on increasing up to the ion fluence of 5.94×10^{18} ions/ cm^2 and then at highest ion fluence, the roughness has been decreased.

3.4 Potentiodynamic polarization studies

As work function is related to corrosion rate, we further performed the corrosion test experiments to validate our findings. Figure 8A shows potentiodynamic polarization curve for pristine and irradiated samples. The corrosion potential (E_{corr}) and corrosion current density (I_{corr}) were obtained from the polarization curve and the values are tabulated in Table 1. From the graph it was observed that as the ion fluence increases, corrosion potential values also increased (shifted right) and corrosion current values were decreased. All measured values of I_{corr} and E_{corr} obtained from the Tafel extrapolation method [34, 39, 40] have been tabulated in Table 1. The graph was further utilized for the calculation of corrosion resistance and corrosion rate. Figure 8B shows a corrosion resistance and corrosion rate as a function of ion fluence at constant ion energy. The corrosion resistance increases, whereas corrosion rates decrease with an increase in ion fluence. The obtained results are in corroboration with our work function values as explained in previous section.

The E_{corr} of all irradiated samples was shifted to more positive as compared to pristine (-0.128 V vs Ag/AgCl), meaning improvement in the corrosion resistance. With an increase in ion fluence from 9.90×10^{17} to 1.18×10^{18} ions/ cm^2 E_{corr} value shifted toward positive -0.106 V vs Ag/AgCl to -0.093 V vs Ag/AgCl, respectively. The 1.18×10^{18} ions/ cm^2 sample exhibits most positive corrosion potential with corresponding lowest corrosion current of 3.42×10^{-7} A/ cm^2 . This positive shift of corrosion potential and reduction in corrosion current implies reduction in surface oxidation of samples with increase in ion fluence. The corrosion current indicates oxidative dissolution of sample species during interaction of electrolyte with sample surface. Hence, the decrease of corrosion current with ion fluence shows less dissolution of sample preventing conversion of Fe to Fe^{+3} Fe^{+2} . This might have happened because of damage created by ions on AISI 304L SS surface, resulting in restriction of Fe to $\text{Fe}^{+3}/\text{Fe}^{+2}$ [29–31].

During the anodic polarization process the following reactions (R) may occur:



Hence from these results, i.e., change in work function due to variation in ion energy (keeping fluence constant) and change in work function due to variation in ion fluence (keeping ion energy constant), we can conclude that ion fluence plays a major role in controlling the work function values. We can either increase or decrease the corrosion by

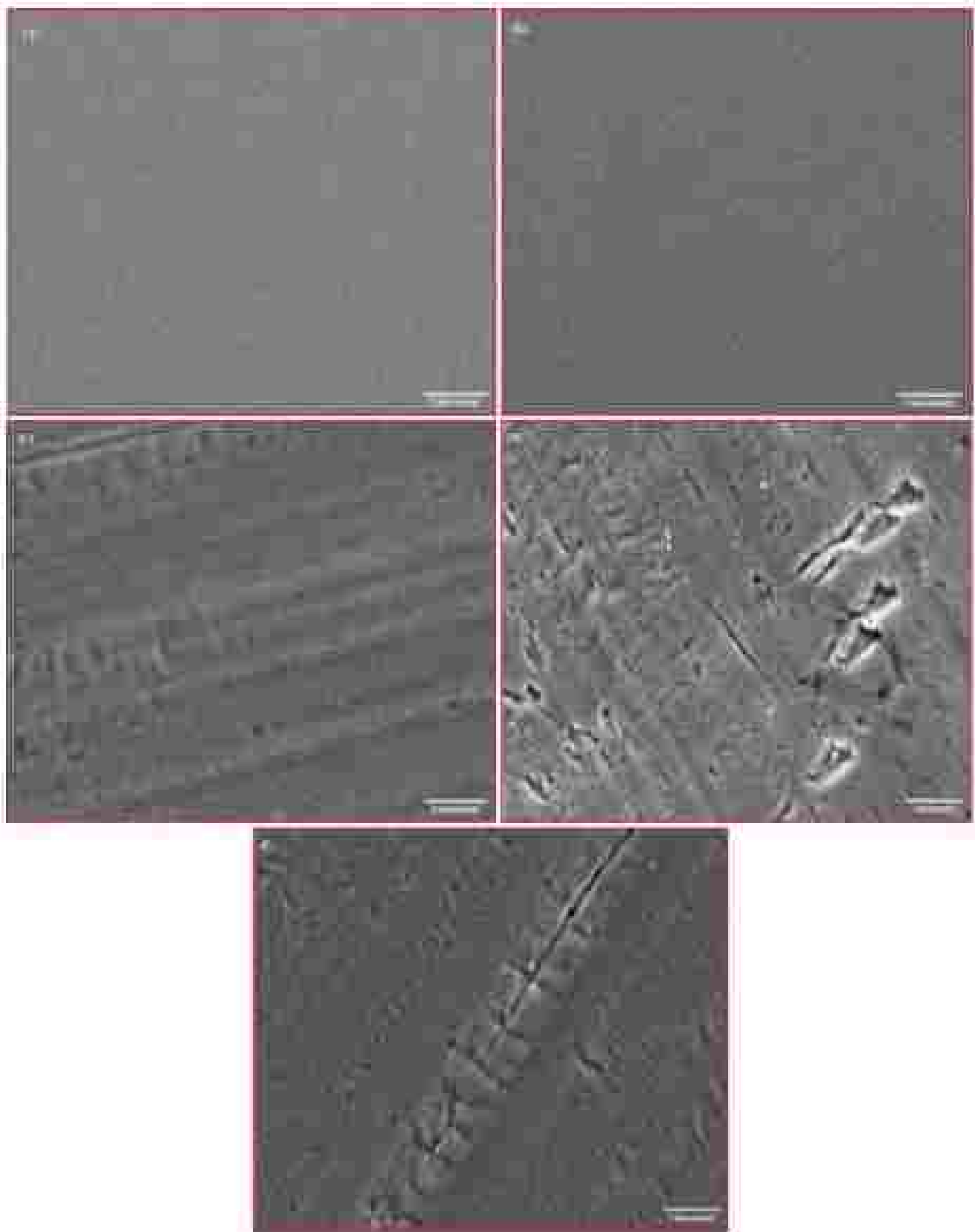


Fig. 7 SEM images of AISI 304L SS samples of **A** pristine, **B** 9.56×10^{17} ions/cm², **C** 2.97×10^{18} ions/cm², **D** 5.94×10^{18} ions/cm², and **E** 1.19×10^{19} ions/cm² ion fluences

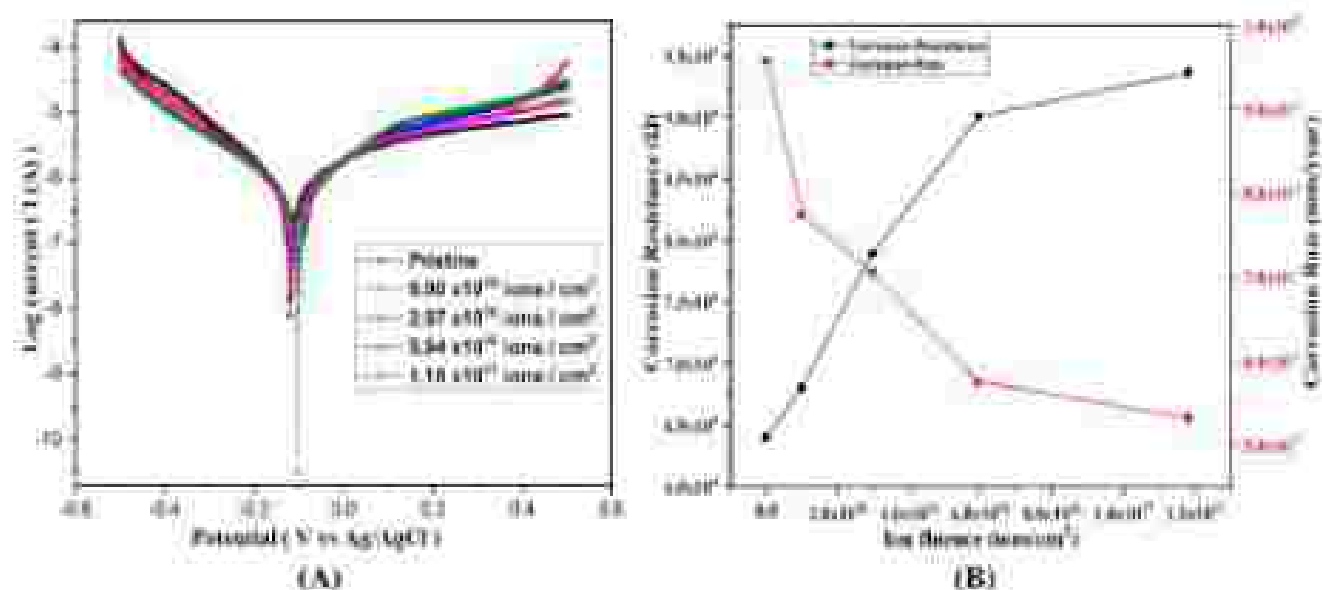


Fig. 8 **A** Potentiodynamic polarization curve for various ion fluences and **B** corrosion resistance and Corrosion rate as a function of ion fluence at a constant ion energy 30 keV

choosing the suitable fluence values. We can either increase or decrease the extraction by choosing the suitable fluence values. As it is known that, work-function is related to corrosion rate too, thus we can also control the corrosion of given sample by properly tuning the ion fluence in the given energy range.

4 Conclusion

The energetic ion induced displacement/damage depends on the energy of incoming ions and its fluence, for a particular material. The irradiation effect due to variation in ion energy and ion fluence on work function of SS-304L samples was explored. Variation in ion irradiation energy up to 40 keV, does not affect the work function of samples. Whereas, if the energy is kept constant and fluence is change it modifies the work function substantially. This change in work function are related to displacement/damage created by primary ions,

which resulted in increase of Wigner-Seitz radius, which is due to change in electrostatic potential ($\delta\phi$) and the electron Fermi energy (ϵ_f) of the SS-304L. The results are useful to control the corrosion stability of stainless-steel material which is applicable in aged nuclear reactors, construction industry, electrical industry, transportation industry and the places, where corrosion stability is required.

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Data availability The authors declare that the data supporting the findings of this study are available within the paper.

Declarations

Conflict of interest The authors declare that they have no conflict of interest.

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Y & M Anjuman Khairul Islam's

POONA COLLEGE OF ARTS, SCIENCE AND COMMERCE

(Affiliated to Savitribai Phule Pune University: ID No. PUPM/ASCI023/1978)

ACTIVITY REPORT

(2022-23)

I. Basic Details:

Name of The Activity: Educational Visit to District Sericulture Office, Wai, District Satara			
Date	Faculty	Department/ Committee	Coordinator Name & Phone no.
26.11.2022	Science	Zoology	Dr. Kalim Shaikh, Mrs. Anjum Pathan & Mr. Sameen Gazikhan (7972224513, 9890485569, 7276936488)
Time 6:00 am to 10:00 pm	Venue District Sericulture Office, Wai	Activity for class/ group & student number S.Y.B.Sc (Zoology) and M.Sc (Zoology) (59)	Nature: Co-curricular

II. Brief Information about the Activity (Criterion no -):

Topic/ Subject of the activity	Educational Visit to District Sericulture Office
Objective for conducting the activity	To experience the students about technicalities of sericulture and also help to setup their own business.
Methodology	Live Demonstration
Outcome	Students experienced live demonstration of Sericulture techniques and they got the importance of this Agro based industry with reference to both Employment and Business.

III. Proofs attached: letters/ student list of participation/ certificate/ document/photos/ any other

1. Permission Letter	2. Student Attendance	3. Photo
4. Detailed Report	5.	6.



Y & M Anjuman Khairul Islam's

POONA COLLEGE OF ARTS, SCIENCE AND COMMERCE

(Affiliated to Savitribai Phule Pune University: ID No. PU/PN/ASC/023/1970)

DEPARTMENT OF ZOOLOGY

Educational Visit to District Sericulture Office,

Wai, District Satara

DETAILED REPORT

Date: 26.11.2022

No. of Participants: 59

With the able guidance and support of Principal, Dr. Aftab Anwar Shaikh, Vice Principal, Mr. Iqbal N. Shaikh Department of Zoology has conducted a Visit to Educational Visit to District Sericulture Office, Wai, District Satara on 26th November 2022 for of S.Y.B.Sc (Zoology) and M.Sc I & II (Zoology) students. The Visit was coordinated by Dr. Kalim Shaikh (replacement of Dr. Mujeeb Shaikh), Mrs. Anjum Pathan & Ms. Sameen Garikhan accompanied with Dr. Shoeb Ahmad and Ms. Raniya Shaikh. Total 59 students from S.Y.B.Sc (Zoology) M.Sc I & II (Zoology) visited to District Sericulture Office, Wai. The main aim of this visit to make students sound with the techniques sericulture to setup Sericulture Unit. Technical Assistant of the District Sericulture Office gave live demonstration to handle the silkworms and he also elaborated the life cycle, habit habitat and disease of silkworms. Hence, with this visit students experienced live demonstration of Sericulture techniques and they got the importance of this Agro based Industry with reference to both Employment and Business.



DEPARTMENT OF ZOOLOGY



Sinhagadwadi Rural, Maharashtra, India
WVVO+KwCjgJhbnatwssd Rissd, Maharashtra 412801, India
Lat: 17.544234E
Long: 73.809611W
20/11/22 11:02 AM GMT +05:30

Technical Assistant of District Sericulture Office explaining silkworm rearing techniques
(Dated: 26.11.2022)



Sinhagadwadi Rural, Maharashtra, India
WVVO+KwCjgJhbnatwssd Rissd, Maharashtra 412801, India
Lat: 17.544234E
Long: 73.809611W
20/11/22 11:02 AM GMT +05:30

Students inside rearing house observing cocoon
(Dated: 26.11.2022)



Sinhagadwadi Rural, Maharashtra, India
WVVO+KwCjgJhbnatwssd Rissd, Maharashtra 412801, India
Lat: 17.544234E
Long: 73.809611W
20/11/22 11:02 AM GMT +05:30

Observing Constitution day at District Sericulture Office, Wai
(Dated: 26.11.2022)



Students at District Sericulture office, Wai
(Dated: 26.11.2022)

Date- 23/11/2022

To,
The Principal,
Purna College,
Camp, Pune-411001.

Subject-M.Sc. I, II and S.Y.B.Sc. Zoology Educational Visit at District Sericulture Office, Wai, Satara.

Respected Sir,

As per syllabus of SPPU Pune, M.Sc. I, II and S.Y.B.Sc. Zoology Students have compulsory Educational Visits study Sericulture techniques. The required rules and regulations prescribed by U.G.C and Savitribai Phule Pune University related to organizing educational visit for students will be followed by making all necessary arrangements. The one day visit is scheduled on 26/11/2022.

You are requested to kindly grant the permission.

Thanking you,

Yours Faithfully,


Mujeeb Shaikh
Head
Department of Zoology

Forwarded
Riaz

In-Charge Teachers
Dr. Mujeeb Shaikh 
Dr. Shoeb Ahmad 
Mrs. Anjum Pathan 
Ms. Sameer Garikhan 
Ms. Raniya Shaikh 

OK
23/11/2022



Anjuman Khairul Islam's
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Pune - 411001 (MS), India

+91-20-2646 4246 / 2644 6315

principal@poonacollege.edu.in
www.poonacollege.edu.in

Professor (Dr.) Aftab Anwar Shaikh

M.Com, Ph.D (Busi. Admin.)

PRINCIPAL

To,
The Office In charge
District Sericulture Office
Wai, District - Satara

Date: 23/11/2022

Sir,

As per syllabus of SPPU Pune, M.Sc I, II and S.Y.II.Sc Zoology Students have compulsory Educational Visits to study Sericulture techniques.

We request your cooperation and guidance to our students about the various aspects related to Sericulture.

Kindly give us suitable date and time as per your convenience.

Thanking you,

Yours Faithfully

Dr. Aftab Anwar Shaikh

Principal

Poona College of Arts, Science & Commerce
Camp, Pune-411001
Principal Office

Aftab Anwar Shaikh
26/11/2022



AKF's Private College of Arts, Science & Commerce, Pune-01

Date of Session: 20/11/2022		Time Slot: 7:00am to 11:00am			
Activity Name	Examination Venue (District/Session/Office No.)	Examination Hall No.	Dr. Kalam Marks		
Examining Dept./Examination: GOVT/SSC		Exam: SSC			
Total Number of Students Appeared		Formal Generated by: Dr. Kalam Marks			
Sr.No.	Name	Roll No.	CMR	Session No.	Signature
1	AJA ATRUB KAJIMAN KHAN	7901	SVBSC (Zoology)	25/11/2022	[Signature]
2	FATMA ANAM SHAIKH	7902	SVBSC (Zoology)	25/11/2022	[Signature]
3	ALFIYA MUSLIM KHAN	7903	SVBSC (Zoology)	25/11/2022	[Signature]
4	ZIYA SHAH SAJJAD	7904	SVBSC (Zoology)	25/11/2022	[Signature]
5	ABHIYA AIZAL SAYYED	7905	SVBSC (Zoology)	25/11/2022	[Signature]
6	KIRIIMA GANU SHAIKH	7906	SVBSC (Zoology)	25/11/2022	[Signature]
7	AMYA WANIM KHAN	7907	SVBSC (Zoology)	25/11/2022	[Signature]
8	PIKA NISAR SHAIKH	7911	SVBSC (Zoology)	25/11/2022	[Signature]
9	MADIK SHAFIK SHAIKH	7912	SVBSC (Zoology)	25/11/2022	[Signature]
10	JANAHENRI THOR NAGIAM	7914	SVBSC (Zoology)	25/11/2022	[Signature]
11	MASHEERA BEGUM BASHIR M.	7915	SVBSC (Zoology)	25/11/2022	[Signature]
12	RUPD SANJOLLE CHANDALYA	7917	SVBSC (Zoology)	25/11/2022	[Signature]
13	JANSHIFA JAVED SHAIKH	7918	SVBSC (Zoology)	25/11/2022	[Signature]
14	MADHUR JALJE KHAN	7920	SVBSC (Zoology)	25/11/2022	[Signature]
15	PREYA S. SHIRASNE	7922	SVBSC (Zoology)	25/11/2022	[Signature]
16	ALFIYA AHMEDAN DE SHIMKHI	7923	SVBSC (Zoology)	25/11/2022	[Signature]
17	ASLIYA AYUB BANJI	7924	SVBSC (Zoology)	25/11/2022	[Signature]
18	MURKAN MURIN PAKHAN	7927	SVBSC (Zoology)	25/11/2022	[Signature]
19	MANISHA PARVINEE S. S.	7929	SVBSC (Zoology)	25/11/2022	[Signature]
20	AYESHA ABID MUKESH MONTE	7930	SVBSC (Zoology)	25/11/2022	[Signature]
21	MUSUMKANAIT SHAIKH	7933	SVBSC (Zoology)	25/11/2022	[Signature]
22	MARIYA DAVID KHAN	7937	SVBSC (Zoology)	25/11/2022	[Signature]
23	LADHA NASHIMUDDIN HOSEIN	7940	SVBSC (Zoology)	25/11/2022	[Signature]
24	HUZAFI DEKHAMAN	7941	SVBSC (Zoology)	25/11/2022	[Signature]
25	AJANNA VADE PATHAN	7944	SVBSC (Zoology)	25/11/2022	[Signature]
26	ANUSHA ABIDA SAYYED	7945	SVBSC (Zoology)	25/11/2022	[Signature]
27	HASAN SHAIKH	7946	SVBSC (Zoology)	25/11/2022	[Signature]
28	FAIZAN SHAIKH	7948	SVBSC (Zoology)	25/11/2022	[Signature]
29	MISHRA AYUB SHAIKH	7949	SVBSC (Zoology)	25/11/2022	[Signature]
30	SANIYA AYUB SHAIKH	7950	SVBSC (Zoology)	25/11/2022	[Signature]
31	ANUSHA QAYYUM SHAIKH	7951	SVBSC (Zoology)	25/11/2022	[Signature]
32	NAZRIN AKIL SHAIKH	7954	SVBSC (Zoology)	25/11/2022	[Signature]
33	DEEPIKA SAMIR KHOT	7955	SVBSC (Zoology)	25/11/2022	[Signature]
34	MIRBAI MOHIT AYAZ ANSARI	7957	SVBSC (Zoology)	25/11/2022	[Signature]
35	MANISHA FATTAZ ANSARI	7958	SVBSC (Zoology)	25/11/2022	[Signature]
36	SANIYA SAMIR SHAIKH	7958	SVBSC (Zoology)	25/11/2022	[Signature]
37	SIFA SAQIB KHOT	7959	SVBSC (Zoology)	25/11/2022	[Signature]
38	ZARIYA ZAKIR SHAIKH	7972	SVBSC (Zoology)	25/11/2022	[Signature]

Page No. 29 of 30 (Total Pages) **Arjun Raju Sankh**

7472 **Sy.BS. (Zoology) Department**
Signature of Faculty Incharge

AKI's Poona college of Arts, Science & commerce, Pune-01

Date of Activity: 26-11-2022		Time: 10:00 am to 11:00 am			
Activity Name:	Tribhuvan's visit to District Sericulture office, War	Teacher in charge:	Ms. Saranya Gadhikar		
Organizing Dept: member Zoology		Title:			
Total Number of Students Attended:		Report Generated by: Ms. Saranya Gadhikar			
Sr. No.	Name	Class	Roll No.	Mobile No.	Signature
1	Khan Aaysha Begum Fakhruddin	M.Sc-I	8401	7806339841	<i>[Signature]</i>
2	Azmat Aatif Irfanul Haq	M.Sc-I	8402	9676676116	<i>[Signature]</i>
3	Lokhande Ravi Nani	M.Sc-I	8403	9218678183	<i>[Signature]</i>
4	Shahh Muskan Abdul Raqeeb	M.Sc-I	8404	8673910271	<i>[Signature]</i>
5	Fard Misha Mubnuob	M.Sc-I	8408	9857988153	<i>[Signature]</i>
6	Shahh Musfiru Karimuddin	M.Sc-I	8410	7299418791	<i>[Signature]</i>
7	Khan Zoya Jewel	M.Sc-I	8411	925024413	<i>[Signature]</i>
8	Singure Madhu Nisar	M.Sc-I	8412	9860270016	<i>[Signature]</i>
9	Naris Farooq	M.Sc-I	8417	98059787	<i>[Signature]</i>
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AKI's Poona college of Arts, Science & commerce, Pune-01

Date of Activity: 26.11.2022

Time Slot: 7:00 am-11:00 am

Activity Name:	Educational visit to District Sericulture office, War	Teacher incharge:	Mrs. Anjum M. Pathan
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Organized by Dept/Committee: Zoology Guest:

Total Number of Students Attended: Report Generated by: Mrs. Anjum Pathan

Sr.No	Name	Class	Roll No	Mobile No.	Signature
1	Patil Tanvir Dhanraj	M.Sc-II	8411	9528234535	
2	Chavhan Fatima Asif	M.Sc-II	8432	9620275746	
3	Shahid Muskan Nasim	M.Sc-II	8434	9209879200	
4	Pravara Thantantjan	M.Sc-II	8435	9366058115	
5	Ompry Lalramjee Chhanga	M.Sc-II	8436	9566153191	
6	Ghanta Sabita Sufyan	M.Sc-II	8437	8530078222	
7	Shinde Mahana angya	M.Sc-II	8438	9267946724	
8	Chavhan Aditya AIT	M.Sc-II	8439	9552833000	
9	Choudhal Adhwal Rajendra	M.Sc-II	8441	8149501167	
10	Tharade S. Shankaran	M.Sc-II	8446	901627841	
11	Shahid Usha Riyaz	M.Sc-II	8467	9867169769	
12	Shahid Madhu S.	M.Sc-II	8468	9709121711	
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Y & M Anjuman Khairul Islam's

POONA COLLEGE OF ARTS, SCIENCE AND COMMERCE

(Affiliated to Savitribai Phule Pune University: ID No. PUPM/ASCI023/1978)

ACTIVITY REPORT

(2022-23)

I. Basic Details:

Name of The Activity: Educational Visit to Directorate of Beekeeping, Mahabaleshwar			
Date	Faculty	Department/ Committee	Coordinator Name & Phone no.
26.11.2022	Science	Zoology	Dr. Shoeb Ahmad (9919509673), Mrs. Anjum Fathan & Ms. Sameen Gazhitan (7972224513, 9890485569, 7276936488)
Time 6:00 am to 10:00 pm	Venue Directorate of Beekeeping Mahabaleshwar	Activity for class/ group & student number S.Y.B.Sc (Zoology)- M.Sc (Zoology) (59)	Nature: Co-curricular

II. Brief Information about the Activity (Criterion no.)::

Topic/ Subject of the activity	Educational Visit to Directorate of Beekeeping
Objective for conducting the activity	To exposed student with Beekeeping techniques and handling of bees with beekeeping equipment
Methodology	Live Demonstration
Outcome	Created an end-to-end implementation framework for beekeeping skill development, which will provide empowerment opportunities and income generation to unemployed youth.

III. Proofs attached: letters/ student list of participation/ certificate/ document/photos/ any other

1. Permission Letter	2. Student Attendance	3. Photo
4. Detailed Report	5.	6.



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DEPARTMENT OF ZOOLOGY

Educational Visit to Directorate of Beekeeping,

Mahabaleshwar

DETAILED REPORT

Date: 26.11.2022

No. of Participants: 59

With the able guidance and support of Principal, Dr. Aftab Anwar Shaikh, Vice Principal, Mr. Iqbal N. Shaikh Department of Zoology has conducted a Visit to Educational Visit to Directorate of Beekeeping, Mahabaleshwar on 26th November 2022 for of S.Y.B.Sc (Zoology) and M.Sc I & II (Zoology) students. The Visit was coordinated by Dr. Shoeb Ahmad, Mrs. Anjum Pathan and Ms. Sameen Garikhan accompanied with Dr. Kalim Shaikh (replacement of Dr. Mujeeb Shaikh), and Ms. Raniya Shaikh. Total 59 students from S.Y.B.Sc (Zoology) M.Sc I & II (Zoology) visited to Directorate of Beekeeping, Mahabaleshwar. The main aim of this visit to exposed student with Beekeeping techniques and handling of bees with beekeeping equipment. Technical Assistant of Directorate of beekeeping gave demo how to handle bees in artificial colony. He also demonstrated the different beekeeping equipment like honey purification unit and bee wax extractor. Hence, this visit created an end-to-end implementation framework for beekeeping skill development, which provides empowerment opportunities and income generation to unemployed youth.



DEPARTMENT OF ZOOLOGY

PHOTOGRAPHS



Technical Assistant of Directorate of Beekeeping demonstrating the Bee Colony (Dated: 26.11.2022)



Technical Assistant of Directorate of Beekeeping demonstrating Honey purification technique (Dated: 26.11.2022)



Technical Assistant of Directorate of Beekeeping explaining honey storage and bottling (Dated: 26.11.2022)



Student group at Directorate of Beekeeping (Dated: 26.11.2022)

Date: 23/11/2022

To,
The Principal,
Poona College,
Camp, Pune-411001.

Subject: M.Sc. I, II and S.Y.B.Sc. Zoology Educational Visit at Directorate of Beekeeping, Maharashtra.

Respected Sir,

As per syllabus of SPPU Pune, M.Sc. I, II and S.Y.B.Sc. Zoology Students have compulsory Educational Visits to study Bee Keeping techniques. The required rules and regulations prescribed by U.G.C and Savitribai Phule Pune University related to organizing Educational visit for students will be followed by making all necessary arrangements. The one day visit is scheduled on 26/11/2022.

You are requested to kindly grant the permission.

Thanking you,

Yours Faithfully,



Dr. Mujeeb Shaikh
Head

Department of Zoology

In-Charge Teachers

Dr. Mujeeb Shaikh

Dr. Shieeb Ahmad

Mrs. Anjum Pathan

Ms. Sameen Qazi

Ms. Raniya Shaikh

Forwarded
By
[Signature]

OK
[Signature]
23/11/22



Anjuman Khairul Islam's POONA COLLEGE OF ARTS, SCIENCE & COMMERCE

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Pune - 411001, (MS), India



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pkc@poonaartscollege.edu.in
www.poonaartscollege.edu.in

Professor (Dr.) Aftab Anwar Shaikh

M.Com, Ph.D (Bus. Admin.)

PRINCIPAL

To
The Office in charge
Directorate of Beekeeping
Mahabaleshwar

Date: 23/11/2022

Sir,

As per syllabus of SPPU Pune, M.Sc I, II and S.Y.B.Sc Zoology Students have compulsory Educational Visit to study beekeeping techniques.

We request your cooperation and guidance to our students about the various aspects related to beekeeping.

Kindly give us suitable date and flow as per your convenience.

Thanking you,

Yours Faithfully

Dr. Aftab Anwar Shaikh

Principal
Poona College of Arts, Science & Commerce
Camp, Pune-411001
Principal Office

Dr. Anwar
20/11/2022
संयोजक
महाराष्ट्र राज्य शासकीय वन्यजीव संरक्षण
संस्थान, अजिंक्यतारा, ज. ५,
अहमदनगर, (म. प्र.)
(फोन - ५१९ ६०६)



AKU's Duma college of Arts, Science & Commerce, Page 01

Date of Activity: 26/11/2022		Time: 10:00 AM to 11:30 AM		
Activity Name	Facilitator/visit to Department of	Teacher Incharge	Dr. Shoaib Ahmad	
Buckingham, Mahabubnagar			NA	
Organizing Dept Committee: ZMS (17-7)			NA	
Total Number of Students Attended		Report contained by:		
Sl. No	Name	Roll No.	Class	Matric No. / Signature
1	M. A. TARIK R. KHAN KHAN	701	SYBSc (Zoology)	1722110101
2	FATIMA ANSARI SHAIKH	702	SYBSc (Zoology)	1722110102
3	ALIYA MENUN KHAN	703	SYBSc (Zoology)	1722110103
4	ZIYA SHAHID SAYYED	704	SYBSc (Zoology)	1722110104
5	ABHIYA AZAL SAYYED	705	SYBSc (Zoology)	1722110105
6	REHMA DARS SHAIKH	706	SYBSc (Zoology)	1722110106
7	ALIYA WAHIM KHAN	707	SYBSc (Zoology)	1722110107
8	UMA NISAR SHAIKH	708	SYBSc (Zoology)	1722110108
9	MAHEK SHAIKH SHAIKH	709	SYBSc (Zoology)	1722110109
10	LASADINSHI THIRUNAGRAM	710	SYBSc (Zoology)	1722110110
11	MASHERA BILGUM BASHIR M	711	SYBSc (Zoology)	1722110111
12	TRIPATI SANGITHI CHANDALIYA	712	SYBSc (Zoology)	1722110112
13	LASMIYA JAVED SHAIKH	713	SYBSc (Zoology)	1722110113
14	MADIRA TALIC KHAN	714	SYBSc (Zoology)	1722110114
15	PREYA S. SHREKHA	715	SYBSc (Zoology)	1722110115
16	ALIYA AHE SAN DEVINI (K)	716	SYBSc (Zoology)	1722110116
17	AMLIYA ATUL BHANGI	717	SYBSc (Zoology)	1722110117
18	MURKAN MUJIB PATHAN	718	SYBSc (Zoology)	1722110118
19	MAANTARA FARVEEN M. I. K.	719	SYBSc (Zoology)	1722110119
20	AYESHA ABIR USATEEN MURAN	720	SYBSc (Zoology)	1722110120
21	NOHVIKASATI SHAIKH	721	SYBSc (Zoology)	1722110121
22	MARIYA JAVED KHAN	722	SYBSc (Zoology)	1722110122
23	FASHA NASHIMUDDIN BOGOL	723	SYBSc (Zoology)	1722110123
24	FUZAE DE RAHMAN	724	SYBSc (Zoology)	1722110124
25	ANANA YAZIR PATHAN	725	SYBSc (Zoology)	1722110125
26	AYESHA ARIFA SAYYED	726	SYBSc (Zoology)	1722110126
27	HASAN SHAIKH	727	SYBSc (Zoology)	1722110127
28	FUZAN SHAIKH	728	SYBSc (Zoology)	1722110128
29	ABIRAJI AYUB SHAIKH	729	SYBSc (Zoology)	1722110129
30	SANIYA ATUL SHAIKH	730	SYBSc (Zoology)	1722110130
31	AFSHA DAYYUM SHAIKH	731	SYBSc (Zoology)	1722110131
32	NAZAN ABE SHAIKH	732	SYBSc (Zoology)	1722110132
33	RAFIK SAMIR KHOT	733	SYBSc (Zoology)	1722110133
34	MUDAH MOHD FAYAAZ ANSARI	734	SYBSc (Zoology)	1722110134
35	MANTAVIA FAYYAZ ANSARI	735	SYBSc (Zoology)	1722110135
36	SANIYA SAMEER SHAIKH	736	SYBSc (Zoology)	1722110136
37	ALI SAQIB KHOT	737	SYBSc (Zoology)	1722110137
38	ZARIYA ZAKIR SHAIKH	738	SYBSc (Zoology)	1722110138
39	Page No. 2/2	7442	Signature of Faculty incharge	

AKI's Poona college of Arts, Science & commerce, Pune-01

Date of Activity: 26/11/2022

Time Slot: 12:00 pm-4:00 pm

Activity Name	Educational visit to Directorate of Reckoning, Maharashtra	Teacher Incharge	Ms. Samona Garkhan
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Organizing Dept/Committee: Zoology Guest:

Total Number of Students Attended: Report Generated by: Ms. Samona Garkhan

Sr. No	Name	Class	Roll No	Mobile No.	Signature
1	Khan Aaysha Begum Fakhruddin	M.Sc-I	8401	7356548961	<i>[Signature]</i>
2	Amari Aarif Irfanul Hasan	M.Sc-I	8402	9116174224	<i>[Signature]</i>
3	Lokhande Raza Nasir	M.Sc-I	8403	8210071190	<i>[Signature]</i>
4	Shaikh Muskan Abdul Raziq	M.Sc-I	8404	862391087	<i>[Signature]</i>
5	Farid Misha Mehboob	M.Sc-I	8405	95985153	<i>[Signature]</i>
6	Shaikh Musfirah Karimuddin	M.Sc-I	8410	724941289	<i>[Signature]</i>
7	Khan Zeiya Javed	M.Sc-I	8411	9325024113	<i>[Signature]</i>
8	Bergam Madhya Nisar	M.Sc-I	8412	8050230016	<i>[Signature]</i>
9	Yasra Farooq	M.Sc-I	8417	9116174224	<i>[Signature]</i>
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AKI's Poona college of Arts, Science & commerce, Pune-01

Date of Activity: 26/11/2022		Time: 10:00 am to 4:00 pm			
Activity Name:	Educational visit to Directorate of Beekeeping, Maharashtra	Teacher In-charge:	Mrs. Anjum M. Patil		
Organizing Dept/Committee: Zoology		Group:			
Total Number of Students Attended:		Report Generated by: Mrs. Anjum Patil			
Sr.No	Name	Class	Roll No	Mobile No.	Signature
1	Pathan Tamir Dastgir	M.Sc-II	8451	9529604124	<i>[Signature]</i>
2	Dhondkar Fatima Araf	M.Sc-II	8452	9601275206	<i>[Signature]</i>
3	Shaikh Muskan Nisam	M.Sc-II	8454	9309870008	<i>[Signature]</i>
4	Pravinika Thosaniyani	M.Sc-II	8455	9356091388	<i>[Signature]</i>
5	Chavhan Lakshman Chhanga	M.Sc-II	8456	926618875	<i>[Signature]</i>
6	Chavhan Sahila Sufian	M.Sc-II	8457	8530079772	<i>[Signature]</i>
7	Shinde Malina suraj	M.Sc-II	8458	9767944724	<i>[Signature]</i>
8	Chavhan Aditya Araf	M.Sc-II	8459	9552833053	<i>[Signature]</i>
9	Chaitral Asthwin Rajendra	M.Sc-II	8461	9822559836	<i>[Signature]</i>
10	Tharashin S. Thankachan	M.Sc-II	8466	904627867	<i>[Signature]</i>
11	Shaikh Uzma Riyaz	M.Sc-II	8467	9067669769	<i>[Signature]</i>
12	Shaikh Musira	M.Sc-II	8468	9709121332	<i>[Signature]</i>
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